1978—Volume 125
Author and Subject Index
Journal of the Electrochemical Society

The Computer-Derived 1978 Journal Index

The Publication Committee of the Society recommended the use of a computer-derived index in 1968, and this practice is planned to be continued. This index is published two months earlier than the usual index and makes possible indexing more information than before. These indices refer only to *Journal* articles, reviews, brief communications, discussions, and news and reviews listed in the contents pages. They do not include meeting papers, abstracts, and news items. These indices were prepared for the *Journal* by the Institute for Scientific Information® , Philadelphia, Pennsylvania.

Using the Index

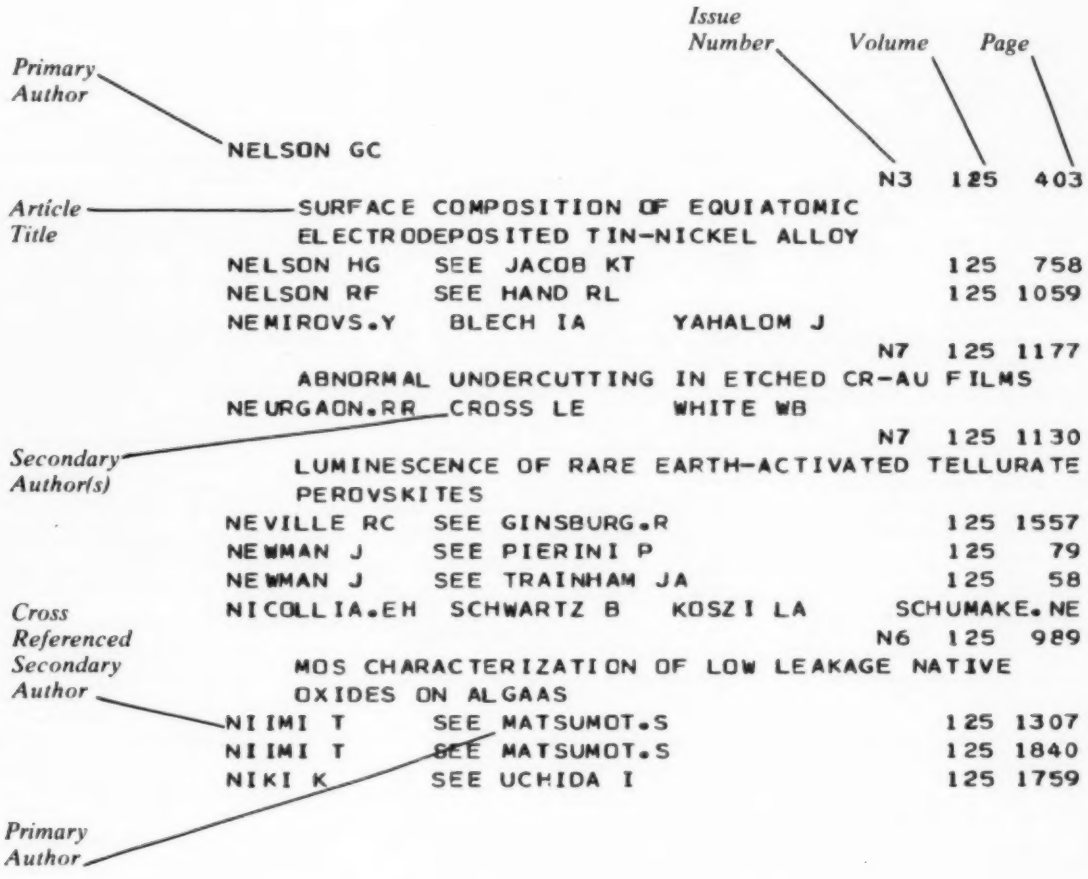
1. Given any author, go directly to his name in the author and title index to find the full paper title with a page citation or, if he is a secondary author, to find a cross-reference to a primary author.
2. Given any topic, go to the subject index and search for the key word itself.
3. For a detailed explanation of symbols and abbreviations, see the sample pages before the individual author and title index and the subject index.
4. Chemical formulae cannot be reproduced directly because the conventional computer printout appears in capital letters only. For example, B13 could be three atoms of bismuth or boron triiodide. To avoid this ambiguity, an attempt has been made to write out chemical formulae.
5. In the author index, an author is always listed with all available initials, which for lack of space sometimes can mean omission of one or two letters from the end of his last name. This truncation is indicated by a period at the end of the last name.

The Publication Committee will appreciate comments on the usefulness and accuracy of this index.

NEWTON SCHWARTZ
Chairman
Publication Committee

JOURNAL ARTICLE AUTHOR AND TITLE INDEX

To locate a full description of a source item, look up the primary author. Under a given name, journal articles of primary authorship are described first. Items of secondary authorship follow. These are cross-referenced to the primary author whose name follows the word SEE.


Issue Number
Volume
Page
Primary Author
NELSON GC
N3 125 403
Article Title
SURFACE COMPOSITION OF EQUIATOMIC
ELECTRODEPOSITED TIN-NICKEL ALLOY
NELSON HG SEE JACOB KT 125 758
NELSON RF SEE HAND RL 125 1059
NEMIROVS.Y BLECH IA YAHALOM J
N7 125 1177
ABNORMAL UNDERCUTTING IN ETCHED CR-AU FILMS
NEURGAON.RR CROSS LE WHITE WB
N7 125 1130
Secondary Author(s)
LUMINESCENCE OF RARE EARTH-ACTIVATED TELLURATE
PEROVSKITES
NEVILLE RC SEE GINSBURG.R 125 1557
NEWMAN J SEE PIERINI P 125 79
NEWMAN J SEE TRAINHAM JA 125 58
NICOLLIA.EH SCHWARTZ B KOSZI LA SCHUMAKE.NE
N6 125 989
Cross Referenced Secondary Author
MOS CHARACTERIZATION OF LOW LEAKAGE NATIVE
OXIDES ON ALGAAS
NIIMI T SEE MATSUMOT.S 125 1307
NIIMI T SEE MATSUMOT.S 125 1840
NIKI K SEE UCHIDA I 125 1759
Primary Author

ACEVES M SEE KENDALL BL 125 1914
AKAO Y SEE MATSUMOT.S 125 1849
AKITA K SEE MARAJIMA K 125 123
ALBELLA JM HORNILLO.A SANZ JM MARTINEZ.JM
N12 125 1950
MATHEMATICAL APPROACH TO C-V PRODUCT IN ALUMINUM ELECTROLYTIC CAPACITORS
ALBELLA JM SEE CLIMENT A 125 746
ALIG RC SEE ZANZUCCH.PJ 125 299
ALKIRE R ERNSBERG.D BECK TR
N9 125 1382
OCCURRENCE OF SALT FILMS DURING REPASSIVATION OF NEWLY GENERATED METAL SURFACES
ALKIRE R BERGH T SANI BL
N12 125 1981
PREDICTING ELECTRODE SHAPE CHANGE WITH USE OF FINITE ELEMENT METHODS
ALKIRE R SEE ENGELMAI.W 125 209
ANDERSON GW SCHMIDT WA CONAS J
N3 125 424
COMPOSITION, CHEMICAL BONDING, AND CONTAMINATION OF LOW TEMPERATURE SIOXNY INSULATING FILMS
ANGERSTE.M SEE HADZIJOR.S 125 1471
ANSON FC SEE MARGEL S 125 241
ANSON FC SEE MARGEL S 125 1232
ANTLER M
N3 125 420
CONTACT RESISTANCE OF TIN-NICKEL ALLOY ELECTRODEPOSITS
ANTONIAD.GA GONZALEZ AG DUTTON RW
N5 125 813
SORUN IN NEAR-INTRINSIC %100< AND %111< SILICON UNDER INERT AND OXIDIZING AMBIENTS - DIFFUSION AND SEGREGATION
APPLEBY AJ BAKER BS
N3 125 404
OXYGEN REDUCTION ON PLATINUM IN TRIFLUOROMETHANE SULFONIC ACID
ARAKAWA H SEE ITO T 125 448
ARNSTRON.HR SEE QUINN RK 125 1790
ARVIA AJ SEE SCHREBLE.RS 125 1578
ARVIA AJ SEE ZEPEIND JO 125 1266
AUGIS JA BENNETT JE
N2 125 330
KINETICS OF TRANSFORMATION OF METASTABLE TIN-NICKEL DEPOSITS .1. DETERMINATION OF AVRAMI EQUATION PARAMETERS BY DSC OR DTA
AUGIS JA BENNETT JE
N2 125 335
KINETICS OF TRANSFORMATION OF METASTABLE TIN-NICKEL DEPOSITS .2. FORMATION AND TRANSFORMATION MECHANISMS
AUGUSTYN.J BALSENC L MINDEN J
N7 125 1093
X-RAY PHOTOELECTRON SPECTROSCOPIC STUDIES OF RUO2-BASED FILM ELECTRODES
AUGUSTYN.WM SEE SCHWARTZ N 125 1812
AUGUSTYN.WM SEE STREMBLO.MM 125 915
BACARELL.AL SEE MCGUIRE GE 125 1801
BACHMANN KJ SEE ROBBINS M 125 631
BACON DD SEE SCHWARTZ N 125 1487
BADER FE SEE SHARMA SP 125 2002
BAGLIN J ONEURLE F ZERINSKY S
N11 125 1854
INTERACTIONS BETWEEN CR AND PT FILMS - NEW CR-PT PHASES
BAKER BS SEE GNIEWEK J 125 17
BAKER BS SEE APPLEBY AJ 125 404
BAKISH R
N6 125 C241
75-YEAR REVIEW SERIES - PROCESS AND EQUIPMENT DEVELOPMENTS IN ELECTROTHERMICS AND METALLURGY OVER LAST 25 YEARS
BALIGA BJ
N4 125 598
ISOTHERMAL SILICON LIQUID PHASE EPITAXY FROM SUPERSATURATED TIN
BALIGA BJ SEE CHANG IF 125 887
BALK P SEE SINGH BR 125 453
BALSENC L SEE AUGUSTYN.J 125 1093
BAN VS
N2 125 317
TRANSPORT PHENOMENA MEASUREMENTS IN EPITAXIAL REACTORS
BANKS E
N10 125 C415
75-YEAR REVIEW SERIES - LUMINESCENCE - PAST 25 YEARS
BARAN EF SEE BASSOUS E 125 1321
BARD AJ SEE LUTTMER JD 125 1423
BARD AJ SEE NOUFI RN 125 246
BARD AJ SEE NOUFI RN 125 375
BARD AJ SEE TENEPANI TH 125 1717
BARD AJ SEE WALLACE WL 125 1433
BARRADAS RG SEE FLETCHER S 125 1960
BARRETT CA SEE SANFORD GJ 125 271
BASSOUS E BARAN EF
N8 125 1321
FABRICATION OF HIGH PRECISION NOZZLES BY ANISOTROPIC ETCHING OF %100< SILICON
BAUGHMAN RJ SEE BIEFELD RM 125 179
BEARLAND DG CHIVERS DJ
N8 125 1331
COLOR-BAND GENERATION DURING HIGH DOSE ION IMPLANTATION OF SILICON WAFERS
BECK TR SEE ALKIRE R 125 1382
BECKER RC SEE REICHMAN.H 125 1765
BEDAIR SM LITTLEJO.MA
N6 125 952
LIQUID PHASE EPITAXY OF II-IV-V2 CHALCOPYRITE COMPOUNDS
BEEBE ED SEE NAMORY RE 125 1053
BELLAMAT.J SEE DOMINGUE.E 125 1521
BENNETT JE SEE AUGIS JA 125 330
BENNETT JE SEE AUGIS JA 125 335
BENNION DN SEE DESHPAND.SL 125 687
BENNION DN SEE SINHA M 125 556
BERGH T SEE ALKIRE R 125 1981
BERMAN A SEE RAIDER SI 125 629
BERTOCCI U
N10 125 1598
PHOTOPOTENTIALS ON COPPER AND COPPER ALLOY ELECTRODES
BHAT R GHANDHI SK
N5 125 771
EFFECT OF CHLORIDE ETCHING ON GAAS EPITAXY USING TMG AND ASH3
BHATTACH.AB CHAUDHAR.PK
N12 125 2012
CHARACTERISTICS OF PLASMA-OXIDIZED NITRIDE MOS STRUCTURES
BIEFELD RM JOHNSON RT BAUGHMAN RJ
N2 125 179
EFFECTS OF COMPOSITION CHANGES, SUBSTITUTIONS, AND HYDROSTATIC PRESSURE ON IONIC CONDUCTIVITY IN LITHIUM ALUMINOSILICATE AND RELATED BETA-EUCRYPTITE MATERIALS
BLANCHAR.B SEE DOMINGUE.E 125 1521
BLANDER M SEE SABOUNGE RL 125 1567
BLECH I SEE MURARKA SP 125 196
BLECH JA SEE MENIROVS.Y 125 1177
BLESSING.GR SEE OKINAKA Y 125 1745
BLURTON KF SEE STETTER JR 125 1804
BOCKRIS JO UDSAKI K
N2 125 223
THEORY OF LIGHT-INDUCED EVOLUTION OF HYDROGEN AT SEMICONDUCTOR ELECTRODES
BOCKRIS JC SEE GNIEWEK J 125 17
BODE U HAUFFE K
N1 125 51
INFLUENCE OF SENSITIZATION OF ELECTRON TRANSFER THROUGH INTERFACE ZINC OXIDE-ELECTROLYTE BY SALT ADDITIONS
BOHG A SEE MAGDO I 125 932
BOISSY NC DIGUET D
N9 125 1505
ZINC ION IMPLANTATION AS A PREDEPOSITION PROCESS IN GALLIUM ARSENIDE
BOMES RJ MARKIN TL
N10 125 1587
POLARIZATION AND CORROSION IN SODIUM-SULFUR CELLS
BONNE RW SCHOONMA.J
N10 125 1628
ELECTRODE PROCESSES OF LEAD HALIDES .2. BETA-PBF2
BONNET MM SEE DUCHEMIN MJ 125 637
BOQUIST CW SEE MATHERS JP 125 1913
BORDI S SEE PAPESCHI G 125 1807
BORNSTEI.NS SEE SNEGGIL JG 125 1283
BORNZIN GA MILLER IF
N3 125 409
PERSISTENT POLARIZATION OF POLYELECTROLYTE MEMBRANES IN AN AQUEOUS ENVIRONMENT
BORUCKA A VCGEL WW IACORANG.CD
N6 125 888
HYDROGEN ELECTRODE IN MOLTEN CARBONATE
BRABEC V CHRISTIA.SD DRYHURST G
N8 125 1236
INTERFACIAL BEHAVIOR OF D-RIBOSE, 2B-DEOXY-D-RIBOSE, AND D-RIBOSE 5B-PHOSPHATE
BRADY MJ
N10 125 1642
FABRICATION PROCESSES FOR A SILICON SUBSTRATE PACKAGE FOR INTEGRATED GALLIUM ARSENIDE LASER ARRAYS
BRAHALL P SEE GILMAN S 125 1924
BRAUNSTE.J SEE VALLET CE 125 1193
BRENNAN MP.J
N8 125 785
INFLUENCE OF CARBON MATRIX CHARACTERISTICS ON PERFORMANCE OF SULFUR ELECTRODES FOR SODIUM-SULFUR CELLS
BRC P
N4 125 674
THERMAL ANALYSIS OF LI-SOCL2 BATTERIES
BRC P SEE DEY AN 125 1574
BRODD RJ KOZAWA A KORDESCH KV
N7 125 C271
75TH ANNIVERSARY REVIEW SERIES - PRIMARY BATTERIES 1951-1976
BRUCKENS.S SEE SHERWOOD WG 125 384
BRUCKENS.S SEE SHERWOOD WG 125 1098
BRUCKENS.S SEE UNTEREKE.DF 125 380
BRUDZEWS.K SEE ORD JL 125 908
BRUININK J KREGTING CG
N9 125 1397
VOLTAMMETRIC BEHAVIOR OF SOME VIOLOGENS AT SNO2 ELECTRODES
BRUMMER SB SEE GARREAU M 125 1990
BRUMMER SB SEE RAUH RD 125 186
BRUMMER MJ SEE CURTIS BJ 125 829
BRYANT WA
N9 125 1534
KINETICS OF TUNGSTEN DEPOSITION BY REACTION OF WF6 AND HYDROGEN
BUCK RP SEE MACKLEMA.D 125 1875
BUEHLER MG THURBER WR
N4 125 645
EXPERIMENTAL STUDY OF VARIOUS CROSS SHEET RESISTOR TEST STRUCTURES
BUEHLER MG GRANT RD THURBER WR
N4 125 650
BRIDGE AND VAN-DER-PAUW SHEET RESISTORS FOR CHARACTERIZING LINE WIDTH OF CONDUCTING LAYERS
BURAS PJ SEE KESZTHEL.CP 125 714
BUTLER MA GINLEY DS
N2 125 228
PREDICTION OF FLATBAND POTENTIALS AT SEMICONDUCTOR-ELECTROLYTE INTERFACES FROM ATOMIC ELECTRONEGATIVITIES
BUTLER MA SEE GINLEY DS 125 1968
BYKER H HOWALD RA GHOSH D KAY CAR
N6 125 889
STANDARD FREE ENERGY OF FORMATION OF ALUMINA
BYVIK CE SEE WALKER GW 125 2034
CAHEN D HODES G MANASSEN J
N10 125 1623
S-SE SUBSTITUTION IN POLYCRYSTALLINE CDSE PHOTOELECTRODES - PHOTOCHEMICAL ENERGY CONVERSION
CAIN OJ VOOK RW
N6 125 882
EPITAXIAL LAYERS OF CUZS GROWN FROM LIQUID SOLUTION AND INVESTIGATED BY RHEED
CALLAHAN WP SEE JOHNSTON WD 125 977
CAMAROT.GP SEE PALOMBAR.G 125 1988
CAMPBELL DA SEE FOSTER LM 125 1689
CARADEC JY SEE PHILIPPA.JL 125 162
CARLA M SEE PAPESCHI G 125 1807
CARPENTE.BS SEE THURBER WR 125 654
CARVER GE GUREV MS SERAPHIN BO
N7 125 1138
PASSIVATING CVD MOLYBDENUM FILMS AGAINST INFRARED REFLECTION LOSSES CAUSED BY OXIDATION
CASSUTO A SEE PHILIPPA.JL 125 162
CHANDRAS.GY SEE FOSTER LM 125 1689
CHANG CC CHANG RPH MURARKA SP
N3 125 481
PLASMA-GROWN OXIDE ON GAAS - SEMIQUANTITATIVE CHEMICAL DEPTH PROFILES OBTAINED USING AUGER SPECTROSCOPY AND NEUTRON ACTIVATION ANALYSIS
CHANG CC PRASER DB GRIECO MJ SHENG TT HASZKO SE KERWIN RE MARCUS RB SINHA AK
N8 125 787
ALUMINUM OXIDATION IN WATER
CHANG CC SEE SHANKOFF TA 125 467
CHANG IF BALIGA BJ GHANDHI SK
N6 125 887
FABRICATING PATTERNS IN TIN OXIDE FILM BY ELECTROCHEMICAL REACTION
CHANG RPH SEE CHANG CC 125 481
CHAUDHAR.PK
N10 125 1687
THRESHOLD VOLTAGE DEGRADATION OF MNOS FET DEVICES
CHAUDHAR.PK SEE BHATTACH.AB 125 2012
CHEN HY SEE VISWANAT.K 125 1616
CHEN MY SEE VISWANAT.K 125 1772
CHIANELL.RR SCANLON JC RAO BNL
N10 125 1963
DYNAMIC X-RAY DIFFRACTION
CHIN DT TSANG CH
N9 125 1461
MASS TRANSFER TO AN IMPINGING JET ELECTRODE
CHIVERS DJ SEE BEARLAND DG 125 1331
CHOI KW YAO NP
N7 125 1811
THERMAL ANALYSIS OF LEAD-ACID CELLS FOR LOAD-LEVELING APPLICATIONS
CHRISTIA.SD SEE BRABEC V 125 1236
CHU SS CHU TL YANG MT HONG KH
N10 125 1668
GALLIUM ARSENIDE FILMS ON TUNGSTEN-GRAPHITE SUBSTRATES
CHU SS SEE CHU TL 125 595
CHU TL CHU SS KELM RW WAKEFIEL.GW
N4 125 595
SOLAR CELLS FROM ZONE-REFINED METALLURGICAL SILICON
CHU TL VANDERLE.GA YOO HI
N4 125 661
PURIFICATION AND CHARACTERIZATION OF METALLURGICAL SILICON
CHU TL SEE CHU SS 125 1668
CIPRIS D MADOR IL
N12 125 1954
ANODE SYNTHESIS OF ORGANIC CARBONATES
CLAUSING RE SEE MCGUIRE GE 125 1801
CLAYTON JC SEE ORD JL 125 908
CLELAND JW SEE PRUSSIN S 125 350
CLIMENT A MARTINEZ.JM ALBELLA JM
N5 125 746
2-LAYER MODEL FOR HEAT-TREATED ANODIC TANTALUM OXIDE
COCHET G MELLOTTE.M CELBOURC.P
N3 125 487
EXPERIMENTAL INVESTIGATION OF GAS PHASE IN A CHEMICAL VAPOR DEPOSITION REACTION - APPLICATION TO SILANE-AMMONIA REACTION LEADING TO SILICON NITRIDE DEPOSITS
COHEN RL RAUB CJ MURAMAKI T
N1 125 34
STATE OF TIN IN TIN-ANODIZED ALUMINUM
COESSON R PARACCHI.C SCHIANCH.G
N4 125 581
ELECTROLUMINESCENCE IN AN EPOXY RESIN
COLEMAN JP SEE WHITE DA 125 1401
CONAS J SEE ANDERSON GW 125 424
CONNER GW SEE COVINO BS 125 370
CONWAY BE CURRIE JC
N2 125 252
SIGNIFICANCE OF EFFECTS OF HIGH PRESSURE ON KINETICS OF ELECTRODE REACTIONS .1. APPLICATIONS TO TRANSITION STATES IN HYDROGEN EVOLUTION REACTION MECHANISMS
CONWAY BE CURRIE JC
N2 125 257
SIGNIFICANCE OF EFFECTS OF HIGH PRESSURE ON KINETICS OF ELECTRODE REACTIONS .2. NATURE OF SOLVENT REORGANIZATION IN ACTIVATION PROCESS OF AN ELECTROCHEMICAL REDOX REACTION
CONWAY BE SEE HADZIJOR.S 125 1471
CONWAY EJ SEE WALKER GH 125 676
CONWAY EJ SEE WALKER GH 125 1726
CONWAY EJ SEE WALKER GH 125 2034
COOK GH
N2 125 C 49
25 YEARS PROGRESS IN ELECTROWINNING AND ELECTROREFINING OF METALS
COOPER JF HOSMER PK HOWSY RV
N1 125 1
ANODIC BEHAVIOR OF LITHIUM IN AQUEOUS LITHIUM HYDROXIDE SOLUTIONS
CORKER GA SVENSSON CH
N11 125 1881
SODIUM-INDUCED WORK FUNCTION SHIFT OF MERCURY AS A METAL-OXIDE-SEMICONDUCTOR ELECTRODE
CORREDOR A SEE TSONG IST 125 2015
COVINO BS SARTWELL BD NEEDHAM PB
N3 125 366
ANODIC APPLICATION BEHAVIOR OF FE-CR SURFACE ALLOYS FORMED BY ION IMPLANTATION
COVINO BS NEEDHAM PB CONNER GR
N3 125 370
ANODIC POLARIZATION BEHAVIOR OF FE-NI ALLOYS FABRICATED BY ION IMPLANTATION
CROOKE M WITTSTOC.S KOCK E
N1 125 166
IRREGULAR GROWTHS OF BIOH<3 ON SURFACE OF OXIDIZED SILICON
CROSS LE SEE NEURGAON.RR 125 1130
CUBICCIO.D LAU KH PERRANTE MJ
N6 125 972
THERMODYNAMICS OF VAPORIZATION AND HIGH TEMPERATURE ENTHALPY OF ZIRCONIUM TETRAIODIDE
CUBICCIO.DD SEE KLEINSCH.PD 125 1843
CUBICCIO.DD JONES RL
N6 125 1001
STRESS CORROSION CRACK INITIATION SITES IN ZIRCONIUM ALLOYS EXPOSED TO IODINE VAPOR
CURRIE JC SEE CONWAY BE 125 252
CURRIE JC SEE CONWAY BE 125 257
CURTIS BJ BRUMMER MJ
N2 125 829
END POINT DETERMINATION OF ALUMINUM CCL4 PLASMA ETCHING BY OPTICAL EMISSION SPECTROSCOPY
DAFLER JR
N6 125 833
RESIN-BONDED CELLULOSE SEPARATORS - OVERVIEW WITH PROGNOSES
DALLASPE.G SEE SINIGAGL.D 125 1199
DALLEK S FOLEY RT
N5 125 731
PROPAGATION OF PITTING ON ALUMINUM ALLOYS
DANILOV IS SEE ROSENFEL.IL 125 1729
DAVANZO DC RUNG RD GAY A DUTTON RW
N7 125 1170
HIGH SPEED IMPLEMENTATION AND EXPERIMENTAL EVALUATION OF MULTILAYER SPREADING RESISTANCE ANALYSIS
DAVIES DE POTTER WD LORENZO JP
N11 125 1849
IMPLANTATION AND PH3 AMBIENT ANNEALING OF INP
DAVIS DD JOHNSON DL
N11 125 1889
PHOTO-ASSISTED CORROSION OF COPPER
DAVIS SM HALL MM
N12 125 1918
ASPECTS OF ALKALINE CELL LEAKAGE
DEAL BE HESS DW PLUMMER JD HO CP
N2 125 339
KINETICS OF THERMAL OXIDATION OF SILICON IN O2-H2O AND O2-CL2 MIXTURES
DEAL BE
N4 125 576
THERMAL OXIDATION KINETICS OF SILICON IN

PYROGENIC H2O AND 5-PERCENT HCL-H2O MIXTURES
DEAL BE HURRLE A SCHULZ WJ
N12 125 2024
CHLORINE CONCENTRATION PROFILES IN O2-HCL AND H2O-HCL THERMAL SILICON OXIDES USING SIMS MEASUREMENTS
DEAL BE SEE MD CP 125 665
DECKERT CA
N2 125 320
ETCHING OF CVD SI3N4 IN ACIDIC FLUORIDE MEDIA
DECLERCK GJ SEE JANSSENS EJ 125 1696
DELBOURG,R SEE COCHET G 125 687
DELCET J MEUS RJ EGAN JJ
N5 125 755
ELECTRONIC CONDUCTIVITY IN SOLID CAF2 AT HIGH TEMPERATURE
DERJAGIN,OG SEE PALEOLOG EN 125 1410
DESHPAND,SL SENNION ON
N5 125 687
LITHIUM DIMETHYL SULFITE GRAPHITE CELL
DETACCON,NP SEE ZERBINO JO 125 1266
DEVEREUX OF GHOSH D KAY DAR
N6 125 890
STANDARD FREE ENERGY OF FORMATION OF ALUMINA
DEVEREUX OF SEE KIM KY 125 1796
DEWINTER JC SEE NAHORY RE 125 1053
DEY AN SEQ P
N10 125 1574
PRIMARY LI-SOCL2 CELLS .4. CATHODE REACTION PROFILES
DHAR S NAG BR
N3 125 508
PULSE METHOD FOR MEASUREMENT OF CONTACT RESISTANCE AND BULK RESISTANCE OF SEMICONDUCTORS SAMPLES
DHEURLE F SEE BAGLIN J 125 1654
DIEGEL RB HASSLER CP
N8 125 1244
MEASUREMENT OF ELECTROCHEMICAL REACTIONS AT ANODIZED TANTALUM ELECTRODE
DIGUET D SEE BOISSY MC 125 1505
DIPAOLA A DIQUARTO F SUNSERI C
N8 125 1344
ELECTROCHROMISM IN ANODICALLY FORMED TUNGSTEN OXIDE FILMS
DIQUARTO F SEE DIPAOLA A 125 1344
DIRKSE TP
N10 125 1591
BEHAVIOR OF ZINC ELECTRODE IN ALKALINE SOLUTIONS .1. EFFECT OF IONIC STRENGTH AT EQUILIBRIUM POTENTIAL
DOBOS BC MIYAZAKI T PARK YS
N2 125 347
TECHNIQUE FOR UNIFORM ETCHING OF POLISHED GALLIUM PHOSPHIDE
DOHERTY CJ SEE STREHLO,HH 125 30
DOMINGUE,E LORATAMA,E BLANCHAR,P BELLANAT,J
N9 125 1521
ANALYTIC STUDY OF SI-B PHASE WHEN B2O3 IS DIFFUSED IN SI
DONG D IRENE EA YOUNG DR
N5 125 819
PREPARATION AND SOME PROPERTIES OF CHEMICALLY VAPOR-DEPOSITED SI-RICH SIO2 AND SI3N4 FILMS
DONG DW SEE IRENE EA 125 1146
DORMUS RM SEE YASUI I 125 1007
DOVIAK MJ SEE WALKER GH 125 2034
DREW LA SEE EVERETT KG 125 309
DRYHURST G SEE BRABEC V 125 1236
DUBOIS JE TOURILLO,G LACAZE PC
N8 125 1257
POLAROGRAPHY-COULOMETRIC RPHT< AND SPECTROSCOPIC SINFRARED-XPSK STUDY OF FORMATION AND MODIFICATIONS OF FILMS FORMED ON A POLARIZED PLATINUM ELECTRODE IN THF-LICLO4 MEDIUM .1. CATHODIC POLARIZATION
DUBOIS JE SEE TOURILLO,G 125 1262
DUCHEMIN MJ BONNET MM KOELSCH MF
N4 125 637
KINETICS OF SILICON GROWTH UNDER LOW HYDROGEN PRESSURE
DUDLEY GJ STEELE BCH
N12 125 1994
MIXED CONDUCTIVITY IN LIFESO8
DUFFY MT STE ZANZUCCH,PJ 125 299
DUIGON FC SEE ROSEN A 125 680
DUNMYRE GR SEE HUFFMAN GP 125 1652
DUTOIT M SOLLBERG,F
N10 125 1648
LATERAL POLYSILICON P-N DIODES
DUTTON RW SEE ANTONIAD,DA 125 813
DUTTON RW SEE DAVANZO DC 125 1170
DYER CK LEACH JSL
N1 125 23
REVERSIBLE OPTICAL CHANGES WITHIN ANODIC OXIDE FILMS ON TITANIUM AND NIOBIUM
DYER CK LEACH JSL
N7 125 1032
BREAKDOWN AND EFFICIENCY OF ANODIC OXIDE GROWTH ON TITANIUM
EGAN JJ SEE DELCET J 125 755
EISELE KM RUTHAROT R
N7 125 1188
STABILIZED FUSED-QUARTZ TUBES WITH REDUCED SODIUM DIFFUSION FOR SEMICONDUCTOR DEVICE TECHNOLOGY
EISENMAN,ET
N5 125 717
KINETICS OF ELECTROCHEMICAL REDUCTION OF DICYANOAURATE
ELKIND MJ SEE SCHINNEL DG 125 152
ELLIOTT JF SEE LIANG WW 125 572
ELLISON BT SCHNEAL WR
N4 125 524
CORROSION OF STEEL IN CONCENTRATED SULFURIC ACID
ELWELL D
N10 125 1721
LOW MELTING-POINT COMPOSITIONS IN ALKALI METAL METAPHOSPHATE-FLUORIDE SYSTEMS APPLICATIONS
ELWELL D
N11 125 1894
LOW MELTING POINT COMPOSITIONS IN ALKALI METAL METAPHOSPHATE-FLUORIDE SYSTEMS
ENGELMAI,W KESSLER T
N1 125 30
INVESTIGATION OF AGITATION EFFECTS ON ELECTROPLATED COPPER IN MULTILAYER BOARD PLATED-THROUGH HOLES IN A FORCED-FLOW PLATING CELL
ENGELMAI,W KESSLER T ALKIRE R
N2 125 209
CURRENT DISTRIBUTION LEVELING RESULTING FROM AUXILIARY BIPOLAR ELECTRODES
ERBACHER JK SEE HUSSEY CL 125 581
ERBACHER JK SEE QUINLAN KP 125 1000
ERICSON SJ SEE EVERETT KG 125 389
ERNSBERG,D SEE ALKIRE R 125 1382
ESTEVEZ SB SCHIFFRI,OJ GIODA AS GIORDANO MC MACAGNO VA
N12 125 1989
PB-PBS2 EXCHANGE REACTION IN PERCHLORATE ACIDIC SOLUTION
EVANS HE NORFOLK DJ SWAN T
N7 125 1180
PERTURBATION OF PARABOLIC KINETICS RESULTING FROM ACCUMULATION OF STRESS IN PROTECTIVE OXIDE LAYERS
EVANS WH SEE MAYO S 125 106
EVERETT KG DREW LA ERICSON SJ SCHRID GM
N3 125 389
FENIC-FENIII< AND HYDROQUINONE-QUINONE REACTIONS ON OXYGEN-COVERED RHODIUM ELECTRODES
FAMIDY TZ SEE FARODQUE M 125 544
FAMIDY TZ SEE FARODQUE M 125 1777
FAIR RB
N2 125 323
ANALYSIS OF PHOSPHORUS-DIFFUSED LAYERS IN SILICON
FAIR RB
N6 125 923
QUANTIFIED CONDITIONS FOR EMITTER-MISFIT DISLOCATION FORMATION IN SILICON
FAIR RB TSAI JCC
N12 125 2050
THEORY AND DIRECT MEASUREMENT OF BORON SEGREGATION IN SIO2 DURING DRY, NEAR DRY, AND WET C-2 OXIDATION
FAIR RB SEE KROGER FA 125 995
FAKTOR MM STEVENSO,JL
N4 125 621
DETECTION OF STRUCTURAL DEFECTS IN GAAS BY ELECTROCHEMICAL ETCHING
FANG WC RAPP RA
N5 125 683
ELECTRICAL CONDUCTIVITY OF BETA-PBF2
FAROOQUE M FAMIDY TZ
N4 125 544
ELECTROCHEMICAL OXIDATION OF HYDROGEN SULFIDE IN TAFEL REGION AND UNDER MASS TRANSPORT CONTROL
FAROOQUE M FAMIDY TZ
N11 125 1777
STUDIES OF NICKEL ELECTRODE IN A ROTATING MULTIPOLAR WIPER-BLADE CELL
FARRELLE,MA SEE VISWANAT,K 125 1772
FASTNACH,RA SEE SINCLAIR WR 125 950
FAULKNER MC
N7 125 C287
RICHARDS,JOSEPH,W. FELLOWSHIP - ELECTROCHEMICAL STUDIES OF OSO-BRIDGED AND SULFIDO-BRIDGED MOLYBDENUM3V< DIMERS
FAULKNER LR SEE MORRIS JL 125 1079
FEDOTOVA AZ SEE PALEOLOG EN 125 1410
FELLONI L SEE PALOMBAR,G 125 1980
FERRANTE MJ SEE CUBICCIO,D 125 972
FERRELL DT SEE SALKIND AJ 125 C311
FINE DA SEE MILES MH 125 1209
FIORDIPO,P PISTOIA G TEMPERON,C
N1 125 14
BEHAVIOR OF B(2O3 AS A CATHODE FOR LITHIUM CELLS
FIORDIPO,P PANEPO S PISTOIA G TEMPERON,C
N4 125 511
NONAQUEOUS BATTERIES WITH BIF3 CATHODES
FIORITO G GASPARRI,G PASSONI D
N2 125 315
POSSIBLE METHOD FOR GROWTH OF HOMOGENEOUS MERCURY CADMIUM TELLURIDE SINGLE CRYSTALS
FLETCHER AN SEE MILES MH 125 1209
FLETCHER S BARFADAS RG PORTER JD
N12 125 1960
ANODIC OXIDATION OF COPPER ANALGAM AND POLYCRYSTALLINE COPPER ELECTRODES IN LIOH SOLUTION
FOLEY MT SEE DALLEK S 125 731
FOLEY MT SEE SARADA T 125 1899
FOLEY MT SEE SUMNER BE 125 1817
FOSTER LM CAMPBELL DR CHANDRAS,GV
N10 125 1689
SELF-DIFFUSION AND NA-K EXCHANGE IN BETA-NA-GALLATE AND BETA5B-NA-GALLATE FAST ION CONDUCTORS
FOULETIE,J KLEITZ M
N5 125 751
DIRECT DETERMINATION OF ELECTRICAL CONDUCTIVITY-NONSTOICHIOMETRY RELATIONSHIP IN IONICALLY CONDUCTING METALLIC OXIDES
FOULKES FR SEE KIRK DW 125 1436
FRANK SN SEE NOUFI RN 125 246
FRASER DB SEE CHANG CC 125 787
FRESE KW SEE KENNEDY JH 125 709
FRESE KW SEE KENNEDY JH 125 723
FRIESER RG POWELL JL TUNNALA RR
N3 125 492
CRYSTALLIZATION IN COPPER-CONTAINING SOLDER GLASSES
FUKUKAWA Y SEE ITO T 125 448
FURNEAUX RC SEE THOMPSON GE 125 1480
FURUYA A NISHI H 125 461
GAIND AK HEARN EW
N1 125 139
PHYSICOCHEMICAL PROPERTIES OF CHEMICAL VAPOR-DEPOSITED SILICON OXYNITRIDE FROM A SIH4-CO2-NH3-N2 SYSTEM
GALLAGHE,PK SEE SINCLAIR WR 125 950
GALVELE JR LUMSDEN JB STAEHLE RW
N8 125 1204
EFFECT OF MOLYBDENUM ON PITTING POTENTIAL OF HIGH PURITY 18-PERCENT CR FERRITIC STAINLESS STEELS
GALVELE JR SEE MAIER IA 125 1594
GARCIA N SEE KENDALL DL 125 1514
GARDINER WC
N1 125 C 22
75TH ANNIVERSARY REVIEW SERIES - ADVANCES IN ELECTROLYTIC PRODUCTION OF INDUSTRIAL CHEMICALS FROM 1952 TO 1977
GARREAU M THEVENIN J WARIN D RAUH RD
REISE TF BRUNNER SD
N12 125 1990
EFFICIENCIES OF CYCLING LITHIUM ON A LITHIUM SUBSTRATE IN PROPYLENE CARBONATE
GASPARRI,G SEE FIORITO G 125 315
GAT A SEE DAVANZO DC 125 1170
GATOS HC SEE HOLMES DE 125 1873
GATOS HC SEE IHAMURA Y 125 1560
GATOS HC SEE JASTRZEB,L 125 1140
GATOS HC SEE KIN KW 125 475
GATOS HC SEE WITT AF 125 1832
GERISCHE,H
N5 125 C210
ELECTROCHEMISTRY OF EXCITED ELECTRONIC STATE
GHANDHI SK SEE BHAT R 125 771
GHANDHI SK SEE CHANG IF 125 887
GHOSH D SEE BYKER H 125 889
GHOSH D SEE DEVEREUX OF 125 890
GHOSHTAG,RN
N1 125 110
MECHANISM OF CVD THIN FILM SNO2 FORMATION
GIBBARD HF
N3 125 383
THERMAL PROPERTIES OF BATTERY SYSTEMS
GILLAUME JC SEE MARBEUF A 125 992
GILMAN S BRANWALL P
N12 125 1924
ELECTROCHEMICAL HEATERS UTILIZING ALUMINUM ALLOY AND MAGNESIUM ANODES
GINLEY DS BUTLER MA
N12 125 1968
FLATBAND POTENTIAL OF CADMIUM SULFIDE XCDS< PHOTOANODES AND ITS DEPENDENCE ON SURFACE ION EFFECTS
GINLEY DS SEE BUTLER MA 125 228
GINSBURG,R MEALD DL NEVILLE RC
N9 125 1557
SILICON NITRIDE CHEMICAL VAPOR DEPOSITION IN A HOT-WALL DIFFUSION SYSTEM
GIODA AS SEE ESTEVEZ SB 125 1989
GIODA AS SEE KAPUSTA SD 125 888
GIORDANO MC SEE ESTEVEZ SB 125 1989
GIORDANO MC SEE KAPUSTA SD 125 888
GLARUM SH
N1 125 84
VARIATIONAL APPROXIMATIONS TO CURRENT DISTRIBUTION PROBLEMS .2. RECTILINEAR ELECTRODES AND BAFFLES
GNIEWEK J PEZY J BAKER BG BOCKRIS JO
N1 125 17
EFFECT OF NOBLE METAL ADDITIONS UPON CORROSION OF COPPER - AUGER-SPECTROSCOPIC STUDY
GOMBAR AM SEE ROSEN A 125 680
GONZALEZ AG SEE ANTONIAD,DA 125 813
GORLA RSR
N6 125 865
UNSTEADY MASS TRANSFER IN BOUNDARY LAYER ON A CONTINUOUS MOVING SHEET ELECTRODE
GOTO KS SEE KAWAKAMI M 125 395
GOTTESFE,S SEE LASER D 125 388
GRANATA RD SEE SARADA T 125 1899
GRANT SD SEE BUEHLER MG 125 650
GRATTON MF WOOLLEY JC
N4 125 687
SOLIDUS ISOTHERMS AND ISOCONCENTRAT.ON LINES IN SYSTEM GA-IN-SB
GRAYDON MF SEE KIRK DW 125 1436
GRIECO MJ SEE CHANG CC 125 787
GRIESS JC SEE MCGUIRE GE 125 1801
GRILVER GA
N10 125 1719
CORROSION OF CARBON BLACK IN PHOSPHORIC ACID
GUPTA SK
N12 125 2064
THERMODYNAMIC AND KINETIC ASPECTS OF BROMINE LAMP CHEMISTRY
GUREV MS SEE CARVER GE 125 1138
GUTIERRE,C LOPEZ MC
N4 125 678
INCREASE OF REST POTENTIAL OF NONSTOICHIOMETRIC LEAD SULFIDE IN 0.1M BORAX WITH ITS P-SEMICONDUCTING CHARACTER
GUTSCHE MW MOODY JW
N1 125 136
POLISHING OF SAPPHIRE WITH COLLOIDAL SILICA
HACKLEMA,D VLASOV YG BUCK RP
N11 125 1875
SIMPLE TECHNIQUE FOR SILICON NITRIDE GROWTH
HADZIJOR,S ANGERSTE,H VUKOVIC M CONWAY BE
N9 125 1471
REVERSIBILITY AND GROWTH BEHAVIOR OF SURFACE OXIDE FILMS AT RUTHENIUM ELECTRODES
HAGANS P SEE YEAGER E 125 348
HAGIWARA T SEE HORIUCHI M 125 766
HALL DE WILDES PD LICHTIN NN
N9 125 1385
ELECTROCIC PHENOMENA AT ANODE OF TOTALLY ILLUMINATED, THIN LAYER IRON-THIONINE PHOTOGALVANIC CELL
HARDY D WIRKKALA J
N7 125 1020
FURTHER EXPERIMENTAL TESTS OF CONVECTIVE FLOW THEORY OF ZN SECONDARY ELECTRODE SHAPE CHANGE-I
HAND RL NELSON RF
N7 125 1059
ANODIC DECOMPOSITION PATHWAYS OF ORTHO-SUBSTITUTED AND META-SUBSTITUTED ANILINES
HANDLEY L MCCANN JF
N12 125 1991
THEORY OF LIGHT-INDUCED EVOLUTION OF HYDROGEN AT SEMICONDUCTOR ELECTRODES
HANSEN LD HART RW
N6 125 842
CHARACTERIZATION OF INTERNAL POWER LOSSES IN PACEMAKER BATTERIES BY CALORIMETRY
HARA T SEE INADA T 125 1525
HARADOME M SEE NITTA M 125 1676
HARKE CJ RENNER J
N11 125 C488
REPORT OF ELECTROLYTIC INDUSTRIES FOR YEAR 1977
HARKE CJ SEE LEITZ FB 125 C 5
HART RW SEE HANSEN LD 125 842
HASHIMOT,T SEE OKUYAMA Y 125 1293
HASSLER CR SEE DIEGEL RB 125 1244
HASZKO SE SEE CHANG CC 125 787
HASZKO SE SEE SHANKOFF TA 125 467
HASZKO SE SEE SINHA AK 125 601
HAUFFE K SEE BODE U 125 51
HAYAKAWA S SEE MATSUOKA Y 125 102
HEALD DL SEE GINSBURG,R 125 1557
HEARN EW SEE GAIND AK 125 139
HEARN EW SEE HEZEL R 125 1848
HEDGES AJ SEE SALKIND AJ 125 C311
HEINBOCK,JH SEE WALKER GH 125 2034
HELLER A SCHWARTZ GP VADIMSKY RG MENEZES S
MILLER B
N7 125 1196
OUTPUT STABILITY OF NORMAL-COSE-NA2S-S-NAOH-C SOLAR CELLS
HELLER A SEE ROBBINS M 125 831
HERMAN CJ SEE WITT AF 125 1832
HESS DW SEE DEAL BE 125 339
HEUS RJ SEE DELCET J 125 755
HEZEL R HEARN EW
N11 125 1848
MECHANICAL STRESS AND ELECTRICAL PROPERTIES OF MNOS DEVICES AS A FUNCTION OF NITRIDE DEPOSITION TEMPERATURE
HIEBERT GB TSEUNG ACC
N1 125 74
HOMOMOLECULAR OXYGEN EXCHANGE AND ELECTROCHEMICAL REDUCTION OF OXYGEN ON SEMICONDUCTING OXIDES
HIJIYA S SEE ITO T 125 448
HILDENBR,DL SEE KLEINSCH,PD 125 1543
HILL DW SEE KATZ LE 125 1151
HINDEN J SEE AUGUSTYN,J 125 1043
HINMAN DF SEE KUDER JE 125 1750
HIROSE K SEE TANIGAKI Y 125 471

MITCHMAN ML SEE WICKER AE 125 1723
MO CP PLUMMER JD REINDL JD DEAL BE
M4 125 665
THERMAL OXIDATION OF HEAVILY PHOSPHORUS-DOPED SILICON
MO CP SEE DEAL BE 125 339
MOORE JP
N11 125 1760
NORMAL OXYGEN POTENTIAL AT A PLATINUM-OXYGEN ALLOY DIAPHRAGM ELECTRODE
MOBBS LH SEE NAGUIB HM 125 169
MOOES G SEE CAHEN D 125 1623
MOORE JD
N2 125 C 55
DIFFUSION OF CHROMIUM IN MAGNETITE AS A FUNCTION OF OXYGEN PARTIAL PRESSURE
MOLLAN L SEE TRANCHAN JC 125 1185
MOLLANDS.RP SEE LITTAUER EL 125 845
MOLLOWAY PH MCGUIRE GE
N12 125 2070
ANALYSIS OF GRAIN BOUNDARY PERMEATION IN SOLIDS
MOLNES OE GATOS HC
N11 125 1873
APPLICATION OF INTERFACE DEMARCATION TO MULTIPHASE SYSTEMS - INSB-SB EUTECTIC
MONSY RV SEE COOPER JF 125 1
MONG KM SEE CHU SS 125 1668
MOPKINS RH SEE RYAN FM 125 1493
MOR AM JACOBS PWM
N3 125 430
THERMALLY STIMULATED SPACE-CHARGE DECAY IN SN-ZE-DOPED SODIUM CHLORIDE AND POTASSIUM CHLORIDE CRYSTALS
MORIUCHI M KAMIGAKI Y MAGIWARA T
N5 125 766
FORMATION AND PROPERTIES OF THIN TUNNELABLE SIO2 FILMS USING A VAPORIZED O-2 SOURCE AT LIQUID N-2 TEMPERATURE
MORNILLO.A SEE ALBELLA JM 125 1950
MOSMEP PH SEE COOPER JF 125 1
MOUNG YM PEARSON GL MATTES BL
N12 125 2058
GROWTH OF SEMI-INSULATING LPE GAAS FOR FET BUFFER LAYERS
MOVEL MJ
N6 125 983
TIO2 ANTIREFLECTION COATINGS BY A LOW TEMPERATURE SPRAY PROCESS
MOWALD RA SEE BYKER H 125 889
MSU L SEE WANG EY 125 1328
MUANG CI SEE JOHNSON BP 125 473
MUANG YH SEE MILES MH 125 1931
MUBLER GK SEE MCCAFFER.E 125 1092
MUFFMAN GP DUNMYRE GN
N10 125 1652
ELECTRON FEERISSION MOSSBAUER STUDY OF ZINPLATE
MUGGINS RA SEE WEPPNER W 125 7
MULETT LO SEE MCGUIRE GE 125 1801
MULL MN SEE DAVIS SM 125 1918
MURALE A SEE DEAL BE 125 2024
MUSSEY CL KING LA ERBACHER JK
N4 125 561
ELECTROCHEMICAL STUDY OF CHROMIUM IN MOLTEN NACL-ALCL3
MUSSEY CL SEE QUINLAN KP 125 1000
MUTCHING.R SEE THOMPSON GE 125 1480
MUTTA JJ SEE QUINLAN KP 125 1000
IACOPANG.CD SEE MORUCKA A 125 888
ILEGEMS M SEE NANDRY BE 125 1053
INAMURA Y JASTRZEB.L GATOS HC
N9 125 1560
SURFACE MORPHOLOGY OF GAAS LAYERS GROWN BY ELECTROEPITAXY AND THERMAL LPE
INAMURA Y SEE JASTRZEB.L 125 1140
INAMURA Y SEE TAKEDA Y 125 130
INADA T OHKUBO T SAWADA T HARA T
NARAJIMA M
N9 125 1525
CHEMICAL VAPOR DEPOSITION OF SILICON NITRIDE ENCAPSULANT LAYERS FOR ANNEALING GALLIUM ARSENIDE
IRENE EA DONG DW
N7 125 1146
SILICON OXIDATION STUDIES - OXIDATION OF HEAVILY P-DOPED AND P-DOPED SINGLE CRYSTAL SILICON
IRENE EA
N10 125 1708
SILICON OXIDATION STUDIES - SOME ASPECTS OF INITIAL OXIDATION REGIME
IRENE EA SEE DONG D 125 819
IRENE EA SEE ZIRINSKY S 125 305
ISAACS TJ SEE LEHMANN W 125 445
ITO T HIJIYA S NOZAKI T ARAKAWA H
SHINODA M FUKUKAWA Y
N3 125 448
VERY THIN SILICON NITRIDE FILMS GROWN BY DIRECT THERMAL REACTION WITH NITROGEN
IWAMATSU S SEE TANIGAKI Y 125 471
JACOB KT
N2 125 175
ELECTROCHEMICAL DETERMINATION OF ACTIVITIES IN CR203-AL203 SOLID SOLUTION
JACOB KT RAO DP NELSON HG
N5 125 758
SOME STUDIES ON A SOLID-STATE SULFUR PROBE FOR COAL GASIFICATION SYSTEMS
JACOBS PWM SEE MOR AM 125 430
JANSSENS EJ CEELERCK GJ
N10 125 1696
USE OF 1,1,1,-TRICHLOROETHANE AS AN OPTIMIZED ADDITIVE TO IMPROVE SILICON THERMAL OXIDATION TECHNOLOGY
JANZ GJ MURPHY RW
N10 125 1605
WETTABILITY OF SOME CARBON SURFACES BY MOLTEN SULFUR AND POLYSULFIDES
JASINSKI RJ
N10 125 1619
N-HEPTYLVIOLOGEN RADICAL CATION FILMS ON TRANSPARENT OXIDE ELECTRODES
JASTRZEB.L INAMURA Y GATOS HC
N7 125 1140
THICKNESS UNIFORMITY OF GAAS LAYERS GROWN BY ELECTROEPITAXY
JASTRZEB.L SEE INAMURA Y 125 1560
JENKO K KINOSHIT.M MATSUMOT.Y
N5 125 827
ETCHING CHARACTERISTICS OF PHOSPHORUS CONTAINING POLYCRYSTALLINE SILICON IN A CF4 PLASMA
JOHNSON BP HUANG CI
N3 125 473
OHMIC CONTACTS TO GAAS TRANSFERRED ELECTRON DEVICES
JOHNSON DL SEE DAVIS DD 125 1889
JOHNSON KE SEE LAM KW 125 1069
JOHNSON RT SEE BIEFELD RW 125 179
JOHNSTON WD CALLAHAN WM
N6 125 977
PROPERTIES OF POLYCRYSTALLINE ALAS-GAAS ON GRAPHITE HETEROJUNCTIONS FOR SOLAR CELL APPLICATIONS
JONES RL SEE CUBICCIO.DD 125 1001
JORDAN J SEE KADISH KM 125 1250
JORNE J
N1 125 94
DYNAMIC-FOAMED ELECTROLYTE HYDROGEN ELECTRODE
JORNE J SEE KIM JT 125 89
JOSE PD SEE RAMANARA.TA 125 1684
JOW T WAGNER JB
N4 125 613
ELECTRICAL PROPERTIES OF CUPROUS IODIDE
KACISH KM JORDAN J
N8 125 1250
ELECTRODE KINETICS OF HEME AND ELECTRON-TRANSFER MECHANISMS OF HEME AND HEMOPROTEINS
KAMIGAKI Y SEE MORIUCHI M 125 766
KAMIHARA M SEE YOSHIE O 125 993
KAMINS TI NANDURAH MM SARASWAT KC
N6 125 927
STRUCTURE AND STABILITY OF LOW PRESSURE CHEMICALLY VAPOR-DEPOSITED SILICON FILMS
KAMINS TI SEE REIF R 125 1860
KAMOSHID.M SEE NAKAMURA K 125 1518
KANEFUSA S SEE NITTA M 125 1676
KANNO K SUZUKI M SATO Y
N9 125 1389
APPLICATION OF COULOSTATIC METHOD FOR RAPID EVALUATION OF METAL CORROSION RATE IN SOLUTION
KAND G SEE TAKAGI M 125 579
KAPUSTA SD GIOIA AS GIORDANO MC MACAGNO VA
N6 125 888
PB-PBZR EXCHANGE REACTION IN PERCHLORATE ACIDIC SOLUTIONS
KASAHARA Y SEE MATSUOKA T 125 102
KATZ LE HILL DW
N7 125 1151
HIGH OXYGEN CZOCHRALSKI SILICON CRYSTAL GROWTH RELATIONSHIP TO EPITAXIAL STACKING FAULTS
KATZ LE KIMERLIN.LC
N10 125 1680
DEFECT FORMATION DURING HIGH PRESSURE, LOW TEMPERATURE STEAM OXIDATION OF SILICON
KATZ LE SEE MORRIS BL 125 762
KATZ M
N4 125 515
ANALYSIS OF ELECTROLYTE SHUNT CURRENTS IN FUEL CELL POWER PLANTS
KAWARAMI M NAGATA K GOTO KS
N3 125 395
ELECTROCHEMICAL DETERMINATION OF INTERDIFFUSIVITY OF CATIONS IN LIQUID LI2O-SIO2 SYSTEM AT 1100-DEGREES-C TO 1350-DEGREES-C
KAY DAB SEE BYKER H 125 889
KAY DAB SEE DEVEREUX OF 125 890
KEE RW SHIOTA I MIYAMOTO N NISHIZAW.J
N6 125 998
AUGER ANALYSIS OF THERMALLY OXIDIZED GAAS SURFACES
KEITH V SEE LESLIE JD 125 44
KELLY JJ KOEL GJ
N6 125 860
ELECTROCHEMICAL ASPECTS OF BEVELING OF SPUTTERED PERMALLOY FILMS
KELM RW SEE CHU TL 125 595
KENDALL DL GARCIA M ACEVES M
N9 125 1514
IMPROVED THEORETICAL PREDICTIONS FOR STEAM OXIDATION OF SILICON AT ANY ELEVATION
KENNEDY JM FRESE KW
N5 125 709
PHOTOOXIDATION OF WATER AT ALPHA-FE2O3 ELECTRODES
KENNEDY JM FRESE KW
N5 125 723
FLATBAND POTENTIALS AND DONOR DENSITIES OF POLYCRYSTALLINE ALPHA-FE2O3 DETERMINED FROM MOTT-SCHOTTKY PLOTS
KENNEDY TA SEE MOLNAR B 125 1318
KENNEY BA SEE KESZTHEL.CP 125 714
KERWIN RE SEE CHANG CC 125 787
KESSLER A
N12 125 2084
THERMALLY STIMULATED SPACE-CHARGE DECAY IN SNZE-DOPED SODIUM CHLORIDE AND POTASSIUM CHLORIDE CRYSTALS
KESSLER T SEE ENGELMAI.W 125 36
KESSLER T SEE ENGELMAI.W 125 209
KESZTHEL.CP KENNEY BA BURAS PJ SOUTWIC.LM WILLIS GH
N5 125 714
COULOMETRIC STUDY OF REDUCTION OF DINITROANILINE COMPOUNDS
KIKKAWA T SEE NAKATSUK.M 125 1829
KILROY WP MCYNIHAN CT
N4 125 520
MEASUREMENT OF BATTERY SEPARATOR RESISTANCES IN LOW IMPEDANCE CONDUCTIVITY CELLS BY A-C BRIDGE TECHNIQUE
KIM JT JORNE J
N1 125 89
MASS TRANSFER OF DISSOLVED CHLORINE TO A ROTATING-ZINC HEMISPHERE IN ZNCL2 SOLUTION
KIM KN WITT AF LICHTENS.M GATOS HC
N3 125 475
QUANTITATIVE ANALYSIS OF EFFECTS OF DESTABILIZING VERTICAL THERMAL GRADIENTS ON CRYSTAL GROWTH AND SEGREGATION - GA-DOPED GE
KIM KY DEVEREUX OF
N11 125 1796
USE OF ALUMINA AS A SHEATH FOR PT, CO-CO2 NA2CO3 REFERENCE ELECTRODE
KIMERLIN.LC SEE KATZ LE 125 1680
KING LA SEE MUSSEY CL 125 561
KING LA SEE QUINLAN KP 125 1000
KINOSHIT.M SEE JENKO K 125 827
KINOSHIT.K SEE SWAROOP RB 125 1799
KIRK DW FOULKES FR GRAYDON WF
N9 125 1436
STUDY OF ANODIC DISSOLUTION OF GOLD IN AQUEOUS ALKALINE CYANIDE
KISS L SEE YERTES A 125 1946
KLEINKNE.HP MEIER H
N5 125 798
OPTICAL MONITORING OF ETCHING OF SIO2 AND SI3N4 ON SI BY USE OF GRATING TEST PATTERNS
KLEINSCH.PD CUBICCIO.D HELDENBR.OL
N9 125 1543
THERMODYNAMICS OF GASEOUS ZIRCONIUM IODIDES
KLEITZ M SEE FOULETIE.J 125 791
KNASTER M SEE PANICKER MP 125 566
KNORR K SEE LESLIE JD 125 44
KNUTSEN GF SEARCY AW
N2 125 327
CHARACTERIZATION OF GASEOUS AND SOLID PRODUCTS OF ALUMINUM SULFATE DECOMPOSITION
KOCH FB SEE OKINAKA Y 125 1765
KOCH VR YOUNG JH
N9 125 1371
STABILITY OF SECONDARY LITHIUM ELECTRODE IN TETRAHYDROFURAN-BASED ELECTROLYTES
KOCK E SEE CROOKE M 125 166
KOEL GJ SEE KELLY JJ 125 860
KOELMANS H KRETSCHM.HJ
N10 125 1715
WATER DROPLET FORMATION DURING LIFE TESTING OF ICS IN A HUMID AMBIENT
KOELSCH MF SEE DUCHEMIN MJ 125 637
KOENINGS J SEE KUPPERS D 125 1298
KOGUCHI T SEE OKUYAMA Y 125 1293
KOHIYAMA K SEE MATSUMOT.S 125 1840
KOHL PA
N7 125 C283
WESTON.EDWARD SUMNER FELLOWSHIP REPORT - PHOTOELECTROCHEMICAL BEHAVIOR OF SEMICONDUCTING N-GAAS AND P-GAAS AND INP ELECTRODES IN ACETONITRILE SOLUTIONS
KOHL PA SEE NOUFI RN 125 246
KOHL PA SEE NOUFI RN 125 375
KOLCZNY A SHAPPIR J
N9 125 1530
DIFFUSION PROPERTIES OF CADMIUM IN INDIUM ANTIMONIDE
KOMIYA S KOTANI T
N12 125 2019
DIRECT OBSERVATION OF DISLOCATIONS IN GAI-XALXAS-GAAS GROWN BY LPE METHOD
KORDESCH KV
N3 125 C 77
25 YEARS OF FUEL CELL DEVELOPMENT 1951-1976<
KORDESCH KV SEE BRODD RJ 125 C271
KOSZI LA SEE NICOLLIA.EP 125 989
KOTANI T SEE KOMIYA S 125 2019
KOTANI T SEE NAKAJIMA K 125 123
KOZAWA A SEE BRODD RJ 125 C271
KRAUS JF SEE TSONG IST 125 2015
KREGTING CG SEE BRUININK J 125 1397
KRETSCHM.HJ SEE KOELMANS H 125 1715
KROGER FA FAIR PB TSAI JCC
N6 125 995
QUANTITATIVE MODEL FOR DIFFUSION OF PHOSPHORUS IN SILICON AND EMITTER DIP EFFECT
KROGER FA
N12 125 2028
CATHODIC DEPOSITION AND CHARACTERIZATION OF METALLIC OR SEMICONDUCTING BINARY ALLOYS OR COMPOUNDS
KROGER FA SEE PANICKER MP 125 566
KROGER FA SEE RAY AK 125 1348
KROGER FA SEE FAY AK 125 1355
KUBO M SEE MORITANI A 125 824
KUCHARSK.M SEE MOSER Z 125 692
KUDER JE POCHAN JM TURNER SR MINHAN DF
N11 125 1750
FLUORENONE DERIVATIVES AS ELECTRON TRANSPORT MATERIALS - RELATIONSHIP OF ELECTRON AFFINITY AND ELECTROCHEMISTRY WITH PHOTOELECTRIC BEHAVIOR
KUMAR V SEE LAL K 125 2079
KUO MC NOBE K
N6 125 853
ELECTRODISSOLUTION KINETICS OF IRON IN CHLORIDE SOLUTIONS .6% CONCENTRATED ACIDIC SOLUTIONS
KUPPERS D KOENINGS J WILSON H
N8 125 1298
DEPOSITION OF FLUORINE-DOPED SILICA LAYERS FROM A SICL4-SIF4-O2 GAS MIXTURE BY PLASMA-CVD METHOD
KUPPERS JR
N1 125 97
REACTIVITY OF METALS WITH MIXTURES OF CARBON TETRACHLORIDE AND ALCOHOLS
KUSUNOKI T SEE NAKAJIMA K 125 123
KUTNER R SEL NOWAK RJ 125 232
LACAZE PC SEE DUBOIS JE 125 1257
LACAZE PC SEE TOURILLO.G 125 1262
LAGOWSKI JJ SEE TEHERANI TH 125 1717
LAITINEN HA
N6 125 C250
75-YEAR REVIEW SERIES - PROGRESS IN ELECTROANALYTICAL CHEMISTRY 1952-1977
LAITINEN HA YAMAMURA Y UCHIDA I
N9 125 1450
EFFECT OF MOISTURE ON CHROMIUM(III)-CHROMIUM(II) ELECTRODE REACTION IN MOLTEN LICL-KCL EUTECTIC
LAITINEN HA SEE UCHIDA I 125 1759
LAL K KUMAR V
N12 125 2079
STUDY OF CRYSTAL PERFECTION OF CVD-GROWN ALPHA-AL2O3 SINGLE CRYSTALS BY TRANSMISSION X-RAY DIFFRACTION TOPOGRAPHY
LAM KW JOHNSON KE LEE DG
N7 125 1869
STUDIES OF RUTHENIUM-OXY SPECIES IN BASIC SOLUTIONS BY CYCLIC VOLTAMMETRY
LAMORECH.VG SEE ROBBINS M 125 831
LANDOLT D SEE MATHIEU JB 125 1039
LANDOLT D SEE MATHIEU JB 125 1044
LASER D YANIV M GOTTESFE.S
N3 125 358
ELECTROCHEMICAL AND OPTICAL PROPERTIES OF THIN OXIDE LAYERS FORMED ON FRESH TITANIUM SURFACES IN ACID SOLUTIONS
LAU KH SEE CUBICCIO.D 125 972
LEACH JSL SEE DYER CK 125 23
LEACH JSL SEE DYER CK 125 1032
LEE DG SEE LAM KW 125 1069
LEHMANN W ISAACS TJ
N3 125 445
LANTHANUM AND YTTRIUM HALO-SILICATE PHOSPHORS
LEIDHEIS.M SEE VERTES A 125 1946
LEITZ FB PARKE CJ
N1 125 C 5
REPORT OF ELECTROLYTIC INDUSTRIES FOR YEAR 1976
LEROY RL
N5 125 697
DESIGN OF AN ELECTROCOATING CELL FOR CONSTANT CURRENT DENSITY OPERATION - FOURIER-TRANSFORM METHOD OF SOLUTION OF LAPLACE EQUATION
LESLIE JD KEITH V KNORR K
N1 125 44
AUGER SPECTROSCOPIC EVIDENCE THAT PLASMA ANODIZATION INVOLVES MASS TRANSFER FROM CATHODE TO ANODE
LEVINSTE.HJ SEE MURARKA SP 125 156
LEVINSTE.HJ SEE SIMHA AK 125 881
LEVY DJ WA DH
N11 125 1741
CHARACTERISTICS OF IMMERSION-PLATED GOLD DEPOSITS ON ALUMINUM
LIANG MW ELLIOTT JF
N4 125 572
STANDARD FREE ENERGY OF FORMATION OF LIQUID

NAZSON 1160-DEGREES-K-1220-DEGREES-K
LICHTENS,M SEE KIM KM 125 475
LICHTENS,M SEE WITT AF 125 1832
LICHTEN MN SEE HALL DE 125 1365
LIN KF
N7 125 1077
SOME ELECTROCAPILLARY-TYPE BEHAVIORS OF GOLD ELECTRODE
LIN LM SEE SINCLAIR WR 125 950
LIN SS
N11 125 1877
MASS SPECTROMETRIC DETECTION OF INTERMEDIATES IN CHEMICAL VAPOR DEPOSITION OF SI3N4 FROM SICL4 AND NH3
LINDBERG G SEE SMITH T 125 1224
LITTAUER EL TSAI KC HOLLANDS,RP
N6 125 845
ANODIC BEHAVIOR OF LITHIUM IN AQUEOUS ELECTROLYTES .3. INFLUENCE OF FLOW VELOCITY, CONTACT PRESSURE, AND CONCENTRATION
LITTLEJO,MA SEE BEDAIR SM 125 952
LIU SS STEVENSO,DA
N7 125 1161
GROWTH KINETICS AND CATALYTIC EFFECTS IN VAPOR PHASE EPITAXY OF GALLIUM NITRIDE
LLOYD JR NAKAMARA S
N12 125 2037
DIFFUSION OF EXCESS VACANCIES TO FREE SURFACES AND VOIDS IN THIN FILMS
LO CC
N3 125 400
4-POINT BEND TEST FOR MEASURING DUCTILITY OF BRITTLE COATINGS
LOPEZ MC SEE GUTIERRE,C 125 678
LORATAMA,E SEE DOMINGUE,E 125 1521
LORENZO JP SEE DAVIES DE 125 1845
LOWN JW SEE RAO GM 125 534
LOWN JW SEE RAO GM 125 540
LU PWT SRINIVAS,S
N2 125 265
NICKEL-BASED ALLOYS AS ELECTROCATALYSTS FOR OXYGEN EVOLUTION FROM ALKALINE SOLUTIONS
LU PWT SRINIVAS,S
N9 125 1416
ELECTROCHEMICAL-ELLIPSOMETRIC STUDIES OF OXIDE FILM FORMED ON NICKEL DURING OXYGEN EVOLUTION
LUNSDEN JB SEE GALVELE JR 125 1204
LUTHRA KL SEE MCKEE DW 125 411
LUTTMER JD BARD AJ
N9 125 1423
ELECTROGENERATED CHEMILUMINESCENCE .33. PRODUCTION OF EXCITED STATES BY DIRECT HETEROGENEOUS ELECTRON TRANSFER FROM SEMICONDUCTOR ELECTRODES
MA DM SEE LEVY DJ 125 1741
MACAGNO VA SEE ESTEVEZ SB 125 1989
MACAGNO VA SEE KAPUSTA SD 125 888
MACDIARM,AG SEE NOWAK RJ 125 232
MACDONAL,DD
N9 125 1443
IMPEDANCE INTERPRETATION OF SMALL AMPLITUDE CYCLIC VOLTAMMETRY .1. THEORETICAL ANALYSIS FOR A REVERSIBLE-CAPACITIVE SYSTEM
MACDONAL,DD
N12 125 1977
IMPEDANCE INTERPRETATION OF SMALL AMPLITUDE CYCLIC VOLTAMMETRY .2. THEORETICAL ANALYSIS OF SYSTEMS THAT EXHIBIT PSEUDOINDUCTIVE BEHAVIOR
MACDONAL,DD
N12 125 2062
METHOD FOR ESTIMATING IMPEDANCE PARAMETERS FOR ELECTROCHEMICAL SYSTEMS THAT EXHIBIT PSEUDOINDUCTANCE
MACDOUGA,B
N11 125 1883
ROLE OF OXIDE DEFECT SITES IN BREAKDOWN OF NIO FILMS
MADOR IL SEE CIPRIS D 125 1954
MAGDO I BOHG A
N6 125 932
FRAMED RECESSED OXIDE SCHEME FOR DISLOCATION-FREE PLANAR SI STRUCTURES
MAIER IA GALVELE JR
N10 125 1594
LOCALIZED CORROSION ON SLIP STEPS OF ALUMINUM STRAINING
MAKI M SEE OGIRIMA M 125 1879
MAKI M SEE SHINTANI A 125 2076
MALOY JT SEE PICKETT DF 125 1026
MANASSEN J SEE CAMEN D 125 1623
MANDHANA MM SEE KANENS TI 125 927
MARBEUF A GILLAUME JC
N6 125 992
DLP MODEL IN GAXINI-XP-N ALLOYS CORRELATION WITH ELECTRONIC PROPERTIES
MARCUS RB SEE CHANG CC 125 787
MARCUS RB SEE SHENG TT 125 432
MARGEL S SMITH W ANSON FC
N2 125 241
ELECTROCHEMISTRY OF 2,2B-BIPYRIDINE COMPLEXES OF COBALT IN PRESENCE OF ACRYLONITRILE
MARGEL S ANSON FC
N8 125 1232
CATALYSIS OF ELECTROREDUCTION OF ALLYL CHLORIDE BY COBALT 2,2B-BIPYRIDINE COMPLEXES
MARINO AA SEE REICHMAN,M 125 1765
MARK MB SEE NOWAK RJ 125 232
MARKIN TL SEE BONES RJ 125 1587
MARR JJ SEE SABOUNGI ML 125 1567
MARSCHOF,CH
N12 125 1992
SIGNIFICANCE OF EFFECT OF HIGH PRESSURE ON KINETICS OF ELECTRODE REACTIONS .1. APPLICATIONS TO TRANSITION STATE IN HYDROGEN EVOLUTION REACTION MECHANISMS
MARTINEZ,JR SEE ALBELLA JM 125 1950
MARTINEZ,JM SEE CLIMENT A 125 746
MATHERS JP BOQUIST CW OLSZANSK,TW
N12 125 1913
POWDER ELECTRODE SEPARATORS FOR HIGH TEMPERATURE LITHIUM-ALUMINUM IRON SULFIDE BATTERIES
MATHIEU HJ SEE MATHIEU JB 125 1039
MATHIEU JB MATHIEU HJ LANDOLT D
N7 125 1039
ELECTROPOLISHING OF TITANIUM IN PERCHLORIC ACID-ACETIC ACID SOLUTION .1. AUGER ELECTRON SPECTROSCOPY STUDY OF ANODIC FILMS
MATHIEU JB LANDOLT D
N7 125 1044
ELECTROPOLISHING OF TITANIUM IN PERCHLORIC ACID-ACETIC SOLUTION .2. POLARIZATION BEHAVIOR AND STOICHIOMETRY
MATSUDAI,S SEE NAKATANI K 125 406
MATSUMOT,S NIIMI T
N8 125 1307
CONCENTRATION DEPENDENCE OF A DIFFUSION COEFFICIENT AT PHOSPHORUS DIFFUSION IN GERMANIUM
MATSUMOT,S AKAO Y KOHIYAMA K NIIMI T
N11 125 1840
EFFECTS OF DIFFUSION-INDUCED STRAIN AND DISLOCATION ON PHOSPHORUS DIFFUSION INTO SILICON
MATSUMOT,Y SEE JINNO K 125 827
MATSUNAM,M SEE SUZUKI A 125 1896
MATSUOKA T KASAMARA Y TSUCHIYA M MITTA T HAYAKAWA S
N1 125 102
PREPARATION AND LOW ENERGY ELECTRON BEAM EXCITATION OF SNO2-EU POWDER PHOSPHOR
MATTAS BL SEE HOUNG YM 125 2058
MAYO S EVANS WH
N1 125 106
THERMODYNAMIC CONSIDERATIONS IN USE OF POLYSILICON OXIDATION TUBES FOR CLEAN SIO2 FILM PREPARATION
MAYUMI S SEE YONEYAMA H 125 68
MCCAFFER,E HUBLER GK
N11 125 1892
ELECTROCHEMICAL BEHAVIOR OF PALLADIUM-IMPLANTED TITANIUM
MCCANN JF SEE MANDLEY L 125 1991
MCFEE JH SEE MELLER BI 125 1310
MCGUIRE GE BACARELL,AL GRIESS JC CLAUSING RE HULETT LD
N11 125 1801
ANALYSIS OF PROTECTIVE OXIDE FILMS ON COPPER-NICKEL ALLOYS BY AUGER SPECTROSCOPY
MCGUIRE GE SEE HOLLOWAY PP 125 2070
MCKEE DW SHORES DA LUTHRA KL
N3 125 411
EFFECT OF SO2 AND NACL ON HIGH TEMPERATURE HOT CORROSION
MCLOUSKI RW PECKERAR MC SCHREURS JJ
N6 125 985
EFFECTS OF HCL RESIDUAL TREATMENT ON MNOS MEMORY TRANSISTORS
MEIER H SEE KLEINKNE,HP 125 798
MEIMOL JD SEE MD CP 125 665
MELENDRE,CA SY CC
N5 125 727
STRUCTURE AND CYCLIC DISCHARGE BEHAVIOR OF LIAL ELECTRODES
MELENDRE,CA SIEGEL S SETTLE J
N11 125 1886
POLARIZATION BEHAVIOR AND STRUCTURE OF LIALMG ALLOY ELECTRODES
MELLIARS,CR SEE STREMBLO,MM 125 915
MELLOTTE,M SEE COCHET G 125 487
MEMMING R
N1 125 117
ROLE OF ENERGY LEVELS IN SEMICONDUCTOR-ELECTROLYTE SOLAR CELLS
MEMMING R SEE TRANCHAN,JC 125 1185
MENEZES S SEE MELLER A 125 1156
MENEZES S SEE ROBBINS M 125 831
MENZIES IA SEE TCHLINSO,WJ 125 279
METZGER M SEE ZAHAVI J 125 438
METZGER M SEE ZAHAVI J 125 574
MEUBUS P
N10 125 1636
HIGH TEMPERATURE REACTION KINETICS OF TUNGSTEN WITH SULFUR DIOXIDE
MILES MM FINE DA FLETCHER AN
N8 125 1209
CALCIUM ANODE IN MOLTEN NITRATE ELECTROLYTES
MILES MM HUANG YH SRINIVAS,S
N12 125 1931
OXYGEN ELECTRODE REACTION IN ALKALINE SOLUTIONS ON OXIDE ELECTRODES PREPARED BY THERMAL DECOMPOSITION METHOD
MILLER B SEE MELLER A 125 1156
MILLER B SEE ROBBINS M 125 831
MILLER BI MCFEE JH
N8 125 1310
GROWTH OF GAYINI-YAS-INP METEROSTRUCTURES BY MOLECULAR BEAM EPITAXY
MILLER IF SEE BORNZIN GA 125 409
MINAGAWA S SEE SHINTANI A 125 2076
MIYAMOTO N SEE KEE RW 125 998
MIYAZAKI T SEE DOBBS BC 125 347
MIYOSHI H TSUBOUCH,N NISHIMOT,A
N11 125 1824
SELECTIVE OXIDATION OF SILICON IN HIGH PRESSURE STEAM
MOHAPATR,SK
N2 125 284
ELECTROCHROMISM IN LIXWO3
MOHAPATR,SK WAGNER S
N10 125 1603
EMF MEASUREMENTS ON ELECTROCHROMIC AMORPHOUS LIXWO3 FILMS
MOLNAR B KENNEDY TA
N8 125 1318
EVALUATION OF S-IMPLANTED AND SE-IMPLANTED GAAS BY CONTACTLESS MOBILITY MEASUREMENT
MOMMA N TANIGUCH,H URA H OGATA T
N6 125 983
GETTERING OF GOLD AND COPPER IN SILICON DURING GALLIUM DIFFUSION
MONKOWSK,J TRESSLER RE STACH J
N11 125 1867
STRUCTURE AND COMPOSITION OF SILICON OXIDES GROWN IN HCL-O2 AMBIENTS
MONKOWSK,J TRESSLER RE STACH J
N12 125 2083
KINETICS OF THERMAL OXIDATION OF SILICON IN O2-H2O AND O2-CL2 MIXTURES
MOODY JW SEE GUTSCHE MW 125 136
MORCOS I
N9 125 1494
METAL-LIQUID INSULATOR INTERFACE IN PRESENCE AND ABSENCE OF AN APPLIED ELECTRIC FIELD
MORI Y WATANABE N
N9 125 1510
NEW ETCHING SOLUTION SYSTEM, H3PO4-H2O2-H2O, FOR GAAS AND ITS KINETICS
MORITANI A KUBO M NAKAI J
N5 125 824
ANODIZATION OF LAYERED SEMICONDUCTORS - METHOD TO COUNT NUMBER OF LAYERS
MORRIS BL KATZ LE
N5 125 782
REDUCTION OF EXCESS PHOSPHORUS AND ELIMINATION OF DEFECTS IN PHOSPHORUS EMITTER DIFFUSIONS
MORRIS JL FAULKNER LR
N7 125 1079
DETAILED TREATMENT OF REACTION ZONE FOR ELECTRON-TRANSFER CHEMILUMINESCENCE
MOSER Z KUCHARSK,M RZYMAN K
N5 125 692
ACTIVITIES AND SURFACE TENSION OF LIQUID AGCL-KCL SOLUTIONS
MOUNTZ JM SEE TIEN HT 125 885
MOYNIHAN CT SEE KILROY WP 125 520
MUENCH RV PETTENPA,E
N2 125 294
PREPARATION OF PURE AND DOPED SILICON CARBIDE BY PYROLYSIS OF SILANE COMPOUNDS
MULDER BJ
N5 125 823
PROTECTIVE GLASSY LAYERS PASSIVATING COPPER AT 500-DEGREES-C
MURAMAKI T SEE COHEN RL 125 34
MURARKA SP LEVINSTE,HJ BLECH I SHENG TT READ WH
N1 125 156
INVESTIGATION OF TI-PT DIFFUSION BARRIER FOR GOLD BEAM LEADS ON ALUMINUM
MURARKA SP SEE CHANG CC 125 481
MURPHY J SEE RYAN FN 125 1493
MURPHY RN SEE JANZ GJ 125 1605
NAG BR SEE DHAR S 125 508
NAGATA K SEE KAWAKAMI M 125 395
NAGUIB HM HOBBS LM
N1 125 169
REDUCTION OF POLY-SI DISSOLUTION AND CONTACT RESISTANCE AT AL-N-POLY-SI INTERFACES IN INTEGRATED CIRCUITS
NAGY Z
N11 125 1809
EFFECT OF FINITE RISE TIME OF PULSE GENERATORS ON SOME RELAXATION TECHNIQUES FOR ELECTRODE KINETIC INVESTIGATIONS
NAHORY RE POLLACK MA BEEBE ED DEWINTER JC ILEGEMS M
N7 125 1053
LIQUID PHASE EPITAXY OF ALYGA1-YAS1-XSBX AND IMPORTANCE OF STRAIN EFFECTS NEAR MISCIBILITY GAP
NAKAHARA S
N7 125 1049
LINEAR DEFECTS OBSERVED IN NICKEL ELECTRODEPOSITS
NAKAHARA S SEE LLOYD JR 125 2037
NAKAI J SEE MORITANI A 125 824
NAKAJIMA K KUSUNOKI T AKITA K KOTANI T
N1 125 123
PHASE DIAGRAM OF IN-GA-AS-P-QUATERNARY SYSTEM AND LPE GROWTH CONDITIONS FOR LATTICE MATCHING ON INP SUBSTRATES
NAKAJIMA M SEE INADA T 125 1525
NAKAJIMA Y SEE OHKAWA S 125 1997
NAKAMURA K KAMOSHID,M
N9 125 1518
IMPLANTED AS REDISTRIBUTION DURING ANNEALING IN OXIDIZING AMBIENT
NAKATANI K MATSUDAI,S TSUBOMUR,H
N3 125 406
PHOTOANODIC BEHAVIOR OF N-TYPE CADMIUM SULFIDE IN ACETONITRILE SOLUTIONS CONTAINING IODIDE ION
NAKATSUK,M TANAKA K KIKKAWA T
N11 125 1829
EFFECTS OF THIN CONDUCTIVE FILM MASK ON ION IMPLANTATION
NAKAYAMA H OSADA Y SHINDO H
N8 125 1302
ROOM TEMPERATURE INSTABILITIES OF P-CHANNEL SILICON GATE MOS TRANSISTORS
NARAYAN R SEE PILLAI KC 125 1393
NARDI JC SEE QUINLAN KP 125 1000
NASH CP
N6 125 875
STANDARD POTENTIAL OF MERCURY-MERCURIC IODATE ELECTRODE
NEEDHAM PB SEE COVINO BS 125 366
NEEDHAM PB SEE COVINO BS 125 370
NEFF VD
N6 125 886
ELECTROCHEMICAL OXIDATION AND REDUCTION OF THIN FILMS OF PRUSSIAN BLUE
NEGRINI P RAVAGLIA A SOLMI S
N4 125 609
BORON PREDEPOSITION IN SILICON USING BBR3
NELSON GC
N3 125 403
SURFACE COMPOSITION OF EQUIATOMIC ELECTRODEPOSITED TIN-NICKEL ALLOY
NELSON MG SEE JACOB KT 125 758
NELSON RP SEE HAND RL 125 1059
NEMIROVS,Y BLECH IA YAHALOM J
N7 125 1177
ABNORMAL UNDERCUTTING IN ETCHED CR-AU FILMS
NEURGAON,RR CROSS LE WHITE WB
N7 125 1130
LUMINESCENCE OF RARE EARTH-ACTIVATED TELLURATE PEROVSKITES
NEVILLE RC SEE GINSBURG,R 125 1557
NEWMAN J SEE PIERINI P 125 79
NEWMAN J SEE TRAINHAM JA 125 58
NICOLLIA,EP SCHWARTZ B KOSZI LA SCHUMAKE,NE
N6 125 989
MOS CHARACTERIZATION OF LOW LEAKAGE NATIVE OXIDES ON ALGAAS
NIINI T SEE MATSUMOT,S 125 1307
NIINI T SEE MATSUMOT,S 125 1840
NIKI K SEE UCHIDA I 125 1759
NISHI H SAKURAI T FURUYA T
N3 125 461
ELECTRICAL ACTIVATION OF IMPLANTED ARSENIC IN SILICON DURING LOW TEMPERATURE ANNEAL
NISHIMAT,S SEE WADA Y 125 1499
NISHIMOT,A SEE MIYOSHI H 125 1824
NISHIZAW,J SEE KEE RW 125 998
NITTA N KANEFUSA S HARADOME M
N10 125 1676
PROPANE GAS DETECTOR USING SNO2 DOPED WITH NB, V, TI, OR MO
NITTA T SEE MATSUOKA T 125 102
NOEE K SEE KUO MC 125 853
NORDINE PC
N3 125 498
HIGH TEMPERATURE KINETICS OF REFRACTORY METAL GASIFICATION BY ATOMIC FLUORINE
NORFOLK DJ SEE EVANS HE 125 1180
NOUFI RN KOHL PA FRANK SN BARD AJ
N2 125 246
SEMICONDUCTOR ELECTRODES .14. ELECTROCHEMISTRY AND ELECTROLUMINESCENCE AT N-TYPE TIO2 IN AQUEOUS SOLUTIONS
NOUFI RN KOHL PA BARD AJ
N3 125 375
SEMICONDUCTOR ELECTRODES .15. PHOTOELECTROCHEMICAL CELLS WITH MIXED POLYCRYSTALLINE N-TYPE CDS-CDSE ELECTRODES
NOWAK RJ KUTNER W MARK MB MACDIARM,AG
N2 125 232
BEHAVIOR OF POLYMERIC SULFUR NITRIDE, (SNNCX)X, ELECTRODES IN AQUEOUS MEDIA
NOWOTNY J SIKORA I
N5 125 781
SURFACE ELECTRICAL PROPERTIES OF WUSTITE PHASE
NOZAKI Y SEE ITO Y 125 448
OGAWA T SEE MOMMA N 125 983
OGDEN C SEE TENCH D 125 194
OGDEN C SEE TENCH D 125 1218
OGDEN C SEE TENCH D 125 1940
OGIRIMA M SAIDA M SUZUKI M NAKI M

N11 C25 1879
MULTIWAFER GROWTH SYSTEM FOR LOW PRESSURE SILICON EPITAXY
OGRADY WE SEE YEAGER E 125 348
OHKAWA S NAKAJIMA Y
N12 135 1997
THERMAL OXIDATION OF ARSENIC-DIFFUSED SILICON
OHKUBO Y SEE INADA T 135 1525
OHTSUKA Y SEE SATO M 125 1735
OKINAKA Y KOCH FB WOLOWODI.C BLESSING.DR
N11 125 1745
POLYMER INCLUSIONS IN COBALT-HARDENED ELECTROPLATED GOLD
OKUYAMA Y HASHIMOT.T KOGUCHI T
N8 135 1293
HIGH DOSE ION IMPLANTATION INTO PHOTORESIST
OLSZANSK.TW SEE MATHERS JP 125 1913
ORANSKAY.RN SEE ROSENFEL.IL 125 1729
ORD JL CLAYTON JC BRUDZEWS.K
N8 125 908
EFFECT OF ELECTROSTRICTION ON ANODIC OXIDATION OF TUNGSTEN
OREN M QUINTON AR PENCHINA CM
N5 125 776
EFFECT OF PROTON DAMAGE ON OPTICAL MODULATION SPECTRA OF GALLIUM ARSENIDE
OREN Y SOFFER A
N6 125 869
ELECTROCHEMICAL PARAMETRIC PUMPING
ORMOND DW SEE SILVESTR.VJ 125 902
OSADA Y SEE NAKAYAMA H 125 1302
OSBURN CW SEE SILVESTR.VJ 125 902
OSTERYOU.RA SEE ROBINSON J 125 1454
OSTERYOU.RA SEE ROBINSON J 125 1784
PALEOLOG EN FEDOTOVA AZ CERJAGIN.OG TOMASHOV ND
N9 125 1410
ANODIC PROCESS KINETICS ON PASSIVE SURFACES OF TITANIUM, NICKEL, AND TITANIUM-NICKEL ALLOYS
PALOMBAR.G CAMBAROT.GP PELLONI L
N12 125 1988
EVALUATION OF CORROSION RATES FROM NONLINEAR POLARIZATION DATA
PANERO S SEE FIORDIPO.P 135 511
PANICKER MP KNASTER J KROGER FA
N4 125 586
CATHODIC DEPOSITION OF COTE FROM AQUEOUS ELECTROLYTES
PAPESCHI G BORDI S CARLA M
N11 125 1807
SOLID-STATE CHLORIDE-SELECTIVE, BROMIDE-SELECTIVE OR IODIDE-SELECTIVE ELECTRODES
PARACCHI.C SEE COISSON R 125 581
PAREKH PC
N10 125 1703
SOME ASPECTS OF OXIDE ISOLATION TECHNOLOGY
PARK SH
N2 125 216
ELECTROCHEMICAL STUDIES OF BETA-CAROTENE, ALL-TRANS-RETINAL AND ALL-TRANS-RETINOL IN TETRAHYDROFURAN
PARK YS SEE DOBOS BC 125 347
PASSONI D SEE FIORITO G 125 315
PAUNOVIC M
N1 125 173
COMPUTER STUDY OF PH EFFECT IN ELECTROLESS COPPER DEPOSITION
PEARSON GL SEE HOUNG YM 125 2056
PECKERAR MC SEE MCLOUSKI RW 125 985
PEER WJ SEE TEPERANI TP 125 1717
PELTON AD SEE RIVIER M 125 1377
PENCHINA CM SEE OREN M 125 776
PERRIERE J RIGO S SIEJKA J
N9 125 1549
INVESTIGATION OF CATION-TRANSPORT PROCESSES DURING ANODIC OXIDATION OF DUPLEX LAYERS OF TANTALUM ON NIOBIUM BY USE OF RUTHERFORD BACKSCATTERING AND NUCLEAR MICROANALYSIS
PETTENPA.E SEE MUENCH WV 125 294
PEZY J SEE GNIEWEK J 125 17
PHILIPPA.JL CARADEC JY WEBER B CASSUTO A
N1 125 102
INTERACTION OF FLUORINE AND FLUORIDES WITH TANTALUM, TUNGSTEN, AND RHENIUM AT LOW PRESSURES AND HIGH TEMPERATURES
PICKETT DF HALOY JT
N7 125 1026
MICROELECTRODE STUDIES OF ELECTROCHEMICALLY COPRECIPITATED COBALT HYDROXIDE IN NICKEL HYDROXIDE ELECTRODES
PICKHARD.VY SEE SMITH DL 125 2042
PIERINI P NEWMAN J
N1 125 79
RING ELECTRODES
PILLAI KC NARAYAN R
N9 125 1393
INHIBITION OF CORROSION OF IRON IN ACIDS BY THIOUREA AND DERIVATIVES
PINSON WE
N12 125 1992
THEORY OF LIGHT-INDUCED EVOLUTION OF HYDROGEN AT SEMICONDUCTOR ELECTRODES
PISTOIA G SEE FIORDIPO.P 125 14
PISTOIA G SEE FIORDIPO.P 125 511
PLAMBECK JA SEE RAO GM 125 534
PLAMBECK JA SEE RAO GM 125 540
PLUMMER JD SEE DEAL BE 125 339
PLUMMER JD SEE MO CP 125 665
POCHAN JM SEE KUDER JE 125 1750
POLLACK GP SEE RUIZ HJ 125 128
POLLACK MA SEE NAMORY RE 125 1053
PORTER JD SEE FLETCHER S 125 1960
POTTER BD SEE DAVIES DE 125 1845
POWELL JL SEE FRIESER RG 125 492
PRENER JS SWANK RK
N4 125 583
STUDIES OF X-RAY IMAGE INTENSIFIER OUTPUT SCREENS
PRUSSIN S CLELAND JW
N2 125 350
APPLICATION OF NEUTRON TRANSMUTATION DOPING FOR PRODUCTION OF HOMOGENEOUS EPITAXIAL LAYERS
QUEIROLO G
N10 125 1672
SPREADING RESISTANCE MEASUREMENTS ON GALLIUM ARSENIDE
QUINLAN KP MUTTA JJ HUSSEY CL NARCI JC
KING LA ERRACHER JK
N6 125 1000
ELECTROLYTIC ETCHING OF ALUMINUM FROM AN AL-ALSNI 2-PHASE MATRIX IN ALUMINUM CHLORIDE CONTAINING MOLTEN SALTS
QUINN RK ARMSTRON.WA
N11 125 1790
ELECTROCHEMICAL AND SURFACE ANALYTICAL CHARACTERIZATION OF TITANIUM AND TITANIUM HYDRIDE THIN FILM ELECTRODE OXIDATION
QUINTANA G SEE SINHA AK 125 601
QUINTON AR SEE OREN M 125 776
RABATIN JG
N6 125 920
LUMINESCENCE OF IRON-ACTIVATED LITHIUM METAGALLATE
RAIDER SI BERMAN A
N4 125 629
NATURE OF FIXED OXIDE CHARGE
RAMANARA.TA JCSE PD
N10 125 1684
INVESTIGATIONS OF DIFFUSION AND NONSTOICHIOMETRY IN CUPROUS SULFIDE AT 400-DEGREES-C
RAND MJ MONSIEBLE.GW
N1 125 99
OPTICAL ABSORPTION AS A CONTROL TEST FOR PLASMA SILICON NITRIDE DEPOSITION
RAO BHL SEE CHIANELL.RR 125 1563
RAO DB SEE JACOB KT 125 758
RAO GM LCWN JW PLAMBECK JA
N6 125 534
ELECTROCHEMICAL STUDIES OF ANTITUMOR ANTIBIOTICS .3. DAUNORUBICIN AND ADRIAMYCIN
RAO GM LCWN JW PLAMBECK JA
N4 125 540
ELECTROCHEMICAL STUDIES OF ANTITUMOR ANTIBIOTICS .4. ELECTROCHEMICAL STUDIES OF DAUNOMYCINONE ANALOGUES
RAPP RA SEE FANG WC 125 683
RAUB CJ SEE COHEN RE 125 34
RAUH RD REISE TF BRUMMER SB
N2 125 186
EFFICIENCIES OF CYCLING LITHIUM ON A LITHIUM SUBSTRATE IN PROPYLENE CARBONATE
RAUH RD SEE GARREAU M 125 1990
RAVAGLIA A SEE MEGRINI P 125 609
RAY AK KROGER FA
N8 125 1348
DEFECT STRUCTURE OF PURE AND DOPED ZNSE
RAY AK KROGER FA
N8 125 1355
DEFECT STRUCTURE OF ZNSE-GA
READ MH SFE MURARKA SP 125 156
REICHMAN.M MARINO AA BECKER RO
N11 125 1765
LAPLACE PLANE ANALYSIS OF SKIN IMPEDANCE - PRELIMINARY INVESTIGATION
REIF R SARASWAT KC KAMINS TI
N11 125 1060
TRANSIENT AND STEADY-STATE RESPONSE OF DOPANT SYSTEM OF A SILICON EPITAXIAL REACTOR - TRANSFER-FUNCTION APPROACH
REISE TF SEE GARREAU M 125 1990
REISE TF SEE RAUH RD 125 186
REISS H
N6 125 937
PHOTOCHARACTERISTICS FOR ELECTROLYTE-SEMICONDUCTOR JUNCTIONS
RENNER J SEE HARKE CJ 125 C455
RIGO S SEE PERRIERE J 125 1549
RIVIER M PELTON AD
N9 125 1377
THERMODYNAMIC PROPERTIES OF LIQUID NA-SN ALLOYS BY EMF MEASUREMENTS WITH BETA-ALUMINA ELECTROLYTES
ROBBINS M BACHMANN KJ LAMBRECH.VG TWIEL FA
THOMSON J VADIMSKY RG MENEZES S
HELLER A MILLER B
N5 125 831
CUINS2 LIQUID JUNCTION SOLAR CELLS
ROBINSON J OSTERYOU.RA
N9 125 1454
ELECTROCHEMICAL BEHAVIOR OF SELENIUM AND SELENIUM COMPOUNDS IN SODIUM TETRACHLOROALUMINATE MELTS
ROBINSON J OSTERYOU.RA
N11 125 1784
ELECTROCHEMICAL BEHAVIOR OF TERIVC IN SODIUM TETRACHLOROALUMINATE MELTS
ROCCO WA SFE URQUHART AW 135 199
ROSEN A SWARTZ GA QUIGON FC GOMBAR AM
N4 125 680
SIMPLE METHOD OF FABRICATING AND PASSIVATING HIGH POWER PIN DIODES
ROSENFEL.IL DANILOV II ORANSKAY.RN
N11 125 1729
BREAKDOWN OF PASSIVE STATE AND REPASSIVATION OF STAINLESS STEELS
ROSNOWSK.W
N6 125 957
ALUMINUM DIFFUSION INTO SILICON IN AN OPEN TUBE HIGH VACUUM SYSTEM
ROY AS
N7 125 1110
PRACTICAL ELECTROCHEMICAL TRANSPORT EQUATION FOR CONCENTRATED SOLUTIONS
RUIZ HJ POLLACK GP
N1 125 128
HIGH TEMPERATURE ANNEALING BEHAVIOR OF OXYGEN IN SILICON
RUNG RD SEE DAVANZO DC 125 1170
RUSSELL AR SEE WEININGE.JL 125 1482
RUTHARDT R SEE EISELE KH 125 1188
RYAN FM WARREN RW HOPKINS RH MURPHY J
N9 125 1493
SELECTIVE SITE LASER EXCITATION AND ESR STUDIES OF ND-3+ IONS IN CASRPO4:F
RYAN RO
N4 125 547
EFFECT OF SLOW 2-ELECTRON TRANSFERS AND DISPROPORTIONATION ON CYCLIC VOLTAMMOGRAMS
RZYMAN K SEE MOSER Z 125 692
SAATHOFF DJ SEE VENKATAS.MV 125 1974
SABOURGE ML MARR JJ BLANDER M
N10 125 1567
SOLUBILITY PRODUCTS OF METAL SULFIDES IN MOLTEN SALTS - MEASUREMENTS AND CALCULATIONS FOR IRON SULFIDE MFESC IN LICL-KCL EUTECTIC COMPOSITION
SAIDA M SEE OGIRIMA M 125 1879
SAKURAI T SEE NISHI M 125 461
SALKIND AJ FERRELL DT HEDGES AJ
N8 125 C311
SECONDARY BATTERIES - 1952-1977
SAMMELLS AF
N10 125 1632
LITHIUM-BORON-SILICON ALLOY LITHIUM ELECTRODES
SANI RL SEE ALKIRE R 125 1981
SANTORO GJ BARRETT CA
N2 125 271
MOLY CORROSION RESISTANCE OF NICKEL-CHROMIUM-ALUMINUM ALLOYS
SANZ JM SEE ALBELLA JM 125 1950
SARADA T GRANATA RD FOLEY RT
N12 125 1899
PROPERTIES OF TRIFLUOROMETHANESULFONIC ACID NONHYDRATE PERTINENT TO ITS USE AS A FUEL CELL ELECTROLYTE
SARASWAT KC SEE KAMINS TI 125 927
SARASWAT KC SEE REIF R 125 1060
SARTWELL BD SEE COVINO BS 125 306
SASAKI A SEE TAKEDA Y 125 130
SATO M OHTSUKA T
N11 125 1735
ANODIC OXIDATION OF COBALT IN NEUTRAL AND BASIC SOLUTION
SATO Y SEE KANNO K 125 1389
SAWADA S SEE INADA T 125 1525
SAWYER PN
N10 125 C419
APPLICATION OF ELECTROCHEMICAL TECHNIQUES TO SOLUTION OF PROBLEMS IN MEDICINE
SCANLON JC SEE CHIANELL.RR 125 1563
SCHIANCH.G SEE COISSON R 125 581
SCHIAVON.LN
N4 125 522
ELECTROLESS GOLD METALLIZATION FOR POLYVINYLIDENE FLUORIDE FILMS
SCHIFFRI.OJ SEE ESTEVEZ SB 125 1989
SCHIMMEL DG ELKIND MJ
N1 125 152
EXAMINATION OF CHEMICAL STAINING OF SILICON
SCHMEAL WR SEE ELLISON BT 125 524
SCHMID GM SEE EVERETT KG 125 389
SCHMIDT WA SEE ANDERSON GW 125 424
SCHOONMA.J SEE BONNE RW 125 1628
SCHREBLE.RS VILCHE JR ARVIA AJ
N10 125 1578
RATE PROCESSES RELATED TO HYDRATED NICKEL HYDROXIDE ELECTRODE IN ALKALINE SOLUTIONS
SCHREURS JJ SEE MCLOUSKI RW 125 985
SCHUBERT R
N7 125 1114
INTERACTION OF NOX AND CU AT VARIOUS RELATIVE HUMIDITIES
SCHUBERT R
N8 125 1215
ANALYSIS OF SNNI ELECTROPLATE BY SECONDARY ION MASS SPECTROMETRY, ION SCATTERING SPECTROMETRY, AND RUTHERFORD BACKSCATTERING
SCHULZ MJ SEE DEAL BE 125 2024
SCHUMAKE.NE SEE NICOLLIA.EP 125 985
SCHWARTZ B SFE NICOLLIA.EM 125 989
SCHWARTZ GP SEE MELLER A 125 1156
SCHWARTZ N EACEN DD
N9 125 1487
SEAT - SIMULATED ENVIRONMENT ACCELERATED TEST
SCHWARTZ N AUGUSTYN.WM
N11 125 1812
TANTALUM ION TRANSPORT NUMBER DURING ANODIC OXIDATION OF BETA-TANTALUM FILMS
SEARCY AW SEE KNUTSEN GP 125 327
SEKI M SEE UMAGAMI T 125 1339
SEN RK SFE ZURILLA RW 125 1103
SERAPHIN BO SEE CARVER GE 125 1138
SETTLE J SEE MELENDRE.CA 125 1866
SHANKOFF TA CHANG CC HASZKO SE
N3 125 467
CONTROLLING INTERFACIAL OXIDE LAYER OF TI-AL CONTACTS WITH CRO3-H3PO4 ETCH
SHAPPIR J SEE KOLODNY A 125 1530
SHARMA DL SEE TALWAR IN 125 434
SHARMA SP THOMAS JH
N10 125 1610
FILM GROWTH ON DILUTE NOBLE METAL ALLOYS
SHARMA SP THOMAS JH BADER FE
N12 125 2002
DEVELOPMENT OF A GENTLE ACCELERATED CORROSION TEST
SHARMA SP
N12 125 2005
ATMOSPHERIC CORROSION OF SILVER, COPPER, AND NICKEL - ENVIRONMENTAL TEST
SHENG TT MARCUS RB
N3 125 432
GATE OXIDE THINNING AT ISOLATION OXIDE WALL
SHENG TT SEE CHANG CC 125 787
SHENG TT SEE MURARKA SP 125 156
SHERWOOD WG UNTEREKE.DF BRUCKENS.S
N3 125 384
COULOSTATIC DEPOSITION OF METALS AT UNDERPOTENTIAL .II. EFFECT OF HETEROGENEOUS CHEMICAL REACTIONS ON POTENTIAL RELAXATION PROCESS
SHERWOOD WG BRUCKENS.S
N7 125 1098
ROTATING RING-DISK ELECTRODE STUDY OF UNDERPOTENTIAL DEPOSITION OF MERCURY ON GOLD
SHERWOOD WG SEE UNTEREKE.DF 135 380
SHIMIZU S
N7 125 1126
CHEMICAL MECHANISMS IN PHOTORESIST SYSTEMS .2. THERMAL REACTIONS OF A BISAZIDE RESIST
SHIMURA M
N2 125 190
BEHAVIOR OF MALEIC ACID DURING ANODIZATION OF ALUMINUM
SHINOD M SEE NAKAYAMA M 125 1302
SHINODA M SEE ITO T 125 448
SHINTANI A TAKANO Y MINAGAWA S WAKI M
N12 125 2076
X-RAY DIFFRACTION TOPOGRAPHY AND CRYSTAL CHARACTERIZATION OF GAN EPITAXIAL LAYERS FOR LIGHT-EMITTING DIODES
SHIOTA I SEE KEE RW 125 998
SHOMIO K SEE TAKENAKA T 125 633
SHORES DA SEE MCKEE DW 125 411
SIEGEL S SEE MELENDRE.CA 125 1866
SIEJKA J SEE PERRIERE J 125 1549
SIKORA I SEE NOWOTNY J 125 781
SILVESTR.VJ CSBURN CW ORMOND DW
N6 125 902
PROPERTIES OF AL2O3 FILMS DEPOSITED FROM ALCL3, CO2, AND H2 SYSTEM
SIM JW SEE SWAROOP RB 125 1799
SIMKOVIC.G
N5 125 C227
WAGNER.CARL 1901-1977
SIMMONS GW SEE VEPTES A 125 1948
SINCLAIR JD
N5 125 734
INSTRUMENTAL GRAVIMETRIC METHOD FOR INDEXING MATERIALS, CONTAMINANTS, AND CORROSION PRODUCTS ACCORDING TO THEIR HYGROSCOPICITY
SINCLAIR WR LIN LH GALLAGHE.PK FASTNACH.RA
N6 125 950
SOME PROPERTIES OF PALLADIUM PHOTOCATHODES USED IN ELECTRON IMAGE PROJECTION SYSTEM XELIPSC
SINGH BR BALK P
N3 125 453
OXIDATION OF SILICON IN PRESENCE OF CHLORINE AND CHLORINE COMPOUNDS
SINHA AK LEVINSTE.MJ SMITH TE QUINTANA G
HASZKO SE
N4 125 601
REACTIVE PLASMA DEPOSITED SI-N FILMS FOR MOS-LSI PASSIVATION
SINHA AK SMITH TE
N5 125 743
KINETICS OF SLOW-TRAPPING INSTABILITY AT SI-SIO2 INTERFACE
SINHA AK SEE CHANG CC 125 787

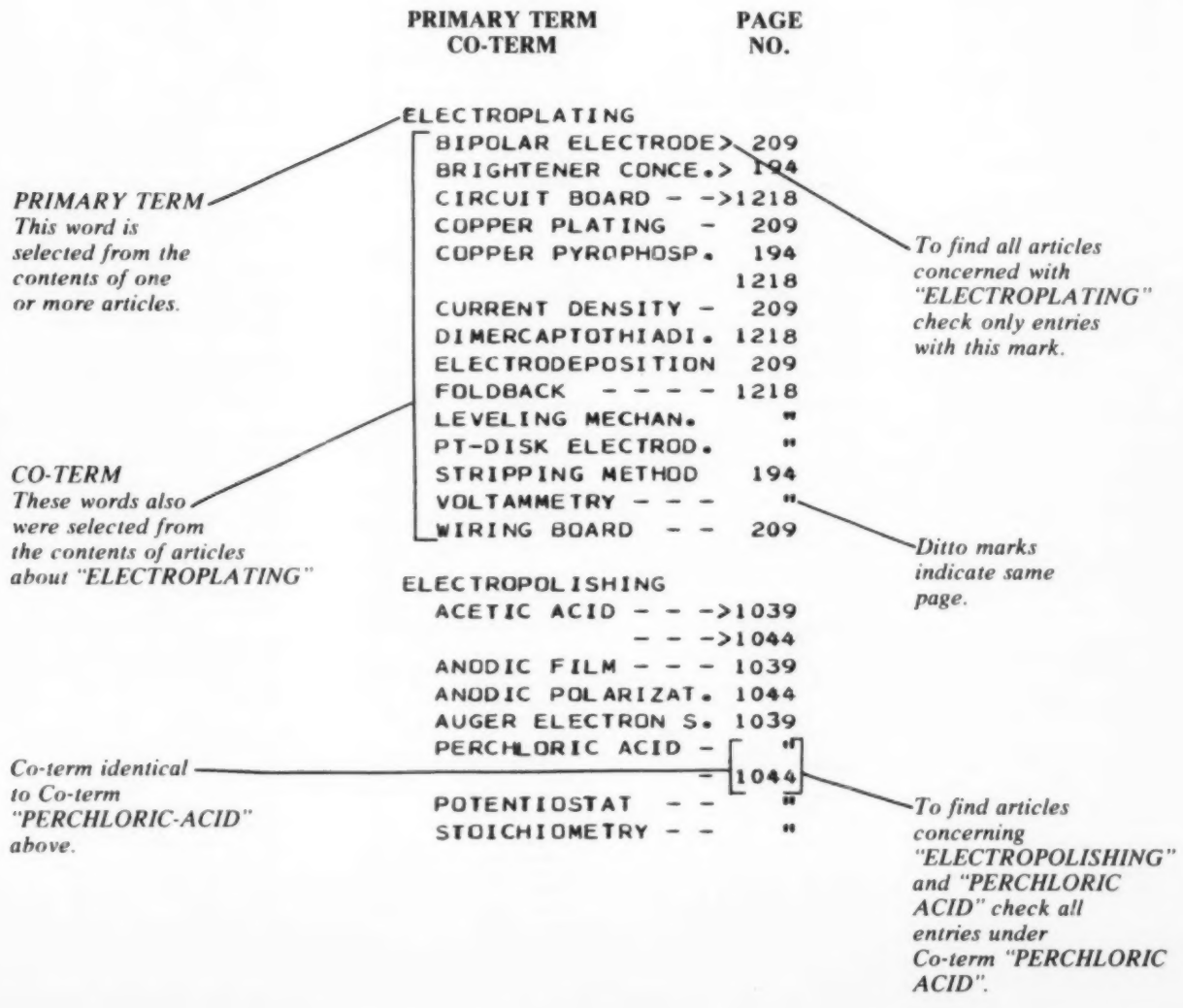
SINHA M BENNION DN
N4 125 556
TRANSPORT PARAMETERS FOR POTASSIUM HYDROXIDE-WATER SOLUTION IN A CATION EXCHANGE MEMBRANE
SINIGAGL.D YACCANI G VICENTIN.B DALLASPE.G
N8 125 1199
ELECTROCHEMICAL BEHAVIOR OF TITANIUM AND SOME TITANIUM ALLOYS UNDER TENSILE STRESS IN BOILING SULFURIC ACID AND ACIDIC CHLORIDE SOLUTIONS
SMEGGIL JG BORNSTEI.NS
N8 125 1203
EFFECT OF NACL%GC ON OXIDATION OF NIAL
SMELTZER WW WHITTLE DP
N7 125 1116
CRITERION FOR ONSET OF INTERNAL OXIDATION BENEATH EXTERNAL SCALES ON BINARY ALLOYS
SMITH DL PICKHARD.VY
N12 125 2042
IMPURITY DOPANT INCORPORATION AND DIFFUSION DURING MOLECULAR BEAM EPITAXIAL GROWTH OF IV-VI-SEMICONDUCTORS
SMITH RT SEE WEITZEL CE 125 792
SMITH V LINDBERG G
N8 125 1224
SURFACE PROPERTIES OF NICKEL AFTER EACH STEP OF ACTIVATION PROCESS FOR NICKEL PLATING
SMITH TE SEE SINHA AK 125 601
SMITH TE SEE SINHA AK 125 743
SMITH W SEE WARGEL S 125 241
SOFFER A SEE OREN Y 125 869
SOLLBERG.F SEE DUTOIT M 125 1648
SOLMI S SEE NEGRINI P 125 609
SOUTHWIC.LH SEE KESZTHEL.CP 125 714
SRINIVAS.GR
N1 125 146
KINETICS OF LATERAL AUTODOPING IN SILICON EPITAXY
SRINIVAS.S SEE LU PWT 125 265
SRINIVAS.S SEE LU PWT 125 1416
SRINIVAS.S SEE NILES MH 125 1931
STACH J SEE MONKOWSK.J 125 1667
STACH J SEE MONKOWSK.J 125 2083
STAEHLE RW SEE GALVELE JR 125 1204
STEELE BCH SEE DUDLEY GJ 125 1994
STETTER JR BLURTON KF VALENTIN.AM TELLEFSE.KA
N11 125 1804
ELECTROCHEMICAL OXIDATION OF HYDRAZINE AND METHYLHYDRAZINE ON GOLD - APPLICATION TO GAS MONITORING
STEVELS ALN
N4 125 568
CE-3+ LUMINESCENCE IN HEXAGONAL ALUMINATES CONTAINING LARGE DIVALENT OR TRIVALENT CATIONS
STEVENS MT
N2 125 288
CATHODOLUMINESCENCE MEASUREMENT TECHNIQUES
STEVENSO.DA SEE LIU SS 125 1161
STEVENSO.JL SEE FAKTOR MM 125 621
STOCK JT SEE WOLTER KO 125 531
STREHBLO.HH DOHERTY CJ
N1 125 30
EXAMINATION OF ALUMINUM COPPER FILMS DURING ANODIC OXIDATION .1. CORROSION STUDIES
STREHBLO.HH WELLIARS.CM AUGUSTYN.WM
N6 125 915
EXAMINATION OF ALUMINUM-COPPER FILMS DURING GALVANOSTATIC FORMATION OF ANODIC OXIDE .2. RUTHERFORD BACKSCATTERING AND DEPTH PROFILING
SUMNER BE FOLEY RT
N11 125 1817
LIQUID-PHASE EPITAXIAL GROWTH OF GALLIUM-DOPED SILICON
SUNAMI H
N6 125 892
THERMAL OXIDATION OF PHOSPHORUS-DOPED POLYCRYSTALLINE SILICON IN WET OXYGEN
SUNSERI C SEE DIPAOLA A 125 1344
SUZUKI A WATSUNAM.H TANAKA T
N11 125 1896
AUGER ELECTRON SPECTROSCOPY ANALYSIS OF THERMAL OXIDE LAYERS OF SILICON CARBIDE
SUZUKI H SEE KANNO K 125 1389
SUZUKI H SEE CGIRIMA H 125 1879
SVENSSON CM SEE CORKER GA 125 1981
SWAN T SEE EVANS HE 125 1180
SWANK RK SEE PRENER JS 125 583
SWAROOP RB SIM JW KINOSHIT.K
N11 125 1799
CORROSION PROTECTION OF MOLTEN CARBONATE FUEL CELL GAS SEALS
SWARTZ GA SEE ROSEN A 125 680
SY CC SEE MELENDRE.CA 125 727
TACCANI G SEE SINIGAGL.D 125 1199
TAFT EA
N6 125 968
OPTICAL CONSTANTS OF SILICON AND DRY OXYGEN OXIDES OF SILICON AT 5461A
TAKAGI H KANO G TERAMOTO I
N4 125 579
THERMAL OXIDATION OF GAAS IN ARSENIC TRIOXIDE VAPOR
TAKAGI T SEE TAKEDA Y 125 130
TAKAHJ Y SEE SHINTANI A 125 2076
TAKEDA Y SASAKI A IMAMURA Y TAKAGI T
N1 125 130
PROPERTIES OF LIQUID PHASE EPITAXIAL IN1-XGAXAS 1X-APPROXIMATELY-EQUAL-0.5C ON INP SUBSTRATE
TAKENAKA T TAKIGAWA H SHOMNO K
N4 125 633
DIFFUSION LAYERS FORMED IN SI SUBSTRATES DURING EPITAXIAL GROWTH OF BP AND APPLICATION TO DEVICES
TAKIGAWA H SEE TAKENAKA T 125 633
TALWAR IN SHARMA DL
N3 125 434
THERMALLY STIMULATED DEPOLARIZATION STUDIES OF PVC POLYMER ELECTRETS
TAMURA H SEE YONEYAMA H 125 68
TANAKA K SEE NAKATSUK.M 125 1829
TANAKA Y SEE SUZUKI A 125 1896
TANIGAKI Y IWAMATSU S HIROBE K
N3 125 471
NEW SELF-ALIGNED CONTACT TECHNOLOGY
TANIGUCH.M SEE MOMMA N 125 963
TANNAUS.DS
N6 125 1277
THEORETICAL ENERGY CONVERSION EFFICIENCY OF A HIGH TEMPERATURE FUEL CELL BASED ON A MIXED CONDUCTION
TAYLOR DF
N5 125 808
THERMODYNAMIC PROPERTIES OF METAL-WATER SYSTEMS AT ELEVATED TEMPERATURES
TEHERANI TH PEER WJ LAGOWSKI JJ BARD AJ
N10 125 1717
ANODIC ELECTRODEPOSITION OF GOLD FROM LIQUID AMMONIA SOLUTIONS
TELLEFSE.KA SEE STETTER JR 125 1804
TEMPERON.C SEE FIORDIPO.P 125 14
TEMPERON.C SEE FIORDIPO.P 125 511
TENCH D OGDEN C
N2 125 194
NEW VOLTAMMETRIC STRIPPING METHOD APPLIED TO DETERMINATION OF BRIGHTENER CONCENTRATION IN COPPER PYROPHOSPHATE PLATING BATHS
TENCH D OGDEN C
N8 125 1218
FUNCTIONING AND MALFUNCTIONING OF DIMERCAPTOTHIADIAZOLES AS LEVELING AGENTS IN CIRCUIT BOARD PLATING FROM COPPER PYROPHOSPHATE BATHS
TENCH D OGDEN C
N12 125 1940
EFFECT OF DEPASSIVATION AT SPECIFIC CRYSTAL FACETS ON STATE OF ACTIVATION OF NICKEL SUBSTRATES FOR ELECTRODEPOSITION
TERAMOTO I SEE TAKAGI H 125 579
THEVENIN J SEE GARREAU M 125 1990
THIEL FA SEE ROBBINS M 125 831
THOMAS JH
N6 125 898
OXIDATION KINETICS OF COBALT DIFFUSING OUT OF HIGH CURRENT DENSITY KHCDC PLATED GOLD
THOMAS JH SEE SHARMA SP 125 1610
THOMAS JH SEE SHARMA SP 125 2002
THOMPSON GE FURNEAUX RC WOOD GC HUTCHING.R
N9 125 1480
STEM-EDAX ANALYSIS OF CELL WALLS IN POROUS ANODIC FILMS FORMED ON ALUMINUM
THOMSON J SEE ROBBINS M 125 831
THURBER WA CARPENTE.BS
N4 125 654
BORON DETERMINATION IN SILICON BY NUCLEAR TRACK TECHNIQUE
THURBER WR SEE BUEHLER MG 125 645
THURBER WR SEE BUEHLER MG 125 650
TIEN HT MOUNTZ JM
N6 125 885
PHOTOGALVANIC EFFECT IN A MODIFIED IRON THIONINE SYSTEM
TOBIAS CW
N5 125 C217
GERISCHER,HEINZ - PALLADIUM MEDALIST
TODD LT
N7 125 1133
INVESTIGATION OF LUMINESCENCE IN GE-DOPED SODALITE POWDERS
TOLK NH SEE TSONG IST 125 2015
TOMASHOV ND SEE PALEOLOG EN 125 1410
TOMKINS OF WAGENKNE.JH
N3 125 372
HPLC ANALYSIS OF STEREOISOMERS OBTAINED BY ELECTROHYDRODIMERIZATION OF PARA-HYDROXYBENZALDEHYDE
TOMLINSO.WJ MENZIES IA
N2 125 279
OXIDATION OF AN FE-9 W-6 NI ALLOY IN CO2 AT 700-DEGREES-1000-DEGREES-C
TOMLINSO.WJ YATES J
N5 125 803
OXIDATION OF COPPER IN CO2 AT 800-DEGREES-1000-DEGREES-C
TOURILLO.G DUBOIS JE LACAZE PC
N8 125 1262
POLAROMICROTRIBOMETRIC %PHT< AND SPECTROSCOPIC %INFRARED-XPS< STUDY OF FORMATION AND MODIFICATIONS OF FILMS FORMED ON A POLARIZED PLATINUM ELECTRODE IN THF-LICLO4 MEDIUM .2. ANODIC POLARIZATION
TOURILLO.G SEE DUBOIS JE 125 1257
TOWNSEND ME ZOCCOLA JC
N8 125 1290
CHROMATE PASSIVATION PROTECTION OF ZN-COATED AND AL-ZN-COATED STEEL SHEET AGAINST WET-STORAGE STAIN
TRAINHAM JA NEWMAN J
N1 125 58
EFFECT OF ELECTRODE PLACEMENT AND FINITE MATRIX CONDUCTIVITY ON PERFORMANCE OF FLOW-THROUGH POROUS ELECTRODES
TRANCHAR.JC HOLLAN L MENNING R
N7 125 1185
LOCALIZED AVALANCHE BREAKDOWN ON GAAS ELECTRODES IN AQUEOUS ELECTROLYTES
TRESSLER RE SEE MONKOWSK.J 125 1867
TRESSLER RE SEE MONKOWSK.J 125 2083
TRIBUTSC.H
N7 125 1086
HOLE REACTIONS FROM D-ENERGY BANDS OF LAYER-TYPE GROUP-VI TRANSITION METAL DICHALCOGENIDES - NEW PERSPECTIVES FOR ELECTROCHEMICAL SOLAR ENERGY CONVERSION
TSAI JCC SEE FAJR RB 125 2050
TSAI JCC SEE KROGER FA 125 995
TSAI KC SEE LITTAUER EL 125 845
TSANG CH SEE CHIN DT 125 1461
TSEUNG ACC YEUNG KLK
N6 125 1003
REDUCTION OF OXYGEN ON TEFLON-BONDED NICO204-GRAPHITE ELECTRODES
TSEUNG ACC
N10 125 1660
SEMICONDUCTING OXIDE OXYGEN ELECTRODES
TSEUNG ACC SEE HIBBERT DB 125 74
TSEUNG ACC SEE YEUNG KLK 125 878
TSONG IST CORREDOR A WHITE WE TOLK NH KRAUS JF
N12 125 2015
ESTIMATION OF QUANTUM YIELD IN CANDOLUMINESCENCE PROCESS BY LOW ENERGY HG ION BOMBARDMENT
TSUBOMUR.H SEE NAKATANI K 125 406
TSUBOUCH.N SEE MIYOSHI H 125 1824
TSUCHIYA H SEE MATSUOKA T 125 102
TUMMALA RR SEE FRIESER RG 125 492
TURNER SR SEE KUDER JE 125 1750
TYMA PD
N7 125 C264
FINK,COLIN,GARFIELD SUMMER FELLOWSHIP REPORT - DETERMINATION OF KINETIC PARAMETERS FROM POLAROGRAPHIC DATA OBTAINED AT SHORT-SAMPLING TIMES
UCHIDA I NIKI K LAITINEN HA
N11 125 1759
SOME REDOX REACTIONS ON SEMICONDUCTING TIN OXIDE ELECTRODES IN MOLTEN LICL-KCL EUTECTIC AT 450-DEGREES-C
UCHIDA I SEE LAITINEN HA 125 1450
UHLIG HH
N2 125 C 58
ADVANCES IN CORROSION OVER PAST 25 YEARS
UNAGAMI T SEKI H
N8 125 1339
STRUCTURE OF POROUS SILICON LAYER AND HEAT-TREATMENT EFFECT
UNTEREKE.DF SHERWOOD WG BRICKENS.S
N3 125 380
COULOSTATIC DEPOSITION OF METALS AT UNDERPOTENTIAL .1. POTENTIAL RELAXATION IN ABSENCE OF CHEMICAL REACTIONS
UNTEREKE.DF
N12 125 1907
USE OF A MICROCALORIMETER FOR ANALYSIS OF LOAD-DEPENDENT PROCESSES OCCURRING IN A PRIMARY BATTERY
UNTEREKE.DF SEE SHERWOOD WG 125 384
UOSAKI K SEE BOCKRIS JO 125 223
URA M SEE MOMMA N 125 983
URQUHART AW VERMILYE.DA ROCCO WA
N2 125 199
MECHANISM FOR EFFECT OF HEAT-TREATMENT ON ACCELERATED CORROSION OF ZIRCALOY-4 IN HIGH TEMPERATURE, HIGH PRESSURE STEAM
VAALER LE
N2 125 204
ELECTROLYTIC PURIFICATION OF NICKEL PLATING SOLUTIONS
VACINSKY RG SEE HELLER A 125 1156
VACINSKY RG SEE ROBBINS M 125 831
VALENTIN.AM SEE STETTER JR 125 1804
VALLET CE BRAUNSTE.J
N8 125 1193
STEADY-STATE COMPOSITION PROFILES IN MIXED MOLTEN SALT ELECTROCHEMICAL DEVICES .1. LITHIUM-SULFUR BATTERY ANALOGS
VANDERLE.GA SEE CHU TL 125 661
VANDERLE.M
N8 125 1361
POSSIBILITY OF BLACK ZINC OXIDE AS SPECTRALLY SELECTIVE COATING FOR LOW TEMPERATURE SOLAR COLLECTORS
VARSANYI ML SEE VERTES A 125 1946
VENKATAS.MV SAATHOFF DJ
N12 125 1974
CONDUCTANCE, CYCLIC VOLTAMMETRIC, AND INFRARED SPECTRAL STUDIES OF ELECTROLYTES IN DIMETHYL SULFOXIDE
VERMILYE.DA SEE URQUHART AW 125 199
VERTES A LEIDMEIS.H VARSANYI ML SIMMONS GW KISS L
N12 125 1965
MOSSBAUER STUDIES OF PASSIVE FILM FORMED ON TIN IN BORATE BUFFER
VICENTIN.B SEE SINIGAGL.D 125 1199
VILCHE JR SEE SCHREBLE.RS 125 1578
VISWANAT.K CHEN HY
N10 125 1616
APPLICATION OF PULSED CURRENT ELECTROLYSIS TO A ROTATING-DISK ELECTRODE SYSTEM .2. ELECTROCHEMICAL KINETICS
VISWANAT.K FARRELLE.MA CHEN HY
N11 125 1772
APPLICATION OF PULSED CURRENT ELECTROLYSIS TO A ROTATING-DISK ELECTRODE SYSTEM .1. MASS TRANSFER
VLASOV YG SEE HACKLEWA.D 125 1875
VOGEL WM SEE BORUCKA A 125 888
VOEK RW SEE CAIN OJ 125 882
VUKOVIC M SEE HADZIJOR.S 125 1471
WACA Y NISHIMAT.S
N9 125 1499
GRAIN GROWTH MECHANISM OF HEAVILY PHOSPHORUS-IMPLANTED POLYCRYSTALLINE SILICON
WAGENKNE.JH SEE TOMKINS OF 125 372
WAGNER JB SEE JOO T 125 613
WAGNER S SEE MOHAPATR.SK 125 1603
WAKEFIEL.GB SEE CHU TL 125 595
WALKER GH CONWAY EJ
N4 125 676
ANNEALING OF GAAS SOLAR CELLS DAMAGED BY ELECTRON IRRADIATION
WALKER GH CONWAY EJ
N10 125 1726
RECOVERY OF SHALLOW JUNCTION GAAS SOLAR CELLS DAMAGED BY ELECTRON IRRADIATION
WALKER GH BYVIK CE CONWAY EJ HEINBOCK.JH OOVIAK WJ
N12 125 2034
ANALYTICAL AND EXPERIMENTAL STUDY OF 1 MEV ELECTRON IRRADIATED GAALAS-GAAS HETEROFACE SOLAR CELLS
WALLACE WL BARD AJ
N9 125 1430
ELECTROGENERATED CHEMILUMINESCENCE .32. ECL FROM ENERGY-DEFICIENT AROMATIC HYDROCARBON ACCEPTOR AND TETRATHIAFULVALENE DONOR SYSTEMS
WANG EY HSU L
N8 125 1328
DETERMINATION OF ELECTRON AFFINITY OF IN2O3 FROM ITS HETEROJUNCTION PHOTOVOLTAIC PROPERTIES
WANG KL
N10 125 1664
QUENCHED-IN BULK DEFECTS AND INTERFACE STATES IN MOS STRUCTURES MEASURED BY TRANSIENT CAPACITANCE SPECTROSCOPY
WARD ID SEE ZAHAVI J 125 574
WARIN D SEE GARREAU M 125 1990
WARREN RW SEE RYAN FM 125 1493
WATANABE N SEE MORI Y 125 1510
WEBER B SEE PHILIPPA.JL 125 182
WEININGE.JL RUSSELL RR
N9 125 1482
CORROSION OF RUTHENIUM OXIDE CATALYST AT ANODE OF A SOLID POLYMER ELECTROLYTE CELL
WEITZEL CE SMITH RT
N5 125 792
SILICON-ON-SAPPHIRE CRYSTALLINE PERFECTION AND MOS TRANSISTOR MOBILITY
WEPPNER W HUGGINS RA
N1 125 7
THERMODYNAMIC PROPERTIES OF INTERMETALLIC SYSTEMS LITHIUM-ANTIMONY AND LITHIUM-BISMUTH
WERKMCVE.C
N4 125 671
DISCLOSURE OF DISLOCATION LOOPS AND DISLOCATION DIPOLES IN GAP BY CHEMICAL ETCHING
WHITE DA COLEMAN JP
N9 125 1401
SYNTHESES WITH ELECTROGENERATED HALOGENS .3. OXIDATION OF PRIMARY ALCOHOLS TO ACETALS OF 2-HALOALDEHYDES
WHITE WB SEE NEURGAON.RR 125 1130
WHITE WB SEE TSONG IST 125 2015
WHITTLE DP SEE SWELTZER WW 125 1116
WIDMER AE HITCHMAN ML
N10 125 1723
OXYGEN DETERMINATION IN SIPOS USING A DIFFERENTIAL THICKNESS MEASUREMENT
WILDES PD SEE HALL DE 125 1385
WILLIS GM SEE KESZTHEL.CP 125 714
WILSON H SEE KUPPERS D 125 1298
WIRKKALA J SEE HAMBY D 125 1020
WITT AF GATOS HC LICHTENS.W HERMAN CJ
N11 125 1832
CRYSTAL GROWTH AND SEGREGATION UNDER ZERO GRAVITY - GE
WITT AF SEE KIM KM 125 475

WITTSTOC,S SEE CRODKE M 125 166
WOLOWODI,C SEE OKINAKA Y 125 1745
WOLTER KO STOCK JT
N4 125 531
PREPARATIVE ELECTROLYSES AT GRAPHITE PASTE ANODES
WONSIOLE,CP SEE RAND MJ 125 99
WOO NYC SEE YEAGER E 125 348
WOOD GC SEE THOMPSON GE 125 1480
WOOLLEY JC SEE GRATTON MF 125 657
YAHALOM J SEE NEMIROVS,Y 125 1177
YAMAGUCH,S
N7 125 1191
DEVICE OF ELECTROSTATIC LENS FOR ELECTRON MICROSCOPY
YAMAMURA Y SEE LAITINEN HA 125 1450
YANG MT SEE CHU SS 125 1660
YANEV M SEE LASER D 125 358
YAO NP SEE CHOI KW 125 1011
YARNELL CF
N12 125 1934
PASTE MIXING AND CURING OF TETRABASIC LEAD SULFATE PLATES FOR LEAD-ACID BATTERY
YASUI I DORENKS RH
N7 125 1007
EFFECTS OF CALCIUM, POTASSIUM, AND IRON IONS ON DEGRADATION OF BETA88-ALUMINA
YATES J SEE TOMLINSO,WJ 125 803
YEAGER E OGRADY WE WOO NYC HAGANS P
N2 125 348
HYDROGEN ADSORPTION ON SINGLE CRYSTAL PLATINUM
YEAGER E SEE ZURILLA RW 125 1103
YEUNG KLK TSEUNG ACC
N6 125 870
REDUCTION OF OXYGEN ON TEFLON-BONDED PEROVSKITE OXIDE ELECTRODES
YEUNG KLK SEE TSEUNG ACC 125 1003
YONEYAMA H MAYUMI S TAMURA H
N1 125 60
EXTENSION OF SPECTRAL RESPONSE OF P-TYPE GALLIUM PHOSPHIDE ELECTRODES BY METAL ACATONS
YOO HI SEE CHU TL 125 661
YOSHIE O KAMIHARA M
N6 125 993
PHASE-MEMORY EFFECT IN A P-TYPE PHOTOCONDUCTOR
YOUNG DR SEE DONG D 125 819
YOUNG JM SEE KOCH VR 125 1371
ZAHAVI J ZANGVIL A METZGER M
N3 125 438
STRUCTURE AND STABILITY OF ANODIC FILMS FORMED ON ALUMINUM CONTAINING DISPERSED AL3FE PHASE
ZAHAVI J WAPD ID METZGER M
N4 125 574
TRANSIENT PITTING DURING FILM GROWTH ON ALUMINUM AT 1000 MV VS SCE
ZANGVIL A SEE ZAHAVI J 125 438
ZANZUCCH,PJ DUFFY MT ALIG RC
N2 125 299
OPTICAL REFLECTANCE METHOD FOR DETERMINING SURFACE QUALITY OF SAPPHIRE %AL2O3<
ZERBINO JO DETACCON,NR ARVIA AJ
N8 125 1266
ACTIVATION AND DEACTIVATION OF IRIDIUM ELECTRODES IN ACID ELECTROLYTES
ZIRINSKY S IRENE EA
N2 125 305
SELECTIVE STUDIES OF CHEMICAL VAPOR-DEPOSITED ALUMINUM NITRIDE-SILICON NITRIDE MIXTURE FILMS
ZIRINSKY S SEE BAGLIN J 125 1854
ZOCCOLA JC SEE TOWNSEND ME 125 1290
ZURILLA RW SEN RK YEAGER E
N7 125 1103
KINETICS OF OXYGEN REDUCTION REACTION ON GOLD IN ALKALINE SOLUTION

JOURNAL ARTICLE SUBJECT INDEX

TO FIND ARTICLES ON A SPECIFIC TOPIC:

1. Locate any one of the words (Primary Terms) that describes the topic. If you want every title that includes primary term, select only the articles marked with an arrow (>). This eliminates unnecessary lookups.
2. To narrow selection, use any of the other words (Co-Terms) listed below that Primary Term. When using co-terms, always disregard arrows.
3. Two word terms occur when they are generally used together to describe a single concept (e.g. heat-transfer). This simplifies multiple co-term lookup.
4. The PAGE NO. refers to the beginning page in the Journal on which the article containing the keyword appears.


PRIMARY TERM
CO-TERM
PAGE NO.
ELECTROPLATING
BIPOLAR ELECTRODE> 209
BRIGHTENER CONCE.> 194
CIRCUIT BOARD - ->1218
COPPER PLATING - 209
COPPER PYROPHOSP. 194
1218
CURRENT DENSITY - 209
DIMERCAPTOTHIADI. 1218
ELECTRODEPOSITION 209
FOLDBACK - - - - 1218
LEVELING MECHAN. "
PT-DISK ELECTROD. "
STRIPPING METHOD 194
VOLTAMMETRY - - - "
WIRING BOARD - - 209
ELECTROPOLISHING
ACETIC ACID - - ->1039
- - ->1044
ANODIC FILM - - - 1039
ANODIC POLARIZAT. 1044
AUGER ELECTRON S. 1039
PERCHLORIC ACID - "
- 1044
POTENTIOSTAT - - "
STOICHIOMETRY - - "
PRIMARY TERM
This word is selected from the contents of one or more articles.
CO-TERM
These words also were selected from the contents of articles about "ELECTROPLATING"
To find all articles concerned with "ELECTROPLATING" check only entries with this mark.
Ditto marks indicate same page.
Co-term identical to Co-term "PERCHLORIC-ACID" above.
To find articles concerning "ELECTROPOLISHING" and "PERCHLORIC ACID" check all entries under Co-term "PERCHLORIC ACID".

PRIMARY TERM / CO-TERM — PAGE NO.

ABSORPTION COEFF.
ALPHA IRON OXIDE > 709
PHOTOOXIDATION - "
TITANIUM DIOXIDE "
WATER - - - - - - "

ACCELERATED TEST
ATMOSPHERIC CORR.>2005
AUGER SPECTROSCO. "
COPPER - - - - - "
CORROSION TEST ->2002
- 2005
HUMIDITY - - - - 2002
KINETIC RATE - - "
NICKEL - - - - - 2005
POLLUTANTS - - - 2002
SILVER - - - - - 2005

ACETAL
ALCOHOL - - - - ->1401
ELECTROLYSIS - - "
HALOALDEHYDE - - "
HYDROGEN HALIDE - "
OXIDATION - - - - "

ACETIC ACID
ANODIC FILM - - ->1039
ANODIC POLARIZAT.>1044
AUGER ELECTRON S. 1039
ELECTROPOLISHING "
1044
PERCHLORIC ACID - 1039
- 1044
POTENTIOSTAT - - "
STOICHIOMETRY - - "

ACETONITRILE
AROMATIC HYDROCA.>1430
CADMIUM SULFIDE -> 406
CHEMILUMINESCENCE 1430
FREE RADICAL - - "
IODIDE ION - - - 406
PHOTOCELL - - - - "
SOLAR ENERGY - - "
TETRATHIAFULVALE. 1430

ACETONITRILE SOL.
GAAS ELECTRODE ->283C
INDIUM PHOSPHIDE "

ACID
CORROSION INHIBI.>1393
IRON - - - - - - - "
THIOUREA - - - - "

ACID FUEL CELL
CORROSION - - - ->1899
MONOHYDRATE-WATER "
PHOSPHORIC ACID - "
SULFURIC ACID - - "
TRIFLUOROMETHANE "

ACIDIC FLUORIDE
CVD SILICON NITR.> 320
DISSOLUTION PROC. "
ETCHING - - - - - "

ACIDITY DEPENDEN.
FUSED SALTS - - ->1454
MELTS - - - - - - "
SELENIUM - - - - "
TETRACHLOROALUMI. "

ACRYLONITRILE
BIPYRIDINE COMPL.> 241
CATALYSIS - - - - "
COBALT - - - - - "
VINYL MONOMER - - "

ACTIVATION
AUGER SPECTROSCO.>1224
ELLIPSOMETRY - - "
NICKEL PLATING - "
PHOTOELECTRON EM. "
SURFACE POTENTIAL "

ACTIVATION ENERGY
DEPOLARIZATION -> 434
INITIAL RISE - - "
PVC - - - - - - - "
THERMOELECTRET - "

ACTIVATION PROCE.
PRESSURE & FECT -> 257
REDOX REACTION - "
SOLVENT REORGANI. "

ACTIVITY COEFFIC.
CRYSTALLOGRAPHY ->1689
FUSED SALTS - - - -> 692
POTASSIUM CHLORI. "
SELF DIFFUSION - 1689
SILVER CHLORIDE - 692
SODIUM GALLATE - 1689
SODIUM MIGRATION "

ADRIAMYCIN
ANTHRACYCLINE - -> 534
ANTITUMOR ANTIBI. "
CHRONOPOTENTIOME. "
CYCLIC VOLTAMMET. "
DAUNORUBICIN - - "
POLAROGRAPHY - - "

ADSORPTION
CATALYSIS - - - - ->1103
GOLD - - - - - - - "
MERCURY ELECTROD.>1236
MOLECULAR AREA - "
OXYGEN REDUCTION 1103
PURINES - - - - - 1236
PYRIMIDINES - - - "
RIBOSE - - - - - - "
ROTATING DISK EL. 1103

ADSORPTION EQUIL.
DICYANOAURATE - -> 717
ELECTROCRYSTALLI. "
EPITAXY - - - - - "
GOLD PLATING - - "

AGING PROCESS
ANODIC OXIDATION >1578
FILM FORMATION - "
NICKEL HYDROXIDE "

AGITATION EFFECT
BRIGHTENER - - - -> 36
COPPER - - - - - "
MORPHOLOGY - - - "
PLATING CELL - - "
PRINTED WIRING - "
THROWING POWER - "

ALCOHOL
ACETAL - - - - ->1401
ELECTROLYSIS - - "
HALOALDEHYDE - - "
HYDROGEN HALIDE - "
OXIDATION - - - - "

ALCOHOL OXIDATION
ANODIC DISSOLUTI.>1777
NICKEL ELECTRODE "
WIPER-BLADE CELL "

ALCOHOLS
CARBON TETRACHLO.> 97
CORROSION - - - - "
ORGANIC SOLVENT - "

ALIGNMENT GROOVE
GAAS LASER - - - ->1642
OPTICAL BENCH - - "
PHOTOLITHOGRAPHY "
SILICON SUBSTRATE "

ALKALI CONTAMINA.
CLEAN FILM - - - -> 106
MICROELECTRONICS "
MOS STRUCTURE - - "
POLYSILICON TUBE. "
SILICON DIOXIDE - "

ALKALI CYANIDE
CHROMIUM - - - - ->1177
ETCHING PATTERNS "
GOLD - - - - - - - "
IODINE ETCH - - - "
UNDERCUTTING - - "

ALKALI METAL
FLUORIDE - - - - ->1894
MELTING POINT - - "
METAPHOSPHATE - - "

ALKALINE CELL
CATION MOBILITY ->1918
CREEPAGE RATE - - "
ELECTROREDUCTION "

ALKALINE COMPOUND
ELECTROLYTIC IND.> 5C
ENERGY SOURCE - - "

ALKALINE COMPOUND (CONTD)
METALS - - - - - 5C

ALKALINE CYANIDE
ANODIC DISSOLUTI.>1436
GOLD - - - - - - - "
REACTION KINETICS "
REACTION MECHANI. "

ALKALINE SOLUTIO.
ELECTROCATALYST -> 265
NICKEL ALLOY - - "
OXIDE FILM - - - "
OXYGEN EVOLUTION "
TAFEL PARAMETER - "

ALKALINE SOLUTION
CATALYST LOADING >1931
OXIDE ELECTRODE - "
TAFEL SLOPE - - - "
THERMAL DECOMPOS. "
TRANSFER COEFFIC. "
WATER ELECTROLYS. "

ALL TRANS RETINAL
ALL TRANS RETINOL> 216
BETA CAROTENE - - "
TETRAHYDROFURAN - "

ALL TRANS RETINOL
ALL TRANS RETINAL> 216
BETA CAROTENE - - "
TETRAHYDROFURAN - "

ALLIUM PHOSPHIDE
METAL ADATOMS - -> 68
PHOTOELECTROCHEM. "
SEMICONDUCTOR - - "
SPECTRAL RESPONSE "
SURFACE STATE - - "

ALLOY DEPOSITION
AQUEOUS ELECTROL.>2028
BINARY ALLOY - - "
CATHODIC DEPOSIT. "
QUASI REST POTEN. "

ALLYL CHLORIDE
BIPYRIDINE - - ->1232
CATALYSIS - - - - "
COBALT - - - - - "
ELECTROREDUCTION "

ALPHA IRON OXIDE
ABSORPTION COEFF.> 709
CAPACITANCE - - -> 723
CONDUCTIVITY - - "
DONOR DENSITY - - "
FLATBAND POTENTI. "
MOTT SCHOTTKY - - "
PHOTOOXIDATION - 709
TITANIUM DIOXIDE "
WATER - - - - - - "

ALPHA TRACK
BORON - - - - - -> 654
DOPANT DENSITY - "
NUCLEAR TRACK - - "
SILICON - - - - - "

ALUMINA
CORUNDUM - - - -> 889
CRYSTAL STRUCTURE> 890
ENERGY OF FORMAT. 889
890
FUSED SALTS - - ->1796
PHASE DIAGRAM - - 890
POLARIZATION - - 1796
REFERENCE ELECTR. "

ALUMINA CATALYST
JUNCTION LEAKAGE >1302
MOS TRANSISTOR - "
THRESHOLD VOLTAGE "
WALK-OUT - - - - "

ALUMINUM
ALUMINUM CHLORID.>1000
ANODIC FILM - - ->1480
ANODIC OXIDE - -> 915
ANODIZATION - - -> 34
- - -> 190
ARSENIC - - - - ->1348
CARBON MONOXIDE - 190
CARBON TETRACHLO.> 829
CATALYSIS - - - - 1800
CELL WALLS - - - 1480

ALUMINUM (CONTD)
CHROMATE - - - ->1290
COPPER - - - - - 915
DEPTH PROFILING - "
DIFFUSION - - - -> 957
DOPING SILICON - "
FILM GROWTH - - -> 574
GLYOXAL - - - - - 190
GOLD PLATING - ->1741
HALL EFFECT - - - 1348
IMMERSION PLATING 1741
MALEIC ACID - - - 190
MICROSCOPIC ANAL. 1480
MOLTEN SALT - - - 1000
MOSSBAUER SPECTR. 34
OPEN TUBE - - - - 957
OPTICAL EMISSION 829
PASSIVATION - - - 1290
PLASMA ETCHING - 829
POTASSIUM HYDROX. 1000
RUTHERFORD BACKS. 915
SELF DIFFUSION - 1348
SINGLE CRYSTAL - "
TIN - - - - - - - - 34
TRANSIENT PITTING 574
VACUUM - - - - - 957
WET STORAGE STAIN 1290
X-RAY ANALYSIS - 1480
ZINC - - - - - - 1290
ZINC SELENIDE - - 1348

ALUMINUM ALLOY
ANION EFFECT - -> 731
CHROMIUM ALLOY -> 271
CORROSION - - - ->1924
CORROSION RESIST. 271
HALIDE EFFECT - - 731
LITHIUM ALLOY - ->1886
MAGNESIUM ALLOY - "
MAGNESIUM ANODE - 1924
MANGANESE DIOXIDE "
NICKEL ALLOY - - 271
PITTING - - - - - 731
POLARIZATION - - 1886
PORTABLE HEATER - 1924
SALINE CELL - - - "
SODIUM SULFATE - 271

ALUMINUM ARSENIDE
GAAS - - - - - -> 977
GRAPHITE - - - - "
HETEROJUNCTION - "
SOLAR CELL - - - "
THIN FILM - - - - "

ALUMINUM CHLORID.
ALUMINUM - - - ->1000
CATALYSIS - - - - "
MOLTEN SALT - - - "
POTASSIUM HYDROX. "

ALUMINUM CONTACT
ETCHING - - - - -> 467
OXIDE THICKNESS - "
TITANIUM ALUMINUM "

ALUMINUM COPPER
ANODIC OXIDATION > 30
CORROSION - - - - "
INTEGRATED CIRCU. "
METAL FILM - - - "
METALLIZATION - - "

ALUMINUM FOIL
ANODIZATION - - ->1950
CV PRODUCT - - - "
ELECTROLYTIC CAP. "
TUNNEL ETCHING - "

ALUMINUM GAAS
COMPOUND SEMICON.> 989
LOW LEAKAGE - - - "
MOS - - - - - - - - "
OXIDE - - - - - - "

ALUMINUM IRON
ANODIC FILM - - -> 438
FILM GROWTH - - - "
PITTING - - - - - "

ALUMINUM METALLI.
BEAM LEADS - - -> 156
DIFFUSION BARRIER "
GOLD - - - - - - "
INTEGRATED CIRCU.> 169
OHMIC CONTACT - - "
POLYSILICON - - - "

PRIMARY TERM / CO-TERM — PAGE NO.

ALUMINUM NITRIDE
CHARGE STORAGE -> 305
CVD - - - - - - - - "
FILM PROPERTY - - "
MEMORY - - - - - - "
SILICON NITRIDE - "

ALUMINUM OXIDATI.
CORROSION - - - -> 787
INSULATOR - - - - "
INTEGRATED CIRCU. "

ALUMINUM OXIDE
ALUMINUM SULFATE > 327
CHROMIUM OXIDE -> 175
CRYSTAL PERFECTI.>2079
CVD - - - - - - - - "
CZOCHRALSKI-GROWN "
DECOMPOSITION - - 327
DEPOSITION RATE -> 902
ELLIPSOMETRY - - "
FILM PROPERTIES - "
GALVANIC CELL - - 175
GASEOUS PRODUCT - 327
INSULATOR - - - - 902
KRAMERS-KRONIG -> 299
METAL REFLECTOR ->1138
MISCIBILITY GAP - 175
MOLYBDENUM FILM - 1138
OPTICAL REFLECTA. 299
PHOTOTHERMAL - - 1138
QUALITY CONTROL - 299
SAPPHIRE - - - - "
SILICON NITRIDE - 1138
SOLID ELECTROLYTE 175
SOLID PRODUCT - - 327
SULFUR DIOXIDE - "
SULFUR TRIOXIDE - "
THERMODYNAMICS - 175
X-RAY DIFFRACTION 2079

ALUMINUM STRAINI.
LOCALIZED CORROS.>1594
PITTING - - - - - "
SEM - - - - - - - "
SLIP STEPS - - - "

ALUMINUM SULFATE
ALUMINUM OXIDE -> 327
DECOMPOSITION - - "
GASEOUS PRODUCT - "
SOLID PRODUCT - - "
SULFUR DIOXIDE - "
SULFUR TRIOXIDE - "

AMMONIA
COPYROLYSIS - - -> 487
CVD - - - - - - - - "
ELECTRODEPOSITION>1717
GOLD - - - - - - - "
POINT TO POINT - 487
SILANE - - - - - "
SILICON NITRIDE - "
THERMOCOUPLE ANA. "

ANILINE
DECOMPOSITION - ->1059
EPR - - - - - - - - "
VOLTAMMETRY - - - "

ANION EFFECT
ALUMINUM ALLOY -> 731
HALIDE EFFECT - - "
PITTING - - - - - "

ANISOTROPIC ETCH.
INK JET PRINTING >1321
NOZZLE FABRICATI. "
SILICON NOZZLE - "
3-D MICROSTRUCTU. "

ANNEALING
CRYSTAL STRUCTURE> 927
CVD - - - - - - - - "
ELECTRON IRRADIA.> 676
EPITAXIAL REACTOR>1845
GAAS - - - - - - - 676
INDIUM PHOSPHIDE 1845
ION IMPLANTATION "
LOW PRESSURE - - 927
RADIATION DAMAGE 676
SILICON FILM - - 927
STRUCTURE - - - - "

ANODE
AUGER SPECTROSCO.> 44
CATHODE - - - - - "

ANODE (CONTD)
MASS TRANSFER - - 44
METAL OXIDE FILM "
PLASMA ANODIZATI. "

ANODE SYNTHESIS
CARBON MONOXIDE ->1954
HALIDE ELECTROLY. "
ORGANIC CARBONATE "
PHOSGENE - - - - "

ANODIC BEHAVIOR
CORROSION - - - -> 1
DISSOLUTION - - - "
LITHIUM - - - - - "
LITHIUM HYDROXIDE "

ANODIC DISCHARGE
CYCLE LIFE - - -> 727
LITHIUM ALUMINUM "
MOLTEN SALT ELEC. "

ANODIC DISSOLUTI.
ALCOHOL OXIDATION>1777
ALKALINE CYANIDE >1436
CADMIUM SULFIDE -> 117
CHARGE TRANSFER - "
EXCHANGE REACTION>1989
GOLD - - - - - - - 1436
III-IV COMPOUNDS 117
LEAD SYSTEM - - - 1989
NICKEL ELECTRODE 1777
PERCHLORATE ACID 1989
PHOTOELECTROLYSIS 117
REACTION KINETICS 1436
REACTION MECHANI. "
REDOX SYSTEM - - 117
WIPER-BLADE CELL 1777

ANODIC FILM
ACETIC ACID - - ->1039
ALUMINUM - - - ->1460
ALUMINUM IRON - -> 438
ANODIC OXIDATION >1735
AUGER ELECTRON S. 1039
CELL WALLS - - - 1480
COBALT - - - - - - 1735
ELECTROPOLISHING 1039
FILM GROWTH - - - 438
MICROSCOPIC ANAL. 1480
PASSIVITY - - - - 1735
PERCHLORIC ACID - 1039
PITTING - - - - - 438
X-RAY ANALYSIS - 1480

ANODIC OXIDATION
AGING PROCESS - ->1578
ALUMINUM COPPER -> 30
ANODIC FILM - - - ->1735
ARGON - - - - - - ->1812
BETA TANTALUM - - "
COBALT - - - - - 1735
COPPER AMALGAM ->1960
CORROSION - - - - 30
ELECTROSTRICTION > 908
ELLIPSOMETRY - - "
FILM FORMATION - 1578
INTEGRATED CIRCU. 30
LITHIUM HYDROXIDE 1960
METAL FILM - - - 30
METALLIZATION - - "
NICKEL - - - - ->1410
NICKEL HYDROXIDE 1578
NIOBIUM - - - - ->1549
NUCLEAR MICROANA. "
NUCLEATION - - - 1960
OXIDE FILM - - - 908
- - - 1410
PASSIVITY - - - - 1735
POLYCRYSTAL COPP. 1960
RUTHERFORD BACKS. 1549
SEMICONDUCTOR - - 1410
TAFEL SLOPE - - - 908
TANTALUM - - - - 1549
TANTALUM ION - - 1812
TITANIUM - - - - 1410
TITANIUM NICKEL - "
TRANSPORT MECHAN. 1549
TRANSPORT NUMBER 1812
TUNGSTEN - - - - 908

ANODIC OXIDE
ALUMINUM - - - -> 915
BREAKDOWN VOLTAGE>1032
COPPER - - - - - 915
CURRENT DENSITY - 1032
DEPTH PROFILING - 915

ANODIC OXIDE (CONTD)
ELLIPSOMETRY - - 1032
RUTHERFORD BACKS. 915
TITANIUM - - - - 1032

ANODIC OXIDE FILM
ELECTROCHROMISM -> 23
ELLIPSOMETRY - - "
HYDROGEN - - - - "
IMPEDANCE - - - - "
NIOBIUM - - - - - "
POLARIZABILITY - "
TITANIUM - - - - "

ANODIC POLARIZAT.
ACETIC ACID - - ->1044
ELECTROPOLISHING "
ION IMPLANTATION > 366
> 370
IRON CHROMIUM - - 366
IRON NICKEL - - - 370
LITHIUM CHLORATE >1262
ORGANIC FILM - - "
PERCHLORIC ACID - 1044
PITTING POTENTIAL 366
370
PLATINUM ELECTRO. 1262
POTENTIOSTAT - - 1044
STOICHIOMETRY - - "
SURFACE ALLOY - - 366
- - 370
TETRAHYDROFURAN - 1262
XPS - - - - - - - "

ANODIZATION
ALUMINUM - - - -> 34
- - - -> 190
ALUMINUM FOIL - ->1950
CARBON MONOXIDE - 190
CV PRODUCT - - - 1950
ELECTROLYTIC CAP. "
GLYOXAL - - - - - 190
LAYERED SEMICOND.> 824
MALEIC ACID - - - 190
MOSSBAUER SPECTR. 34
NONPASSIVE-PASSI. 824
TIN - - - - - - - 34
TUNNEL ETCHING - 1950

ANTHRACYCLINE
ADRIAMYCIN - - -> 534
ANTITUMOR ANTIBI. "
CHRONOPOTENTIOME. "
CYCLIC VOLTAMMET. "
DAUNORUBICIN - - "
POLAROGRAPHY - - "

ANTIREFLECTION
DEPOSITION TEMPE.> 983
TITANIUM DIOXIDE "

ANTITHROMBOGENIC
HEMOSTASIS - - ->419C
IMMUNE RESPONSE - "
MEDICAL ELECTROC. "

ANTITUMOR ANTIBI.
ADRIAMYCIN - - -> 534
ANTHRACYCLINE - - "
CHRONOPOTENTIOME. "
CYCLIC VOLTAMMET. "
> 540
DAUNOMYCINONE - - "
DAUNORUBICIN - - 534
POLAROGRAPHY - - "
QUINONE - - - - - 540

AQUEOUS ELECTROL.
ALLOY DEPOSITION >2028
BINARY ALLOY - - "
CATHODIC DEPOSIT. "
CURRENT RISE - ->1185
GAAS ELECTRODE - "
QUASI REST POTEN. 2028
SEMICONDUCTOR - - 1185

AQUEOUS SOLUTION
LUMINESCENCE - -> 246
SEMICONDUCTOR - - "
SURFACE STATE - - "
TITANIUM DIOXIDE "

ARGON
ANODIC OXIDATION >1812
BETA TANTALUM - - "
TANTALUM ION - - "
TRANSPORT NUMBER "

AROMATIC HYDROCA.
ACETONITRILE - ->1430
CHEMILUMINESCENCE "
FREE RADICAL - - "
TETRATHIAFULVALE. "

ARSENIC
ALUMINUM - - - ->1348
CRYSTAL ORIENTAT.> 461
ELECTRICAL ACTIV. "
EPITAXIAL REGROW. "
HALL EFFECT - - - 1348
ION IMPLANTATION >1518
RECRYSTALLIZATION 461
REDISTRIBUTION - 1518
SELF DIFFUSION - 1348
SILICON - - - - - 461
SINGLE CRYSTAL - 1348
SPREADING RESIST. 1518
ZINC SELENIDE - - 1348

ARSENIC DIFFUSION
AUTODOPING - - -> 146
SILICON EPITAXY - "
SILICON OXIDE - ->1997
THERMAL OXIDATION "
TRANSPORT KINETI. 146

ARSENIC TRIOXIDE
ETCHING - - - - -> 579
GAAS - - - - - - "
THERMAL OXIDATION "

ARSINE
CHLORIDE ETCHING > 771
DOPANT SYSTEM - ->1860
GAAS EPITAXY - - 771
GROWTH RATE - - - "
SILANE - - - - - 1860
SILICON EPITAXY - "
TRANSFER FUNCTION "
TRIMETHYLGALLIUM 771

ATMOSPHERIC CORR.
ACCELERATED TEST >2005
AUGER SPECTROSCO. "
COPPER - - - - - "
CORROSION TEST - "
NICKEL - - - - - "
SILVER - - - - - "

ATOMIC OXYGEN
COLD WALL REACTO.> 110
CVD - - - - - - - "
KINETIC MECHANISM "
TIN CHLORIDE - - "
TIN OXIDE - - - - "

AUGER
ELECTROSORPTION -> 348
HYDROGEN ADSORPT. "
LEED - - - - - - - "
PLATINUM - - - - "
SINGLE CRYSTAL - "

AUGER ANALYSIS
CHROMIUM - - - ->1204
GAAS - - - - - ->998
MOLYBDENUM - - - 1204
PITTING - - - - - "
STAINLESS STEEL - "
THERMAL OXIDATION 998

AUGER ELECTRON S.
ACETIC ACID - - ->1039
ANODIC FILM - - - "
ELECTROPOLISHING "
PERCHLORIC ACID - "

AUGER SPECTROSCO.
ACCELERATED TEST >2005
ACTIVATION - - ->1224
ANODE - - - - - -> 44
ATMOSPHERIC CORR. 2005
CATHODE - - - - - 44
COPPER - - - - - 2005
COPPER ALLOY - ->1801
COPPER CORROSION > 17
CORROSION TEST - 2005
CUPRONICKEL - - - 1801
DEPTH PROFILE - - 17
- -> 481
DISSOLUTION RATE 17
ELLIPSOMETRY - - 1224
GAAS - - - - - - 481
MASS TRANSFER - - 44
METAL OXIDE FILM "

PRIMARY TERM / CO-TERM	PAGE NO.
AUGER SPECTROSCO. (CONTD)	
NEUTRON ACTIVATI.	481
NICKEL	2005
NICKEL ALLOY	1801
NICKEL PLATING	1224
NOBLE METAL	17
OXIDE FILM	1801
PALLADIUM	17
PASSIVITY	"
PHOTOELECTRON EM.	1224
PLASMA ANODIZATI.	44
PLASMA OXIDATION	481
SILICON CARBIDE	->1896
SILVER	2005
SURFACE POTENTIAL	1224
THERMAL OXIDE	1896
AUTODOPING	
ARSENIC DIFFUSION>	146
GROWTH KINETICS	-> 637
LOW PRESSURE	->1879
MULTIWAFER GROWTH	"
REDUCED PRESSURE	637
SILICON EPITAXY	146, 1879
SILICON GROWTH	637
TRANSPORT KINETI.	146
AUTOMOTIVE BATTE.	
PRODUCT CHANGES	->311C
SECONDARY BATTE.	"
AVRAMI EQUATION	
DSC	-> 330
DTA	"
METASTABLE ALLOY	"
TIN NICKEL	"
BACKSCATTERING	
CHROMIUM	->1854
DEPTH PROFILE	->1215
EQUILIBRIUM DIAG.	1854
MASS SPECTROMETRY	1215
NICKEL	"
ORDERING TRANSFO.	1854
PLATINUM	"
RUTHERFORD	1215
TIN	"
BAFFLE	
CURRENT DISTRIBU.>	84
FLAT STRIP ELECT.	"
RECTANGULAR CELL	"
BAND BENDING	
BUTLER VOLMER	-> 937
DEPLETION LAYER	"
DIFFUSION THEORY	"
OVERVOLTAGE	"
PHOTOELECTRODE	"
RECOMBINATION	"
BATTERY SEPARATOR	
CAPACITANCE	-> 520
LOW IMPEDENCE	"
RESISTIVITY	"
WHEATSTONE BRIDGE	"
BATTERY SYSTEM	
CALCULATION	-> 353
HEAT FLOW	"
THERMAL EFFICIEN.	"
BEAM LEADS	
ALUMINUM METALLI.>	156
DIFFUSION BARRIER	"
GOLD	"
BETA ALUMINA	
CALCIUM	->1007
CERAMIC	"
CONCENTRATION CE.>	1377
EMF MEASUREMENT	"
ENERGY STORAGE	1007
IRON	"
LIQUID ALLOY	1377
POTASSIUM	1007
SODIUM TIN ALLOY	1377
BETA CAROTENE	
ALL TRANS RETINAL>	216
ALL TRANS RETINOL	"
TETRAHYDROFURAN	"
BETA EUCRYPTITE	
GLASS CERAMICS	-> 179
IONIC CONDUCTIVI.	"
BETA EUCRYPTITE (CONTD)	
LITHIUM ALUMINOS.	179
SOLID ELECTROLYTE	"
BETA LEAD FLUORI.	
CONDUCTION	-> 683
ELECTROLYTIC DOM.	"
HEBB WAGNER POLA.	"
BETA TANTALUM	
ANODIC OXIDATION	>1812
ARGON	"
TANTALUM ION	"
TRANSPORT NUMBER	"
BEVELING	
ETCHING	-> 860
PERMALLOY	"
POLARIZATION	"
TRANSDUCER	"
BIBLIOGRAPHY	
CORROSION CONTROL>	58C
CORROSION RESEAR.	"
STRESS CRACKING	"
BINARY ALLOY	
ALLOY DEPOSITION	>2028
AQUEOUS ELECTROL.	"
CATHODIC DEPOSIT.	"
INTERNAL OXIDATI.	>1116
QUASI REST POTEN.	2028
TERNARY DIFFUSION	1116
WAGNER	"
BIPOLAR DEVICE	
CONDUCTIVE FILM	->1829
ION IMPLANTATION	"
PULSIVE NOISE	"
BIPOLAR ELECTRODE	
COPPER PLATING	-> 209
CURRENT DENSITY	"
ELECTRODEPOSITION	"
ELECTROPLATING	"
WIRING BOARD	"
BIPOLAR TRANSIST.	
EMITTER DIFFUSION>	762
PHOSPHORUS DIFFU.	"
SILICON DEFECT	"
BIPYRIDINE	
ALLYL CHLORIDE	->1232
CATALYSIS	"
COBALT	"
ELECTROREDUCTION	"
BIPYRIDINE COMPL.	
ACRYLONITRILE	-> 241
CATALYSIS	"
COBALT	"
VINYL MONOMER	"
BIRDS BEAK	
OXIDE ISOLATION	-> 932
OXIDE SCHEME	"
SILICON STRUCTURE	"
BISAZIDE	
CROSSLINKING	->1126
PHOTORESIST SYST.	"
POLYMERIZATION	"
BISMUTH FLUORIDE	
CYCLIC VOLTAMMET.	511
LITHIUM BATTERY	"
NONAQUEOUS SOLVE.	"
BISMUTH TRIOXIDE	
BUTTON ORGANIC	-> 14
CATHODE	"
LITHIUM CELL	"
NONAQUEOUS SOLVE.	"
BISMUTH TRITELLU.	
EPITAXY	->2042
IMPURITY DOPANT	"
MOLECULAR BEAM	"
NONSTOICHIOMETRY	"
SEMICONDUCTOR	"
THALLIUM	"
VAPOR PRESSURE	"
BLOCKING EFFECTS	
ELECTRODE KINETI.	> 389
IRON	"
BLOCKING EFFECTS (CONTD)	
OXYGEN COVERAGE	- 389
QUINONE	"
RHODIUM ELECTRODE	"
BLUE TUNGSTEN	
ELECTROCHROMISM	->1344
HYDROGEN TUNGSTEN	"
OXIDE FILM	"
TUNGSTEN OXIDE	"
BOLTZMANN-MATANO	
CADMIUM	->1530
DIFFUSION PROFILE	"
GRADED C-V	"
INDIUM ANTIMONIDE	"
BORATE BUFFER	
MOSSBAUER STUDY	->1946
PASSIVE FILM	"
POLARIZATION CUR.	"
TIN OXIDE	"
BORON	
ALPHA TRACK	-> 654
DIFFUSION	->2050
DIFFUSIVITY	-> 813
DOPANT DENSITY	654
ION IMPLANTATION	2050
LEAD SULFIDE	-> 678
LITHIUM	->1632
LITHIUM ELECTRODE	"
NUCLEAR TRACK	654
OXIDATION	2050
REST POTENTIAL	678
SEGREGATION	813, 2050
SEMICONDUCTANCE	678
SILICON	654, 813, 1632
SILICON MIGRATION	"
SILICON OXIDE	2050
TERNARY ALLOY	1632
BORON DEPOSITION	
ORTHOBORIC ACID	-> 166
OXIDIZED SILICON	"
BORON DIFFUSION	
BORON OXIDE	->1521
BOROSILICATES	"
DOPING	"
SILICON	"
BORON MONOPHOSPH.	
EPITAXIAL GROWTH	> 633
SILICON SUBSTRATE	"
SOLAR CELL	"
TRANSISTOR	"
BORON OXIDE	
BORON DIFFUSION	->1521
BOROSILICATES	"
DOPING	"
SILICON	"
BORON TRIBROMIDE	
DOPING	-> 609
PREDEPOSITION	"
SILICON	"
BOROSILICATES	
BORON DIFFUSION	->1521
BORON OXIDE	"
DOPING	"
SILICON	"
BOUNDARY LAYER	
ELECTRODEPOSITION>	865
MASS TRANSPORT	"
SHEET ELECTRODE	"
TRANSIENTS	"
BREAKDOWN VOLTAGE	
ANODIC OXIDE	->1032
CURRENT DENSITY	"
ELLIPSOMETRY	"
TITANIUM	"
BRIDGMAN APPROACH	
CADMIUM TELLURIDE>	315
INFRARED MATERIAL	"
MERCURY TELLURIDE	"
PSEUDOBINARY ALL.	"
SINGLE CRYSTAL	"
BRIGHTENER	
AGITATION EFFECT	> 36
COPPER	"
MORPHOLOGY	"
PLATING CELL	"
PRINTED WIRING	"
THROWING POWER	"
BRIGHTENER CONCE.	
COPPER PYROPHOSP.	> 194
ELECTROPLATING	"
STRIPPING METHOD	"
VOLTAMMETRY	"
BRITTLE COATING	
DUCTILITY	-> 400
FOUR POINT BEND	"
BROAD BAND EMITT.	
CANDOLUMINESCENCE>	2015
HYDROGEN ION BEAM	"
ION EXCHANGE	"
LIN. EMITTER	"
QUANTUM YIELD	"
BROMIDE ELECTRODE	
CHLORIDE ELECTRO.	>1807
HALIDE SELECTIVE	"
IODIDE ELECTRODE	"
BROMINE LAMP	
KINETIC MODEL	->2064
LAMP CHEMISTRY	"
TUNGSTEN HALOGEN	"
BUFFER LAYER	
CHROMIUM	->2058
FET	"
GAAS	"
LPE	"
SEMIINSULATING	"
BUTLER VOLMER	
BAND BENDING	-> 937
DEPLETION LAYER	"
DIFFUSION THEORY	"
OVERVOLTAGE	"
PHOTOELECTRODE	"
RECOMBINATION	"
BUTTON ORGANIC	
BISMUTH TRIOXIDE	> 14
CATHODE	"
LITHIUM CELL	"
NONAQUEOUS SOLVE.	"
CADMIUM	
BOLTZMANN-MATANO	>1530
DIFFUSION PROFILE	"
GRADED C-V	"
INDIUM ANTIMONIDE	"
CADMIUM SELENIDE	
CADMIUM SULFIDE	-> 375
ENERGY CONVERSION>	1623
PHOTOELECTROCHEM.	375
PHOTOELECTRODE	1623
SOLAR CELL	375
SULFUR SUBSTITUT.	1623
XPS	"
CADMIUM SULFIDE	
ACETONITRILE	-> 406
ANODIC DISSOLUTI.	> 117
CADMIUM SELENIDE	> 375
CHARGE TRANSFER	117
ENERGY CONVERSION>	1968
FLATBAND POTENTI.	"
III-IV COMPOUNDS	117
IODIDE ION	406
PHOTOCELL	"
PHOTOELECTROCHEM.	375
PHOTOELECTROLYSIS	117
REDOX SYSTEM	"
SOLAR CELL	375
SOLAR ENERGY	406
SURFACE ION	1968
WET PHOTOVOLTAIC	"
CADMIUM TELLURIDE	
BRIDGMAN APPROACH>	315
CATHODIC DEPOSIT.	> 586
INFRARED MATERIAL	315
MERCURY TELLURIDE	"
POURBAIX DIAGRAM	586
PSEUDOBINARY ALL.	315
SINGLE CRYSTAL	"

PRIMARY TERM / CO-TERM	PAGE NO.
CALCIUM	
BETA ALUMINA - ->1007	
CERAMIC - - - - -	"
ENERGY STORAGE -	"
IRON - - - - - -	"
POTASSIUM - - - -	"
CALCIUM ANODE	
CALORIMETRY - - ->1209	
CURRENT EFFICIEN.	"
HALIDE SALTS - -	"
NITRATE ELECTROL.	"
PASSIVATING LAYER	"
CALCIUM FLUORIDE	
COAL GASIFICATION> 758	
CONDUCTIVITY - -> 755	
MASS TRANSPORT -	"
POLARIZATION - -	"
SOLID ELECTROLYTE	"
	758
SULFUR PROBE - -	"
CALCIUM FLUOROPH.	
ESR - - - - - - ->1493	
LASER SPECTROSCO.	"
NEODYMIUM - - - -	"
OPTICAL PROPERTY	"
CALCULATION	
BATTERY SYSTEM -> 353	
ELECTRODE POTENT.> 808	
ENTROPY - - - - -	"
HEAT CAPACITY - -	"
HEAT FLOW - - - - 353	
METAL WATER SYST. 809	
THERMAL EFFICIEN. 353	
CALORIMETRY	
CALCIUM ANODE - ->1209	
CURRENT EFFICIEN.	"
DISCHARGE REACTI.> 674	
HALIDE SALTS - - 1209	
LITHIUM - - - - -> 842	
LITHIUM CELL - - 674	
MERCURY - - - - - 842	
NITRATE ELECTROL. 1209	
PACEMAKER BATTER. 842	
PASSIVATING LAYER 1209	
SILVER - - - - - 842	
SULFOXYDICHLORID. 674	
ZINC - - - - - - 842	
CANDOLUMINESCENCE	
BROAD BAND EMITT.>2015	
HYDROGEN ION BEAM	"
ION EXCHANGE - -	"
LINE EMITTER - -	"
QUANTUM YIELD - -	"
CAPACITANCE	
ALPHA IRON OXIDE > 723	
BATTERY SEPARATOR> 520	
CONDUCTIVITY - - 723	
COULOSTATIC DEPO.> 380	
CUPROUS IODIDE -> 613	
DONOR DENSITY - - 723	
DOUBLE LAYER - - 380	
ELECTRICAL CONDU. 613	
ELECTROCAPILLARY >1077	
FLATBAND POTENTI. 723	
GOLD ELECTRODE - 1077	
LOW IMPEDENCE - - 520	
MOTT SCHOTTKY - - 723	
POTENTIAL RELAXA. 380	
RESISTIVITY - - - 520	
STRESS-STRAIN - - 1077	
TRANSFERENCE NUM. 613	
UNDERPOTENTIAL - 380	
WHEATSTONE BRIDGE 520	
CAPACITOR	
DIELECTRIC PROPE.> 746	
HEAT TREATMENT -	"
MAXWELL WAGNER -	"
TANTALUM OXIDE -	"
TWO LAYER MODEL -	"
CAPACITY LOSS	
CORROSION - - - ->1587	
POLARIZATION - -	"
SODIUM SULFUR - -	"
STAINLESS STEEL -	"
CARBON BLACK	
CORROSION - - - ->1719	
PHOSPHORIC ACID -	"
CARBON ELECTRODE	
DESALINATION - -> 869	
PARAMETRIC PUMP -	"
SEPARATION - - -	"
CARBON MATRIX	
RECHARGEABILITY -> 705	
SODIUM-SULFUR CE.	"
SURFACE PROPERTY	"
CARBON MONOXIDE	
ALUMINUM - - - -> 190	
ANODE SYNTHESIS ->1954	
ANODIZATION - - - 190	
GLYOXAL - - - - -	"
HALIDE ELECTROLY. 1954	
MALEIC ACID - - - 190	
MOLTEN CARBONATES> 888	
NITROGEN - - - -	"
OPEN CIRCUIT - -	"
ORGANIC CARBONATE 1954	
PHOSGENE - - - -	"
CARBON TETRACHLO.	
ALCOHOLS - - - -> 97	
ALUMINUM - - - -> 829	
CORROSION - - - - 97	
OPTICAL EMISSION 829	
ORGANIC SOLVENT - 97	
PLASMA ETCHING - 829	
CARBON TETRAFLUO.	
PHOSPHORUS EFFECT> 827	
PLASMA ETCHING -	"
SILICON - - - - -	"
CARBONATE CELL	
CORROSION PROTEC.>1799	
LITHIUM ALUMINATE	"
STAINLESS STEEL -	"
WET SEAL - - - -	"
CARDIAC PACEMAKER	
LOAD DEPENDENT ->1907	
MICROCALORIMETER	"
PRIMARY BATTERY -	"
SELF DISCHARGE -	"
CARRIER CONCENTR.	
CRYSTALLINE QUAL.>2076	
DIODE - - - - - -	"
GALLIUM NITRIDE -	"
SURFACE MORPHOLO.	"
X-RAY DIFFRACTION	"
CATALYSIS	
ACRYLONITRILE - -> 241	
ADSORPTION - - ->1103	
ALLYL CHLORIDE ->1232	
ALUMINUM - - - ->1000	
ALUMINUM CHLORID.	"
BIPYRIDINE - - - 1232	
BIPYRIDINE COMPL. 241	
COBALT - - - - -	"
- - - - - 1232	
ELECTROREDUCTION	"
GOLD - - - - - - 1103	
MOLTEN SALT - - - 1000	
OXYGEN REDUCTION 1103	
POTASSIUM HYDROX. 1000	
ROTATING DISK EL. 1103	
VINYL MONOMER - - 241	
CATALYST LOADING	
ALKALINE SOLUTION>1931	
OXIDE ELECTRODE -	"
TAFEL SLOPE - - -	"
THERMAL DECOMPOS.	"
TRANSFER COEFFIC.	"
WATER ELECTROLYS.	"
CATALYTIC WAVES	
COULOMETRY - - ->1069	
CYCLIC VOLTAMMET.	"
RUTHENIUM DIOXID.	"
RUTHENIUM OXIDE -	"
CATHODE	
ANODE - - - - - -> 44	
AUGER SPECTROSCO.	"
BISMUTH TRIOXIDE > 14	
BUTTON ORGANIC -	"
LITHIUM CELL - -	"
MASS TRANSFER - - 44	
METAL OXIDE FILM	"
NONAQUEOUS SOLVE. 14	
PLASMA ANODIZATI. 44	
CATHODE REACTION	
CURRENT DENSITY ->1574	
LITHIUM CELL - -	"
MASS TRANSPORT -	"
SULFONYL CHLORIDE	"
CATHODIC DEPOSIT.	
ALLOY DEPOSITION >2028	
AQUEOUS ELECTROL.	"
BINARY ALLOY - -	"
CADMIUM TELLURIDE> 566	
POURBAIX DIAGRAM	"
QUASI REST POTEN. 2023	
CATHODIC POLARIZ.	
LITHIUM CHLORATE >1257	
LITHIUM HYDROXIDE	"
PLATINUM ELECTRO.	"
TETRAHYDROFURAN -	"
XPS - - - - - - -	"
CATHODIC REDUCTI.	
COULOMETRY - - -> 714	
DINITROANALINE -	"
MERCURY POOL - -	"
PH DEPENDENCY - -	"
CATHODOCHROMISM	
EMISSION SPECTRA >1133	
F CENTERS - - - -	"
GERMANIUM DOPED -	"
REFLECTANCE SPEC.	"
SODALITE - - - -	"
CATHODOLUMINESCE.	
COPRECIPITATION -> 102	
EUROPIUM - - - -	"
LOW ENERGY ELECT.	"
MULTIEXCITATION -> 288	
PHOSPHORS - - - -	"
POWDER PHOSPHOR - 102	
RASTER - - - - - 288	
SATURATION PROPE.	"
TIN DIOXIDE - - - 102	
CATION EXCHANGE	
DIFFUSION COEFFI.> 556	
POTASSIUM HYDROX.	"
TRANSFERENCE - -	"
TRANSPORT PARAME.	"
CATION MOBILITY	
ALKALINE CELL - ->1918	
CREEPAGE RATE - -	"
ELECTROREDUCTION	"
CAUSTIC SODA	
CHLORINE COMPOUND>455C	
ELECTROLYTIC IND.	"
METALS - - - - -	"
CELL FABRICATION	
ELECTRON AFFINITY>1328	
INDIUM OXIDE - -	"
PHOTOVOLTAIC CELL	"
CELL WALLS	
ALUMINUM - - - ->1480	
ANODIC FILM - - -	"
MICROSCOPIC ANAL.	"
X-RAY ANALYSIS -	"
CELLULOSE	
HYDROLYSIS - - -> 833	
LEAD ACID BATTERY	"
POLYMERIZATION -	"
SEPARATOR - - - -	"
CERAMIC	
BETA ALUMINA - ->1007	
CALCIUM - - - - -	"
ENERGY STORAGE -	"
IRON - - - - - -	"
POTASSIUM - - - -	"
CERAMIC POWDER	
ELECTRODE SEPARA.>1913	
FIBROUS SEPARATOR	"
FUSED SALTS - - -	"
IRON SULFIDE - -	"
LITHIUM ALUMINUM	"
CERIUM DIOXIDE	
ENERGY CONVERSION>1277	
FUEL CELL - - - -	"
MIXED CONDUCTOR -	"
TRANSPORT THEORY	"
CERIUM LUMINESCE.	
ENERGY TRANSFER -> 588	
HEXAGONAL ALUMIN.	"
CHALCOCITE	
CHEMICAL DIFFUSI.>1684	
COPPER SULFIDE -	"
NONSTOICHIOMETRY	"
CHALCOPYRITE	
II-IV-V2 COMPOUND> 952	
LPE - - - - - - -	"
SINGLE CRYSTAL -	"
ZINC TIN ARSENIDE	"
CHARGE ACCUMULAT.	
DUAL DIELECTRICS >1657	
MNOS FET DEVICE -	"
THRESHOLD VOLTAGE	"
CHARGE DELOCALIZ.	
HYDROGEN EVOLUTI.>1992	
PROTON TRANSFER -	"
CHARGE STORAGE	
ALUMINUM NITRIDE > 305	
CVD - - - - - - -	"
FILM PROPERTY - -	"
MEMORY - - - - -	"
SILICON NITRIDE -	"
CHARGE TRANSFER	
ANODIC DISSOLUTI.> 117	
CADMIUM SULFIDE -	"
HYDROGEN EVOLUTI.>1991	
III-IV COMPOUNDS 117	
PHOTOELECTROCHEM. 1991	
PHOTOELECTROLYSIS 117	
RATE DETERMINING 1991	
REDOX SYSTEM - - 117	
SEMICONDUCTOR - - 1991	
TUNNELING - - - -	"
CHEMICAL BONDING	
COMPOSITION - - -> 424	
CONTAMINATION - -	"
INSULATING FILM -	"
SILICON OXYNITRI.	"
CHEMICAL DIFFUSI.	
CHALCOCITE - - ->1684	
COPPER SULFIDE -	"
NONSTOICHIOMETRY	"
CHEMICAL ETCHING	
DISLOCATION DIPO.> 671	
DISLOCATION LOOP	"
GALLIUM PHOSPHIDE	"
CHEMICAL LAPPING	
SILICON ETCHING -> 152	
SILICON WAFER - -	"
STAIN FILMS - - -	"
CHEMILUMINESCENCE	
ACETONITRILE - ->1430	
AROMATIC HYDROCA.	"
DIFFUSION - - - ->1079	
ELECTRON TRANSFER>1423	
EXCITED STATES -	"
FREE RADICAL - - 1430	
REACTION ZONE - - 1079	
SEMICONDUCTOR - - 1423	
TETRATHIAFULVALE. 1430	
TRIPLET LIFETIME 1079	
CHEMISORPTION	
HYDROGEN SULFIDE > 544	
MASS TRANSPORT -	"
OXYGEN REDUCTION > 878	
	>1660
PARAMAGNETICS - -	"
PEROVSKITE OXIDE 878	
PSEUDOSPLITTING - 1660	
ROTATING ELECTRO. 544	
TEFLON BONDED EL. 878	
CHLOR-ALKALI	
DIAPHRAGM CELL -> 22C	
FLUORINE - - - -	"
INDUSTRIAL CHEMI.	"
CHLORIDE ELECTRO.	
BROMIDE ELECTRODE>1807	
HALIDE SELECTIVE	"
IODIDE ELECTRODE	"

PRIMARY TERM / CO-TERM	PAGE NO.
CHLORIDE ETCHING	
ARSINE - - - - ->	771
GAAS EPITAXY - -	"
GROWTH RATE - - -	"
TRIMETHYLGALLIUM	"
CHLORIDE SOLUTIO.	
CORROSION - - - ->	853
DISSOLUTION KINE.	"
ELECTRODISSOLUTI.	"
HYDROGEN EVOLUTI.>	1199
IRON - - - - - -	853
LOCALIZED CORROS.	1199
SULFURIC ACID - -	"
TENSILE STRESS -	"
TITANIUM ALLOY -	"
TRANSPASSIVITY -	"
CHLORINE	
ELECTRICAL EFFECT>	453
GETTERING - - - -	"
OXYGEN CHLORINE ->	339
OXYGEN WATER - -	"
SILICON - - - - -	"
SILICON OXIDATION	453
THERMAL OXIDATION	339
CHLORINE BATTERY	
DIFFUSION COEFFI.>	89
MASS TRANSFER - -	"
ROTATING HEMISPH.	"
ZINC BATTERY - -	"
ZINC HEMISPHERE -	"
CHLORINE COMPOUND	
CAUSTIC SODA - ->455C	
ELECTROLYTIC IND.	"
METALS - - - - -	"
CHLORINE CONCENT.	
OXIDATION - - - ->2024	
SILICON OXIDE - -	"
SIMS - - - - - -	"
SPECTROMETRY - -	"
CHLORINE EVOLUTI.	
RUBIDIUM OXIDE ->1093	
SURFACE ANALYSIS	"
X-RAY PHOTOELECT.	"
CHROMATE	
ALUMINUM - - - ->1290	
PASSIVATION - - -	"
WET STORAGE STAIN	"
ZINC - - - - - -	"
CHROMIUM	
ALKALI CYANIDE ->1177	
AUGER ANALYSIS ->1204	
BACKSCATTERING ->1854	
BUFFER LAYER - ->2058	
CORROSION - - - ->2062	
DIFFUSION CHARAC.>	55C
ELECTRODE KINETI.	2062
EQUILIBRIUM DIAG.	1854
ETCHING PATTERNS	1177
EUTECTIC - - - ->1450	
FET - - - - - - -	2058
GAAS - - - - - -	"
GOLD - - - - - -	1177
HYDROLYSIS - - -	1450
IMPEDANCE PARAME.	2062
IODINE ETCH - - -	1177
LPE - - - - - - -	2058
MAGNETITE - - - -	55C
MOISTURE - - - -	1450
MOLTEN SALTS - -	"
MOLYBDENUM - - -	1204
ORDERING TRANSFO.	1854
OXYGEN PRESSURE -	55C
PITTING - - - - -	1204
PLATINUM - - - -	1854
PSEUDOINDUCTANCE	2062
SEMIINSULATING -	2058
STAINLESS STEEL -	1204
SULFURIC ACID - -	2062
UNDERCUTTING - -	1177
CHROMIUM ALLOY	
ALUMINUM ALLOY ->	271
CORROSION RESIST.	"
NICKEL ALLOY - -	"
SODIUM SULFATE -	"
CHROMIUM CHLORIDE	
CHRONOAMPEROMETRY>	561
CYCLIC VOLTAMMET.	"
CHROMIUM CHLORIDE (CONTD)	
MOLTEN SALT - - -	561
CHROMIUM OXIDE	
ALUMINUM OXIDE ->	175
GALVANIC CELL - -	"
MISCIBILITY GAP -	"
SOLID ELECTROLYTE	"
THERMODYNAMICS -	"
CHRONOAMPEROMETRY	
CHROMIUM CHLORIDE>	561
CHRONOCOULOMETRY	>1026
COBALT HYDROXIDE	"
CYCLIC VOLTAMMET.	561 1026
MOLTEN SALT - - -	561
NICKEL HYDROXIDE	1026
CHRONOCOULOMETRY	
CHRONOAMPEROMETRY>	1026
COBALT HYDROXIDE	"
CYCLIC VOLTAMMET.	"
NICKEL HYDROXIDE	"
CHRONOPOTENTIOME.	
ADRIAMYCIN - - ->	534
ANTHRACYCLINE - -	"
ANTITUMOR ANTIBI.	"
CYCLIC VOLTAMMET.	"
DAUNORUBICIN - -	"
ELECTRODE KINETI.>	1809
FINITE RISE TIME	"
POLAROGRAPHY - -	534
PULSE GENERATOR -	1809
RELAXATION - - -	"
CIRCUIT BOARD	
COPPER PYROPHOSP.>	1218
DIMERCAPTOTHIADI.	"
ELECTROPLATING -	"
FOLDBACK - - - -	"
LEVELING MECHAN.	"
PT-DISK ELECTROD.	"
CLEAN FILM	
ALKALI CONTAMINA.>	106
MICROELECTRONICS	"
MOS STRUCTURE - -	"
POLYSILICON TUBE.	"
SILICON DIOXIDE -	"
COAL GASIFICATION	
CALCIUM FLUORIDE >	758
SOLID ELECTROLYTE	"
SULFUR PROBE - -	"
COBALT	
ACRYLONITRILE - ->	241
ALLYL CHLORIDE ->1232	
ANODIC FILM - - ->1735	
ANODIC OXIDATION	"
BIPYRIDINE - - -	1232
BIPYRIDINE COMPL.	241
CATALYSIS - - - -	" - - - - 1232
ELECTROREDUCTION	"
PASSIVITY - - - -	1735
VINYL MONOMER - -	241
COBALT CYANIDES	
COBALT HARDENING	>1745
GOLD ELECTROPLAT.	"
IMPURITY - - - -	"
COBALT DIFFUSION	
COBALT OXIDE FILM>	898
FILM GROWTH - - -	"
GOLD - - - - - -	"
OXIDATION KINETI.	"
COBALT HARDENING	
COBALT CYANIDES ->1745	
GOLD ELECTROPLAT.	"
IMPURITY - - - -	"
COBALT HYDROXIDE	
CHRONOAMPEROMETRY>	1026
CHRONOCOULOMETRY	"
CYCLIC VOLTAMMET.	"
NICKEL HYDROXIDE	"
COBALT OXIDE FILM	
COBALT DIFFUSION >	898
FILM GROWTH - - -	"
GOLD - - - - - -	"
OXIDATION KINETI.	"
COLD WALL REACTO.	
ATOMIC OXYGEN - ->	110
CVD - - - - - - -	"
KINETIC MECHANISM	"
TIN CHLORIDE - -	"
TIN OXIDE - - - -	"
COLLOIDAL SILICA	
NONABRASION - - ->	136
POLISHING - - - -	"
SAPPHIRE - - - -	"
COLOR BAND	
ION IMPLANTATION	>1331
SILICON - - - - -	"
SILICON WAFER - -	"
TEMPERATURE VARI.	"
COMPOSITION	
CHEMICAL BONDING >	424
CONTAMINATION - -	"
INSULATING FILM -	"
SILICON OXYNITRI.	"
COMPOUND SEMICON.	
ALUMINUM GAAS - ->	989
LOW LEAKAGE - - -	"
MOS - - - - - - -	"
OXIDE - - - - - -	"
CONCENTRATION CE.	
BETA ALUMINA - ->1377	
EMF MEASUREMENT -	"
LIQUID ALLOY - -	"
SODIUM TIN ALLOY	"
CONDENSED PHASE	
HYDROGEN EVOLUTI.>	252
IONIC CONDUCTANC.	"
IONIC EQUILIBRIA	"
PRESSURE EFFECT -	"
CONDUCTANCE	
CYCLIC VOLTAMMET.>	1974
DIMETHYL SULFOXI.	"
INFRARED SPECTRA	"
ION-SOLVENT - - -	"
CONDUCTION	
BETA LEAD FLUORI.>	683
DIFFUSION - - - ->1994	
ELECTROLYTIC DON.	683
HEBB WAGNER POLA.	"
IONIC CONDUCTIVI.	1994
LITHIUM FERRITE -	"
LITHIUM ION - - -	"
CONDUCTIVE FILM	
BIPOLAR DEVICE ->1829	
ION IMPLANTATION	"
PULSIVE NOISE - -	"
CONDUCTIVITY	
ALPHA IRON OXIDE >	723
CALCIUM FLUORIDE >	755
CAPACITANCE - - -	723
DONOR DENSITY - -	"
FLATBAND POTENTI.	"
IONIC TRANSPORT ->	751
MASS TRANSPORT -	755
MOTT SCHOTTKY - -	723
NONSTOICHIOMETRY	751
POLARIZATION - -	755
SOLID ELECTROLYTE	"
ZIRCONIA - - - -	751
CONTACT RESISTAN.	
GAAS - - - - - ->	473
INTERFACE - - - ->	508
PULSE MEASUREMENT	"
SULFUR DIFFUSION	473
TRANSFERRED ELEC.	"
CONTACTLESS MOBI.	
GAAS SUBSTRATE ->1318	
SELENIUM - - - -	"
SEMICONDUCTOR - -	"
SULFUR - - - - -	"
CONTAMINATION	
CHEMICAL BONDING >	424
COMPOSITION - - -	"
INSULATING FILM -	"
SILICON OXYNITRI.	"
CONVECTIVE DIFFU.	
IMPINGING JET - ->1461	
CONVECTIVE DIFFU. (CONTD)	
LIMITING CURRENT	1461
MASS TRANSFER - -	"
UNIFORM ACCESSIB.	"
CONVECTIVE FLOW	
MERCURY OXIDE - ->1020	
SILVER OXIDE - -	"
ZINC ELECTRODE -	"
CONVECTIVE TRANS.	
CORROSION INHIBI.>	524
STEEL - - - - - -	"
SULFURIC ACID - -	"
CONVERGING ELECT.	
CURRENT DENSITY ->	697
ELECTROCOATING -	"
FOURIER TRANSFORM	"
LAPLACE EQUATION	"
COPPER	
ACCELERATED TEST >	2005
AGITATION EFFECT >	36
ALUMINUM - - - ->	915
ANODIC OXIDE - -	"
ATMOSPHERIC CORR.	2005
AUGER SPECTROSCO.	"
BRIGHTENER - - -	36
COPPER OXIDE - ->	492
CORROSION TEST -	2005
CRYSTALLIZATION -	492
CVD - - - - - - ->	823
DEPTH PROFILING -	915
GALLIUM DIFFUSION>	963
GETTERING - - - -	"
GLASSY LAYER - -	823
GOLD - - - - - -	963
HEAT EFFECT - - -	492
IMPURITY SINK - -	963
MORPHOLOGY - - -	36
NEUTRON ACTIVATI.	963
NICKEL - - - - -	2005
NITROGEN OXIDE ->1114	
PASSIVATION - - -	823
PLATING CELL - -	36
PRINTED WIRING -	"
RELATIVE HUMIDITY	1114
RUTHERFORD BACKS.	915
SILICON - - - - -	963
SILICON DIOXIDE -	823
SILVER - - - - -	2005
SOLDER GLASS - -	492
THROWING POWER -	36
COPPER ALLOY	
AUGER SPECTROSCO.>	1801
COPPER ELECTRODE >	1598
CUPRONICKEL - - -	1801
NICKEL ALLOY - -	"
OXIDE FILM - - -	1598 - - - 1801
PHOTOPOTENTIAL -	1598
WHITE LIGHT - - -	"
COPPER AMALGAM	
ANODIC OXIDATION >	1960
LITHIUM HYDROXIDE	"
NUCLEATION - - -	"
POLYCRYSTAL COPP.	"
COPPER CORROSION	
AUGER SPECTROSCO.>	17
DEPTH PROFILE - -	"
DISSOLUTION RATE	"
NOBLE METAL - - -	"
PALLADIUM - - - -	"
PASSIVITY - - - -	"
PHOTOLYSIS - - ->1889	
COPPER DEPOSITION	
CURRENT DISTRIBU.>	58
ELECTRODE CONFIG.	"
ELECTROLESS PLAT.>	173
FORMALDEHYDE - -	"
MASS TRANSFER - -	58
MATRIX CONDUCTIV.	"
MIXED POTENTIAL -	173
POROUS ELECTRODE	58
POTENTIAL DISTRI.	"
SILVER DEPOSITIO.	"
COPPER ELECTRODE	
COPPER ALLOY - ->1598	
OXIDE FILM - - -	"
PHOTOPOTENTIAL -	"
WHITE LIGHT - - -	"

PRIMARY TERM — CO-TERM — PAGE NO.

COPPER INDIUM SU.
LIQUID JUNCTION -> 831
SOLAR CELL - - - "

COPPER OXIDATION
LINEAR KINETICS -> 803
NUCLEATION - - - "

COPPER OXIDE
COPPER - - - - - -> 492
CRYSTALLIZATION - "
HEAT EFFECT - - - "
SOLDER GLASS - - "

COPPER PLATING
BIPOLAR ELECTRODE> 209
CURRENT DENSITY - "
ELECTRODEPOSITION "
ELECTROPLATING - "
WIRING BOARD - - "

COPPER PYROPHOSP.
BRIGHTENER CONCE.> 194
CIRCUIT BOARD - ->1218
DIMERCAPTOTHIADI. "
ELECTROPLATING - 194
- 1218
FOLDBACK - - - - "
LEVELING MECHAN. "
PT-DISK ELECTROD. "
STRIPPING METHOD 194
VOLTAMMETRY - - - "

COPPER SULFIDE
CHALCOCITE - - ->1684
CHEMICAL DIFFUSI. "
EPITAXIAL LAYERS > 882
LIQUID SOLUTION - "
METHANOL - - - - "
NONSTOICHIOMETRY 1684
RHEED - - - - - - 882

COPRECIPITATION
CATHODOLUMINESCE.> 102
EUROPIUM - - - - "
LOW ENERGY ELECT. "
POWDER PHOSPHOR - "
TIN DIOXIDE - - - "

COPYROLYSIS
AMMONIA - - - - -> 487
CVD - - - - - - - "
POINT TO POINT - "
SILANE - - - - - "
SILICON NITRIDE - "
THERMOCOUPLE ANA. "

CORROSION
ACID FUEL CELL ->1899
ALCOHOLS - - - -> 97
ALUMINUM ALLOY ->1924
ALUMINUM COPPER -> 30
ALUMINUM OXIDATI.> 787
ANODIC BEHAVIOR -> 1
ANODIC OXIDATION 30
CAPACITY LOSS - ->1587
CARBON BLACK - ->1719
CARBON TETRACHLO. 97
CHLORIDE SOLUTIO.> 853
CHROMIUM - - - ->2062
CYCLIC VOLTAMMET.>1977
DISSOLUTION - - - 1
- - - ->1729
DISSOLUTION KINE. 853
ELECTROCATALYST ->1482
ELECTRODE KINETI. 2062
ELECTRODE KINETIC 1977
ELECTRODISSOLUTI. 853
ELECTRON MICROSC. 1482
ELECTRON TRANSFER 1729
GAS TURBINE - - ->1283
HEAT TREATMENT -> 199
HYDROGEN EFFECT - "
IMPEDANCE PARAME. 2062
INSULATOR - - - - 787
INTEGRATED CIRCU. 30
787
ION EXCHANGE - - 1482
IRON - - - - - - 853
LINEAR POLARIZAT. 1977
LITHIUM - - - - - 1
LITHIUM HYDROXIDE "
MAGNESIUM ANODE - 1924
MANGANESE DIOXIDE "
METAL FILM - - - 30
METALLIZATION - - "
MONOHYDRATE-WATER 1899

CORROSION (CONTD)
NICKEL ALUMINIDE 1283
ORGANIC SOLVENT - 97
PHOSPHORIC ACID - 1719
- 1899
POLARIZATION - - 1587
PORTABLE HEATER - 1924
PSEUDOINDUCTANCE 1977
2062
REPASSIVATION - - 1729
RUTHENIUM OXIDE - 1482
SALINE CELL - - - 1924
SODIUM CHLORIDE - 1283
SODIUM SULFUR - - 1587
SOLID POLYMER - - 1482
STAINLESS STEEL - 1587
- 1729
STEAM - - - - - - 199
SULFURIC ACID - - 1899
- - 2062
TRIFLUOROMETHANE 1899
WHISKERS - - - - 1283
ZIRCALOY 4 - - - 199

CORROSION CONTROL
BIBLIOGRAPHY - -> 58C
CORROSION RESEAR. "
STRESS CRACKING - "

CORROSION INHIBI.
ACID - - - - - ->1393
CONVECTIVE TRANS.> 524
IRON - - - - - - 1393
STEEL - - - - - - 524
SULFURIC ACID - - "
THIOUREA - - - - 1393

CORROSION KINETI.
FICKS LAW - - - ->1610
FILM GROWTH - - - "
NOBLE METAL ALLOY "
SOLUTE SEGREGATI. "

CORROSION PROTEC.
CARBONATE CELL ->1799
LITHIUM ALUMINATE "
STAINLESS STEEL - "
WET SEAL - - - - "

CORROSION RATE
COULOSTATIC METH.>1389
HIGH IMPEDANCE - "
POTENTIAL DECAY - "
STEEL - - - - - - "

CORROSION RATES
POLARIZATION DATA>1988
TAFEL SLOPE - - - "

CORROSION RESEAR.
BIBLIOGRAPHY - -> 58C
CORROSION CONTROL "
STRESS CRACKING - "

CORROSION RESIST.
ALUMINUM ALLOY -> 271
CHROMIUM ALLOY - "
NICKEL ALLOY - - "
PASSIVATION - - -> 420
RELATIVE HUMIDITY "
SODIUM SULFATE - 271
SURFACE ROUGHNESS 420
TIN NICKEL ALLOY "

CORROSION TEST
ACCELERATED TEST >2002
>2005
ATMOSPHERIC CORR. "
AUGER SPECTROSCO. "
COPPER - - - - - "
HUMIDITY - - - - 2002
KINETIC RATE - - "
NICKEL - - - - - 2005
POLLUTANTS - - - 2002
SILVER - - - - - 2005

CORUNDUM
ALUMINA - - - - -> 889
ENERGY OF FORMAT. "

COULOMETRIC TITR.
ENTHALPY - - - -> 7
ENTROPY - - - - - "
GALVANIC CELL - - "
GIBBS FREE ENERGY "
INTERMETALLIC - - "
LITHIUM ANTIMONY "

COULOMETRIC TITR. (CONTD)
LITHIUM BISMUTH - 7

COULOMETRY
CATALYTIC WAVES ->1069
CATHODIC REDUCTI.> 714
CYCLIC VOLTAMMET. 1069
>1250
DINITROANALINE - 714
FERRIHEME - - - - 1250
MARCUS THEORY - - "
MERCURY POOL - - 714
PH DEPENDENCY - - "
POLAROGRAPHY - - 1250
RUTHENIUM DIOXID. 1069
RUTHENIUM OXIDE - "

COULOSTATIC DEPO.
CAPACITANCE - - -> 380
DOUBLE LAYER - - "
GOLD - - - - - -> 384
MERCURY - - - - - "
POTENTIAL RELAXA. 380
384
UNDERPOTENTIAL - 380
- 384

COULOSTATIC METH.
CORROSION RATE ->1389
HIGH IMPEDANCE - "
POTENTIAL DECAY - "
STEEL - - - - - - "

CREEPAGE RATE
ALKALINE CELL - ->1918
CATION MOBILITY - "
ELECTROREDUCTION "

CROSS BRIDGE STR.
DIFFUSED LAYER -> 650
LINE WIDTH - - - "
PROCESS CONTROL - "
SHEET RESISTANCE "
VAN DER PAUW - - "

CROSS STRUCTURE
DIFFUSED LAYER -> 645
LEAKAGE CURRENT - "
SHEET RESISTANCE "
VAN DER PAUW - - "

CROSSLINKING
BISAZIDE - - - ->1126
PHOTORESIST SYST. "
POLYMERIZATION - "

CRYSTAL FACET
CRYSTAL ORIENTAT.>1940
DEPASSIVATION - - "
ELECTRODEPOSITION "
NICKEL SUBSTRATE "
PHOSPHORIC ACID - "

CRYSTAL GROWTH
CRYSTAL SEGREGAT.>1832
DIFFUSION CONTROL "
ELECTROTHERMICS ->241C
EXTRACTIVE METAL. "
GAAS - - - - - -> 130
GALLIUM DOPING -> 475
- 1832
GERMANIUM - - - - 475
- - - - 1832
HETEROEPITAXY - - 130
INDIUM PHOSPHIDE "
LPE - - - - - - - "
MELT FLOW - - - - 475
THERMAL GRADIENT "
VACUUM METALLURG. 241C
ZERO GRAVITY - - 1832

CRYSTAL ORIENTAT.
ARSENIC - - - - -> 461
CRYSTAL FACET - ->1940
DEPASSIVATION - - "
ELECTRICAL ACTIV. 461
ELECTRODEPOSITION 1940
EPITAXIAL REGROW. 461
NICKEL SUBSTRATE 1940
PHOSPHORIC ACID - "
RECRYSTALLIZATION 461
SILICON - - - - - "

CRYSTAL PERFECTI.
ALUMINUM OXIDE ->2079
CVD - - - - - - - "
CZOCHRALSKI-GROWN "

CRYSTAL PERFECTI. (CONTD)
X-RAY DIFFRACTION 2079

CRYSTAL SEGREGAT.
CRYSTAL GROWTH ->1832
DIFFUSION CONTROL "
GALLIUM DOPING - "
GERMANIUM - - - - "
ZERO GRAVITY - - "

CRYSTAL STRUCTURE
ALUMINA - - - - -> 890
ANNEALING - - - -> 927
CVD - - - - - - - "
ENERGY OF FORMAT. 890
LOW PRESSURE - - 927
PHASE DIAGRAM - - 890
SILICON FILM - - 927
STRUCTURE - - - - "

CRYSTALLINE PERF.
FET MOBILITY - -> 792
MOS TRANSISTOR - "
SAPPHIRE - - - - "
SILICON - - - - - "
X-RAY DIFFRACTOM. "

CRYSTALLINE QUAL.
CARRIER CONCENTR.>2076
DIODE - - - - - - "
GALLIUM NITRIDE - "
SURFACE MORPHOLO. "
X-RAY DIFFRACTION "

CRYSTALLIZATION
COPPER - - - - -> 492
COPPER OXIDE - - "
HEAT EFFECT - - - "
SOLDER GLASS - - "

CRYSTALLOGRAPHY
ACTIVITY COEFFIC.>1689
SELF DIFFUSION - "
SODIUM GALLATE - "
SODIUM MIGRATION "

CUPRONICKEL
AUGER SPECTROSCO.>1801
COPPER ALLOY - - "
NICKEL ALLOY - - "
OXIDE FILM - - - "

CUPROUS IODIDE
CAPACITANCE - - -> 613
ELECTRICAL CONDU. "
TRANSFERENCE NUM. "

CURRENT DECAY
ELLIPSOMETRY - ->1416
NICKEL - - - - - "
OXIDE FILM - - - "
OXYGEN EVOLUTION "
REJUVENATION - - "

CURRENT DENSITY
ANODIC OXIDE - ->1032
BIPOLAR ELECTRODE> 209
BREAKDOWN VOLTAGE 1032
CATHODE REACTION >1574
CONVERGING ELECT.> 697
COPPER PLATING - 209
ELECTROCOATING - 697
ELECTRODEPOSITION 209
ELECTROPLATING - "
ELLIPSOMETRY - - 1032
EQUILIBRIUM POTE.>1591
FOURIER TRANSFORM 697
IONIC STRENGTH - 1591
LAPLACE EQUATION 697
LITHIUM CELL - - 1574
MASS TRANSPORT - "
POTASSIUM HYDROX. 1591
SULFONYL CHLORIDE 1574
TITANIUM - - - - 1032
WIRING BOARD - - 209
ZINC ELECTRODE - 1591

CURRENT DISTRIBU.
BAFFLE - - - - -> 84
COPPER DEPOSITION> 58
ELECTRODE CONFIG. "
ELECTRODEPOSITION>1981
FINITE ELEMENT - "
FLAT STRIP ELECT. 84
MASS TRANSFER - - 58
- - -> 79
MATHEMATICAL MOD. 1981

PRIMARY TERM CO-TERM	PAGE NO.
CURRENT DISTRIBU. (CONTD)	
MATRIX CONDUCTIV.	58
POROUS ELECTRODE	"
POTENTIAL DISTRI.	" 1981
PRIMARY CURRENT -	79
PRIMARY RESISTAN.	"
RECTANGULAR CELL	84
RING ELECTRODE -	79
SECONDARY CURRENT	"
SHAPE CHANGE - -	1981
SILVER DEPOSITIO.	58
CURRENT EFFICIEN.	
CALCIUM ANODE -	->1209
CALORIMETRY - - -	"
HALIDE SALTS - -	"
NITRATE ELECTROL.	"
PASSIVATING LAYER	"
CURRENT RISE	
AQUEOUS ELECTROL.	>1185
GAAS ELECTRODE -	"
SEMICONDUCTOR - -	"
CV PRODUCT	
ALUMINUM FOIL -	->1950
ANODIZATION - - -	"
ELECTROLYTIC CAP.	"
TUNNEL ETCHING -	"
CVD	
ALUMINUM NITRIDE	> 305
ALUMINUM OXIDE	->2079
AMMONIA - - - - -	-> 487
ANNEALING - - -	-> 927
ATOMIC OXYGEN -	-> 110
CHARGE STORAGE -	305
COLD WALL REACTO.	110
COPPER - - - - -	-> 823
COPYROLYSIS - - -	487
CRYSTAL PERFECTI.	2079
CRYSTAL STRUCTURE	927
CZOCHRALSKI-GROWN	2079
DIELECTRIC FILM	-> 819
DIFFUSION - - -	->1557
ENCAPSULANT FILM	>1525
FILM PROPERTY - -	305
FILM STRESS - -	-> 139
GAAS - - - - - -	1525
GAAS FILM - - -	->1668
GLASSY LAYER - -	823
GRAPHITE - - - -	1668
HOT-WALL - - - -	1557
INTEGRATED CIRCU.	> 601 1557
ION IMPLANTATION	1525
KINETIC MECHANISM	110
LOW PRESSURE - -	927
MASS SPECTROMETRY	>1877
MEMORY - - - - -	305
MOS LSI PASSIVAT.	601
OXIDATION BARRIER	139
OXYGEN - - - - -	->1298
PASSIVATION - - -	823
PLASMA CHEMISTRY	1298
POINT TO POINT -	487
REACTION MECHANI.	>1534
REACTIVE PLASMA -	601
SILANE - - - - -	487
SILICON DIOXIDE -	139 - 819 - 823
SILICON FILM - -	927
SILICON NITRIDE -	139 - 305 - 487 - 601 - 819 - 1525 - 1557 - 1877
SOLAR CELL - - -	1668
STRUCTURE - - - -	927
TETRACHLOROSILANE	1298
TETRAFLUOROSILANE	"
THERMOCOUPLE ANA.	487
TIN CHLORIDE - -	110
TIN OXIDE - - - -	"
TUNGSTEN - - - -	1668
TUNGSTEN DEPOSIT.	1534
TUNGSTEN HEXAFLU.	"
X-RAY DIFFRACTION	2079
CVD REACTOR	
EPITAXIAL REACTOR	> 317
SILICON DEPOSITI.	"
CVD REACTOR (CONTD)	
TRANSPORT PHENOM.	317
CVD SILICON NITR.	
ACIDIC FLUORIDE ->	320
DISSOLUTION PROC.	"
ETCHING - - - - -	"
CYCLE LIFE	
ANODIC DISCHARGE >	727
LITHIUM ALUMINUM	"
MOLTEN SALT ELEC.	"
CYCLIC VOLTAMMET.	
ADRIAMYCIN - - -	-> 534
ANTHRACYCLINE - -	"
ANTITUMOR ANTIBI.	" > 540
BISMUTH FLUORIDE	> 511
CATALYTIC WAVES	->1069
CHROMIUM CHLORIDE	> 561
CHRONOAMPEROMETRY	" >1026
CHRONOCOULOMETRY	"
CHRONOPOTENTIOME.	534
COBALT HYDROXIDE	1026
CONDUCTANCE - - -	->1974
CORROSION - - - -	->1977
COULOMETRY - - -	1069 - - ->1250
DAUNOMYCINONE - -	540
DAUNORUBICIN - -	534
DIMETHYL SULFOXI.	1974
DISPROPORTIONATI.	> 547
EE MECHANISM - -	"
ELECTRODE KINETIC	1977
EQUIVALENT CIRCU.	>1443
FERRIHEME - - - -	1250
HYSTERESIS - - -	1443
IMPEDANCE - - - -	"
INFRARED SPECTRA	1974
ION-SOLVENT - - -	"
LINEAR POLARIZAT.	1443 1977
LITHIUM BATTERY -	511
MARCUS THEORY - -	1250
MOLTEN SALT - - -	561
NICKEL HYDROXIDE	1026
NONAQUEOUS SOLVE.	511
POLAROGRAPHY - -	534 - - 1250
PSEUDOINDUCTANCE	1977
QUINONE - - - - -	540
RESISTIVE-CAPACI.	1443
RUTHENIUM DIOXID.	1069
RUTHENIUM OXIDE -	"
TRANSFORM ANALYS.	1443
TWO ELECTRON - -	547
CYCLING EFFICIEN.	
LITHIUM BATTERY -	>1371
ORGANIC ELECTROL.	"
TETRAHYDROFURAN -	"
CZOCHRALSKI CRYS.	
DIFFUSION LENGTH >	661
HALL MOBILITY - -	"
PURIFICATION - -	"
SILICON - - - - -	"
SOLIDIFICATION -	"
CZOCHRALSKI PULL.	
FLOATING ZONE - -	> 595
P-N JUNCTION - -	"
PURIFIED SILICON	"
SOLAR CELL - - -	"
VAPOR DEPOSITION	"
CZOCHRALSKI-GROWN	
ALUMINUM OXIDE -	>2079
CRYSTAL PERFECTI.	"
CVD - - - - - - -	"
X-RAY DIFFRACTION	"
D-C RESPONSE	
HYDROCHLORIC ACID	> 985
MNOS TRANSISTOR -	"
PULSE - - - - - -	"
D-ENERGY BAND	
HOLE REACTION - -	>1086
MOLYBDENUM SELEN.	"
SOLAR ENERGY - -	"
DAUNOMYCINONE	
ANTITUMOR ANTIBI.	> 540
CYCLIC VOLTAMMET.	"
DAUNOMYCINONE (CONTD)	
QUINONE - - - - -	540
DAUNORUBICIN	
ADRIAMYCIN - - -	-> 534
ANTHRACYCLINE - -	"
ANTITUMOR ANTIBI.	"
CHRONOPOTENTIOME.	"
CYCLIC VOLTAMMET.	"
POLAROGRAPHY - -	"
DECOMPOSITION	
ALUMINUM OXIDE	-> 327
ALUMINUM SULFATE	"
ANILINE - - - - -	->1059
EPR - - - - - - -	"
GASEOUS PRODUCT -	327
SOLID PRODUCT - -	"
SULFUR DIOXIDE -	"
SULFUR TRIOXIDE -	"
VOLTAMMETRY - - -	1059
DEEP DIFFUSION	
PIN DIODE - - - -	-> 680
PLASMA PASSIVATI.	"
DEEP LEVEL DEFECT	
INTERFACE STATE	->1664
MOS - - - - - - -	"
SLOW COOLING - -	"
TRANSIENT CAPACI.	"
DEFECT FORMATION	
SILICON - - - -	->1680
STACKING FAULT -	"
STEAM OXIDATION -	"
DEFECT STRUCTURE	
GALLIUM - - - -	->1355
HALL EFFECT - - -	"
PRECIPITATES - -	"
RESISTIVITY - - -	"
ZINC SELENIDE - -	"
DELIQUESCENCE	
GRAVIMETRIC ANAL.	> 734
HYGROSCOPICITY -	"
RELATIVE HUMIDITY	"
DELTA LATTICE PA.	
ELECTRONIC PROPE.	> 992
DEPASSIVATION	
CRYSTAL FACET -	->1940
CRYSTAL ORIENTAT.	"
ELECTRODEPOSITION	"
NICKEL SUBSTRATE	"
PHOSPHORIC ACID -	"
DEPLETION LAYER	
BAND BENDING - -	-> 937
BUTLER VOLMER - -	"
DIFFUSION THEORY	"
OVERVOLTAGE - - -	"
PHOTOELECTRODE -	"
RECOMBINATION - -	"
DEPOLARIZATION	
ACTIVATION ENERGY	> 434
INITIAL RISE - -	"
PVC - - - - - - -	"
THERMOELECTRET -	"
DEPOSITION	
DIPYRIDINIUM COM.	>1397
NUCLEATION - - -	"
TIN OXIDE - - - -	"
VIOLOGENS - - - -	"
DEPOSITION RATE	
ALUMINUM OXIDE	-> 902
ELLIPSOMETRY - -	"
FILM PROPERTIES -	"
INSULATOR - - - -	"
DEPOSITION TEMPE.	
ANTIREFLECTION	-> 983
TITANIUM DIOXIDE	"
DEPTH PROFILE	
AUGER SPECTROSCO.	> 17 > 48
BACKSCATTERING	->1215
COPPER CORROSION	17
DISSOLUTION RATE	"
GAAS - - - - - -	481
MASS SPECTROMETRY	1215
DEPTH PROFILE (CONTD)	
NEUTRON ACTIVATI.	481
NICKEL - - - - -	1215
NOBLE METAL - - -	17
PALLADIUM - - - -	"
PASSIVITY - - - -	"
PLASMA OXIDATION	481
RUTHERFORD - - -	1215
TIN - - - - - - -	"
DEPTH PROFILING	
ALUMINUM - - - -	-> 915
ANODIC OXIDE - -	"
COPPER - - - - -	"
RUTHERFORD BACKS.	"
DESALINATION	
CARBON ELECTRODE >	869
PARAMETRIC PUMP -	"
SEPARATION - - -	"
DIAPHRAGM CELL	
CHLOR-ALKALI - -	> 22C
FLUORINE - - - -	"
INDUSTRIAL CHEMI.	"
DICYANOAURATE	
ADSORPTION EQUIL.	> 717
ELECTROCRYSTALLI.	"
EPITAXY - - - - -	"
GOLD PLATING - -	"
DIELECTRIC	
ELECTRIC FIELD	->1244
TANTALUM - - - -	"
TISSUE STIMULATI.	"
DIELECTRIC CHAOS	
DOPED HALIDES -	->2084
SPACE CHARGE - -	"
THERMAL DEPOLARI.	"
DIELECTRIC FILM	
CVD - - - - - - -	-> 819
SILICON DIOXIDE -	"
SILICON NITRIDE -	"
DIELECTRIC ISOLA.	
OXIDE DEFECT -	->1703
OXIDE ISOLATION -	"
STAIN PROFILE - -	"
DIELECTRIC PROPE.	
CAPACITOR - - -	-> 746
HEAT TREATMENT -	"
MAXWELL WAGNER -	"
TANTALUM OXIDE -	"
TWO LAYER MODEL -	"
DIELECTRICS	
ELECTRON DIFFRAC.	>1191
ELECTROSTATIC - -	"
LENS - - - - - -	"
DIFFUSED LAYER	
CROSS BRIDGE STR.	> 650
CROSS STRUCTURE ->	645
LEAKAGE CURRENT -	"
LINE WIDTH - - -	650
PROCESS CONTROL -	"
SHEET RESISTANCE	645 650
VAN DER PAUW - -	645 - - 650
DIFFUSION	
ALUMINUM - - - -	-> 957
BORON - - - - - -	->2050
CHEMILUMINESCENCE	>1079
CONDUCTION - - -	->1994
CVD - - - - - - -	->1557
DOPING SILICON -	957
HOT-WALL - - - -	1557
INTEGRATED CIRCU.	"
ION IMPLANTATION	2050
IONIC CONDUCTIVI.	1994
LITHIUM BATTERY	->1193
LITHIUM CHLORIDE	"
LITHIUM FERRITE -	1994
LITHIUM ION - - -	"
MIGRATION PROCESS	1193
MOLTEN SALT - - -	"
OPEN TUBE - - - -	957
OXIDATION - - - -	2050
POTASSIUM CHLORI.	1193
REACTION ZONE - -	1079
SEGREGATION - - -	2050

PRIMARY TERM / CO-TERM — PAGE NO.

DIFFUSION (CONTD)
SILICON NITRIDE - 1557
SILICON OXIDE - - 2050
TRIPLET LIFETIME 1079
VACUUM - - - - - 957

DIFFUSION BARRIER
ALUMINUM METALLI.> 156
BEAM LEADS - - - "
GOLD - - - - - - "

DIFFUSION CHARAC.
CHROMIUM - - - -> 55C
MAGNETITE - - - - "
OXYGEN PRESSURE - "

DIFFUSION COEFFI.
CATION EXCHANGE -> 556
CHLORINE BATTERY > 89
GRAIN BOUNDARY ->2070
MASS TRANSFER - - 89
PERMEATION ANALY. 2070
POTASSIUM HYDROX. 556
ROTATING HEMISPH. 89
TRANSFERENCE - - 556
TRANSPORT PARAME. "
ZINC BATTERY - - 89
ZINC HEMISPHERE - "

DIFFUSION CONTROL
CRYSTAL GROWTH ->1832
CRYSTAL SEGREGAT. "
GALLIUM DOPING - "
GERMANIUM - - - - "
ZERO GRAVITY - - "

DIFFUSION FLUX
FUSED SALTS - - ->1110
TRANSPORT COEFFI. "

DIFFUSION LAYER
LIMITING CURRENT > 845
LITHIUM - - - - - "
LITHIUM HYDROXIDE "
MASS TRANSFER - ->1772
POLARIZATION - - 845
PULSED ELECTROLY. 1772
ROTATING DISK EL. "

DIFFUSION LENGTH
CZOCHRALSKI CRYS.> 661
GAAS - - - - - ->2034
HALL MOBILITY - - 661
MODELING - - - - 2034
PURIFICATION - - 661
RADIATION DAMAGE 2034
SILICON - - - - - 661
SOLAR CELL - - - 2034
SOLIDIFICATION - 661
SURFACE RECOMBIN. 2034

DIFFUSION PROFILE
BOLTZMANN-MATANO >1530
CADMIUM - - - - - "
DOPANT CONCENTRA.>1672
GAAS - - - - - - "
GRADED C-V - - - 1530
INDIUM ANTIMONIDE "
SPREADING RESIST. 1672

DIFFUSION THEORY
BAND BENDING - -> 937
BUTLER VOLMER - - "
DEPLETION LAYER - "
OVERVOLTAGE - - - "
PHOTOELECTRODE - "
RECOMBINAT.ON - - "

DIFFUSIVITY
BORON - - - - - -> 813
SEGREGATION - - - "
SILICON - - - - - "

DIMERCAPTOTHIADI.
CIRCUIT BOARD - ->1218
COPPER PYROPHOSP. "
ELECTROPLATING - "
FOLDBACK - - - - "
LEVELING MECHAN. "
PT-DISK ELECTROD. "

DIMETHYL SULFITE
GRAPHITE - - - -> 687
LITHIUM PERCHLOR. "
RADICAL CATION - "

DIMETHYL SULFOXI.
CONDUCTANCE - - ->1974
CYCLIC VOLTAMMET. "
INFRARED SPECTRA "
ION-SOLVENT - - - "

DINITROANALINE
CATHODIC REDUCTI.> 714
COULOMETRY - - - "
MERCURY POOL - - "
PH DEPENDENCY - - "

DIODE
CARRIER CONCENTR.>2076
CRYSTALLINE QUAL. "
GAAS - - - - - ->1505
GALLIUM NITRIDE - 2076
ION IMPLANTATION 1505
PREDEPOSITION - - "
SEMICONDUCTOR - - "
SURFACE MORPHOLO. 2076
X-RAY DIFFRACTION "
ZINC - - - - - - 1505

DIPYRIDINIUM CON.
DEPOSITION - - ->1397
NUCLEATION - - - "
TIN OXIDE - - - - "
VIOLOGENS - - - - "

DISCHARGE REACTI.
CALORIMETRY - - -> 674
LITHIUM CELL - - "
SULFOXYDICHLORID. "

DISLOCATION
GERMANIUM - - - ->1840
PHOSPHORUS DIFFU. "
SILICON - - - - - "
STRAIN - - - - - "

DISLOCATION DIPO.
CHEMICAL ETCHING > 671
DISLOCATION LOOP "
GALLIUM PHOSPHIDE "

DISLOCATION LOOP
CHEMICAL ETCHING > 671
DISLOCATION DIPO. "
GALLIUM PHOSPHIDE "

DISLOCATIONS
ELECTROETCHING -> 621
GAAS - - - - - - "
STRIATIONS - - - "

DISPROPORTIONATI.
CYCLIC VOLTAMMET.> 547
EE MECHANISM - - "
TWO ELECTRON - - "

DISSOLUTION
ANODIC BEHAVIOR -> 1
CORROSION - - - - "
- - - ->1729
ELECTRON TRANSFER "
GROWTH BEHAVIOR ->1471
LITHIUM - - - - - 1
LITHIUM HYDROXIDE "
NOBLE METAL - - - 1471
OXIDE FILM - - - "
REPASSIVATION - - 1729
RUTHENIUM ELECTR. 1471
STAINLESS STEEL - 1729

DISSOLUTION KINE.
CHLORIDE SOLUTIO.> 853
CORROSION - - - - "
ELECTRODISSOLUTI. "
IRON - - - - - - "

DISSOLUTION PROC.
ACIDIC FLUORIDE -> 320
CVD SILICON NITR. "
ETCHING - - - - - "

DISSOLUTION RATE
AUGER SPECTROSCO.> 17
COPPER CORROSION "
DEPTH PROFILE - - "
NOBLE METAL - - - "
PALLADIUM - - - - "
PASSIVITY - - - - "

DL-MESO RATIO
ELECTROHYDRODIME.> 372
LIQUID CHROMATOG. "

DL-MESO RATIO (CONTD)
P-HYDROXYBENZALD. 372
STEREOISOMER - - "

DOMAIN VELOCITY
P-TYPE - - - - -> 993
PHASE MEMORY - - "
PHOTOCONDUCTOR - "

DONOR DENSITY
ALPHA IRON OXIDE > 723
CAPACITANCE - - - "
CONDUCTIVITY - - "
FLATBAND POTENTI. "
MOTT SCHOTTKY - - "

DOPANT CONCENTRA.
DIFFUSION PROFILE>1672
GAAS - - - - - - "
SPREADING RESIST. "

DOPANT DENSITY
ALPHA TRACK - - -> 654
BORON - - - - - - "
NUCLEAR TRACK - - "
SILICON - - - - - "

DOPANT SYSTEM
ARSINE - - - - ->1860
SILANE - - - - - "
SILICON EPITAXY - "
TRANSFER FUNCTION "

DOPED ALKALI HAL.
POTASSIUM CHLORI.> 430
QUENCHED CRYSTALS "
SODIUM CHLORIDE - "
THERMAL DEPOLARI. "

DOPED HALIDES
DIELECTRIC CHAOS >2084
SPACE CHARGE - - "
THERMAL DEPOLARI. "

DOPING
BORON DIFFUSION ->1521
BORON OXIDE - - - "
BORON TRIBROMIDE > 609
BOROSILICATES - - 1521
EPITAXIAL LAYER -> 350
EPITAXIAL WAFER - "
NEUTRON IRRADIAT. "
NEUTRON TRANSMUT. "
OXIDATION KINETI.> 665
PHOSPHORUS - - - "
PREDEPOSITION - - 609
PROPANE GAS - - ->1676
RATE CONSTANT - - 665
SENSOR - - - - - 1676
SILICON - - - - - 350
- - - - - 609
- - - - - 665
- - - - - 1521
TIN OXIDE - - - - 1676
TRANSITION METALS "

DOPING LEVEL
JUNCTION LEAKAGE >1648
P-N DIODE - - - - "
POLYSILICON - - - "

DOPING SILICON
ALUMINUM - - - -> 957
DIFFUSION - - - - "
OPEN TUBE - - - - "
VACUUM - - - - - "

DOUBLE LAYER
CAPACITANCE - - -> 380
COULOSTATIC DEPO. "
POTENTIAL RELAXA. "
UNDERPOTENTIAL - "

DSC
AVRAMI EQUATION -> 330
DTA - - - - - - - "
METASTABLE ALLOY "
TIN NICKEL - - - "

DTA
AVRAMI EQUATION -> 330
DSC - - - - - - - "
METASTABLE ALLOY "
TIN NICKEL - - - "

DUAL DIELECTRICS
CHARGE ACCUMULAT.>1657

DUAL DIELECTRICS (CONTD)
MNOS FET DEVICE - 1657
THRESHOLD VOLTAGE "

DUCTILITY
BRITTLE COATING -> 400
FOUR POINT BEND - "

DUMMYING
ELECTROLYSIS - -> 204
NICKEL PLATING - "
PURIFICATION - - "

DURABILITY
EMISSIVITY - - ->1361
SELECTIVE COATING "
SOLAR COLLECTOR - "
ZINC OXIDE - - - "

DYE ADSORPTION
DYE SENSITIZATIO.> 51
FLUORESCENCE - - "
PHOTOSENSITIZATI. "
QUENCHING - - - - "
SALT ADDITION - - "
ZINC OXIDE - - - "

DYE SENSITIZATIO.
DYE ADSORPTION -> 51
FLUORESCENCE - - "
PHOTOSENSITIZATI. "
QUENCHING - - - - "
SALT ADDITION - - "
ZINC OXIDE - - - "

EDTA
MOLYBDENUM DIMERS>287C
OXYGEN - - - - - "
SULFUR - - - - - "

EE MECHANISM
CYCLIC VOLTAMMET.> 547
DISPROPORTIONATI. "
TWO ELECTRON - - "

ELECTRET
POLARIZATION - -> 409
POLYELECTROLYTE - "

ELECTRIC FIELD
DIELECTRIC - - ->1244
INSULATING LIQUID>1404
MENISCUS RISE - - "
TANTALUM - - - - 1244
TISSUE STIMULATI. "
YOUNG AND DUPREE 1404

ELECTRIC INSTABI.
OXIDE CHARGE - -> 629
SILICON - - - - - "
SURFACE STATE - - "

ELECTRICAL ACTIV.
ARSENIC - - - - -> 461
CRYSTAL ORIENTAT. "
EPITAXIAL REGROW. "
RECRYSTALLIZATION "
SILICON - - - - - "

ELECTRICAL ANALOG
FUEL CELL ASSEMB.> 515
MANIFOLD MODEL - "
PARASITIC CURREN. "
SHUNT CURRENTS - "

ELECTRICAL CONDU.
CAPACITANCE - - -> 613
CUPROUS IODIDE - "
TRANSFERENCE NUM. "

ELECTRICAL EFFECT
CHLORINE - - - -> 453
GETTERING - - - - "
SILICON OXIDATION "

ELECTRICAL PROPE.
INTERFACE CHARGE >1848
MECHANICAL STRESS "
MNOS MEMORY - - - "
SILICON NITRIDE - "

ELECTROABSORPTION
ELECTROREFLECTAN.> 776
GAAS - - - - - - "
ION IMPLANTATION "
PROTON DAMAGE - - "

PRIMARY TERM / CO-TERM	PAGE NO.
ELECTROANALYSIS	
GAS SENSING	->2506
SPECTROELECTROCH.	"
VOLTAMMETRY	"
ELECTROCAPILLARY	
CAPACITANCE	->1077
GOLD ELECTRODE	"
STRESS-STRAIN	"
ELECTROCATALYSIS	
ISOTOPIC EXCHANGE>	74
LANTHANUM COBALT	"
NICKEL OXIDE	"
OXYGEN REDUCTION >	484
PLATINUM	"
ELECTROCATALYST	
ALKALINE SOLUTIO.>	265
CORROSION	->1482
ELECTRON MICROSC.	"
ION EXCHANGE	"
NICKEL ALLOY	265
OXIDE FILM	"
OXYGEN EVOLUTION	"
RUTHENIUM OXIDE	1482
SOLID POLYMER	"
TAFEL PARAMETER	265
ELECTROCHROMICS	
HEPTYLVIOLOGEN	->1619
INDIUM OXIDE	"
TIN OXIDE	"
TRANSPARENT ELEC.	"
ELECTROCHROMISM	
ANODIC OXIDE FILM>	23
BLUE TUNGSTEN	->1344
ELLIPSOMETRY	23
EMF	->1603
GALVANOSTATIC	-> 284
HYDROGEN	23
HYDROGEN TUNGSTEN	1344
IMPEDANCE	23
LITHIUM TUNGSTEN.	284
NIOBIUM	23
OXIDE FILM	1344
POLARIZABILITY	23
POTENTIOSTATIC	284
TITANIUM	23
TUNGSTEN BRONZE	1603
TUNGSTEN OXIDE	1344
ELECTROCOATING	
CONVERGING ELECT.>	697
CURRENT DENSITY	"
FOURIER TRANSFORM	"
LAPLACE EQUATION	"
ELECTROCRYSTALLI.	
ADSORPTION EQUIL.>	717
DICYANOAURATE	"
EPITAXY	"
GOLD PLATING	"
HYDROGEN	->1049
LINEAR DEFECT	"
NICKEL	"
TEM	"
THIN FILM	"
ELECTRODE ACTIVA.	
IRIDIUM	->1266
MOLTEN SALTS	"
OXIDE LAYER	"
POTENTIODYNAMICS	"
ELECTRODE CONFIG.	
COPPER DEPOSITION>	58
CURRENT DISTRIBU.	"
MASS TRANSFER	"
MATRIX CONDUCTIV.	"
POROUS ELECTRODE	"
POTENTIAL DISTRI.	"
SILVER DEPOSITIO.	"
ELECTRODE KINETI.	
BLOCKING EFFECTS >	389
CHROMIUM	->2062
CHRONOPOTENTIOME.>	1809
CORROSION	2062
FINITE RISE TIME	1809
IMPEDANCE PARAME.	2062
IRON	389
OXYGEN COVERAGE	"
PSEUDOINDUCTANCE	2062
PULSE GENERATOR	1809
QUINONE	389
ELECTRODE KINETI. (CONTD)	
RELAXATION	1809
RHODIUM ELECTRODE	389
SULFURIC ACID	2062
ELECTRODE KINETIC	
CORROSION	->1977
CYCLIC VOLTAMMET.	"
LINEAR POLARIZAT.	"
PSEUDOINDUCTANCE	"
ELECTRODE OXIDAT.	
PASSIVATION	->1790
THIN FILM	"
TITANIUM HYDRIDE	"
ELECTRODE POTENT.	
CALCULATION	-> 808
ENTROPY	"
HEAT CAPACITY	"
METAL WATER SYST.	"
ELECTRODE REACTI.	
LEAD FLUORIDE	->1628
LEAD HALIDES	"
ELECTRODE SEPARA.	
CERAMIC POWDER	->1913
FIBROUS SEPARATOR	"
FUSED SALTS	"
IRON SULFIDE	"
LITHIUM ALUMINUM	"
ELECTRODEPOSITION	
AMMONIA	->1717
BIPOLAR ELECTRODE>	209
BOUNDARY LAYER	-> 865
COPPER PLATING	209
CRYSTAL FACET	->1940
CRYSTAL ORIENTAT.	"
CURRENT DENSITY	209
CURRENT DISTRIBU.>	1981
DEPASSIVATION	1940
ELECTROPLATING	209
FINITE ELEMENT	1981
GOLD	->1717
INDIUM PHOSPHIDE >1721	
MASS TRANSPORT	865
MATHEMATICAL MOD.	1981
MELTING POINT	1721
NICKEL SUBSTRATE	1940
PHOSPHORIC ACID	"
POTENTIAL DISTRI.	1981
SHAPE CHANGE	"
SHEET ELECTRODE	865
TRANSIENTS	"
WIRING BOARD	209
ELECTRODISSOLUTI.	
CHLORIDE SOLUTIO.>	853
CORROSION	"
DISSOLUTION KINE.	"
IRON	"
ELECTROEPITAXY	
GAAS	->1140
	->1560
LAYER THICKNESS	1140
LPE	"
SURFACE MORPHOLO.	1560
THERMAL LPE	"
ELECTROETCHING	
DISLOCATIONS	-> 621
GAAS	"
STRIATIONS	"
ELECTROHYDRODIME.	
DL-MESO RATIO	-> 372
LIQUID CHROMATOG.	"
P-HYDROXYBENZALD.	"
STEREOISOMER	"
ELECTROLESS PLAT.	
COPPER DEPOSITION>	173
FORMALDEHYDE	"
GOLD METALLIZATI.>	522
MIXED POTENTIAL	173
PVDF FILMS	522
ELECTROLITHIATION	
LITHIUM ANODE	->1563
TITANIUM SULFIDE	"
X-RAY DIFFRACTION	"
ELECTROLUMINESCE.	
EPOXY RESIN	-> 581
ELECTROLUMINESCE. (CONTD)	
UV RADIATION	581
X-RAY	"
ELECTROLYSIS	
ACETAL	->1401
ALCOHOL	"
DUMMYING	-> 204
EXCITED STATE	->2180
HALOALDEHYDE	1401
HYDROGEN HALIDE	"
NICKEL PLATING	204
OXIDATION	1401
PURIFICATION	204
REACTIVITY	2180
SEMICONDUCTOR	"
ELECTROLYTIC CAP.	
ALUMINUM FOIL	->1950
ANODIZATION	"
CV PRODUCT	"
TUNNEL ETCHING	"
ELECTROLYTIC DON.	
BETA LEAD FLUORI.>	683
CONDUCTION	"
HEGB WAGNER POLA.	"
ELECTROLYTIC IND.	
ALKALINE COMPOUND>	50
CAUSTIC SODA	->4550
CHLORINE COMPOUND	"
ENERGY SOURCE	50
METALS	"
	4550
ELECTRON AFFINITY	
CELL FABRICATION	>1328
ELECTRON TRANSPO.	>1750
ELECTRONEGATIVIT.>	228
FLATBAND POTENTI.	"
FLUORENONE DERIV.	1750
INDIUM OXIDE	1328
PHOTOCONDUCTIVITY	1750
PHOTOELECTROLYSIS	228
PHOTOVOLTAIC CELL	1328
POLAROGRAPHY	1750
SEMICONDUCTOR	228
	1750
VOLTAMMETRY	"
ZETA POTENTIAL	228
ELECTRON DIFFRAC.	
DIELECTRICS	->1191
ELECTROSTATIC	"
LENS	"
ELECTRON IMAGE	
PALLADIUM	-> 950
PHOTOCATHODES	"
ELECTRON IRRADIA.	
ANNEALING	-> 676
GAAS	"
RADIATION DAMAGE	"
ELECTRON MICROSC.	
CORROSION	->1482
ELECTROCATALYST	"
ION EXCHANGE	"
RUTHENIUM OXIDE	"
SOLID POLYMER	"
ELECTRON PROBE	
IRON NICKEL ALLOY>	279
OXIDATION	"
OXIDE MORPHOLOGY	"
ELECTRON TRANSFER	
CHEMILUMINESCENCE>	1423
CORROSION	->1729
DISSOLUTION	"
EXCITED STATES	1423
REPASSIVATION	1729
SEMICONDUCTOR	1423
STAINLESS STEEL	1729
ELECTRON TRANSPO.	
ELECTRON AFFINITY>	1750
FLUORENONE DERIV.	"
PHOTOCONDUCTIVITY	"
POLAROGRAPHY	"
SEMICONDUCTOR	"
VOLTAMMETRY	"
ELECTRONEGATIVIT.	
ELECTRON AFFINITY>	228
ELECTRONEGATIVIT. (CONTD)	
FLATBAND POTENTI.	228
PHOTOELECTROLYSIS	"
SEMICONDUCTOR	"
ZETA POTENTIAL	"
ELECTRONIC PROPE.	
DELTA LATTICE PA.>	992
ELECTROOXIDATION	
ELECTROSYNTHESIS >	531
GRAPHITE PASTE	"
TYRAMINE	"
ELECTROPLATING	
BIPOLAR ELECTRODE>	209
BRIGHTENER CONCE.>	194
CIRCUIT BOARD	->1218
COPPER PLATING	209
COPPER PYROPHOSP.	194
	1218
CURRENT DENSITY	209
DIMERCAPTOTHIADI.	1218
ELECTRODEPOSITION	209
FOLDBACK	1218
LEVELING MECHAN.	"
PT-DISK ELECTROD.	"
STRIPPING METHOD	194
VOLTAMMETRY	"
WIRING BOARD	209
ELECTROPOLISHING	
ACETIC ACID	->1039
	->1044
ANODIC FILM	1039
ANODIC POLARIZAT.	1044
AUGER ELECTRON S.	1039
PERCHLORIC ACID	"
	1044
POTENTIOSTAT	"
STOICHIOMETRY	"
ELECTROREDUCTION	
ALKALINE CELL	->1918
ALLYL CHLORIDE	->1232
BIPYRIDINE	"
CATALYSIS	"
CATION MOBILITY	1918
COBALT	1232
CREEPAGE RATE	1918
ELECTROREFINING	
ELECTROWINNING	-> 490
FUSED SALT SYSTEM	"
METAL PRODUCTION	"
ELECTROREFLECTAN.	
ELECTROABSORPTION>	776
GAAS	"
ION IMPLANTATION	"
PROTON DAMAGE	"
ELECTROSORPTION	
AUGER	-> 348
HYDROGEN ADSORPT.	"
LEED	"
PLATINUM	"
SINGLE CRYSTAL	"
ELECTROSTATIC	
DIELECTRICS	->1191
ELECTRON DIFFRAC.	"
LENS	"
ELECTROSTRICTION	
ANODIC OXIDATION >	908
ELLIPSOMETRY	"
OXIDE FILM	"
TAFEL SLOPE	"
TUNGSTEN	"
ELECTROSYNTHESIS	
ELECTROOXIDATION >	531
GRAPHITE PASTE	"
TYRAMINE	"
ELECTROTHERMICS	
CRYSTAL GROWTH	->2410
EXTRACTIVE METAL.	"
VACUUM METALLURG.	"
ELECTROWINNING	
ELECTROREFINING ->	490
FUSED SALT SYSTEM	"
METAL PRODUCTION	"

PRIMARY TERM / CO-TERM — PAGE NO.

ELLIPSOMETRY
ACTIVATION - - ->1224
ALUMINUM OXIDE -> 902
ANODIC OXIDATION > 908
ANODIC OXIDE - ->1032
ANODIC OXIDE FILM> 23
AUGER SPECTROSCO. 1224
BREAKDOWN VOLTAGE 1032
CURRENT DECAY - ->1416
CURRENT DENSITY - 1032
DEPOSITION RATE - 902
ELECTROCHROMISM - 23
ELECTROSTRICTION 908
FILM PROPERTIES - 902
HYDROGEN - - - - 23
IMPEDANCE - - - - "
INSULATOR - - - - 902
NICKEL - - - - - 1416
NICKEL PLATING - 1224
NIOBIUM - - - - - 23
OPTICAL PROPERTY > 358
OXIDATION KINETI.>1146
OXIDE FILM - - - 908
- - - 1416
OXYGEN EVOLUTION "
PHOTOELECTRON EM. 1224
POLARIZABILITY - 23
REFRACTIVE INDEX > 968
REJUVENATION - - 1416
SILICON OXIDATION 1146
SILICON OXIDE - - 968
SURFACE POTENTIAL 1224
TAFEL SLOPE - - - 908
TEMPERATURE DEPE. 968
THERMAL OXIDATION 1146
THIN OXIDE LAYERS 358
TITANIUM - - - - 23
- - - - 358
- - - - 1032
TUNGSTEN - - - - 908

EMF
ELECTROCHROMISM ->1603
TUNGSTEN BRONZE - "

EMF MEASUREMENT
BETA ALUMINA - ->1377
CONCENTRATION CE. "
FORMATION ENERGY > 572
LIQUID ALLOY - - 1377
SODIUM SULFATE - 572
SODIUM TIN ALLOY 1377

EMISSION SPECTRA
CATHODOCHROMISM ->1133
F CENTERS - - - - "
GERMANIUM DOPED - "
REFLECTANCE SPEC. "
SODALITE - - - - "

EMISSIVITY
DURABILITY - - ->1361
SELECTIVE COATING "
SOLAR COLLECTOR - "
ZINC OXIDE - - - "

EMITTER DIFFUSION
BIPOLAR TRANSIST.> 762
PHOSPHORUS DIFFU. "
SILICON DEFECT - "

EMITTER DIP EFFE.
IMPURITY PROFILE >1170
MULTILAYER ANALY. "
P-N JUNCTION - - "
PHOSPHORUS - - -> 995
SHEET RESISTANCE 1170
SILICON - - - - - 995
SPREADING RESIST. 1170

ENCAPSULANT FILM
CVD - - - - - - ->1525
GAAS - - - - - - - "
ION IMPLANTATION "
SILICON NITRIDE - "

ENERGY CONVERSION
CADMIUM SELENIDE >1623
CADMIUM SULFIDE ->1968
CERIUM DIOXIDE ->1277
FLATBAND POTENTI. 1968
FUEL CELL - - - - 1277
MIXED CONDUCTOR - "
PHOTOELECTRODE - 1623
SULFUR SUBSTITUT. "
SURFACE ION - - - 1968
TRANSPORT THEORY 1277

ENERGY CONVERSION (CONTD)
WET PHOTOVOLTAIC 1968
XPS - - - - - - - - 1623

ENERGY OF FORMAT.
ALUMINA - - - - -> 889
- - - - -> 890
CORUNDUM - - - - 889
CRYSTAL STRUCTURE 890
PHASE DIAGRAM - - "

ENERGY SOURCE
ALKALINE COMPOUND> 5C
ELECTROLYTIC IND. "
METALS - - - - - - "

ENERGY STORAGE
BETA ALUMINA - ->1007
CALCIUM - - - - - "
CERAMIC - - - - - "
IRON - - - - - - - "
POTASSIUM - - - - "

ENERGY TRANSFER
CERIUM LUMINESCE.> 588
HEXAGONAL ALUMIN. "

ENTHALPY
COULOMETRIC TITR.> 7
ENTROPY - - - - - "
GALVANIC CELL - - "
GASEOUS EQUILIBR.>1543
GIBBS FREE ENERGY 7
INTERMETALLIC - - "
LITHIUM ANTIMONY "
LITHIUM BISMUTH - "
MASS SPECTROMETRY 1543
ZIRCONIUM IODIDES "

ENTROPY
CALCULATION - - -> 808
COULOMETRIC TITR.> 7
ELECTRODE POTENT. 808
ENTHALPY - - - - 7
GALVANIC CELL - - "
GIBBS FREE ENERGY "
HEAT CAPACITY - - 808
- - -> 972
INTERMETALLIC - - 7
LITHIUM ANTIMONY "
LITHIUM BISMUTH - "
MERCURIC IODATE -> 875
MERCURY - - - - - "
METAL WATER SYST. 808
STANDARD POTENTI. 875
VAPORIZATION - - 972
ZIRCONIUM TETRAI. "

ENVIRONMENT TEST
POLLUTANTS - - ->1487
SYSTEM RELIABILI. "

EPITAXIAL FAULTS
SILICON CRYSTALS >1151
SILICON GROWTH - "

EPITAXIAL GROWTH
BORON MONOPHOSPH.> 633
GALLIUM DOPING ->1817
LPE - - - - - - - - "
SILICON - - - - -> 598
- - - - - 1817
SILICON SUBSTRATE 633
SOLAR CELL - - - "
SUPERSATURATION - 598
TIN MELT - - - - "
TRANSISTOR - - - 633

EPITAXIAL LAYER
DOPING - - - - -> 350
EPITAXIAL WAFER - "
NEUTRON IRRADIAT. "
NEUTRON TRANSMUT. "
SILICON - - - - - "

EPITAXIAL LAYERS
COPPER SULFIDE -> 882
LIQUID SOLUTION - "
METHANOL - - - - "
RHEED - - - - - - "

EPITAXIAL REACTOR
ANNEALING - - - ->1845
CVD REACTOR - - -> 317
INDIUM PHOSPHIDE 1845
ION IMPLANTATION "
SILICON DEPOSITI. 317

EPITAXIAL REACTOR (CONTD)
TRANSPORT PHENOM. 317

EPITAXIAL REGROW.
ARSENIC - - - - -> 461
CRYSTAL ORIENTAT. "
ELECTRICAL ACTIV. "
RECRYSTALLIZATION "
SILICON - - - - - "

EPITAXIAL WAFER
DOPING - - - - -> 350
EPITAXIAL LAYER - "
NEUTRON IRRADIAT. "
NEUTRON TRANSMUT. "
SILICON - - - - - "

EPITAXY
ADSORPTION EQUIL.> 717
BISMUTH TRITELLU.>2042
DICYANOAURATE - - 717
ELECTROCRYSTALLI. "
GALLIUM - - - - ->1310
GOLD PLATING - - 717
IMPURITY DOPANT - 2042
INDIUM - - - - - 1310
INDIUM PHOSPHIDE "
MOLECULAR BEAM - 2042
NONSTOICHIOMETRY "
PHOTOLUMINESCENCE 1310
SEMICONDUCTOR - - 2042
TENSILE STRESS - 1310
THALLIUM - - - - 2042
VAPOR PRESSURE - "

EPOXY RESIN
ELECTROLUMINESCE.> 581
UV RADIATION - - "
X-RAY - - - - - - "

EPR
ANILINE - - - - ->1059
DECOMPOSITION - - "
VOLTAMMETRY - - - "

EQUIATOMIC
SURFACE PASSIVITY> 403
TIN NICKEL ALLOY "

EQUILIBRIUM COMP.
HYDROCHLORIC ACID>2083
SILICON - - - - - "
THERMAL OXIDATION "

EQUILIBRIUM DIAG.
BACKSCATTERING ->1854
CHROMIUM - - - - "
ORDERING TRANSFO. "
PLATINUM - - - - "

EQUILIBRIUM POTE.
CURRENT DENSITY ->1591
IONIC STRENGTH - "
POTASSIUM HYDROX. "
ZINC ELECTRODE - "

EQUIVALENT CIRCU.
CYCLIC VOLTAMMET.>1443
HYSTERESIS - - - "
IMPEDANCE - - - - "
LINEAR POLARIZAT. "
RESISTIVE-CAPACI. "
TRANSFORM ANALYS. "

ESR
CALCIUM FLUOROPH.>1493
LASER SPECTROSCO. "
NEODYMIUM - - - - "
OPTICAL PROPERTY "

ETCH PIT
LPE - - - - - - - ->2019
THREADING DISLOC. "
X-RAY TOPOGRAPHY "

ETCHING
ACIDIC FLUORIDE -> 320
ALUMINUM CONTACT > 467
ARSENIC TRIOXIDE > 579
BEVELING - - - - -> 860
CVD SILICON NITR. 320
DISSOLUTION PROC. "
GAAS - - - - - - - 579
GALLIUM PHOSPHIDE> 347
HYDROCHLORIC ACID> 887
>1867
MONITORING - - -> 798

ETCHING (CONTD)
OXIDE STRUCTURE - 1867
OXIDE THICKNESS - 467
PERMALLOY - - - - 860
PHASE SEPARATION 1867
POLARIZATION - - 860
SILICON DIOXIDE - 798
SILICON NITRIDE - "
SILICON OXIDE - - 1867
THERMAL OXIDATION 579
TIN OXIDE - - - - 887
TITANIUM ALUMINUM 467
TRANSDUCER - - - 860
UNDERETCHING - - 798

ETCHING KINETICS
GALLIUM ARSENIC ->1510
PHOSPHORIC ACID - "

ETCHING PATTERNS
ALKALI CYANIDE ->1177
CHROMIUM - - - - "
GOLD - - - - - - "
IODINE ETCH - - - "
UNDERCUTTING - - "

EUROPIUM
CATHODOLUMINESCE.> 102
COPRECIPITATION - "
LOW ENERGY ELECT. "
LUMINESCENCE - ->1130
PEROVSKITE STRUC. "
POWDER PHOSPHOR - 102
TELLURATE - - - - 1130
TIN DIOXIDE - - - 102

EUTECTIC
CHROMIUM - - - ->1450
HYDROLYSIS - - - "
INDIUM ANTIMONIDE>1873
INTERFACE DEMARC. "
MOISTURE - - - - 1450
MOLTEN SALTS - - "
MULTIPHASE SYSTEM 1873

EXCHANGE REACTION
ANODIC DISSOLUTI.>1989
LEAD SYSTEM - - - "
PERCHLORATE ACID "

EXCITED STATE
ELECTROLYSIS - ->218C
REACTIVITY - - - "
SEMICONDUCTOR - - "

EXCITED STATES
CHEMILUMINESCENCE>1423
ELECTRON TRANSFER "
SEMICONDUCTOR - - "

EXTRACTIVE METAL.
CRYSTAL GROWTH ->241C
ELECTROTHERMICS - "
VACUUM METALLURG. "

EXTRAPOLATION
LEAD - - - - - - -> 888
PERCHLORATE ACID "
POLARIZATION - - "

F CENTERS
CATHODOCHROMISM ->1133
EMISSION SPECTRA "
GERMANIUM DOPED - "
REFLECTANCE SPEC. "
SODALITE - - - - "

FAIR TSAI MODEL
ION IMPLANTATION > 323
PHOSPHORUS DIFFU. "
SILICON - - - - - "

FERMI ENERGY
IRON OXIDE - - -> 781
NONSTOICHIOMETRY "
SURFACE POTENTIAL "
WORK FUNCTION - - "
WUSTITE PHASE - - "

FERRI-FERROCYANI.
FIRST ORDER REAC.>1616
LEAD DEPOSITION -> 232
POLYMERIC ELECTR. "
POLYTHIAZYL - - - "
PULSED ELECTROLY. 1616
ROTATING DISK EL. "
SULFUR NITRIDE - 232

PRIMARY TERM / CO-TERM	PAGE NO.
FERRIHEME	
COULOMETRY	->1250
CYCLIC VOLTAMMET.	"
MARCUS THEORY	"
POLAROGRAPHY	"
FET	
BUFFER LAYER	->2058
CHROMIUM	"
GAAS	"
LPE	"
SEMIINSULATING	"
FET MOBILITY	
CRYSTALLINE PERF.	> 792
MOS TRANSISTOR	"
SAPPHIRE	"
SILICON	"
X-RAY DIFFRACTOM.	"
FIBROUS SEPARATOR	
CERAMIC POWDER	->1913
ELECTRODE SEPARA.	"
FUSED SALTS	"
IRON SULFIDE	"
LITHIUM ALUMINUM	"
FICKS LAW	
CORROSION KINETI.	>1610
FILM GROWTH	"
GERMANIUM	->1307
NOBLE METAL ALLOY	1610
PHOSPHORUS DIFFU.	1307
SOLUTE SEGREGATI.	1610
FIELD EFFECT	
SILICON NITRIDE	->1875
FILM FORMATION	
AGING PROCESS	->1578
ANODIC OXIDATION	"
NICKEL HYDROXIDE	"
FILM GROWTH	
ALUMINUM	-> 574
ALUMINUM IRON	-> 438
ANODIC FILM	"
COBALT DIFFUSION	> 898
COBALT OXIDE FILM	"
CORROSION KINETI.	>1610
FICKS LAW	"
GOLD	898
NOBLE METAL ALLOY	1610
OXIDATION KINETI.	898
PITTING	438
SOLUTE SEGREGATI.	1610
TRANSIENT PITTING	574
FILM PROPERTIES	
ALUMINUM OXIDE	-> 902
DEPOSITION RATE	"
ELLIPSOMETRY	"
INSULATOR	"
FILM PROPERTY	
ALUMINUM NITRIDE	> 305
CHARGE STORAGE	"
CVD	"
MEMORY	"
SILICON NITRIDE	"
FILM STRESS	
CVD	-> 139
OXIDATION BARRIER	"
SILICON DIOXIDE	"
SILICON NITRIDE	"
FILM STRUCTURE	
HEAT TREATMENT	->1339
POROUS SILICON	"
FINITE ELEMENT	
CURRENT DISTRIBU.	>1981
ELECTRODEPOSITION	"
MATHEMATICAL MOD.	"
POTENTIAL DISTRI.	"
SHAPE CHANGE	"
FINITE RISE TIME	
CHRONOPOTENTIOME.	>1809
ELECTRODE KINETI.	"
PULSE GENERATOR	"
RELAXATION	"
FIRST ORDER REAC.	
FERRI-FERROCYANI.	>1616
PULSED ELECTROLY.	"
FIRST ORDER REAC. (CONTD)	
ROTATING DISK EL.	1616
FLAT STRIP ELECT.	
BAFFLE	-> 84
CURRENT DISTRIBU.	"
RECTANGULAR CELL	"
FLATBAND POTENTI.	
ALPHA IRON OXIDE	> 723
CADMIUM SULFIDE	->1968
CAPACITANCE	723
CONDUCTIVITY	"
DONOR DENSITY	"
ELECTRON AFFINITY	> 228
ELECTRONEGATIVIT.	"
ENERGY CONVERSION	1968
MOTT SCHOTTKY	723
PHOTOELECTROLYSIS	228
SEMICONDUCTOR	"
SURFACE ION	1968
WET PHOTOVOLTAIC	"
ZETA POTENTIAL	228
FLOATING ZONE	
CZOCHRALSKI PULL.	> 595
P-N JUNCTION	"
PURIFIED SILICON	"
SOLAR CELL	"
VAPOR DEPOSITION	"
FLUORENONE DERIV.	
ELECTRON AFFINITY	>1750
ELECTRON TRANSPO.	"
PHOTOCONDUCTIVITY	"
POLAROGRAPHY	"
SEMICONDUCTOR	"
VOLTAMMETRY	"
FLUORESCENCE	
DYE ADSORPTION	-> 51
DYE SENSITIZATIO.	"
PHOTOSENSITIZATI.	"
QUENCHING	"
SALT ADDITION	"
ZINC OXIDE	"
FLUORIDE	
ALKALI METAL	->1894
MELTING POINT	"
METAPHOSPHATE	"
FLUORINE	
CHLOR-ALKALI	-> 22C
DIAPHRAGM CELL	"
GASIFICATION	-> 498
INDUSTRIAL CHEMI.	22C
IRIDIUM	498
MASS SPECTROMETRY	> 162
PLATINUM	498
RHENIUM	162
TANTALUM	498
TANTALUM FLUORIDE	162
TEMPERATURE KINE.	498
TUNGSTEN	162
FOAMED ELECTROLY.	
FUEL CELL	-> 94
LIMITING CURRENT	"
MASS TRANSFER	"
FOLDBACK	
CIRCUIT BOARD	->1218
COPPER PYROPHOSP.	"
DIMERCAPTOTHIADI.	"
ELECTROPLATING	"
LEVELING MECHAN.	"
PT-DISK ELECTROD.	"
FORMALDEHYDE	
COPPER DEPOSITION	> 173
ELECTROLESS PLAT.	"
MIXED POTENTIAL	"
FORMATION ENERGY	
EMF MEASUREMENT	-> 572
SODIUM SULFATE	"
FORMATION MECHAN.	
METASTABLE ALLOY	> 335
NUCLEATION KINET.	"
TIN NICKEL	"
TRANSFORMATION	"
FOUR POINT BEND	
BRITTLE COATING	-> 400
DUCTILITY	"
FOURIER TRANSFORM	
CONVERGING ELECT.	> 697
CURRENT DENSITY	"
ELECTROCOATING	"
LAPLACE EQUATION	"
FREE RADICAL	
ACETONITRILE	->1430
AROMATIC HYDROCA.	"
CHEMILUMINESCENCE	"
TETRATHIAFULVALE.	"
FREE SURFACES	
GOLD FILM	->2037
RESISTIVITY DECAY	"
VACANCY DIFFUSION	"
VOID GROWTH	"
FUEL CELL	
CERIUM DIOXIDE	->1277
ENERGY CONVERSION	"
FOAMED ELECTROLY.	> 94
LIMITING CURRENT	"
MASS TRANSFER	"
MIXED CONDUCTOR	1277
OUTLOOK	-> 77C
SURVEY	"
TRANSPORT THEORY	1277
FUEL CELL ASSEMB.	
ELECTRICAL ANALOG	> 515
MANIFOLD MODEL	"
PARASITIC CURREN.	"
SHUNT CURRENTS	"
FUSED QUARTZ	
SEMICONDUCTOR	->1188
SILICON DIOXIDE	"
SODIUM DIFFUSION	"
FUSED SALT SYSTEM	
ELECTROREFINING	-> 49C
ELECTROWINNING	"
METAL PRODUCTION	"
FUSED SALTS	
ACIDITY DEPENDEN.	>1454
ACTIVITY COEFFIC.	> 692
ALUMINA	->1796
CERAMIC POWDER	->1913
DIFFUSION FLUX	->1110
ELECTRODE SEPARA.	1913
FIBROUS SEPARATOR	"
IRON SULFIDE	"
LITHIUM ALUMINUM	"
MELTS	1454
POLARIZATION	1796
POLYSULFIDES	->1605
POTASSIUM CHLORI.	692
REFERENCE ELECTR.	1796
SELENIUM	1454
SILVER CHLORIDE	692
SULFUR	1605
TETRACHLOROALUMI.	1454
TRANSPORT COEFFI.	1110
TRANSPORT PROPER.	1605
WETTABILITY	"
GAAS	
ALUMINUM ARSENIDE	> 977
ANNEALING	-> 676
ARSENIC TRIOXIDE	> 579
AUGER ANALYSIS	-> 998
AUGER SPECTROSCO.	> 481
BUFFER LAYER	->2058
CHROMIUM	"
CONTACT RESISTAN.	> 473
CRYSTAL GROWTH	-> 130
CVD	->1525
DEPTH PROFILE	481
DIFFUSION LENGTH	>2034
DIFFUSION PROFILE	>1672
DIODE	->1505
DISLOCATIONS	-> 621
DOPANT CONCENTRA.	1672
ELECTROABSORPTION	> 776
ELECTROEPITAXY	->1140 ->1560
ELECTROETCHING	621
ELECTRON IRRADIA.	676
ELECTROREFLECTAN.	776
ENCAPSULANT FILM	1525
ETCHING	579
FET	2058
GRAPHITE	977
HETEROEPITAXY	130
HETEROJUNCTION	977
GAAS (CONTD)	
INDIUM PHOSPHIDE	130
ION IMPLANTATION	776, 1505, 1525
LAYER THICKNESS	1140
LPE	130, 1140, 2058
MODELING	2034
NEUTRON ACTIVATI.	481
PLASMA OXIDATION	"
PREDEPOSITION	1505
PROTON DAMAGE	776
RADIATION DAMAGE	676, >1726, 2034
SEMICONDUCTOR	1505
SEMIINSULATING	2058
SILICON NITRIDE	1525
SOLAR CELL	977, 1726, 2034
SPREADING RESIST.	1672
STRIATIONS	621
SULFUR DIFFUSION	473
SURFACE MORPHOLO.	1560
SURFACE RECOMBIN.	2034
THERMAL LPE	1560
THERMAL OXIDATION	579, 998
THIN FILM	977
TRANSFERRED ELEC.	473
ZINC	1505
GAAS ELECTRODE	
ACETONITRILE SOL.	>283C
AQUEOUS ELECTROL.	>1185
CURRENT RISE	"
INDIUM PHOSPHIDE	283C
SEMICONDUCTOR	1185
GAAS EPITAXY	
ARSINE	-> 771
CHLORIDE ETCHING	"
GROWTH RATE	"
TRIMETHYLGALLIUM	"
GAAS FILM	
CVD	->1668
GRAPHITE	"
SOLAR CELL	"
TUNGSTEN	"
GAAS LASER	
ALIGNMENT GROOVE	>1642
OPTICAL BENCH	"
PHOTOLITHOGRAPHY	"
SILICON SUBSTRATE	"
GAAS SUBSTRATE	
CONTACTLESS MOBI.	>1318
SELENIUM	"
SEMICONDUCTOR	"
SULFUR	"
GALLIUM	
DEFECT STRUCTURE	>1355
EPITAXY	->1310
HALL EFFECT	1355
INDIUM	1310
INDIUM PHOSPHIDE	"
PHOTOLUMINESCENCE	"
PRECIPITATES	1355
RESISTIVITY	"
TENSILE STRESS	1310
ZINC SELENIDE	1355
GALLIUM ANTIMONY	
INDIUM ANTIMONY	-> 657
SOLIDUS ISOCONCE.	"
SOLIDUS ISOTHERM.	"
TERNARY DIAGRAM	"
GALLIUM ARSENIC	
ETCHING KINETICS	>1510
PHOSPHORIC ACID	"
GALLIUM DIFFUSION	
COPPER	-> 963
GETTERING	"
GOLD	"
IMPURITY SINK	"
NEUTRON ACTIVATI.	"
SILICON	"

PRIMARY TERM / CO-TERM — PAGE NO.

GALLIUM DOPING
CRYSTAL GROWTH -> 475
->1832
CRYSTAL SEGREGAT. "
DIFFUSION CONTROL "
EPITAXIAL GROWTH >1817
GERMANIUM - - - - 475
- - - - 1832
LPE - - - - - - - 1817
MELT FLOW - - - - 475
SILICON - - - - - 1817
THERMAL GRADIENT 475
ZERO GRAVITY - - 1832

GALLIUM NITRIDE
CARRIER CONCENTR.>2076
CRYSTALLINE QUAL. "
DIODE - - - - - - "
GIBBS FREE ENERGY>1161
GROWTH KINETICS - "
SURFACE MORPHOLO. 2076
VPE - - - - - - - - 1161
X-RAY DIFFRACTION 2076

GALLIUM PHOSPHIDE
CHEMICAL ETCHING > 671
DISLOCATION DIPO. "
DISLOCATION LOOP "
ETCHING - - - - -> 347

GALVANIC CELL
ALUMINUM OXIDE -> 175
CHROMIUM OXIDE - "
COULOMETRIC TITR.> 7
ENTHALPY - - - - "
ENTROPY - - - - - "
GIBBS FREE ENERGY "
INTERMETALLIC - - "
LITHIUM ANTIMONY "
LITHIUM BISMUTH - "
MISCIBILITY GAP - 175
SOLID ELECTROLYTE "
THERMODYNAMICS - "

GALVANOSTATIC
ELECTROCHROMISM -> 284
LITHIUM TUNGSTEN. "
POTENTIOSTATIC - "

GAS MONITORING
HYDRAZINE - - - ->1804
METHYLHYDRAZINE - "

GAS SENSING
ELECTROANALYSIS ->250C
SPECTROELECTROCH. "
VOLTAMMETRY - - - "

GAS TURBINE
CORROSION - - - ->1283
NICKEL ALUMINIDE "
SODIUM CHLORIDE - "
WHISKERS - - - - "

GASEOUS EQUILIBR.
ENTHALPY - - - ->1543
MASS SPECTROMETRY "
ZIRCONIUM IODIDES "

GASEOUS PRODUCT
ALUMINUM OXIDE -> 327
ALUMINUM SULFATE "
DECOMPOSITION - - "
SOLID PRODUCT - - "
SULFUR DIOXIDE - "
SULFUR TRIOXIDE - "

GASIFICATION
FLUORINE - - - -> 498
IRIDIUM - - - - - "
PLATINUM - - - - "
TANTALUM - - - - "
TEMPERATURE KINE. "

GATE OXIDE
MOS DEVICE - - -> 432
OXIDE WALL - - - "
THINNING - - - - "

GERMANIUM
CRYSTAL GROWTH -> 475
->1832
CRYSTAL SEGREGAT. "
DIFFUSION CONTROL "
DISLOCATION - - ->1840
FICKS LAW - - - ->1307
GALLIUM DOPING - 475

GERMANIUM (CONTD)
GALLIUM DOPING - 1832
MELT FLOW - - - - 475
PHOSPHORUS DIFFU. 1307
1840
SILICON - - - - - "
STRAIN - - - - - "
THERMAL GRADIENT 475
ZERO GRAVITY - - 1832

GERMANIUM DOPED
CATHODOCHROMISM ->1133
EMISSION SPECTRA "
F CENTERS - - - - "
REFLECTANCE SPEC. "
SODALITE - - - - "

GETTERING
CHLORINE - - - -> 453
COPPER - - - - -> 963
ELECTRICAL EFFECT 453
GALLIUM DIFFUSION 963
GOLD - - - - - - "
IMPURITY SINK - - "
NEUTRON ACTIVATI. "
SILICON - - - - - "
SILICON OXIDATION 453

GIBBS FREE ENERGY
COULOMETRIC TITR.> 7
ENTHALPY - - - - "
ENTROPY - - - - - "
GALLIUM NITRIDE ->1161
GALVANIC CELL - - 7
GROWTH KINETICS - 1161
INTERMETALLIC - - 7
LITHIUM ANTIMONY "
LITHIUM BISMUTH - "
VPE - - - - - - - 1161

GLASS CERAMICS
BETA EUCRYPTITE -> 179
IONIC CONDUCTIVI. "
LITHIUM ALUMINOS. "
SOLID ELECTROLYTE "

GLASSY LAYER
COPPER - - - - -> 823
CVD - - - - - - - "
PASSIVATION - - - "
SILICON DIOXIDE - "

GLYOXAL
ALUMINUM - - - -> 190
ANODIZATION - - - "
CARBON MONOXIDE - "
MALEIC ACID - - - "

GOLD
ADSORPTION - - ->1103
ALKALI CYANIDE ->1177
ALKALINE CYANIDE >1436
ALUMINUM METALLI.> 156
AMMONIA - - - - ->1717
ANODIC DISSOLUTI. 1436
BEAM LEADS - - - 156
CATALYSIS - - - - 1103
CHROMIUM - - - - 1177
COBALT DIFFUSION > 898
COBALT OXIDE FILM "
COPPER - - - - -> 963
COULOSTATIC DEPO.> 384
DIFFUSION BARRIER 156
ELECTRODEPOSITION 1717
ETCHING PATTERNS 1177
FILM GROWTH - - - 898
GALLIUM DIFFUSION 963
GETTERING - - - - "
IMPURITY SINK - - "
IODINE ETCH - - - 1177
MERCURY - - - - - 384
- - - - ->1098
NEUTRON ACTIVATI. 963
OXIDATION KINETI. 898
OXYGEN REDUCTION 1103
POTENTIAL RELAXA. 384
REACTION KINETICS 1436
REACTION MECHANI. "
RING DISK ELECTR. 1098
ROTATING DISK EL. 1103
SILICON - - - - - 963
UNDERCUTTING - - 1177
UNDERPOTENTIAL - 384
- 1098

GOLD ELECTRODE
CAPACITANCE - - ->1077

GOLD ELECTRODE (CONTD)
ELECTROCAPILLARY 1077
STRESS-STRAIN - - "

GOLD ELECTROPLAT.
COBALT CYANIDES ->1745
COBALT HARDENING "
IMPURITY - - - - "

GOLD FILM
FREE SURFACES - ->2037
RESISTIVITY DECAY "
VACANCY DIFFUSION "
VOID GROWTH - - - "

GOLD METALLIZATI.
ELECTROLESS PLAT.> 522
PVDF FILMS - - - "

GOLD PLATING
ADSORPTION EQUIL.> 717
ALUMINUM - - - ->1741
DICYANOAURATE - - 717
ELECTROCRYSTALLI. "
EPITAXY - - - - - "
IMMERSION PLATING 1741

GRADED C-V
BOLTZMANN-MATANO >1530
CADMIUM - - - - - "
DIFFUSION PROFILE "
INDIUM ANTIMONIDE "

GRAIN BOUNDARY
DIFFUSION COEFFI.>2070
ION IMPLANTATION > 892
OXIDATION KINETI. "
PERMEATION ANALY. 2070
PHOSPHORUS DOPED 892
RESISTIVITY - - - "
SILICON - - - - - "

GRAIN GROWTH
ION IMPLANTATION >1499
PHOSPHORUS DOPING "
RECRYSTALLIZATION "
SILICON - - - - - "

GRAPHITE
ALUMINUM ARSENIDE> 977
CVD - - - - - - ->1668
DIMETHYL SULFITE > 687
GAAS - - - - - - 977
GAAS FILM - - - - 1668
HETEROJUNCTION - 977
LITHIUM PERCHLOR. 687
NICKEL COBALTOXI.>1003
OXYGEN REDUCTION "
RADICAL CATION - 687
SOLAR CELL - - - 977
- - - 1668
SPINEL - - - - - 1003
THIN FILM - - - - 977
TUNGSTEN - - - - 1668

GRAPHITE PASTE
ELECTROOXIDATION > 531
ELECTROSYNTHESIS "
TYRAMINE - - - - "

GRAPHITIZATION
INTEGRATED CIRCU.>1293
ION IMPLANTATION "
PHOTOMASK - - - - "
PHOTORESIST FILM "

GRATE REDUCTION
INTEGRATED CIRCU.> 471
SELF ALIGNMENT - "

GRAVIMETRIC ANAL.
DELIQUESCENCE - -> 734
HYGROSCOPICITY - "
RELATIVE HUMIDITY "

GROWTH BEHAVIOR
DISSOLUTION - - ->1471
NOBLE METAL - - - "
OXIDE FILM - - - "
RUTHENIUM ELECTR. "

GROWTH KINETICS
AUTODOPING - - -> 637
GALLIUM NITRIDE ->1161
GIBBS FREE ENERGY "
REDUCED PRESSURE 637
SILICON GROWTH - "

GROWTH KINETICS (CONTD)
VPE - - - - - - - 1161

GROWTH PARAMETERS
PYROLYSIS - - - -> 294
SILANE COMPOUND - "
SILICON CARBIDE - "
VAN ARKEL PROCESS "

GROWTH RATE
ARSINE - - - - -> 771
CHLORIDE ETCHING "
GAAS EPITAXY - - "
TRIMETHYLGALLIUM "

HALIDE EFFECT
ALUMINUM ALLOY -> 731
ANION EFFECT - - "
PITTING - - - - - "

HALIDE ELECTROLY.
ANODE SYNTHESIS ->1954
CARBON MONOXIDE - "
ORGANIC CARBONATE "
PHOSGENE - - - - "

HALIDE SALTS
CALCIUM ANODE - ->1209
CALORIMETRY - - - "
CURRENT EFFICIEN. "
NITRATE ELECTROL. "
PASSIVATING LAYER "

HALIDE SELECTIVE
BROMIDE ELECTRODE>1807
CHLORIDE ELECTRO. "
IODIDE ELECTRODE "

HALL EFFECT
ALUMINUM - - - ->1348
ARSENIC - - - - - "
DEFECT STRUCTURE >1355
GALLIUM - - - - - "
PRECIPITATES - - "
RESISTIVITY - - - "
SELF DIFFUSION - 1348
SINGLE CRYSTAL - "
ZINC SELENIDE - - "
- - 1355

HALL MOBILITY
CZOCHRALSKI CRYS.> 661
DIFFUSION LENGTH "
PURIFICATION - - "
SILICON - - - - - "
SOLIDIFICATION - "

HALOALDEHYDE
ACETAL - - - - ->1401
ALCOHOL - - - - - "
ELECTROLYSIS - - "
HYDROGEN HALIDE - "
OXIDATION - - - - "

HALOSILICATE
LANTHANUM - - - -> 445
LUMINESCENCE - - "
PHOSPHORS - - - - "
RARE EARTH ELEME. "
YTTRIUM - - - - - "

HEAT CAPACITY
CALCULATION - - -> 808
ELECTRODE POTENT. "
ENTROPY - - - - - "
- - - - -> 972
METAL WATER SYST. 808
VAPORIZATION - - 972
ZIRCONIUM TETRAI. "

HEAT EFFECT
COPPER - - - - -> 492
COPPER OXIDE - - "
CRYSTALLIZATION - "
SOLDER GLASS - - "

HEAT FLOW
BATTERY SYSTEM -> 353
CALCULATION - - - "
THERMAL EFFICIEN. "

HEAT TREATMENT
CAPACITOR - - - -> 746
CORROSION - - - -> 199
DIELECTRIC PROPE. 746
FILM STRUCTURE ->1339
HYDROGEN EFFECT - 199

PRIMARY TERM / CO-TERM	PAGE NO.
HEAT TREATMENT (CONTD)	
MAXWELL WAGNER -	746
POROUS SILICON -	1339
STEAM - - - - - -	199
TANTALUM OXIDE -	746
TWO LAYER MODEL -	"
ZIRCALOY 4 - - -	199
HEBB WAGNER POLA.	
BETA LEAD FLUORI.>	683
CONDUCTION - - -	"
ELECTROLYTIC DON.	"
HELIUM	
REACTION KINETICS>	1636
SULFUR DIOXIDE -	"
TUNGSTEN - - - -	"
HEMOSTASIS	
ANTITHROMBOGENIC >	419C
IMMUNE RESPONSE -	"
MEDICAL ELECTROC.	"
HEPTYLVIOLOGEN	
ELECTROCHROMICS ->	1619
INDIUM OXIDE - -	"
TIN OXIDE - - - -	"
TRANSPARENT ELEC.	"
HETEROEPITAXY	
CRYSTAL GROWTH ->	130
GAAS - - - - - - -	"
INDIUM PHOSPHIDE	"
LPE - - - - - - - -	"
HETEROJUNCTION	
ALUMINUM ARSENIDE>	977
GAAS - - - - - -	"
GRAPHITE - - - -	"
INDIUM PHOSPHATE >	123
LIGHT EMITTER - -	"
LPE CONDITIONS -	"
PHASE EQUILIBRIUM	"
QUATERNARY SYSTEM	"
SOLAR CELL - - -	977
THIN FILM - - - -	"
HEXAGONAL ALUMIN.	
CERIUM LUMINESCE.>	588
ENERGY TRANSFER -	"
HIGH IMPEDANCE	
CORROSION RATE ->	1389
COULOSTATIC METH.	"
POTENTIAL DECAY -	"
STEEL - - - - - -	"
HOLE REACTION	
O-ENERGY BAND - ->	1086
MOLYBDENUM SELEN.	"
SOLAR ENERGY - -	"
HOT CORROSION	
SALT DEPOSITS - ->	411
SODIUM CHLORIDE -	"
SODIUM SULFATE -	"
SULFUR DIOXIDE -	"
HOT-WALL	
CVD - - - - - - - ->	1557
DIFFUSION - - - -	"
INTEGRATED CIRCU.	"
SILICON NITRIDE -	"
HUMIDITY	
ACCELERATED TEST >	2002
CORROSION TEST -	"
IC - - - - - - - ->	1715
KINETIC RATE - -	2002
POLLUTANTS - - -	"
WATER DROPLET - -	1715
HYDRAZINE	
GAS MONITORING ->	1804
METHYLHYDRAZINE -	"
HYDROCHLORIC ACID	
D-C RESPONSE - ->	985
EQUILIBRIUM CONP.>	2083
ETCHING - - - - ->	887
- - - - ->	1867
MNOS TRANSISTOR -	985
OXIDE STRUCTURE -	1867
PHASE SEPARATION	"
PULSE - - - - - -	985
SILICON - - - - -	2083
SILICON OXIDE - -	1867
HYDROCHLORIC ACID (CONTD)	
THERMAL OXIDATION	2083
TIN OXIDE - - - -	887
HYDROGEN	
ANODIC OXIDE FILM>	23
ELECTROCHROMISM -	"
ELECTROCRYSTALLI.>	1049
ELLIPSOMETRY - -	23
IMPEDANCE - - - -	"
LINEAR DEFECT - -	1049
NICKEL - - - - -	"
NIOBIUM - - - - -	23
POLARIZABILITY -	"
TEM - - - - - - -	1049
THIN FILM - - - -	"
TITANIUM - - - -	23
HYDROGEN ADSORPT.	
AUGER - - - - - ->	348
ELECTROSORPTION -	"
LEED - - - - - -	"
PLATINUM - - - -	"
SINGLE CRYSTAL -	"
HYDROGEN EFFECT	
CORROSION - - - ->	199
HEAT TREATMENT -	"
STEAM - - - - - -	"
ZIRCALOY 4 - - -	"
HYDROGEN EVOLUTI.	
CHARGE DELOCALIZ.>	1992
CHARGE TRANSFER ->1991	
CHLORIDE SOLUTIO.>	1199
CONDENSED PHASE ->	252
IONIC CONDUCTANC.	"
IONIC EQUILIBRIA	"
LOCALIZED CORROS.	1199
PHOTOEFFECT - - ->	223
PHOTOELECTROCHEM.	1991
PRESSURE EFFECT -	252
PROTON TRANSFER -	1992
RATE DETERMINING	1991
SEMICONDUCTOR - -	223
- ->1992	
- - 1991	
SULFURIC ACID - -	1199
TENSILE STRESS -	"
TITANIUM ALLOY -	"
TRANSPASSIVITY -	"
TUNNELING - - - -	1991
WKB APPROXIMATIO.	223
HYDROGEN HALIDE	
ACETAL - - - - ->1401	
ALCOHOL - - - - -	"
ELECTROLYSIS - -	"
HALOALDEHYDE - -	"
OXIDATION - - - -	"
HYDROGEN ION BEAM	
BROAD BAND EMITT.>	2015
CANDOLUMINESCENCE	"
ION EXCHANGE - -	"
LINE EMITTER - -	"
QUANTUM YIELD - -	"
HYDROGEN SULFIDE	
CHEMISORPTION - ->	544
MASS TRANSPORT -	"
ROTATING ELECTRO.	"
HYDROGEN TUNGSTEN	
BLUE TUNGSTEN - ->1344	
ELECTROCHROMISM -	"
OXIDE FILM - - -	"
TUNGSTEN OXIDE -	"
HYDROLYSIS	
CELLULOSE - - - ->	933
CHROMIUM - - - ->1450	
EUTECTIC - - - -	"
LEAD ACID BATTERY	833
MOISTURE - - - -	1450
MOLTEN SALTS - -	"
POLYMERIZATION -	833
SEPARATOR - - - -	"
HYGROSCOPICITY	
DELIQUESCENCE - ->	734
GRAVIMETRIC ANAL.	"
RELATIVE HUMIDITY	"
HYSTERESIS	
CYCLIC VOLTAMMET.>	1443
EQUIVALENT CIRCU.	"
HYSTERESIS (CONTD)	
IMPEDANCE - - - -	1443
LINEAR POLARIZAT.	"
RESISTIVE-CAPACI.	"
TRANSFORM ANALYS.	"
IC	
HUMIDITY - - - ->1715	
WATER DROPLET - -	"
II-IV-V2 COMPOUND	
CHALCOPYRITE - ->	952
LPE - - - - - - - -	"
SINGLE CRYSTAL -	"
ZINC TIN ARSENIDE	"
III-IV COMPOUNDS	
ANODIC DISSOLUTI.>	117
CADMIUM SULFIDE -	"
CHARGE TRANSFER -	"
PHOTOELECTROLYSIS	"
REDOX SYSTEM - -	"
IMMERSION PLATING	
ALUMINUM - - - ->1741	
GOLD PLATING - -	"
IMMUNE RESPONSE	
ANTITHROMBOGENIC >419C	
HEMOSTASIS - - -	"
MEDICAL ELECTROC.	"
IMPEDANCE	
ANODIC OXIDE FILM>	23
CYCLIC VOLTAMMET.>	1443
ELECTROCHROMISM -	23
ELLIPSOMETRY - -	"
EQUIVALENT CIRCU.	1443
HYDROGEN - - - -	23
HYSTERESIS - - -	1443
LINEAR POLARIZAT.	"
NIOBIUM - - - - -	23
POLARIZABILITY -	"
RESISTIVE-CAPACI.	1443
TITANIUM - - - -	23
TRANSFORM ANALYS.	1443
IMPEDANCE PARAME.	
CHROMIUM - - - ->2062	
CORROSION - - - -	"
ELECTRODE KINETI.	"
PSEUDOINDUCTANCE	"
SULFURIC ACID - -	"
IMPINGING JET	
CONVECTIVE DIFFU.>	1461
LIMITING CURRENT	"
MASS TRANSFER - -	"
UNIFORM ACCESSIB.	"
IMPURITY	
COBALT CYANIDES ->1745	
COBALT HARDENING	"
GOLD ELECTROPLAT.	"
IMPURITY DOPANT	
BISMUTH TRITELLU.>	2042
EPITAXY - - - - -	"
MOLECULAR BEAM -	"
NONSTOICHIOMETRY	"
SEMICONDUCTOR - -	"
THALLIUM - - - -	"
VAPOR PRESSURE -	"
IMPURITY PROFILE	
EMITTER DIP EFFE.>	1170
MULTILAYER ANALY.	"
P-N JUNCTION - -	"
SHEET RESISTANCE	"
SPREADING RESIST.	"
IMPURITY SINK	
COPPER - - - - ->	963
GALLIUM DIFFUSION	"
GETTERING - - - -	"
GOLD - - - - - -	"
NEUTRON ACTIVATI.	"
SILICON - - - - -	"
INDIUM	
EPITAXY - - - - ->1310	
GALLIUM - - - - -	"
INDIUM PHOSPHIDE	"
PHOTOLUMINESCENCE	"
TENSILE STRESS -	"
INDIUM ANTIMONIDE	
BOLTZMANN-MATANO >	1530
CADMIUM - - - - -	"
DIFFUSION PROFILE	"
EUTECTIC - - - ->1873	
GRADED C-V - - -	1530
INTERFACE DEMARC.	1873
MULTIPHASE SYSTEM	"
INDIUM ANTIMONY	
GALLIUM ANTIMONY >	657
SOLIDUS ISOCONCE.	"
SOLIDUS ISOTHERM.	"
TERNARY DIAGRAM -	"
INDIUM OXIDE	
CELL FABRICATION >	1328
ELECTROCHROMICS ->1619	
ELECTRON AFFINITY	1328
HEPTYLVIOLOGEN -	1619
PHOTOVOLTAIC CELL	1328
TIN OXIDE - - - -	1619
TRANSPARENT ELEC.	"
INDIUM PHOSPHATE	
HETEROJUNCTION ->	123
LIGHT EMITTER - -	"
LPE CONDITIONS -	"
PHASE EQUILIBRIUM	"
QUATERNARY SYSTEM	"
INDIUM PHOSPHIDE	
ACETONITRILE SOL.>	283C
ANNEALING - - - ->1845	
CRYSTAL GROWTH ->	130
ELECTRODEPOSITION>	1721
EPITAXIAL REACTOR	1845
EPITAXY - - - - ->1310	
GAAS - - - - - -	130
GAAS ELECTRODE -	283C
GALLIUM - - - - -	1310
HETEROEPITAXY - -	130
INDIUM - - - - -	1310
ION IMPLANTATION	1845
LPE - - - - - - - -	130
MELTING POINT - -	1721
PHOTOLUMINESCENCE	1310
TENSILE STRESS -	"
INDUSTRIAL CHEMI.	
CHLOR-ALKALI - ->	22C
DIAPHRAGM CELL -	"
FLUORINE - - - -	"
INFRARED MATERIAL	
BRIDGMAN APPROACH>	315
CADMIUM TELLURIDE	"
MERCURY TELLURIDE	"
PSEUDOBINARY ALL.	"
SINGLE CRYSTAL -	"
INFRARED SPECTRA	
CONDUCTANCE - - ->1974	
CYCLIC VOLTAMMET.	"
DIMETHYL S'LFOXI.	"
ION-SOLVENT - - -	"
INITIAL REGIME	
OXIDATION KINETI.>1708	
SILICON DIOXIDE -	"
SINGLE CRYSTAL -	"
THIN FILM - - - -	"
INITIAL RISE	
ACTIVATION ENERGY>	434
DEPOLARIZATION -	"
PVC - - - - - - -	"
THERMOELECTRET -	"
INK JET PRINTING	
ANISOTROPIC ETCH.>1321	
NOZZLE FABRICATI.	"
SILICON NOZZLE -	"
3-D MICROSTRUCTU.	"
INSULATING FILM	
CHEMICAL BONDING >	424
COMPOSITION - - -	"
CONTAMINATION - -	"
SILICON OXYNITRI.	"
INSULATING LIQUID	
ELECTRIC FIELD ->1404	
MENISCUS RISE - -	"
YOUNG AND DUPREE	"

PRIMARY TERM / CO-TERM — PAGE NO.

INSULATOR
ALUMINUM OXIDATI.-> 787
ALUMINUM OXIDE -> 902
CORROSION - - - - 787
DEPOSITION RATE - 902
ELLIPSOMETRY - - "
FILM PROPERTIES - "
INTEGRATED CIRCU. 787

INTEGRATED CIRCU.
ALUMINUM COPPER -> 30
ALUMINUM METALLI.-> 169
ALUMINUM OXIDATI.-> 787
ANODIC OXIDATION 30
CORROSION - - - - "
- - - - 787
CVD - - - - - - -> 601
- - - - - - ->1557
DIFFUSION - - - - "
GRAPHITIZATION ->1293
GRATE REDUCTION -> 471
HOT-WALL - - - - 1557
INSULATOR - - - - 787
ION IMPLANTATION 1293
METAL FILM - - - 30
METALLIZATION - - "
MOS LSI PASSIVAT. 601
OHMIC CONTACT - - 169
PHOTOMASK - - - - 1293
PHOTORESIST FILM "
POLYSILICON - - - 169
REACTIVE PLASMA - 601
SELF ALIGNMENT - 471
SILICON NITRIDE - 601
- 1557

INTERDIFFUSIVITY
LITHIUM OXIDE - -> 395
OXIDE MELTS - - - "
POLARIZATION - - "
SILICON DIOXIDE - "

INTERFACE
CONTACT RESISTAN.> 508
PULSE MEASUREMENT "

INTERFACE CHARGE
ELECTRICAL PROPE.>1848
MECHANICAL STRESS "
MNOS MEMORY - - - "
SILICON NITRIDE - "

INTERFACE DEMARC.
EUTECTIC - - - ->1873
INDIUM ANTIMONIDE "
MULTIPHASE SYSTEM "

INTERFACE STATE
DEEP LEVEL DEFECT>1664
MOS - - - - - - - - "
SLOW COOLING - - "
TRANSIENT CAPACI. "

INTERMETALLIC
COULOMETRIC TITR.> 7
ENTHALPY - - - - "
ENTROPY - - - - - "
GALVANIC CELL - - "
GIBBS FREE ENERGY "
LITHIUM ANTIMONY "
LITHIUM BISMUTH - "

INTERNAL OXIDATI.
BINARY ALLOY - ->1116
TERNARY DIFFUSION "
WAGNER - - - - - "

IODIDE ELECTRODE
BROMIDE ELECTRODE>1807
CHLORIDE ELECTRO. "
HALIDE SELECTIVE "

IODIDE ION
ACETONITRILE - -> 406
CADMIUM SULFIDE - "
PHOTOCELL - - - - "
SOLAR ENERGY - - "

IODINE ETCH
ALKALI CYANIDE ->1177
CHROMIUM - - - - "
ETCHING PATTERNS "
GOLD - - - - - - - "
UNDERCUTTING - - "

IODINE VAPOR
NUCLEATION - - ->1001

IODINE VAPOR (CONTD)
STRESS CRACKING - 1001
ZIRCONIUM - - - - "

ION EXCHANGE
BROAD BAND EMITT.>2015
CANDOLUMINESCENCE "
CORROSION - - - ->1482
ELECTROCATALYST - "
ELECTRON MICROSC. "
HYDROGEN ION BEAM 2015
LINE EMITTER - - "
QUANTUM YIELD - - "
RUTHENIUM OXIDE - 1482
SOLID POLYMER - - "

ION IMPLANTATION
ANNEALING - - - ->1845
ANODIC POLARIZAT.> 366
> 370
ARSENIC - - - - ->1518
BIPOLAR DEVICE ->1829
BORON - - - - - ->2050
COLOR BAND - - ->1331
CONDUCTIVE FILM - 1829
CVD - - - - - - - ->1525
DIFFUSION - - - - 2050
DIODE - - - - - ->1505
ELECTROABSORPTION> 776
ELECTROREFLECTAN. "
ENCAPSULANT FILM 1525
EPITAXIAL REACTOR 1845
FAIR TSAI MODEL -> 323
GAAS - - - - - - - 776
- - - - - - 1505
- - - - - - 1525
GRAIN BOUNDARY -> 892
GRAIN GROWTH - ->1499
GRAPHITIZATION ->1293
INDIUM PHOSPHIDE 1845
INTEGRATED CIRCU. 1293
IRON CHROMIUM - - 366
IRON NICKEL - - - 370
OXIDATION - - - - 2050
OXIDATION KINETI. 892
PALLADIUM - - - ->1892
PHOSPHORUS DIFFU. 323
PHOSPHORUS DOPED 892
PHOSPHORUS DOPING 1499
PHOTOMASK - - - - 1293
PHOTORESIST FILM "
PITTING POTENTIAL 366
370
PREDEPOSITION - - 1505
PROTON DAMAGE - - 776
PULSIVE NOISE - - 1829
RECRYSTALLIZATION 1499
REDISTRIBUTION - 1518
RESISTIVITY - - - 892
SEGREGATION - - - 2050
SEMICONDUCTOR - - 1505
SILICON - - - - - 323
- - - - - 892
- - - - - 1331
- - - - - 1499
SILICON NITRIDE - 1525
SILICON OXIDE - - 2050
SILICON WAFER - - 1331
SPREADING RESIST. 1518
SURFACE ALLOY - - 366
- - 370
TEMPERATURE VARI. 1331
TITANIUM - - - - 1892
ZINC - - - - - - 1505

ION-SOLVENT
CONDUCTANCE - - ->1974
CYCLIC VOLTAMMET. "
DIMETHYL SULFOXI. "
INFRARED SPECTRA "

IONIC CONDUCTANC.
CONDENSED PHASE -> 252
HYDROGEN EVOLUTI. "
IONIC EQUILIBRIA "
PRESSURE EFFECT - "

IONIC CONDUCTIVI.
BETA EUCRYPTITE -> 179
CONDUCTION - - ->1994
DIFFUSION - - - - "
GLASS CERAMICS - 179
LITHIUM ALUMINOS. "
LITHIUM FERRITE - 1994
LITHIUM ION - - - "
SOLID ELECTROLYTE 179

IONIC EQUILIBRIA
CONDENSED PHASE -> 252
HYDROGEN EVOLUTI. "
IONIC CONDUCTANC. "
PRESSURE EFFECT - "

IONIC STRENGTH
CURRENT DENSITY ->1591
EQUILIBRIUM POTE. "
POTASSIUM HYDROX. "
ZINC ELECTRODE - "

IONIC TRANSPORT
CONDUCTIVITY - -> 751
NONSTOICHIOMETRY "
ZIRCONIA - - - - "

IRIDIUM
ELECTRODE ACTIVA.>1266
FLUORINE - - - -> 498
GASIFICATION - - "
MOLTEN SALTS - - 1266
OXIDE LAYER - - - "
PLATINUM - - - - 498
POTENTIODYNAMICS 1266
TANTALUM - - - - 498
TEMPERATURE KINE. "

IRON
ACID - - - - - ->1393
BETA ALUMINA - ->1007
BLOCKING EFFECTS > 389
CALCIUM - - - - - 1007
CERAMIC - - - - - "
CHLORIDE SOLUTIO.> 853
CORROSION - - - - "
CORROSION INHIBI. 1393
DISSOLUTION KINE. 853
ELECTRODE KINETI. 389
ELECTRODISSOLUTI. 853
ENERGY STORAGE - 1007
MATHEMATICAL MOD.>1382
METAL SURFACE - - "
OXYGEN COVERAGE - 389
POTASSIUM - - - - 1007
QUINONE - - - - - 389
REPASSIVATION - - 1382
RHODIUM ELECTRODE 389
SALT FILM - - - - 1382
THIOUREA - - - - 1393
TITANIUM - - - - 1382

IRON ACTIVATION
LITHIUM METAGALL.> 920
LUMINESCENCE - - "
PHOSPHORS - - - - "

IRON CHROMIUM
ANODIC POLARIZAT.> 366
ION IMPLANTATION "
PITTING POTENTIAL "
SURFACE ALLOY - - "

IRON NICKEL
ANODIC POLARIZAT.> 370
ION IMPLANTATION "
PITTING POTENTIAL "
SURFACE ALLOY - - "

IRON NICKEL ALLOY
ELECTRON PROBE -> 279
OXIDATION - - - - "
OXIDE MORPHOLOGY "

IRON OXIDE
FERMI ENERGY - -> 781
NONSTOICHIOMETRY "
SURFACE POTENTIAL "
WORK FUNCTION - - "
WUSTITE PHASE - - "

IRON SULFIDE
CERAMIC POWDER ->1913
ELECTRODE SEPARA. "
FIBROUS SEPARATOR "
FUSED SALTS - - - "
LITHIUM ALUMINUM "
LITHIUM SULFIDE ->1567
MOLTEN SALTS - - "
SOLUBILITY PRODU. "

IRON THIONINE
PHOTOGALVANIC - ->1365
PHOTOREDOX REACT. "
TIN OXIDE - - - - "

IRON TIN ALLOY
MOSSBAUER - - - ->1652
THICKNESS DETERM. "
TIN OXIDE - - - - "
TINPLATE - - - - "

ISOTOPIC EXCHANGE
ELECTROCATALYSIS > 74
LANTHANUM COBALT "
NICKEL OXIDE - - "

JUNCTION LEAKAGE
ALUMINA CATALYST >1302
DOPING LEVEL - ->1648
MOS TRANSISTOR - 1302
P-N DIODE - - - - 1648
POLYSILICON - - - "
THRESHOLD VOLTAGE 1302
WALK-OUT - - - - "

KINETIC MECHANISM
ATOMIC OXYGEN - -> 110
COLD WALL REACTO. "
CVD - - - - - - - - "
TIN CHLORIDE - - "
TIN OXIDE - - - - "

KINETIC MODEL
BROMINE LAMP - ->2064
LAMP CHEMISTRY - "
TUNGSTEN HALOGEN "

KINETIC PARAMETE.
OVERPOTENTIAL - ->284C
POLAROGRAPHICS - "

KINETIC RATE
ACCELERATED TEST >2002
CORROSION TEST - "
HUMIDITY - - - - "
POLLUTANTS - - - "

KRAMERS-KRONIG
ALUMINUM OXIDE -> 299
OPTICAL REFLECTA. "
QUALITY CONTROL - "
SAPPHIRE - - - - "

LAMP CHEMISTRY
BROMINE LAMP - ->2064
KINETIC MODEL - - "
TUNGSTEN HALOGEN "

LANTHANUM
HALOSILICATE - -> 445
LUMINESCENCE - - "
PHOSPHORS - - - - "
RARE EARTH ELEME. "
YTTRIUM - - - - - "

LANTHANUM COBALT
ELECTROCATALYSIS > 74
ISOTOPIC EXCHANGE "
NICKEL OXIDE - - "

LAPLACE ANALYSIS
PHASE ANGLE - - ->1765
SKIN IMPEDANCE - "

LAPLACE EQUATION
CONVERGING ELECT.> 697
CURRENT DENSITY - "
ELECTROCOATING - "
FOURIER TRANSFORM "

LASER SPECTROSCO.
CALCIUM FLUOROPH.>1493
ESR - - - - - - - - "
NEODYMIUM - - - - "
OPTICAL PROPERTY "

LASERS
LUMINESCENCE - ->415C
PHOSPHORS - - - - "

LAYER THICKNESS
ELECTROEPITAXY ->1140
GAAS - - - - - - - "
LPE - - - - - - - - "

LAYERED SEMICOND.
ANODIZATION - - -> 824
NONPASSIVE-PASSI. "

LEAD
EXTRAPOLATION - -> 888
PERCHLORATE ACID "

PRIMARY TERM / CO-TERM — PAGE NO.

LEAD (CONTD)
POLARIZATION - - 888

LEAD ACID BATTERY
CELLULOSE - - - -> 833
HYDROLYSIS - - - "
PASTE MIXING - ->1934
PLATE CURING - - "
POLYMERIZATION - 833
SEPARATOR - - - - "
TETRABASIC LEAD - 1934

LEAD ACID CELL
LOAD LEVELING - ->1011
TEMPERATURE DIST. "
WATER COOLING - - "

LEAD DEPOSITION
FERRI-FERROCYANI.> 232
POLYMERIC ELECTR. "
POLYTHIAZYL - - - "
SULFUR NITRIDE - "

LEAD FLUORIDE
ELECTRODE REACTI.>1628
LEAD HALIDES - - "

LEAD HALIDES
ELECTRODE REACTI.>1628
LEAD FLUORIDE - - "

LEAD SULFIDE
BORON - - - - - - -> 678
REST POTENTIAL - "
SEMICONDUCTANCE - "

LEAD SYSTEM
ANODIC DISSOLUTI.>1989
EXCHANGE REACTION "
PERCHLORATE ACID "

LEAKAGE CURRENT
CROSS STRUCTURE -> 645
DIFFUSED LAYER - "
SHEET RESISTANCE "
VAN DER PAUW - - "

LECLANCHE CELL
LITHIUM BATTERY ->271C
PRIMARY BATTERY - "
ZINC AIR CELL - - "

LEED
AUGER - - - - - - -> 348
ELECTROSORPTION - "
HYDROGEN ADSORPT. "
PLATINUM - - - - "
SINGLE CRYSTAL - "

LENS
DIELECTRICS - - ->1191
ELECTRON DIFFRAC. "
ELECTROSTATIC - - "

LEVELING MECHAN.
CIRCUIT BOARD - ->1218
COPPER PYROPHOSP. "
DIMERCAPTOTHIADI. "
ELECTROPLATING - "
FOLDBACK - - - - "
PT-DISK ELECTROD. "

LIGHT EMITTER
HETEROJUNCTION -> 123
INDIUM PHOSPHATE "
LPE CONDITIONS - "
PHASE EQUILIBRIUM "
QUATERNARY SYSTEM "

LIMITING CURRENT
CONVECTIVE DIFFU.>1461
DIFFUSION LAYER -> 845
FOAMED ELECTROLY.> 94
FUEL CELL - - - - "
IMPINGING JET - - 1461
LITHIUM - - - - - 845
LITHIUM HYDROXIDE "
MASS TRANSFER - - 94
- - 1461
POLARIZATION - - 845
UNIFORM ACCESSIB. 1461

LINE EMITTER
BROAD BAND EMITT.>2015
CANDOLUMINESCENCE "
HYDROGEN ION BEAM "
ION EXCHANGE - - "

LINE EMITTER (CONTD)
QUANTUM YIELD - - 2015

LINE WIDTH
CROSS BRIDGE STR.> 650
DIFFUSED LAYER - "
PROCESS CONTROL - "
SHEET RESISTANCE "
VAN DER PAUW - - "

LINEAR DEFECT
ELECTROCRYSTALLI.>1049
HYDROGEN - - - - "
NICKEL - - - - - "
TEM - - - - - - - "
THIN FILM - - - - "

LINEAR KINETICS
COPPER OXIDATION > 803
NUCLEATION - - - "

LINEAR POLARIZAT.
CORROSION - - - ->1977
CYCLIC VOLTAMMET.>1443
1977
ELECTRODE KINETIC "
EQUIVALENT CIRCU. 1443
HYSTERESIS - - - "
IMPEDANCE - - - - "
PSEUDOINDUCTANCE 1977
RESISTIVE-CAPACI. 1443
TRANSFORM ANALYS. "

LIQUID ALLOY
BETA ALUMINA - ->1377
CONCENTRATION CE. "
EMF MEASUREMENT - "
SODIUM TIN ALLOY "

LIQUID CHROMATOG.
DL-MESO RATIO - -> 372
ELECTROHYDRODIME. "
P-HYDROXYBENZALD. "
STEREOISOMER - - "

LIQUID JUNCTION
COPPER INDIUM SU.> 831
PHOTOANODE - - ->1156
PHOTOELECTROCHEM. "
SEMICONDUCTOR - - "
SOLAR CELL - - - 831

LIQUID OXYGEN
OXIDATION KINETI.> 766
SILICON DIOXIDE - "
TUNNELABLE OXIDE "

LIQUID SOLUTION
COPPER SULFIDE -> 882
EPITAXIAL LAYERS "
METHANOL - - - - "
RHEED - - - - - - "

LITHIUM
ANODIC BEHAVIOR -> 1
BORON - - - - - ->1632
CALORIMETRY - - -> 842
CORROSION - - - - 1
DIFFUSION LAYER -> 845
DISSOLUTION - - - 1
LIMITING CURRENT 845
LITHIUM ELECTRODE 1632
LITHIUM HYDROXIDE 1
845
MERCURY - - - - - 842
PACEMAKER BATTER. "
POLARIZATION - - 845
SILICON - - - - - 1632
SILICON NIGRATION "
SILVER - - - - - 842
TERNARY ALLOY - - 1632
ZINC - - - - - - 842

LITHIUM ALLOY
ALUMINUM ALLOY ->1886
MAGNESIUM ALLOY - "
POLARIZATION - - "

LITHIUM ALUMINATE
CARBONATE CELL ->1799
CORROSION PROTEC. "
STAINLESS STEEL - "
WET SEAL - - - - "

LITHIUM ALUMINOS.
BETA EUCRYPTITE -> 179
GLASS CERAMICS - "

LITHIUM ALUMINOS. (CONTD)
IONIC CONDUCTIVI. 179
SOLID ELECTROLYTE "

LITHIUM ALUMINUM
ANODIC DISCHARGE > 727
CERAMIC POWDER ->1913
CYCLE LIFE - - - 727
ELECTRODE SEPARA. 1913
FIBROUS SEPARATOR "
FUSED SALTS - - - "
IRON SULFIDE - - "
MOLTEN SALT ELEC. 727

LITHIUM ANODE
ELECTROLITHIATION>1563
TITANIUM SULFIDE "
X-RAY DIFFRACTION "

LITHIUM ANTIMONY
COULOMETRIC TITR.> 7
ENTHALPY - - - - "
ENTROPY - - - - - "
GALVANIC CELL - - "
GIBBS FREE ENERGY "
INTERMETALLIC - - "
LITHIUM BISMUTH - "

LITHIUM BATTERY
BISMUTH FLUORIDE > 511
CYCLIC VOLTAMMET. "
CYCLING EFFICIEN.>1371
DIFFUSION - - - ->1193
LECLANCHE CELL ->271C
LITHIUM CHLORIDE 1193
LITHIUM CYCLING -> 186
LITHIUM ELECTRODE "
MIGRATION PROCESS 1193
MOLTEN SALT - - - "
NONAQUEOUS SOLVE. 511
ORGANIC ELECTROL. 1371
POTASSIUM CHLORI. 1193
PRIMARY BATTERY - 271C
PROPYLENE CARBON. 186
TETRAHYDROFURAN - 1371
ZINC AIR CELL - - 271C

LITHIUM BISMUTH
COULOMETRIC TITR.> 7
ENTHALPY - - - - "
ENTROPY - - - - - "
GALVANIC CELL - - "
GIBBS FREE ENERGY "
INTERMETALLIC - - "
LITHIUM ANTIMONY "

LITHIUM CELL
BISMUTH TRIOXIDE > 14
BUTTON ORGANIC - "
CALORIMETRY - - -> 674
CATHODE - - - - - 14
CATHODE REACTION >1574
CURRENT DENSITY - "
DISCHARGE REACTI. 674
MASS TRANSPORT - 1574
NONAQUEOUS SOLVE. 14
SULFONYL CHLORIDE 1574
SULFOXYDICHLORID. 674

LITHIUM CHLORATE
ANODIC POLARIZAT.>1262
CATHODIC POLARIZ.>1257
LITHIUM HYDROXIDE "
ORGANIC FILM - - 1262
PLATINUM ELECTRO. 1257
1262
TETRAHYDROFURAN - 1257
- 1262
XPS - - - - - - - 1257
- - - - - - - 1262

LITHIUM CHLORIDE
DIFFUSION - - - ->1193
LITHIUM BATTERY - "
MIGRATION PROCESS "
MOLTEN SALT - - - "
POTASSIUM CHLORI. "

LITHIUM CYCLING
LITHIUM BATTERY -> 186
LITHIUM ELECTRODE "
LITHIUM SUBSTRATE>1990
PROPYLENE CARBON. 186
1990

LITHIUM ELECTRODE
BORON - - - - - ->1632

LITHIUM ELECTRODE (CONTD)
LITHIUM - - - - - 1632
LITHIUM BATTERY -> 186
LITHIUM CYCLING - "
PROPYLENE CARBON. "
SILICON - - - - - 1632
SILICON NIGRATION "
TERNARY ALLOY - - "

LITHIUM FERRITE
CONDUCTION - - ->1994
DIFFUSION - - - - "
IONIC CONDUCTIVI. "
LITHIUM ION - - - "

LITHIUM HYDROXIDE
ANODIC BEHAVIOR -> 1
ANODIC OXIDATION >1960
CATHODIC POLARIZ.>1257
COPPER AMALGAM - 1960
CORROSION - - - - 1
DIFFUSION LAYER -> 845
DISSOLUTION - - - 1
LIMITING CURRENT 845
LITHIUM - - - - - 1
- - - - - 845
LITHIUM CHLORATE 1257
NUCLEATION - - - 1960
PLATINUM ELECTRO. 1257
POLARIZATION - - 845
POLYCRYSTAL COPP. 1960
TETRAHYDROFURAN - 1257
XPS - - - - - - - "

LITHIUM ION
CONDUCTION - - ->1994
DIFFUSION - - - - "
IONIC CONDUCTIVI. "
LITHIUM FERRITE - "

LITHIUM METAGALL.
IRON ACTIVATION -> 920
LUMINESCENCE - - "
PHOSPHORS - - - - "

LITHIUM OXIDE
INTERDIFFUSIVITY > 395
OXIDE MELTS - - - "
POLARIZATION - - "
SILICON DIOXIDE - "

LITHIUM PERCHLOR.
DIMETHYL SULFITE > 687
GRAPHITE - - - - "
RADICAL CATION - "

LITHIUM SUBSTRATE
LITHIUM CYCLING ->1990
PROPYLENE CARBON. "

LITHIUM SULFIDE
IRON SULFIDE - ->1567
MOLTEN SALTS - - "
SOLUBILITY PRODU. "

LITHIUM TUNGSTEN.
ELECTROCHROMISM -> 284
GALVANOSTATIC - - "
POTENTIOSTATIC - "

LOAD DEPENDENT
CARDIAC PACEMAKER>1907
MICROCALORIMETER "
PRIMARY BATTERY - "
SELF DISCHARGE - "

LOAD LEVELING
LEAD ACID CELL ->1011
TEMPERATURE DIST. "
WATER COOLING - - "

LOCALIZED CORROS.
ALUMINUM STRAINI.>1594
CHLORIDE SOLUTIO.>1199
HYDROGEN EVOLUTI. "
PITTING - - - - - 1594
SEM - - - - - - - "
SLIP STEPS - - - "
SULFURIC ACID - - 1199
TENSILE STRESS - "
TITANIUM ALLOY - "
TRANSPASSIVITY - "

LOW ENERGY ELECT.
CATHODOLUMINESCE.> 102
COPRECIPITATION - "
EUROPIUM - - - - "

PRIMARY TERM / CO-TERM	PAGE NO.
LOW ENERGY ELECT. (CONTD)	
POWDER PHOSPHOR	102
TIN DIOXIDE	"
LOW IMPEDENCE	
BATTERY SEPARATOR	520
CAPACITANCE	"
RESISTIVITY	"
WHEATSTONE BRIDGE	"
LOW LEAKAGE	
ALUMINUM GAAS	989
COMPOUND SEMICON.	"
MOS	"
OXIDE	"
LOW PRESSURE	
ANNEALING	927
AUTODOPING	1879
CRYSTAL STRUCTURE	927
CVD	"
MULTIWAFER GROWTH	1879
SILICON EPITAXY	"
SILICON FILM	927
STRUCTURE	"
LPE	
BUFFER LAYER	2058
CHALCOPYRITE	952
CHROMIUM	2058
CRYSTAL GROWTH	130
ELECTROEPITAXY	1140
EPITAXIAL GROWTH	1817
ETCH PIT	2019
FET	2058
GAAS	130
	1140
	2058
GALLIUM DOPING	1817
HETEROEPITAXY	130
II-IV-V2 COMPOUND	952
INDIUM PHOSPHIDE	130
LAYER THICKNESS	1140
MISCIBILITY GAP	1053
QUATERNARY CRYST.	"
SEMIINSULATING	2058
SILICON	1817
SINGLE CRYSTAL	952
STRAIN EFFECT	1053
THREADING DISLOC.	2019
X-RAY TOPOGRAPHY	"
ZINC TIN ARSENIDE	952
LPE CONDITIONS	
HETEROJUNCTION	123
INDIUM PHOSPHATE	"
LIGHT EMITTER	"
PHASE EQUILIBRIUM	"
QUATERNARY SYSTEM	"
LUMINESCENCE	
AQUEOUS SOLUTION	246
EUROPIUM	1130
HALOSILICATE	445
IRON ACTIVATION	920
LANTHANUM	445
LASERS	415C
LITHIUM METAGALL.	920
PEROVSKITE STRUC.	1130
PHOSPHORS	445
	920
	415C
RARE EARTH ELEME.	445
SEMICONDUCTOR	246
SURFACE STATE	"
TELLURATE	1130
TITANIUM DIOXIDE	246
YTTRIUM	445
MAGNESIUM ALLOY	
ALUMINUM ALLOY	1886
LITHIUM ALLOY	"
POLARIZATION	"
MAGNESIUM ANODE	
ALUMINUM ALLOY	1924
CORROSION	"
MANGANESE DIOXIDE	"
PORTABLE HEATER	"
SALINE CELL	"
MAGNETITE	
CHROMIUM	55C
DIFFUSION CHARAC.	"
OXYGEN PRESSURE	"
MALEIC ACID	
ALUMINUM	190
ANODIZATION	"
CARBON MONOXIDE	"
GLYOXAL	"
MANGANESE DIOXIDE	
ALUMINUM ALLOY	1924
CORROSION	"
MAGNESIUM ANODE	"
PORTABLE HEATER	"
SALINE CELL	"
MANIFOLD MODEL	
ELECTRICAL ANALOG	515
FUEL CELL ASSEMB.	"
PARASITIC CURREN.	"
SHUNT CURRENTS	"
MARCUS THEORY	
COULOMETRY	1250
CYCLIC VOLTAMMET.	"
FERRIHEME	"
POLAROGRAPHY	"
MASKING EFFECT	
OXIDANT ELIMINAT.	448
SILICON NITRIDE	"
THERMAL NITRIDAT.	"
MASS SPECTROMETRY	
BACKSCATTERING	1215
CVD	1877
DEPTH PROFILE	1215
ENTHALPY	1543
FLUORINE	162
GASEOUS EQUILIBR.	1543
NICKEL	1215
RHENIUM	162
RUTHERFORD	1215
SILICON NITRIDE	1877
TANTALUM FLUORIDE	162
TIN	1215
TUNGSTEN	162
ZIRCONIUM IODIDES	1543
MASS TRANSFER	
ANODE	44
AUGER SPECTROSCO.	"
CATHODE	"
CHLORINE BATTERY	89
CONVECTIVE DIFFU.	1461
COPPER DEPOSITION	58
CURRENT DISTRIBU.	"
	79
DIFFUSION COEFFI.	89
DIFFUSION LAYER	1772
ELECTRODE CONFIG.	58
FOAMED ELECTROLY.	94
FUEL CELL	"
IMPINGING JET	1461
LIMITING CURRENT	94
	1461
MATRIX CONDUCTIV.	58
METAL OXIDE FILM	44
PLASMA ANODIZATI.	"
POROUS ELECTRODE	58
POTENTIAL DISTRI.	"
PRIMARY CURRENT	79
PRIMARY RESISTAN.	"
PULSED ELECTROLY.	1772
RING ELECTRODE	79
ROTATING DISK EL.	1772
ROTATING HEMISPH.	89
SECONDARY CURRENT	79
SILVER DEPOSITIO.	58
UNIFORM ACCESSIB.	1461
ZINC BATTERY	89
ZINC HEMISPHERE	"
MASS TRANSPORT	
BOUNDARY LAYER	865
CALCIUM FLUORIDE	755
CATHODE REACTION	1574
CHEMISORPTION	544
CONDUCTIVITY	755
CURRENT DENSITY	1574
ELECTRODEPOSITION	865
HYDROGEN SULFIDE	544
LITHIUM CELL	1574
POLARIZATION	755
ROTATING ELECTRO.	544
SHEET ELECTRODE	865
SOLID ELECTROLYTE	755
SULFONYL CHLORIDE	1574
TRANSIENTS	865
MATHEMATICAL MOD.	
CURRENT DISTRIBU.	1981
ELECTRODEPOSITION	"
FINITE ELEMENT	"
IRON	1382
METAL SURFACE	"
POTENTIAL DISTRI.	1981
REPASSIVATION	1382
SALT FILM	"
SHAPE CHANGE	1981
TITANIUM	1382
MATRIX CONDUCTIV.	
COPPER DEPOSITION	58
CURRENT DISTRIBU.	"
ELECTRODE CONFIG.	"
MASS TRANSFER	"
POROUS ELECTRODE	"
POTENTIAL DISTRI.	"
SILVER DEPOSITIO.	"
MAXWELL WAGNER	
CAPACITOR	746
DIELECTRIC PROPE.	"
HEAT TREATMENT	"
TANTALUM OXIDE	"
TWO LAYER MODEL	"
MECHANICAL STRESS	
ELECTRICAL PROPE.	1848
INTERFACE CHARGE	"
MNOS MEMORY	"
SILICON NITRIDE	"
MEDICAL ELECTROC.	
ANTITHROMBOGENIC	419C
HEMOSTASIS	"
IMMUNE RESPONSE	"
MELT FLOW	
CRYSTAL GROWTH	475
GALLIUM DOPING	"
GERMANIUM	"
THERMAL GRADIENT	"
MELTING POINT	
ALKALI METAL	1894
ELECTRODEPOSITION	1721
FLUORIDE	1894
INDIUM PHOSPHIDE	1721
METAPHOSPHATE	1894
MELTS	
ACIDITY DEPENDEN.	1454
FUSED SALTS	"
SELENIUM	"
TETRACHLOROALUMI.	"
MEMORY	
ALUMINUM NITRIDE	305
CHARGE STORAGE	"
CVD	"
FILM PROPERTY	"
SILICON NITRIDE	"
MENISCUS RISE	
ELECTRIC FIELD	1404
INSULATING LIQUID	"
YOUNG AND DUPREE	"
MERCURIC IODATE	
ENTROPY	875
MERCURY	"
STANDARD POTENTI.	"
MERCURY	
CALORIMETRY	842
COULOSTATIC DEPO.	384
ENTROPY	875
GOLD	384
	1098
LITHIUM	842
MERCURIC IODATE	875
PACEMAKER BATTER.	842
POTENTIAL RELAXA.	384
RING DISK ELECTR.	1098
SEMICONDUCTOR	1881
SILVER	842
STANDARD POTENTI.	875
UNDERPOTENTIAL	384
	1098
WORK FUNCTION	1881
ZINC	842
MERCURY ELECTROD.	
ADSORPTION	1236
MOLECULAR AREA	"
MERCURY ELECTROD. (CONTD)	
PURINES	1236
PYRIMIDINES	"
RIBOSE	"
MERCURY OXIDE	
CONVECTIVE FLOW	1020
SILVER OXIDE	"
ZINC ELECTRODE	"
MERCURY POOL	
CATHODIC REDUCTI.	714
COULOMETRY	"
DINITROANALINE	"
PH DEPENDENCY	"
MERCURY TELLURIDE	
BRIDGMAN APPROACH	315
CADMIUM TELLURIDE	"
INFRARED MATERIAL	"
PSEUDOBINARY ALL.	"
SINGLE CRYSTAL	"
METAL ADATOMS	
ALLIUM PHOSPHIDE	68
PHOTOELECTROCHEM.	"
SEMICONDUCTOR	"
SPECTRAL RESPONSE	"
SURFACE STATE	"
METAL FILM	
ALUMINUM COPPER	30
ANODIC OXIDATION	"
CORROSION	"
INTEGRATED CIRCU.	"
METALLIZATION	"
METAL OXIDE FILM	
ANODE	44
AUGER SPECTROSCO.	"
CATHODE	"
MASS TRANSFER	"
PLASMA ANODIZATI.	"
METAL PRODUCTION	
ELECTROREFINING	49C
ELECTROWINNING	"
FUSED SALT SYSTEM	"
METAL REFLECTOR	
ALUMINUM OXIDE	1138
MOLYBDENUM FILM	"
PHOTOTHERMAL	"
SILICON NITRIDE	"
METAL SURFACE	
IRON	1382
MATHEMATICAL MOD.	"
REPASSIVATION	"
SALT FILM	"
TITANIUM	"
METAL WATER SYST.	
CALCULATION	808
ELECTRODE POTENT.	"
ENTROPY	"
HEAT CAPACITY	"
METALLIZATION	
ALUMINUM COPPER	30
ANODIC OXIDATION	"
CORROSION	"
INTEGRATED CIRCU.	"
METAL FILM	"
METALS	
ALKALINE COMPOUND	5C
CAUSTIC SODA	455C
CHLORINE COMPOUND	"
ELECTROLYTIC IND.	5C
	455C
ENERGY SOURCE	5C
METAPHOSPHATE	
ALKALI METAL	1894
FLUORIDE	"
MELTING POINT	"
METASTABLE ALLOY	
AVRAMI EQUATION	330
DSC	"
DTA	"
FORMATION MECHAN.	335
NUCLEATION KINET.	"
TIN NICKEL	330
	335
TRANSFORMATION	"

PRIMARY TERM / CO-TERM	PAGE NO.
METHANOL	
COPPER SULFIDE ->	882
EPITAXIAL LAYERS	"
LIQUID SOLUTION -	"
RHEED - - - - - -	"
METHYLHYDRAZINE	
GAS MONITORING ->1804	
HYDRAZINE - - - -	"
MICROCALORIMETER	
CARDIAC PACEMAKER>1907	
LOAD DEPENDENT -	"
PRIMARY BATTERY -	"
SELF DISCHARGE -	"
MICROELECTRONICS	
ALKALI CONTAMINA.>	106
CLEAN FILM - - -	"
MOS STRUCTURE - -	"
POLYSILICON TUBE.	"
SILICON DIOXIDE -	"
MICROSCOPIC ANAL.	
ALUMINUM - - - ->1480	
ANODIC FILM - - -	"
CELL WALLS - - -	"
X-RAY ANALYSIS -	"
MIGRATION PROCESS	
DIFFUSION - - - ->1193	
LITHIUM BATTERY -	"
LITHIUM CHLORIDE	"
MOLTEN SALT - - -	"
POTASSIUM CHLORI.	"
MINORITY CARRIER	
MOS STRUCTURE - ->1696	
OXIDE QUALITY - -	"
THERMAL OXIDATION	"
TRICHLOROETHANE -	"
MISCIBILITY GAP	
ALUMINUM OXIDE ->	175
CHROMIUM OXIDE -	"
GALVANIC CELL - -	"
LPE - - - - - - - ->1053	
QUATERNARY CRYST.	"
SOLID ELECTROLYTE	175
STRAIN EFFECT - -	1053
THERMODYNAMICS -	175
MISFIT DISLOCATI.	
PHOSPHORUS DIFFU.>	923
SILICON - - - - -	"
VAN DER MERWE - -	"
MIXED CONDUCTOR	
CERIUM DIOXIDE ->1277	
ENERGY CONVERSION	"
FUEL CELL - - - -	"
TRANSPORT THEORY	"
MIXED POTENTIAL	
COPPER DEPOSITION>	173
ELECTROLESS PLAT.	"
FORMALDEHYDE - -	"
MNOS FET DEVICE	
CHARGE ACCUMULAT.>1657	
DUAL DIELECTRICS	"
THRESHOLD VOLTAGE	"
MNOS MEMORY	
ELECTRICAL PROPE.>1848	
INTERFACE CHARGE	"
MECHANICAL STRESS	"
SILICON NITRIDE -	"
MNOS TRANSISTOR	
D-C RESPONSE - ->	985
HYDROCHLORIC ACID	"
PULSE - - - - - -	"
MODELING	
DIFFUSION LENGTH >2034	
GAAS - - - - - -	"
RADIATION DAMAGE	"
SOLAR CELL - - -	"
SURFACE RECOMBIN.	"
MODULATION TRANS.	
OUTPUT SCREEN - ->	583
PHOSPHORS - - - -	"
SPATIAL NOISE - -	"
X-RAY IMAGE INTE.	"
MOISTURE	
CHROMIUM - - - ->1450	
EUTECTIC - - - -	"
HYDROLYSIS - - -	"
MOLTEN SALTS - -	"
MOLECULAR AREA	
ADSORPTION - - ->1236	
MERCURY ELECTROD.	"
PURINES - - - - -	"
PYRIMIDINES - - -	"
RIBOSE - - - - -	"
MOLECULAR BEAM	
BISMUTH TRITELLU.>2042	
EPITAXY - - - - -	"
IMPURITY DOPANT -	"
NONSTOICHIOMETRY	"
SEMICONDUCTOR - -	"
THALLIUM - - - -	"
VAPOR PRESSURE -	"
MOLTEN CARBONATES	
CARBON MONOXIDE ->	888
NITROGEN - - - -	"
OPEN CIRCUIT - -	"
MOLTEN SALT	
ALUMINUM - - - ->1000	
ALUMINUM CHLORID.	"
CATALYSIS - - - -	"
CHROMIUM CHLORIDE>	561
CHRONOAMPEROMETRY	"
CYCLIC VOLTAMMET.	"
DIFFUSION - - - ->1193	
LITHIUM BATTERY -	"
LITHIUM CHLORIDE	"
MIGRATION PROCESS	"
POTASSIUM CHLORI.	"
POTASSIUM HYDROX.	1000
MOLTEN SALT ELEC.	
ANODIC DISCHARGE >	727
CYCLE LIFE - - -	"
LITHIUM ALUMINUM	"
MOLTEN SALTS	
CHROMIUM - - - ->1450	
ELECTRODE ACTIVA.>1266	
EUTECTIC - - - -	1450
HYDROLYSIS - - -	"
IRIDIUM - - - - -	1266
IRON SULFIDE - ->1567	
LITHIUM SULFIDE -	"
MOISTURE - - - -	1450
OXIDE LAYER - - -	1266
POTENTIODYNAMICS	"
SOLUBILITY PRODU.	1567
MOLYBDENUM	
AUGER ANALYSIS ->1204	
CHROMIUM - - - -	"
PITTING - - - - -	"
STAINLESS STEEL -	"
MOLYBDENUM DIMERS	
EDTA - - - - - ->287C	
OXYGEN - - - - -	"
SULFUR - - - - -	"
MOLYBDENUM FILM	
ALUMINUM OXIDE ->1138	
METAL REFLECTOR -	"
PHOTOTHERMAL - -	"
SILICON NITRIDE -	"
MOLYBDENUM SELEN.	
D-ENERGY BAND - ->1086	
HOLE REACTION - -	"
SOLAR ENERGY - -	"
MONITORING	
ETCHING - - - - ->	798
SILICON DIOXIDE -	"
SILICON NITRIDE -	"
UNDERETCHING - -	"
MONOHYDRATE-WATER	
ACID FUEL CELL ->1899	
CORROSION - - - -	"
PHOSPHORIC ACID -	"
SULFURIC ACID - -	"
TRIFLUOROMETHANE	"
MORPHOLOGY	
AGITATION EFFECT >	36
BRIGHTENER - - -	"
MORPHOLOGY (CONTD)	
COPPER - - - - -	36
PLATING CELL - -	"
PRINTED WIRING -	"
THROWING POWER -	"
MOS	
ALUMINUM GAAS - ->	989
COMPOUND SEMICON.	"
DEEP LEVEL DEFECT>1664	
INTERFACE STATE -	"
LOW LEAKAGE - - -	989
OXIDE - - - - - -	"
SLOW COOLING - -	1664
TRANSIENT CAPACI.	"
MOS DEVICE	
GATE OXIDE - - ->	432
OXIDE WALL - - -	"
SILICON - - - - ->	743
SILICON DIOXIDE -	"
SLOW-TRAPPING - -	"
SURFACE STATE - -	"
THINNING - - - -	432
MOS LSI PASSIVAT.	
CVD - - - - - - ->	601
INTEGRATED CIRCU.	"
REACTIVE PLASMA -	"
SILICON NITRIDE -	"
MOS LSI PROCESS	
SELECTIVE OXIDAT.>1824	
SILICON NITRIDE -	"
SILICON OXIDATION	"
STEAM - - - - - -	"
MOS STRUCTURE	
ALKALI CONTAMINA.>	106
CLEAN FILM - - -	"
MICROELECTRONICS	"
MINORITY CARRIER >1696	
OXIDE NITRIDE - ->2012	
OXIDE QUALITY - -	1696
PLASMA OXIDIZED -	2012
POLYSILICON TUBE.	106
REFRACTION - - -	2012
SILICON DIOXIDE -	106
SILICON NITRIDE -	2012
THERMAL OXIDATION	1696
TRICHLOROETHANE -	"
MOS TRANSISTOR	
ALUMINA CATALYST >1302	
CRYSTALLINE PERF.>	792
FET MOBILITY - -	"
JUNCTION LEAKAGE	1302
SAPPHIRE - - - -	792
SILICON - - - - -	"
THRESHOLD VOLTAGE	1302
WALK-OUT - - - -	"
X-RAY DIFFRACTOM.	792
MOSSBAUER	
IRON TIN ALLOY ->1652	
THICKNESS DETERM.	"
TIN OXIDE - - - -	"
TINPLATE - - - -	"
MOSSBAUER SPECTR.	
ALUMINUM - - - ->	34
ANODIZATION - - -	"
TIN - - - - - - -	"
MOSSBAUER STUDY	
BORATE BUFFER - ->1946	
PASSIVE FILM - -	"
POLARIZATION CUR.	"
TIN OXIDE - - - -	"
MOTT SCHOTTKY	
ALPHA IRON OXIDE >	723
CAPACITANCE - - -	"
CONDUCTIVITY - -	"
DONOR DENSITY - -	"
FLATBAND POTENTI.	"
MULTIEXCITATION	
CATHODOLUMINESCE.>	288
PHOSPHORS - - - -	"
RASTER - - - - -	"
SATURATION PROPE.	"
MULTILAYER ANALY.	
EMITTER DIP EFFE.>1170	
IMPURITY PROFILE	"
P-N JUNCTION - -	"
MULTILAYER ANALY. (CONTD)	
SHEET RESISTANCE	1170
SPREADING RESIST.	"
MULTIPHASE SYSTEM	
EUTECTIC - - - ->1873	
INDIUM ANTIMONIDE	"
INTERFACE DEMARC.	"
MULTIWAFER GROWTH	
AUTODOPING - - ->1879	
LOW PRESSURE - -	"
SILICON EPITAXY -	"
NEODYMIUM	
CALCIUM FLUOROPH.>1493	
ESR - - - - - - -	"
LASER SPECTROSCO.	"
OPTICAL PROPERTY	"
NEUTRON ACTIVATI.	
AUGER SPECTROSCO.>	481
COPPER - - - - ->	963
DEPTH PROFILE - -	481
GAAS - - - - - -	"
GALLIUM DIFFUSION	963
GETTERING - - - -	"
GOLD - - - - - -	"
IMPURITY SINK - -	"
PLASMA OXIDATION	481
SILICON - - - - -	963
NEUTRON IRRADIAT.	
DOPING - - - - ->	350
EPITAXIAL LAYER -	"
EPITAXIAL WAFER -	"
NEUTRON TRANSMUT.	"
SILICON - - - - -	"
NEUTRON TRANSMUT.	
DOPING - - - - ->	350
EPITAXIAL LAYER -	"
EPITAXIAL WAFER -	"
NEUTRON IRRADIAT.	"
SILICON - - - - -	"
NICKEL	
ACCELERATED TEST >2005	
ANODIC OXIDATION >1410	
ATMOSPHERIC CORR.	2005
AUGER SPECTROSCO.	"
BACKSCATTERING ->1215	
COPPER - - - - -	2005
CORROSION TEST -	"
CURRENT DECAY - ->1416	
DEPTH PROFILE - -	1215
ELECTROCRYSTALLI.>1049	
ELLIPSOMETRY - -	1416
HYDROGEN - - - -	1049
LINEAR DEFECT - -	"
MASS SPECTROMETRY	1215
OXIDE FILM - - -	1410
- - -	1416
OXYGEN EVOLUTION	"
REJUVENATION - -	"
RUTHERFORD - - -	1215
SEMICONDUCTOR - -	1410
SILVER - - - - -	2005
TEM - - - - - - -	1049
THIN FILM - - - -	"
TIN - - - - - - -	1215
TITANIUM - - - -	1410
TITANIUM NICKEL -	"
NICKEL ALLOY	
ALKALINE SOLUTIO.>	265
ALUMINUM ALLOY ->	271
AUGER SPECTROSCO.>1801	
CHROMIUM ALLOY -	271
COPPER ALLOY - -	1801
CORROSION RESIST.	271
CUPRONICKEL - - -	1801
ELECTROCATALYST -	265
OXIDE FILM - - -	"
- - -	1801
OXYGEN EVOLUTION	265
SODIUM SULFATE -	271
TAFEL PARAMETER -	265
NICKEL ALUMINIDE	
CORROSION - - - ->1283	
GAS TURBINE - - -	"
SODIUM CHLORIDE -	"
WHISKERS - - - -	"
NICKEL COBALTOXI.	
GRAPHITE - - - ->1003	

PRIMARY TERM — CO-TERM — PAGE NO.

NICKEL COBALTOXI. (CONTD)
OXYGEN REDUCTION 1003
SPINEL - - - - - "

NICKEL ELECTRODE
ALCOHOL OXIDATION>1777
ANODIC DISSOLUTI. "
WIPER-BLADE CELL "

NICKEL HYDROXIDE
AGING PROCESS - ->1578
ANODIC OXIDATION "
CHRONOAMPEROMETRY>1026
CHRONOCOULOMETRY "
COBALT HYDROXIDE "
CYCLIC VOLTAMMET. "
FILM FORMATION - 1578

NICKEL OXIDE
ELECTROCATALYSIS > 74
ISOTOPIC EXCHANGE "
LANTHANUM COBALT "

NICKEL OXIDE FILM
OXIDE DEFECT - ->1883
SINGLE CRYSTAL - "

NICKEL PLATING
ACTIVATION - - ->1224
AUGER SPECTROSCO. "
DUMMYING - - - -> 204
ELECTROLYSIS - - "
ELLIPSOMETRY - - 1224
PHOTOELECTRON EM. "
PURIFICATION - - 204
SURFACE POTENTIAL 1224

NICKEL SUBSTRATE
CRYSTAL FACET - ->1940
CRYSTAL ORIENTAT. "
DEPASSIVATION - - "
ELECTRODEPOSITION "
PHOSPHORIC ACID - "

NIOBIUM
ANODIC OXIDATION >1549
ANODIC OXIDE FILM> 23
ELECTROCHROMISM - "
ELLIPSOMETRY - - "
HYDROGEN - - - - "
IMPEDANCE - - - - "
NUCLEAR MICROANA. 1549
POLARIZABILITY - 23
RUTHERFORD BACKS. 1549
TANTALUM - - - - "
TITANIUM - - - - 23
TRANSPORT MECHAN. 1549

NITRATE ELECTROL.
CALCIUM ANODE - ->1209
CALORIMETRY - - - "
CURRENT EFFICIEN. "
HALIDE SALTS - - "
PASSIVATING LAYER "

NITROGEN
CARBON MONOXIDE -> 888
MOLTEN CARBONATES "
OPEN CIRCUIT - - "

NITROGEN OXIDE
COPPER - - - - ->1114
RELATIVE HUMIDITY "

NOBLE METAL
AUGER SPECTROSCO.> 17
COPPER CORROSION "
DEPTH PROFILE - - "
DISSOLUTION - - ->1471
DISSOLUTION RATE 17
GROWTH BEHAVIOR - 1471
OXIDE FILM - - - "
PALLADIUM - - - - 17
PASSIVITY - - - - "
RUTHENIUM ELECTR. 1471

NOBLE METAL ALLOY
CORROSION KINETI.>1610
FICKS LAW - - - - "
FILM GROWTH - - - "
SOLUTE SEGREGATI. "

NONABRASION
COLLOIDAL SILICA > 136
POLISHING - - - - "
SAPPHIRE - - - - "

NONAQUEOUS SOLVE.
BISMUTH FLUORIDE > 511
BISMUTH TRIOXIDE > 14
BUTTON ORGANIC - "
CATHODE - - - - - "
CYCLIC VOLTAMMET. 511
LITHIUM BATTERY - "
LITHIUM CELL - - 14

NONPASSIVE-PASSI.
ANODIZATION - - - -> 824
LAYERED SEMICOND. "

NONSTOICHIOMETRY
BISMUTH TRITELLU.>2042
CHALCOCITE - - - ->1684
CHEMICAL DIFFUSI. "
CONDUCTIVITY - - -> 751
COPPER SULFIDE - 1684
EPITAXY - - - - - 2042
FERMI ENERGY - - -> 781
IMPURITY DOPANT - 2042
IONIC TRANSPORT - 751
IRON OXIDE - - - 781
MOLECULAR BEAM - 2042
SEMICONDUCTOR - - "
SURFACE POTENTIAL 781
THALLIUM - - - - 2042
VAPOR PRESSURE - "
WORK FUNCTION - - 781
WUSTITE PHASE - - "
ZIRCONIA - - - - 751

NOZZLE FABRICATI.
ANISOTROPIC ETCH.>1321
INK JET PRINTING "
SILICON NOZZLE - "
3-D MICROSTRUCTU. "

NUCLEAR MICROANA.
ANODIC OXIDATION >1549
NIOBIUM - - - - - "
RUTHERFORD BACKS. "
TANTALUM - - - - "
TRANSPORT MECHAN. "

NUCLEAR TRACK
ALPHA TRACK - - -> 654
BORON - - - - - - "
DOPANT DENSITY - "
SILICON - - - - - "

NUCLEATION
ANODIC OXIDATION >1960
COPPER AMALGAM - "
COPPER OXIDATION > 803
DEPOSITION - - ->1397
DIPYRIDINIUM COM. "
IODINE VAPOR - ->1001
LINEAR KINETICS - 803
LITHIUM HYDROXIDE 1960
POLYCRYSTAL COPP. "
STRESS CRACKING - 1001
TIN OXIDE - - - - 1397
VIOLOGENS - - - - "
ZIRCONIUM - - - - 1001

NUCLEATION KINET.
FORMATION MECHAN.> 335
METASTABLE ALLOY "
TIN NICKEL - - - "
TRANSFORMATION - "

OHMIC CONTACT
ALUMINUM METALLI.> 169
INTEGRATED CIRCU. "
POLYSILICON - - - "

OPEN CIRCUIT
CARBON MONOXIDE -> 888
MOLTEN CARBONATES "
NITROGEN - - - - "

OPEN TUBE
ALUMINUM - - - -> 957
DIFFUSION - - - - "
DOPING SILICON - "
VACUUM - - - - - "

OPTICAL ABSORPTI.
PLASMA NITRIDE -> 99
PLASMA POLYMERIZ. "
PLASMA SILICON - "
THIN FILM - - - - "

OPTICAL BENCH
ALIGNMENT GROOVE >1642

OPTICAL BENCH (CONTD)
GAAS LASER - - - 1642
PHOTOLITHOGRAPHY "
SILICON SUBSTRATE "

OPTICAL EMISSION
ALUMINUM - - - -> 829
CARBON TETRACHLO. "
PLASMA ETCHING - "

OPTICAL PROPERTY
CALCIUM FLUOROPH.>1493
ELLIPSOMETRY - -> 358
ESR - - - - - - - 1493
LASER SPECTROSCO. "
NEODYMIUM - - - - "
THIN OXIDE LAYERS 358
TITANIUM - - - - "

OPTICAL REFLECTA.
ALUMINUM OXIDE -> 299
KRAMERS-KRONIG - "
QUALITY CONTROL - "
SAPPHIRE - - - - "

ORDERING TRANSFO.
BACKSCATTERING ->1854
CHROMIUM - - - - "
EQUILIBRIUM DIAG. "
PLATINUM - - - - "

ORGANIC CARBONATE
ANODE SYNTHESIS ->1954
CARBON MONOXIDE - "
HALIDE ELECTROLY. "
PHOSGENE - - - - "

ORGANIC ELECTROL.
CYCLING EFFICIEN.>1371
LITHIUM BATTERY - "
TETRAHYDROFURAN - "

ORGANIC FILM
ANODIC POLARIZAT.>1262
LITHIUM CHLORATE "
PLATINUM ELECTRO. "
TETRAHYDROFURAN - "
XPS - - - - - - - "

ORGANIC SOLVENT
ALCOHOLS - - - -> 97
CARBON TETRACHLO. "
CORROSION - - - - "

ORTHOBORIC ACID
BORON DEPOSITION > 166
OXIDIZED SILICON "

OUTLOOK
FUEL CELL - - - -> 77C
SURVEY - - - - - "

OUTPUT SCREEN
MODULATION TRANS.> 583
PHOSPHORS - - - - "
SPATIAL NOISE - - "
X-RAY IMAGE INTE. "

OVERPOTENTIAL
KINETIC PARAMETE.>284C
POLAROGRAPHICS - "

OVERVOLTAGE
BAND BENDING - -> 937
BUTLER VOLMER - - "
DEPLETION LAYER - "
DIFFUSION THEORY "
PHOTOELECTRODE - "
RECOMBINATION - - "

OXIDANT ELIMINAT.
MASKING EFFECT -> 448
SILICON NITRIDE - "
THERMAL NITRIDAT. "

OXIDATION
ACETAL - - - - ->1401
ALCOHOL - - - - - "
BORON - - - - - ->2050
CHLORINE CONCENT.>2024
DIFFUSION - - - - 2050
ELECTROLYSIS - - 1401
ELECTRON PROBE -> 279
HALOALDEHYDE - - 1401
HYDROGEN HALIDE - "
ION IMPLANTATION 2050
IRON NICKEL ALLOY 279

OXIDATION (CONTD)
OXIDE MORPHOLOGY 279
PRUSSIAN BLUE - -> 886
REDUCTION - - - - "
SEGREGATION - - - 2050
SILICON OXIDE - - 2024
- - 2050
SIMS - - - - - - 2024
SPECTROMETRY - - "
THIN FILM - - - - 886

OXIDATION BARRIER
CVD - - - - - - - -> 139
FILM STRESS - - - "
SILICON DIOXIDE - "
SILICON NITRIDE - "

OXIDATION KINETI.
COBALT DIFFUSION > 898
COBALT OXIDE FILM "
DOPING - - - - -> 665
ELLIPSOMETRY - ->1146
FILM GROWTH - - - 898
GOLD - - - - - - "
GRAIN BOUNDARY -> 892
INITIAL REGIME ->1708
ION IMPLANTATION 892
LIQUID OXYGEN - -> 766
OXIDE LAYER - - ->1180
PARABOLIC KINETI. "
PHOSPHORUS - - - 665
PHOSPHORUS DOPED 892
RATE CONSTANT - - 665
RESISTIVITY - - - 892
SILICON - - - - - 665
- - - - - 892
SILICON DIOXIDE - 766
- 1708
SILICON OXIDATION 1146
SINGLE CRYSTAL - 1708
STRESS - - - - - 1180
THERMAL OXIDATION 1146
THIN FILM - - - - 1708
TUNNELABLE OXIDE 766
ZIRCALOY 2 - - - 1180

OXIDE
ALUMINUM GAAS - -> 989
COMPOUND SEMICON. "
LOW LEAKAGE - - - "
MOS - - - - - - - "

OXIDE CHARGE
ELECTRIC INSTABI.> 629
SILICON - - - - - "
SURFACE STATE - - "

OXIDE DEFECT
DIELECTRIC ISOLA.>1703
NICKEL OXIDE FILM>1883
OXIDE ISOLATION - 1703
SINGLE CRYSTAL - 1883
STAIN PROFILE - - 1703

OXIDE ELECTRODE
ALKALINE SOLUTION>1931
CATALYST LOADING "
TAFEL SLOPE - - - "
THERMAL DECOMPOS. "
TRANSFER COEFFIC. "
WATER ELECTROLYS. "

OXIDE FILM
ALKALINE SOLUTIO.> 265
ANODIC OXIDATION > 908
>1410
AUGER SPECTROSCO.>1801
BLUE TUNGSTEN - ->1344
COPPER ALLOY - ->1598
- - 1801
COPPER ELECTRODE 1598
CUPRONICKEL - - - 1801
CURRENT DECAY - ->1416
DISSOLUTION - - ->1471
ELECTROCATALYST - 265
ELECTROCHROMISM - 1344
ELECTROSTRICTION 908
ELLIPSOMETRY - - "
- - 1416
GROWTH BEHAVIOR - 1471
HYDROGEN TUNGSTEN 1344
NICKEL - - - - - 1410
- - - - - 1416
NICKEL ALLOY - - 265
- - 1801
NOBLE METAL - - - 1471
OXYGEN EVOLUTION 265

PRIMARY TERM / CO-TERM — PAGE NO.

OXIDE FILM (CONTD)
OXYGEN EVOLUTION 1416
PHOTOPOTENTIAL - 1598
REJUVENATION - - 1416
RUTHENIUM ELECTR. 1471
SEMICONDUCTOR - - 1410
TAFEL PARAMETER - 265
TAFEL SLOPE - - - 908
TITANIUM - - - - 1410
TITANIUM NICKEL - "
TUNGSTEN - - - - 908
TUNGSTEN OXIDE - 1344
WHITE LIGHT - - - 1598

OXIDE ISOLATION
BIRDS BEAK - - -> 932
DIELECTRIC ISOLA.>1703
OXIDE DEFECT - - "
OXIDE SCHEME - - 932
SILICON STRUCTURE "
STAIN PROFILE - - 1703

OXIDE LAYER
ELECTRODE ACTIVA.>1266
IRIDIUM - - - - - "
MOLTEN SALTS - - "
OXIDATION KINETI.>1180
PARABOLIC KINETI. "
POTENTIODYNAMICS 1266
STRESS - - - - - 1180
ZIRCALOY 2 - - - "

OXIDE MELTS
INTERDIFFUSIVITY > 395
LITHIUM OXIDE - - "
POLARIZATION - - "
SILICON DIOXIDE - "

OXIDE MORPHOLOGY
ELECTRON PROBE -> 279
IRON NICKEL ALLOY "
OXIDATION - - - - "

OXIDE NITRIDE
MOS STRUCTURE - ->2012
PLASMA OXIDIZED - "
REFRACTION - - - "
SILICON NITRIDE - "

OXIDE QUALITY
MINORITY CARRIER >1696
MOS STRUCTURE - - "
THERMAL OXIDATION "
TRICHLOROETHANE - "

OXIDE SCHEME
BIRDS BEAK - - -> 932
OXIDE ISOLATION - "
SILICON STRUCTURE "

OXIDE STRUCTURE
ETCHING - - - - ->1867
HYDROCHLORIC ACID "
PHASE SEPARATION "
SILICON OXIDE - - "

OXIDE THICKNESS
ALUMINUM CONTACT > 467
ETCHING - - - - - "
TITANIUM ALUMINUM "

OXIDE WALL
GATE OXIDE - - -> 432
MOS DEVICE - - - "
THINNING - - - - "

OXIDIZED SILICON
BORON DEPOSITION > 166
ORTHOBORIC ACID - "

OXYGEN
CVD - - - - - - ->1298
EDTA - - - - - ->287C
MOLYBDENUM DIMERS "
PLASMA CHEMISTRY 1298
SULFUR - - - - - 287C
TETRACHLOROSILANE 1298
TETRAFLUOROSILANE "

OXYGEN CHLORINE
CHLORINE - - - -> 339
OXYGEN WATER - - "
SILICON - - - - - "
THERMAL OXIDATION "

OXYGEN COVERAGE
BLOCKING EFFECTS > 389

PRIMARY TERM / CO-TERM — PAGE NO.

OXYGEN COVERAGE (CONTD)
ELECTRODE KINETI. 389
IRON - - - - - - "
QUINONE - - - - - "
RHODIUM ELECTRODE "

OXYGEN DETERMINA.
POLYSILICON - - ->1723
THERMAL OXIDATION "

OXYGEN DIFFUSION
OXYGEN DONOR - -> 128
SILICON PROCESSI. "
SPREADING RESIST. "

OXYGEN DONOR
OXYGEN DIFFUSION > 128
SILICON PROCESSI. "
SPREADING RESIST. "

OXYGEN ELECTRODE
OXYGEN POTENTIAL >1768
PLATINUM ALLOY - "
PLATINUM DIAPHRA. "

OXYGEN EVOLUTION
ALKALINE SOLUTIO.> 265
CURRENT DECAY - ->1416
ELECTROCATALYST - 265
ELLIPSOMETRY - - 1416
NICKEL - - - - - "
NICKEL ALLOY - - 265
OXIDE FILM - - - "
- - - 1416
REJUVENATION - - "
TAFEL PARAMETER - 265

OXYGEN POTENTIAL
OXYGEN ELECTRODE >1768
PLATINUM ALLOY - "
PLATINUM DIAPHRA. "

OXYGEN PRESSURE
CHROMIUM - - - -> 55C
DIFFUSION CHARAC. "
MAGNETITE - - - - "

OXYGEN REDUCTION
ADSORPTION - - ->1103
CATALYSIS - - - - "
CHEMISORPTION - -> 878
- ->1660
ELECTROCATALYSIS > 404
GOLD - - - - - - 1103
GRAPHITE - - - ->1003
NICKEL COBALTOXI. "
PARAMAGNETICS - - 1660
PEROVSKITE OXIDE 878
PLATINUM - - - - 404
PSEUDOSPLITTING - 1660
ROTATING DISK EL. 1103
SPINEL - - - - - 1003
TEFLON BONDED EL. 878

OXYGEN WATER
CHLORINE - - - -> 339
OXYGEN CHLORINE - "
SILICON - - - - - "
THERMAL OXIDATION "

P-HYDROXYBENZALD.
DL-MESO RATIO - -> 372
ELECTROHYDRODIME. "
LIQUID CHROMATOG. "
STEREOISOMER - - "

P-N DIODE
DOPING LEVEL - ->1648
JUNCTION LEAKAGE "
POLYSILICON - - - "

P-N JUNCTION
CZOCHRALSKI PULL.> 595
EMITTER DIP EFFE.>1170
FLOATING ZONE - - 595
IMPURITY PROFILE 1170
MULTILAYER ANALY. "
PURIFIED SILICON 595
SHEET RESISTANCE 1170
SOLAR CELL - - - 595
SPREADING RESIST. 1170
VAPOR DEPOSITION 595

P-TYPE
DOMAIN VELOCITY -> 993
PHASE MEMORY - - "
PHOTOCONDUCTOR - "

PRIMARY TERM / CO-TERM — PAGE NO.

PACEMAKER BATTER.
CALORIMETRY - - -> 842
LITHIUM - - - - - "
MERCURY - - - - - "
SILVER - - - - - "
ZINC - - - - - - "

PALLADIUM
AUGER SPECTROSCO.> 17
COPPER CORROSION "
DEPTH PROFILE - - "
DISSOLUTION RATE "
ELECTRON IMAGE -> 950
ION IMPLANTATION >1892
NOBLE METAL - - - 17
PASSIVITY - - - - "
PHOTOCATHODES - - 950
TITANIUM - - - - 1892

PARABOLIC KINETI.
OXIDATION KINETI.>1180
OXIDE LAYER - - - "
STRESS - - - - - "
ZIRCALOY 2 - - - "

PARAMAGNETICS
CHEMISORPTION - ->1660
OXYGEN REDUCTION "
PSEUDOSPLITTING - "

PARAMETRIC PUMP
CARBON ELECTRODE > 869
DESALINATION - - "
SEPARATION - - - "

PARASITIC CURREN.
ELECTRICAL ANALOG> 515
FUEL CELL ASSEMB. "
MANIFOLD MODEL - "
SHUNT CURRENTS - "

PASSIVATING LAYER
CALCIUM ANODE - ->1209
CALORIMETRY - - - "
CURRENT EFFICIEN. "
HALIDE SALTS - - "
NITRATE ELECTROL. "

PASSIVATION
ALUMINUM - - - ->1290
CHROMATE - - - - "
COPPER - - - - -> 823
CORROSION RESIST.> 420
CVD - - - - - - - 823
ELECTRODE OXIDAT.>1790
GLASSY LAYER - - 823
RELATIVE HUMIDITY 420
SILICON DIOXIDE - 823
SURFACE ROUGHNESS 420
THIN FILM - - - - 1790
TIN NICKEL ALLOY 420
TITANIUM HYDRIDE 1790
WET STORAGE STAIN 1290
ZINC - - - - - - "

PASSIVE FILM
BORATE BUFFER - ->1946
MOSSBAUER STUDY - "
POLARIZATION CUR. "
TIN OXIDE - - - - "

PASSIVITY
ANODIC FILM - - ->1735
ANODIC OXIDATION "
AUGER SPECTROSCO.> 17
COBALT - - - - - 1735
COPPER CORROSION 17
DEPTH PROFILE - - "
DISSOLUTION RATE "
NOBLE METAL - - - "
PALLADIUM - - - - "

PASTE MIXING
LEAD ACID BATTERY>1934
PLATE CURING - - "
TETRABASIC LEAD - "

PERCHLORATE ACID
ANODIC DISSOLUTI.>1989
EXCHANGE REACTION "
EXTRAPOLATION - -> 888
LEAD - - - - - - "
LEAD SYSTEM - - - 1989
POLARIZATION - - 888

PERCHLORIC ACID
ACETIC ACID - - ->1039

PRIMARY TERM / CO-TERM — PAGE NO.

PERCHLORIC ACID (CONTD)
ACETIC ACID - - ->1044
ANODIC FILM - - - 1039
ANODIC POLARIZAT. 1044
AUGER ELECTRON S. 1039
ELECTROPOLISHING "
1044
POTENTIOSTAT - - "
STOICHIOMETRY - - "

PERMALLOY
BEVELING - - - -> 860
ETCHING - - - - - "
POLARIZATION - - "
TRANSDUCER - - - "

PERMEATION ANALY.
DIFFUSION COEFFI.>2070
GRAIN BOUNDARY - "

PEROVSKITE OXIDE
CHEMISORPTION - -> 878
OXYGEN REDUCTION "
TEFLON BONDED EL. "

PEROVSKITE STRUC.
EUROPIUM - - - ->1130
LUMINESCENCE - - "
TELLURATE - - - - "

PH DEPENDENCY
CATHODIC REDUCTI.> 714
COULOMETRY - - - "
DINITROANALINE - "
MERCURY POOL - - "

PHASE ANGLE
LAPLACE ANALYSIS >1765
SKIN IMPEDANCE - "

PHASE DIAGRAM
ALUMINA - - - - -> 890
CRYSTAL STRUCTURE "
ENERGY OF FORMAT. "

PHASE EQUILIBRIUM
HETEROJUNCTION -> 123
INDIUM PHOSPHATE "
LIGHT EMITTER - - "
LPE CONDITIONS - "
QUATERNARY SYSTEM "

PHASE MEMORY
DOMAIN VELOCITY -> 993
P-TYPE - - - - - "
PHOTOCONDUCTOR - "

PHASE SEPARATION
ETCHING - - - - ->1867
HYDROCHLORIC ACID "
OXIDE STRUCTURE - "
SILICON OXIDE - - "

PHOSGENE
ANODE SYNTHESIS ->1954
CARBON MONOXIDE - "
HALIDE ELECTROLY. "
ORGANIC CARBONATE "

PHOSPHORIC ACID
ACID FUEL CELL ->1899
CARBON BLACK - ->1719
CORROSION - - - - "
- - - - 1899
CRYSTAL FACET - ->1940
CRYSTAL ORIENTAT. "
DEPASSIVATION - - "
ELECTRODEPOSITION "
ETCHING KINETICS >1510
GALLIUM ARSENIC - "
MONOHYDRATE-WATER 1899
NICKEL SUBSTRATE 1940
SULFURIC ACID - - 1899
TRIFLUOROMETHANE "

PHOSPHORS
CATHODOLUMINESCE.> 288
HALOSILICATE - -> 445
IRON ACTIVATION -> 920
LANTHANUM - - - - 445
LASERS - - - - ->415C
LITHIUM METAGALL. 920
LUMINESCENCE - - 445
- - 920
- - 415C
MODULATION TRANS.> 583
MULTIEXCITATION - 288

PRIMARY TERM / CO-TERM — PAGE NO.

PHOSPHORS (CONTD)
OUTPUT SCREEN - - 583
RARE EARTH ELEME. 445
RASTER - - - - - 288
SATURATION PROPE. "
SPATIAL NOISE - - 583
X-RAY IMAGE INTE. "
YTTRIUM - - - - - 445

PHOSPHORUS
DOPING - - - - -> 665
EMITTER DIP EFFE.> 995
OXIDATION KINETI. 665
RATE CONSTANT - - "
SILICON - - - - - "
- - - - - 995

PHOSPHORUS DIFFU.
BIPOLAR TRANSIST.> 762
DISLOCATION - - ->1840
EMITTER DIFFUSION 762
FAIR TSAI MODEL -> 323
FICKS LAW - - - ->1307
GERMANIUM - - - - "
- - - - 1840
ION IMPLANTATION 323
MISFIT DISLOCATI.> 923
SILICON - - - - - 323
- - - - - 923
- - - - - 1840
SILICON DEFECT - 762
STRAIN - - - - - 1840
VAN DER MERWE - - 923

PHOSPHORUS DOPED
GRAIN BOUNDARY -> 892
ION IMPLANTATION "
OXIDATION KINETI. "
RESISTIVITY - - - "
SILICON - - - - - "

PHOSPHORUS DOPING
GRAIN GROWTH - ->1499
ION IMPLANTATION "
RECRYSTALLIZATION "
SILICON - - - - - "

PHOSPHORUS EFFECT
CARBON TETRAFLUO.> 827
PLASMA ETCHING - "
SILICON - - - - - "

PHOTOANODE
LIQUID JUNCTION ->1156
PHOTOELECTROCHEM. "
SEMICONDUCTOR - - "

PHOTOCATHODES
ELECTRON IMAGE -> 950
PALLADIUM - - - - "

PHOTOCELL
ACETONITRILE - -> 406
CADMIUM SULFIDE - "
IODIDE ION - - - "
PHOTOELECTROCHEM.> 885
PHOTOGALVANIC - - "
SOLAR ENERGY - - 406
- - 885
THIONINE SYSTEM - "

PHOTOCONDUCTIVITY
ELECTRON AFFINITY>1750
ELECTRON TRANSPO. "
FLUORENONE DERIV. "
POLAROGRAPHY - - "
SEMICONDUCTOR - - "
VOLTAMMETRY - - - "

PHOTOCONDUCTOR
DOMAIN VELOCITY -> 993
P-TYPE - - - - - "
PHASE MEMORY - - "

PHOTOEFFECT
HYDROGEN EVOLUTI.> 223
SEMICONDUCTOR - - "
WKB APPROXIMATIO. "

PHOTOELECTROCHEM.
ALLIUM PHOSPHIDE > 68
CADMIUM SELENIDE > 375
CADMIUM SULFIDE - "
CHARGE TRANSFER ->1991
HYDROGEN EVOLUTI. "
LIQUID JUNCTION ->1156
METAL ADATOMS - - 68

PHOTOELECTROCHEM. (CONTD)
PHOTOANODE - - - 1156
PHOTOCELL - - - -> 885
PHOTOGALVANIC - - "
RATE DETERMINING 1991
SEMICONDUCTOR - - 68
- - 1156
- - 1991
SOLAR CELL - - - 375
SOLAR ENERGY - - 885
SPECTRAL RESPONSE 68
SURFACE STATE - - "
THIONINE SYSTEM - 885
TUNNELING - - - - 1991

PHOTOELECTRODE
BAND BENDING - -> 937
BUTLER VOLMER - - "
CADMIUM SELENIDE >1623
DEPLETION LAYER - 937
DIFFUSION THEORY "
ENERGY CONVERSION 1623
OVERVOLTAGE - - - 937
RECOMBINATION - - "
SULFUR SUBSTITUT. 1623
XPS - - - - - - - "

PHOTOELECTROLYSIS
ANODIC DISSOLUTI.> 117
CADMIUM SULFIDE - "
CHARGE TRANSFER - "
ELECTRON AFFINITY> 228
ELECTRONEGATIVIT. "
FLATBAND POTENTI. "
III-IV COMPOUNDS 117
REDOX SYSTEM - - "
SEMICONDUCTOR - - 228
ZETA POTENTIAL - "

PHOTOELECTRON EM.
ACTIVATION - - ->1224
AUGER SPECTROSCO. "
ELLIPSOMETRY - - "
NICKEL PLATING - "
SURFACE POTENTIAL "

PHOTOGALVANIC
IRON THIONINE - ->1365
PHOTOCELL - - - -> 885
PHOTOELECTROCHEM. "
PHOTOREDOX REACT. 1365
SOLAR ENERGY - - 885
THIONINE SYSTEM - "
TIN OXIDE - - - - 1365

PHOTOLITHOGRAPHY
ALIGNMENT GROOVE >1642
GAAS LASER - - - "
OPTICAL BENCH - - "
SILICON SUBSTRATE "

PHOTOLUMINESCENCE
EPITAXY - - - - ->1310
GALLIUM - - - - - "
INDIUM - - - - - "
INDIUM PHOSPHIDE "
TENSILE STRESS - "

PHOTOLYSIS
COPPER CORROSION >1889

PHOTOMASK
GRAPHITIZATION ->1293
INTEGRATED CIRCU. "
ION IMPLANTATION "
PHOTORESIST FILM "

PHOTOOXIDATION
ABSORPTION COEFF.> 709
ALPHA IRON OXIDE "
TITANIUM DIOXIDE "
WATER - - - - - - "

PHOTOPOTENTIAL
COPPER ALLOY - ->1598
COPPER ELECTRODE "
OXIDE FILM - - - "
WHITE LIGHT - - - "

PHOTOREDOX REACT.
IRON THIONINE - ->1365
PHOTOGALVANIC - - "
TIN OXIDE - - - - "

PHOTORESIST FILM
GRAPHITIZATION ->1293
INTEGRATED CIRCU. "

PHOTORESIST FILM (CONTD)
ION IMPLANTATION 1293
PHOTOMASK - - - - "

PHOTORESIST SYST.
BISAZIDE - - - ->1126
CROSSLINKING - - "
POLYMERIZATION - "

PHOTOSENSITIZATI.
DYE ADSORPTION -> 51
DYE SENSITIZATIO. "
FLUORESCENCE - - "
QUENCHING - - - - "
SALT ADDITION - - "
ZINC OXIDE - - - "

PHOTOTHERMAL
ALUMINUM OXIDE ->1138
METAL REFLECTOR - "
MOLYBDENUM FILM - "
SILICON NITRIDE - "

PHOTOVOLTAIC CELL
CELL FABRICATION >1328
ELECTRON AFFINITY "
INDIUM OXIDE - - "

PIN DIODE
DEEP DIFFUSION -> 680
PLASMA PASSIVATI. "

PITTING
ALUMINUM ALLOY -> 731
ALUMINUM IRON - -> 438
ALUMINUM STRAINI.>1594
ANION EFFECT - - 731
ANODIC FILM - - - 438
AUGER ANALYSIS ->1204
CHROMIUM - - - - "
FILM GROWTH - - - 438
HALIDE EFFECT - - 731
LOCALIZED CORROS. 1594
MOLYBDENUM - - - 1204
SEM - - - - - - - 1594
SLIP STEPS - - - "
STAINLESS STEEL - 1204

PITTING POTENTIAL
ANODIC POLARIZAT.> 366
> 370
ION IMPLANTATION 366
370
IRON CHROMIUM - - 366
IRON NICKEL - - - 370
SURFACE ALLOY - - 366
- - 370

PLASMA ANODIZATI.
ANODE - - - - - -> 44
AUGER SPECTROSCO. "
CATHODE - - - - - "
MASS TRANSFER - - "
METAL OXIDE FILM "

PLASMA CHEMISTRY
CVD - - - - - - - ->1298
OXYGEN - - - - - "
TETRACHLOROSILANE "
TETRAFLUOROSILANE "

PLASMA ETCHING
ALUMINUM - - - - -> 629
CARBON TETRACHLO. "
CARBON TETRAFLUO.> 827
OPTICAL EMISSION 829
PHOSPHORUS EFFECT 827
SILICON - - - - - "

PLASMA NITRIDE
OPTICAL ABSORPTI.> 99
PLASMA POLYMERIZ. "
PLASMA SILICON - "
THIN FILM - - - - "

PLASMA OXIDATION
AUGER SPECTROSCO.> 481
DEPTH PROFILE - - "
GAAS - - - - - - "
NEUTRON ACTIVATI. "

PLASMA OXIDIZED
MOS STRUCTURE - ->2012
OXIDE NITRIDE - - "
REFRACTION - - - "
SILICON NITRIDE - "

PLASMA PASSIVATI.
DEEP DIFFUSION -> 680
PIN DIODE - - - - "

PLASMA POLYMERIZ.
OPTICAL ABSORPTI.> 99
PLASMA NITRIDE - "
PLASMA SILICON - "
THIN FILM - - - - "

PLASMA SILICON
OPTICAL ABSORPTI.> 99
PLASMA NITRIDE - "
PLASMA POLYMERIZ. "
THIN FILM - - - - "

PLATE CURING
LEAD ACID BATTERY>1934
PASTE MIXING - - "
TETRABASIC LEAD - "

PLATING CELL
AGITATION EFFECT > 36
BRIGHTENER - - - "
COPPER - - - - - "
MORPHOLOGY - - - "
PRINTED WIRING - "
THROWING POWER - "

PLATINUM
AUGER - - - - - -> 348
BACKSCATTERING ->1854
CHROMIUM - - - - "
ELECTROCATALYSIS > 404
ELECTROSORPTION - 348
EQUILIBRIUM DIAG. 1854
FLUORINE - - - -> 498
GASIFICATION - - "
HYDROGEN ADSORPT. 348
IRIDIUM - - - - - 498
LEED - - - - - - - 348
ORDERING TRANSFO. 1854
OXYGEN REDUCTION 404
SINGLE CRYSTAL - 348
TANTALUM - - - - 498
TEMPERATURE KINE. "

PLATINUM ALLOY
OXYGEN ELECTRODE >1768
OXYGEN POTENTIAL "
PLATINUM DIAPHRA. "

PLATINUM DIAPHRA.
OXYGEN ELECTRODE >1768
OXYGEN POTENTIAL "
PLATINUM ALLOY - "

PLATINUM ELECTRO.
ANODIC POLARIZAT.>1262
CATHODIC POLARIZ.>1257
LITHIUM CHLORATE "
1262
LITHIUM HYDROXIDE 1257
ORGANIC FILM - - 1262
TETRAHYDROFURAN - 1257
- 1262
XPS - - - - - - - 1257
- - - - - - - 1262

POINT TO POINT
AMMONIA - - - - -> 487
COPYROLYSIS - - - "
CVD - - - - - - - "
SILANE - - - - - "
SILICON NITRIDE - "
THERMOCOUPLE ANA. "

POLARIZABILITY
ANODIC OXIDE FILM> 23
ELECTROCHROMISM - "
ELLIPSOMETRY - - "
HYDROGEN - - - - "
IMPEDANCE - - - - "
NIOBIUM - - - - - "
TITANIUM - - - - "

POLARIZATION
ALUMINA - - - - ->1796
ALUMINUM ALLOY ->1586
BEVELING - - - -> 860
CALCIUM FLUORIDE > 755
CAPACITY LOSS - ->1587
CONDUCTIVITY - - 755
CORROSION - - - - 1587
DIFFUSION LAYER -> 845
ELECTRET - - - -> 409
ETCHING - - - - - 860

PRIMARY TERM / CO-TERM	PAGE NO.
POLARIZATION (CONTD)	
EXTRAPOLATION - ->	888
FUSED SALTS - - -	1796
INTERDIFFUSIVITY >	395
LEAD - - - - - -	888
LIMITING CURRENT	845
LITHIUM - - - - -	"
LITHIUM ALLOY - -	1886
LITHIUM HYDROXIDE	845
LITHIUM OXIDE - -	395
MAGNESIUM ALLOY -	1886
MASS TRANSPORT -	755
OXIDE MELTS - - -	395
PERCHLORATE ACID	888
PERMALLOY - - - -	860
POLYELECTROLYTE -	409
REFERENCE ELECTR.	1796
SILICON DIOXIDE -	395
SODIUM SULFUR - -	1587
SOLID ELECTROLYTE	755
STAINLESS STEEL -	1587
TRANSDUCER - - -	860
POLARIZATION CUR.	
BORATE BUFFER - ->	1946
MOSSBAUER STUDY -	"
PASSIVE FILM - -	"
TIN OXIDE - - - -	"
POLARIZATION DATA	
CORROSION RATES ->	1988
TAFEL SLOPE - - -	"
POLAROGRAPHICS	
KINETIC PARAMETE.>	284C
OVERPOTENTIAL - -	"
POLAROGRAPHY	
ADRIAMYCIN - - ->	534
ANTHRACYCLINE - -	"
ANTITUMOR ANTIBI.	"
CHRONOPOTENTIOME.	"
COULOMETRY - - ->	1250
CYCLIC VOLTAMMET.	534, 1250
DAUNORUBICIN - -	534
ELECTRON AFFINITY>	1750
ELECTRON TRANSPO.	"
FERRIHEME - - - -	1250
FLUORENONE DERIV.	1750
MARCUS THEORY - -	1250
PHOTOCONDUCTIVITY	1750
SEMICONDUCTOR - -	"
VOLTAMMETRY - - -	"
POLISHING	
COLLOIDAL SILICA >	136
NONABRASION - - -	"
SAPPHIRE - - - -	"
POLLUTANTS	
ACCELERATED TEST >	2002
CORROSION TEST -	"
ENVIRONMENT TEST >	1487
HUMIDITY - - - -	2002
KINETIC RATE - -	"
SYSTEM RELIABILI.	1487
POLYCRYSTAL COPP.	
ANODIC OXIDATION >	1960
COPPER AMALGAM -	"
LITHIUM HYDROXIDE	"
NUCLEATION - - -	"
POLYELECTROLYTE	
ELECTRET - - - ->	409
POLARIZATION - -	"
POLYMERIC ELECTR.	
FERRI-FERROCYANI.>	232
LEAD DEPOSITION -	"
POLYTHIAZYL - - -	"
SULFUR NITRIDE -	"
POLYMERIZATION	
BISAZIDE - - - ->	1126
CELLULOSE - - - ->	833
CROSSLINKING - -	1126
HYDROLYSIS - - -	833
LEAD ACID BATTERY	"
PHOTORESIST SYST.	1126
SEPARATOR - - - -	833
POLYSILICON	
ALUMINUM METALLI.>	169
DOPING LEVEL - ->	1648
INTEGRATED CIRCU.	169
POLYSILICON (CONTD)	
JUNCTION LEAKAGE	1648
OHMIC CONTACT - -	169
OXYGEN DETERMINA.>	1723
P-N DIODE - - - -	1648
THERMAL OXIDATION	1723
POLYSILICON TUBE.	
ALKALI CONTAMINA.>	106
CLEAN FILM - - -	"
MICRODELECTRONICS	"
MOS STRUCTURE - -	"
SILICON DIOXIDE -	"
POLYSULFIDES	
FUSED SALTS - - ->	1605
SULFUR - - - - -	"
TRANSPORT PROPER.	"
WETTABILITY - - -	"
POLYTHIAZYL	
FERRI-FERROCYANI.>	232
LEAD DEPOSITION -	"
POLYMERIC ELECTR.	"
SULFUR NITRIDE -	"
POROUS ELECTRODE	
COPPER DEPOSITION>	58
CURRENT DISTRIBU.	"
ELECTRODE CONFIG.	"
MASS TRANSFER - -	"
MATRIX CONDUCTIV.	"
POTENTIAL DISTRI.	"
SILVER DEPOSITIO.	"
POROUS SILICON	
FILM STRUCTURE ->	1339
HEAT TREATMENT -	"
PORTABLE HEATER	
ALUMINUM ALLOY ->	1924
CORROSION - - - -	"
MAGNESIUM ANODE -	"
MANGANESE DIOXIDE	"
SALINE CELL - - -	"
POTASSIUM	
BETA ALUMINA - ->	1007
CALCIUM - - - - -	"
CERAMIC - - - - -	"
ENERGY STORAGE -	"
IRON - - - - - -	"
POTASSIUM CHLORI.	
ACTIVITY COEFFIC.>	692
DIFFUSION - - - ->	1193
DOPED ALKALI HAL.>	430
FUSED SALTS - - -	692
LITHIUM BATTERY -	1193
LITHIUM CHLORIDE	"
MIGRATION PROCESS	"
MOLTEN SALT - - -	"
QUENCHED CRYSTALS	430
SILVER CHLORIDE -	692
SODIUM CHLORIDE -	430
THERMAL DEPOLARI.	"
POTASSIUM HYDROX.	
ALUMINUM - - - ->	1000
ALUMINUM CHLORID.	"
CATALYSIS - - - -	"
CATION EXCHANGE ->	556
CURRENT DENSITY ->	1591
DIFFUSION COEFFI.	556
EQUILIBRIUM POTE.	1591
IONIC STRENGTH -	"
MOLTEN SALT - - -	1000
TRANSFERENCE - -	556
TRANSPORT PARAME.	"
ZINC ELECTRODE -	1591
POTENTIAL DECAY	
CORROSION RATE ->	1389
COULOSTATIC METH.	"
HIGH IMPEDANCE -	"
STEEL - - - - - -	"
POTENTIAL DISTRI.	
COPPER DEPOSITION>	58
CURRENT DISTRIBU.	" >1981
ELECTRODE CONFIG.	58
ELECTRODEPOSITION	1981
FINITE ELEMENT -	"
MASS TRANSFER - -	58
MATHEMATICAL MOD.	1981
MATRIX CONDUCTIV.	58
POTENTIAL DISTRI. (CONTD)	
POROUS ELECTRODE	58
SHAPE CHANGE - -	1981
SILVER DEPOSITIO.	58
POTENTIAL RELAXA.	
CAPACITANCE - - ->	380
COULOSTATIC DEPO.	" > 384
DOUBLE LAYER - -	380
GOLD - - - - - -	384
MERCURY - - - - -	"
UNDERPOTENTIAL -	380, - 384
POTENTIODYNAMICS	
ELECTRODE ACTIVA.>	1266
IRIDIUM - - - - -	"
MOLTEN SALTS - -	"
OXIDE LAYER - - -	"
POTENTIOSTAT	
ACETIC ACID - - ->	1044
ANODIC POLARIZAT.	"
ELECTROPOLISHING	"
PERCHLORIC ACID -	"
STOICHIOMETRY - -	"
POTENTIOSTATIC	
ELECTROCHROMISM ->	284
GALVANOSTATIC - -	"
LITHIUM TUNGSTEN.	"
POURBAIX DIAGRAM	
CADMIUM TELLURIDE>	566
CATHODIC DEPOSIT.	"
POWDER PHOSPHOR	
CATHODOLUMINESCE.>	102
COPRECIPITATION -	"
EUROPIUM - - - -	"
LOW ENERGY ELECT.	"
TIN DIOXIDE - - -	"
PRECIPITATES	
DEFECT STRUCTURE >	1355
GALLIUM - - - - -	"
HALL EFFECT - - -	"
RESISTIVITY - - -	"
ZINC SELENIDE - -	"
PREDEPOSITION	
BORON TRIBROMIDE >	609
DIODE - - - - - ->	1505
DOPING - - - - -	609
GAAS - - - - - -	1505
ION IMPLANTATION	"
SEMICONDUCTOR - -	"
SILICON - - - - -	609
ZINC - - - - - -	1505
PREEXPONENTIALS	
PROCESS CONTROL ->	1514
SILICON - - - - -	"
STEAM OXIDATION -	"
PRESSURE EFFECT	
ACTIVATION PROCE.>	257
CONDENSED PHASE ->	252
HYDROGEN EVOLUTI.	"
IONIC CONDUCTANC.	"
IONIC EQUILIBRIA	"
REDOX REACTION -	257
SOLVENT REORGANI.	"
PRIMARY BATTERY	
CARDIAC PACEMAKER>	1907
LECLANCHE CELL ->	271C
LITHIUM BATTERY -	"
LOAD DEPENDENT -	1907
MICROCALORIMETER	"
SELF DISCHARGE -	"
ZINC AIR CELL - -	271C
PRIMARY CURRENT	
CURRENT DISTRIBU.>	79
MASS TRANSFER - -	"
PRIMARY RESISTAN.	"
RING ELECTRODE -	"
SECONDARY CURRENT	"
PRIMARY RESISTAN.	
CURRENT DISTRIBU.>	79
MASS TRANSFER - -	"
PRIMARY CURRENT -	"
RING ELECTRODE -	"
SECONDARY CURRENT	"
PRINTED WIRING	
AGITATION EFFECT >	36
BRIGHTENER - - -	"
COPPER - - - - -	"
MORPHOLOGY - - -	"
PLATING CELL - -	"
THROWING POWER -	"
PROCESS CONTROL	
CROSS BRIDGE STR.>	650
DIFFUSED LAYER -	"
LINE WIDTH - - -	"
PREEXPONENTIALS ->	1514
SHEET RESISTANCE	650
SILICON - - - - -	1514
STEAM OXIDATION -	"
VAN DER PAUW - -	650
PRODUCT CHANGES	
AUTOMOTIVE BATTE.>	311C
SECONDARY BATTE.	"
PROPANE GAS	
DOPING - - - - ->	1676
SENSOR - - - - -	"
TIN OXIDE - - - -	"
TRANSITION METALS	"
PROPYLENE CARBON.	
LITHIUM BATTERY ->	186
LITHIUM CYCLING -	" ->1990
LITHIUM ELECTRODE	186
LITHIUM SUBSTRATE	1990
PROTON DAMAGE	
ELECTROABSORPTION>	776
ELECTROREFLECTAN.	"
GAAS - - - - - -	"
ION IMPLANTATION	"
PROTON TRANSFER	
CHARGE DELOCALIZ.>	1992
HYDROGEN EVOLUTI.	"
PRUSSIAN BLUE	
OXIDATION - - - ->	886
REDUCTION - - - -	"
THIN FILM - - - -	"
PSEUDOBINARY ALL.	
BRIDGMAN APPROACH>	315
CADMIUM TELLURIDE	"
INFRARED MATERIAL	"
MERCURY TELLURIDE	"
SINGLE CRYSTAL -	"
PSEUDOINDUCTANCE	
CHROMIUM - - - ->	2062
CORROSION - - - ->	1977, - - - - 2062
CYCLIC VOLTAMMET.	1977
ELECTRODE KINETI.	2062
ELECTRODE KINETIC	1977
IMPEDANCE PARAME.	2062
LINEAR POLARIZAT.	1977
SULFURIC ACID - -	2062
PSEUDOSPLITTING	
CHEMISORPTION - ->	1660
OXYGEN REDUCTION	"
PARAMAGNETICS - -	"
PT-DISK ELECTROD.	
CIRCUIT BOARD - ->	1218
COPPER PYROPHOSP.	"
DIMERCAPTOTHIADI.	"
ELECTROPLATING -	"
FOLDBACK - - - -	"
LEVELING MECHAN.	"
PULSE	
D-C RESPONSE - ->	985
HYDROCHLORIC ACID	"
MNOS TRANSISTOR -	"
PULSE GENERATOR	
CHRONOPOTENTIOME.>	1809
ELECTRODE KINETI.	"
FINITE RISE TIME	"
RELAXATION - - -	"
PULSE MEASUREMENT	
CONTACT RESISTAN.>	508
INTERFACE - - - -	"

PRIMARY TERM / CO-TERM — PAGE NO.

PULSED ELECTROLY. — 1772
DIFFUSION LAYER — 1772
FERRI-FERROCYANI. — 1616
FIRST ORDER REAC. — "
MASS TRANSFER — 1772
ROTATING DISK EL. — 1616, 1772

PULSIVE NOISE
BIPOLAR DEVICE — 1829
CONDUCTIVE FILM — "
ION IMPLANTATION — "

PURIFICATION
CZOCHRALSKI CRYS. — 661
DIFFUSION LENGTH — "
DUMMYING — 204
ELECTROLYSIS — "
HALL MOBILITY — 661
NICKEL PLATING — 204
SILICON — 661
SOLIDIFICATION — "

PURIFIED SILICON
CZOCHRALSKI PULL. — 595
FLOATING ZONE — "
P-N JUNCTION — "
SOLAR CELL — "
VAPOR DEPOSITION — "

PURINES
ADSORPTION — 1236
MERCURY ELECTROD. — "
MOLECULAR AREA — "
PYRIMIDINES — "
RIBOSE — "

PVC
ACTIVATION ENERGY — 434
DEPOLARIZATION — "
INITIAL RISE — "
THERMOELECTRET — "

PVOF FILMS
ELECTROLESS PLAT. — 522
GOLD METALLIZATI. — "

PYRIMIDINES
ADSORPTION — 1236
MERCURY ELECTROD. — "
MOLECULAR AREA — "
PURINES — "
RIBOSE — "

PYROGENIC SYSTEM
SILICON — 576
THERMAL OXIDATION — "

PYROLYSIS
GROWTH PARAMETERS — 294
SILANE COMPOUND — "
SILICON CARBIDE — "
VAN ARKEL PROCESS — "

QUALITY CONTROL
ALUMINUM OXIDE — 299
KRAMERS-KRONIG — "
OPTICAL REFLECTA. — "
SAPPHIRE — "

QUANTUM YIELD
BROAD BAND EMITT. — 2015
CANDOLUMINESCENCE — "
HYDROGEN ION BEAM — "
ION EXCHANGE — "
LINE EMITTER — "

QUASI REST POTEN.
ALLOY DEPOSITION — 2028
AQUEOUS ELECTROL. — "
BINARY ALLOY — "
CATHODIC DEPOSIT. — "

QUATERNARY CRYST.
LPE — 1053
MISCIBILITY GAP — "
STRAIN EFFECT — "

QUATERNARY SYSTEM
HETEROJUNCTION — 123
INDIUM PHOSPHATE — "
LIGHT EMITTER — "
LPE CONDITIONS — "
PHASE EQUILIBRIUM — "

QUENCHED CRYSTALS
DOPED ALKALI HAL. — 430

QUENCHED CRYSTALS (CONTD)
POTASSIUM CHLORI. — 430
SODIUM CHLORIDE — "
THERMAL DEPOLARI. — "

QUENCHING
DYE ADSORPTION — 51
DYE SENSITIZATIO. — "
FLUORESCENCE — "
PHOTOSENSITIZATI. — "
SALT ADDITION — "
ZINC OXIDE — "

QUINONE
ANTITUMOR ANTIBI. — 540
BLOCKING EFFECTS — 389
CYCLIC VOLTAMMET. — 540
DAUNOMYCINONE — "
ELECTRODE KINETI. — 389
IRON — "
OXYGEN COVERAGE — "
RHODIUM ELECTRODE — "

RADIATION DAMAGE
ANNEALING — 676
DIFFUSION LENGTH — 2034
ELECTRON IRRADIA. — 676
GAAS — "
— 1726
— 2034
MODELING — "
SOLAR CELL — 1726
— 2034
SURFACE RECOMBIN. — "

RADICAL CATION
DIMETHYL SULFITE — 687
GRAPHITE — "
LITHIUM PERCHLOR. — "

RARE EARTH ELEME.
HALOSILICATE — 445
LANTHANUM — "
LUMINESCENCE — "
PHOSPHORS — "
YTTRIUM — "

RASTER
CATHODOLUMINESCE. — 288
MULTIEXCITATION — "
PHOSPHORS — "
SATURATION PROPE. — "

RATE CONSTANT
DOPING — 665
OXIDATION KINETI. — "
PHOSPHORUS — "
SILICON — "

RATE DETERMINING
CHARGE TRANSFER — 1991
HYDROGEN EVOLUTI. — "
PHOTOELECTROCHEM. — "
SEMICONDUCTOR — "
TUNNELING — "

REACTION KINETICS
ALKALINE CYANIDE — 1436
ANODIC DISSOLUTI. — "
GOLD — "
HELIUM — 1636
REACTION MECHANI. — 1436
SULFUR DIOXIDE — 1636
TUNGSTEN — "

REACTION MECHANI.
ALKALINE CYANIDE — 1436
ANODIC DISSOLUTI. — "
CVD — 1534
GOLD — 1436
REACTION KINETICS — "
TELLURIUM — 1784
TETRACHLOROALUMI. — "
TUNGSTEN DEPOSIT. — 1534
TUNGSTEN HEXAFLU. — "
VOLTAMMETRY — 1784

REACTION ZONE
CHEMILUMINESCENCE — 1079
DIFFUSION — "
TRIPLET LIFETIME — "

REACTIVE PLASMA
CVD — 601
INTEGRATED CIRCU. — "
MOS LSI PASSIVAT. — "
SILICON NITRIDE — "

REACTIVITY
ELECTROLYSIS — 2180
EXCITED STATE — "
SEMICONDUCTOR — "

RECHARGEABILITY
CARBON MATRIX — 705
SODIUM-SULFUR CE. — "
SURFACE PROPERTY — "

RECOMBINATION
BAND BENDING — 937
BUTLER VOLMER — "
DEPLETION LAYER — "
DIFFUSION THEORY — "
OVERVOLTAGE — "
PHOTOELECTRODE — "

RECRYSTALLIZATION
ARSENIC — 461
CRYSTAL ORIENTAT. — "
ELECTRICAL ACTIV. — "
EPITAXIAL REGROW. — "
GRAIN GROWTH — 1499
ION IMPLANTATION — "
PHOSPHORUS DOPING — "
SILICON — 461
— 1499

RECTANGULAR CELL
BAFFLE — 84
CURRENT DISTRIBU. — "
FLAT STRIP ELECT. — "

REDISTRIBUTION
ARSENIC — 1518
ION IMPLANTATION — "
SPREADING RESIST. — "

REDOX REACTION
ACTIVATION PROCE. — 257
PRESSURE EFFECT — "
SEMICONDUCTOR — 1759
SOLVENT REORGANI. — 257
TIN OXIDE ELECTR. — 1759

REDOX SYSTEM
ANODIC DISSOLUTI. — 117
CADMIUM SULFIDE — "
CHARGE TRANSFER — "
III-IV COMPOUNDS — "
PHOTOELECTROLYSIS — "

REDUCED PRESSURE
AUTODOPING — 637
GROWTH KINETICS — "
SILICON GROWTH — "

REDUCTION
OXIDATION — 886
PRUSSIAN BLUE — "
THIN FILM — "

REFERENCE ELECTR.
ALUMINA — 1796
FUSED SALTS — "
POLARIZATION — "

REFLECTANCE SPEC.
CATHODOCHROMISM — 1133
EMISSION SPECTRA — "
F CENTERS — "
GERMANIUM DOPED — "
SODALITE — "

REFRACTION
MOS STRUCTURE — 2012
OXIDE NITRIDE — "
PLASMA OXIDIZED — "
SILICON NITRIDE — "

REFRACTIVE INDEX
ELLIPSOMETRY — 968
SILICON OXIDE — "
TEMPERATURE DEPE. — "

REJUVENATION
CURRENT DECAY — 1416
ELLIPSOMETRY — "
NICKEL — "
OXIDE FILM — "
OXYGEN EVOLUTION — "

RELATIVE HUMIDITY
COPPER — 1114
CORROSION RESIST. — 420
DELIQUESCENCE — 734

RELATIVE HUMIDITY (CONTD)
GRAVIMETRIC ANAL. — 734
HYGROSCOPICITY — "
NITROGEN OXIDE — 1114
PASSIVATION — 420
SURFACE ROUGHNESS — "
TIN NICKEL ALLOY — "

RELAXATION
CHRONOPOTENTIOME. — 1809
ELECTRODE KINETI. — "
FINITE RISE TIME — "
PULSE GENERATOR — "

REPASSIVATION
CORROSION — 1729
DISSOLUTION — "
ELECTRON TRANSFER — "
IRON — 1382
MATHEMATICAL MOD. — "
METAL SURFACE — "
SALT FILM — "
STAINLESS STEEL — 1729
TITANIUM — 1382

RESISTIVE-CAPACI.
CYCLIC VOLTAMMET. — 1443
EQUIVALENT CIRCU. — "
HYSTERESIS — "
IMPEDANCE — "
LINEAR POLARIZAT. — "
TRANSFORM ANALYS. — "

RESISTIVITY
BATTERY SEPARATOR — 520
CAPACITANCE — "
DEFECT STRUCTURE — 1355
GALLIUM — "
GRAIN BOUNDARY — 892
HALL EFFECT — 1355
ION IMPLANTATION — 892
LOW IMPEDENCE — 520
OXIDATION KINETI. — 892
PHOSPHORUS DOPED — "
PRECIPITATES — 1355
SILICON — 892
WHEATSTONE BRIDGE — 520
ZINC SELENIDE — 1355

RESISTIVITY DECAY
FREE SURFACES — 2037
GOLD FILM — "
VACANCY DIFFUSION — "
VOID GROWTH — "

REST POTENTIAL
BORON — 678
LEAD SULFIDE — "
SEMICONDUCTANCE — "

RHEED
COPPER SULFIDE — 882
EPITAXIAL LAYERS — "
LIQUID SOLUTION — "
METHANOL — "

RHENIUM
FLUORINE — 162
MASS SPECTROMETRY — "
TANTALUM FLUORIDE — "
TUNGSTEN — "

RHODIUM ELECTRODE
BLOCKING EFFECTS — 389
ELECTRODE KINETI. — "
IRON — "
OXYGEN COVERAGE — "
QUINONE — "

RIBOSE
ADSORPTION — 1236
MERCURY ELECTROD. — "
MOLECULAR AREA — "
PURINES — "
PYRIMIDINES — "

RING DISK ELECTR.
GOLD — 1098
MERCURY — "
UNDERPOTENTIAL — "

RING ELECTRODE
CURRENT DISTRIBU. — 79
MASS TRANSFER — "
PRIMARY CURRENT — "
PRIMARY RESISTAN. — "
SECONDARY CURRENT — "

PRIMARY TERM
CO-TERM — PAGE NO.

ROTATING DISK EL.
ADSORPTION - - -> 1103
CATALYSIS - - - - "
DIFFUSION LAYER -> 1772
FERRI-FERROCYANI. > 1616
FIRST ORDER REAC. "
GOLD - - - - - - 1103
MASS TRANSFER - - 1772
OXYGEN REDUCTION 1103
PULSED ELECTROLY. 1616
1772

ROTATING ELECTRO.
CHEMISORPTION - -> 544
HYDROGEN SULFIDE "
MASS TRANSPORT - "

ROTATING HEMISPH.
CHLORINE BATTERY > 89
DIFFUSION COEFFI. "
MASS TRANSFER - - "
ZINC BATTERY - - "
ZINC HEMISPHERE - "

RUBIDIUM OXIDE
CHLORINE EVOLUTI. > 1093
SURFACE ANALYSIS "
X-RAY PHOTOELECT. "

RUTHENIUM DIOXID.
CATALYTIC WAVES -> 1069
COULOMETRY - - - "
CYCLIC VOLTAMMET. "
RUTHENIUM OXIDE - "

RUTHENIUM ELECTR.
DISSOLUTION - - -> 1471
GROWTH BEHAVIOR - "
NOBLE METAL - - - "
OXIDE FILM - - - "

RUTHENIUM OXIDE
CATALYTIC WAVES -> 1069
CORROSION - - - -> 1482
COULOMETRY - - - 1069
CYCLIC VOLTAMMET. "
ELECTROCATALYST - 1482
ELECTRON MICROSC. "
ION EXCHANGE - - "
RUTHENIUM DIOXID. 1069
SOLID POLYMER - - 1482

RUTHERFORD
BACKSCATTERING -> 1215
DEPTH PROFILE - - "
MASS SPECTROMETRY "
NICKEL - - - - - "
TIN - - - - - - - "

RUTHERFORD BACKS.
ALUMINUM - - - - -> 915
ANODIC OXIDATION > 1549
ANODIC OXIDE - - 915
COPPER - - - - - "
DEPTH PROFILING - "
NIOBIUM - - - - - 1549
NUCLEAR MICROANA. "
TANTALUM - - - - "
TRANSPORT MECHAN. "

SALINE CELL
ALUMINUM ALLOY -> 1924
CORROSION - - - - "
MAGNESIUM ANODE - "
MANGANESE DIOXIDE "
PORTABLE HEATER - "

SALT ADDITION
DYE ADSORPTION -> 51
DYE SENSITIZATIO. "
FLUORESCENCE - - "
PHOTOSENSITIZATI. "
QUENCHING - - - - "
ZINC OXIDE - - - "

SALT DEPOSITS
HOT CORROSION - -> 411
SODIUM CHLORIDE - "
SODIUM SULFATE - "
SULFUR DIOXIDE - "

SALT FILM
IRON - - - - - - -> 1382
MATHEMATICAL MOD. "
METAL SURFACE - - "
REPASSIVATION - - "
TITANIUM - - - - "

SAPPHIRE
ALUMINUM OXIDE -> 299
COLLOIDAL SILICA > 136
CRYSTALLINE PERF. > 792
FET MOBILITY - - "
KRAMERS-KRONIG - 299
MOS TRANSISTOR - 792
NONABRASION - - - 136
OPTICAL REFLECTA. 299
POLISHING - - - - 136
QUALITY CONTROL - 299
SILICON - - - - - 792
X-RAY DIFFRACTOM. "

SATURATION PROPE.
CATHODOLUMINESCE. > 288
MULTIEXCITATION - "
PHOSPHORS - - - - "
RASTER - - - - - "

SECONDARY BATTE.
AUTOMOTIVE BATTE. > 311C
PRODUCT CHANGES - "

SECONDARY CURRENT
CURRENT DISTRIBU. > 79
MASS TRANSFER - - "
PRIMARY CURRENT - "
PRIMARY RESISTAN. "
RING ELECTRODE - "

SEGREGATION
BORON - - - - - -> 813
- - - - - ->2050
DIFFUSION - - - - "
DIFFUSIVITY - - - 813
ION IMPLANTATION 2050
OXIDATION - - - - "
SILICON - - - - - 813
SILICON OXIDE - - 2050

SELECTIVE COATING
DURABILITY - - ->1361
EMISSIVITY - - - "
SOLAR COLLECTOR - "
ZINC OXIDE - - - "

SELECTIVE OXIDAT.
MOS LSI PROCESS -> 1624
SILICON NITRIDE - "
SILICON OXIDATION "
STEAM - - - - - - "

SELENIUM
ACIDITY DEPENDEN. > 1454
CONTACTLESS MOBI. > 1318
FUSED SALTS - - - 1454
GAAS SUBSTRATE - 1318
MELTS - - - - - - 1454
SEMICONDUCTOR - - 1318
SULFUR - - - - - "
TETRACHLOROALUMI. 1454

SELF ALIGNMENT
GRATE REDUCTION -> 471
INTEGRATED CIRCU. "

SELF DIFFUSION
ACTIVITY COEFFIC. > 1689
ALUMINUM - - - ->1348
ARSENIC - - - - - "
CRYSTALLOGRAPHY - 1689
HALL EFFECT - - - 1348
SINGLE CRYSTAL - "
SODIUM GALLATE - 1689
SODIUM MIGRATION "
ZINC SELENIDE - - 1348

SELF DISCHARGE
CARDIAC PACEMAKER > 1907
LOAD DEPENDENT - "
MICROCALORIMETER "
PRIMARY BATTERY - "

SEM
ALUMINUM STRAINI. > 1594
LOCALIZED CORROS. "
PITTING - - - - - "
SLIP STEPS - - - "

SEMICONDUCTANCE
BORON - - - - - -> 678
LEAD SULFIDE - - "
REST POTENTIAL - "

SEMICONDUCTOR
ALLIUM PHOSPHIDE > 68

SEMICONDUCTOR (CONTD)
ANODIC OXIDATION > 1410
AQUEOUS ELECTROL. > 1185
AQUEOUS SOLUTION > 246
BISMUTH TRITELLU. > 2042
CHARGE TRANSFER -> 1991
CHEMILUMINESCENCE > 1423
CONTACTLESS MOBI. > 1318
CURRENT RISE - - 1185
DIODE - - - - - -> 1505
ELECTROLYSIS - -> 218C
ELECTRON AFFINITY > 228
>1750
ELECTRON TRANSFER 1423
ELECTRON TRANSPO. 1750
ELECTRONEGATIVIT. 228
EPITAXY - - - - - 2042
EXCITED STATE - - 218C
EXCITED STATES - 1423
FLATBAND POTENTI. 228
FLUORENONE DERIV. 1750
FUSED QUARTZ - ->1188
GAAS - - - - - - 1505
GAAS ELECTRODE - 1185
GAAS SUBSTRATE - 1318
HYDROGEN EVOLUTI. > 223
>1992
1991
IMPURITY DOPANT - 2042
ION IMPLANTATION 1505
LIQUID JUNCTION -> 1156
LUMINESCENCE - - 246
MERCURY - - - - ->1881
METAL ADATOMS - - 68
MOLECULAR BEAM - 2042
NICKEL - - - - - 1410
NONSTOICHIOMETRY 2042
OXIDE FILM - - - 1410
PHOTOANODE - - - 1156
PHOTOCONDUCTIVITY 1750
PHOTOEFFECT - - - 223
PHOTOELECTROCHEM. 68
1156
1991
PHOTOELECTROLYSIS 228
POLAROGRAPHY - - 1750
PREDEPOSITION - - 1505
RATE DETERMINING 1991
REACTIVITY - - - 218C
REDOX REACTION ->1759
SELENIUM - - - - 1318
SILICON DIOXIDE - 1188
SODIUM DIFFUSION "
SPECTRAL RESPONSE 68
SULFUR - - - - - 1318
SURFACE STATE - - 68
- - 246
THALLIUM - - - - 2042
TIN OXIDE ELECTR. 1759
TITANIUM - - - - 1410
TITANIUM DIOXIDE 246
TITANIUM NICKEL - 1410
TUNNELING - - - - 1991
VAPOR PRESSURE - 2042
VOLTAMMETRY - - - 1750
WKB APPROXIMATIO. 223
WORK FUNCTION - - 1881
ZETA POTENTIAL - 228
ZINC - - - - - - 1505

SEMIINSULATING
BUFFER LAYER - ->2058
CHROMIUM - - - - "
FET - - - - - - - "
GAAS - - - - - - "
LPE - - - - - - - "

SENSOR
DOPING - - - - ->1676
PROPANE GAS - - - "
TIN OXIDE - - - - "
TRANSITION METALS "

SEPARATION
CARBON ELECTRODE > 869
DESALINATION - - "
PARAMETRIC PUMP - "

SEPARATOR
CELLULOSE - - - -> 833
HYDROLYSIS - - - "
LEAD ACID BATTERY "
POLYMERIZATION - "

SHAPE CHANGE
CURRENT DISTRIBU. > 1981
ELECTRODEPOSITION "

SHAPE CHANGE (CONTD)
FINITE ELEMENT - 1981
MATHEMATICAL MOD. "
POTENTIAL DISTRI. "

SHEET ELECTRODE
BOUNDARY LAYER -> 865
ELECTRODEPOSITION "
MASS TRANSPORT - "
TRANSIENTS - - - "

SHEET RESISTANCE
CROSS BRIDGE STR. > 650
CROSS STRUCTURE -> 645
DIFFUSED LAYER - "
- 650
EMITTER DIP EFFE. > 1170
IMPURITY PROFILE "
LEAKAGE CURRENT - 645
LINE WIDTH - - - 650
MULTILAYER ANALY. 1170
P-N JUNCTION - - "
PROCESS CONTROL - 650
SPREADING RESIST. 1170
VAN DER PAUW - - 645
- - 650

SHUNT CURRENTS
ELECTRICAL ANALOG > 515
FUEL CELL ASSEMB. "
MANIFOLD MODEL - "
PARASITIC CURREN. "

SILANE
AMMONIA - - - - -> 487
ARSINE - - - - ->1860
COPYROLYSIS - - - 487
CVD - - - - - - - "
DOPANT SYSTEM - - 1860
POINT TO POINT - 487
SILICON EPITAXY - 1860
SILICON NITRIDE - 487
THERMOCOUPLE ANA. "
TRANSFER FUNCTION 1860

SILANE COMPOUND
GROWTH PARAMETERS > 294
PYROLYSIS - - - - "
SILICON CARBIDE - "
VAN ARKEL PROCESS "

SILICON
ALPHA TRACK - - -> 654
ARSENIC - - - - -> 461
BORON - - - - - - 654
- - - - - -> 813
- - - - - ->1632
BORON DIFFUSION ->1521
BORON OXIDE - - - "
BORON TRIBROMIDE > 609
BOROSILICATES - - 1521
CARBON TETRAFLUO. > 827
CHLORINE - - - -> 339
COLOR BAND - - ->1331
COPPER - - - - -> 963
CRYSTAL ORIENTAT. 461
CRYSTALLINE PERF. > 792
CZOCHRALSKI CRYS. > 661
DEFECT FORMATION >1680
DIFFUSION LENGTH 661
DIFFUSIVITY - - - 813
DISLOCATION - - ->1840
DOPANT DENSITY - 654
DOPING - - - - -> 350
- - - - - 609
- - - - -> 665
- - - - - 1521
ELECTRIC INSTABI. > 629
ELECTRICAL ACTIV. 461
EMITTER DIP EFFE. > 995
EPITAXIAL GROWTH > 598
>1817
EPITAXIAL LAYER - 350
EPITAXIAL REGROW. 461
EPITAXIAL WAFER - 350
EQUILIBRIUM COMP. > 2083
FAIR TSAI MODEL -> 323
FET MOBILITY - - 792
GALLIUM DIFFUSION 963
GALLIUM DOPING - 1817
GERMANIUM - - - - 1840
GETTERING - - - - 963
GOLD - - - - - - "
GRAIN BOUNDARY -> 892
GRAIN GROWTH - ->1499
HALL MOBILITY - - 661
HYDROCHLORIC ACID 2083

PRIMARY TERM / CO-TERM — PAGE NO.

SILICON (CONTD)
IMPURITY SINK - - 963
ION IMPLANTATION 323
892
1331
1499
LITHIUM - - - - - 1632
LITHIUM ELECTRODE "
LPE - - - - - - - 1817
MISFIT DISLOCATI.> 923
MOS DEVICE - - -> 743
MOS TRANSISTOR - 792
NEUTRON ACTIVATI. 963
NEUTRON IRRADIAT. 350
NEUTRON TRANSMUT. "
NUCLEAR TRACK - - 654
OXIDATION KINETI. 665
892
OXIDE CHARGE - - 629
OXYGEN CHLORINE - 339
OXYGEN WATER - - "
PHOSPHORUS - - - 665
- - - 995
PHOSPHORUS DIFFU. 323
923
1840
PHOSPHORUS DOPED 892
PHOSPHORUS DOPING 1499
PHOSPHORUS EFFECT 827
PLASMA ETCHING - "
PREDEPOSITION - - 609
PREEXPONENTIALS ->1514
PROCESS CONTROL - "
PURIFICATION - - 661
PYROGENIC SYSTEM > 576
RATE CONSTANT - - 665
RECRYSTALLIZATION 461
1499
RESISTIVITY - - - 892
SAPPHIRE - - - - 792
SEGREGATION - - - 813
SILICON DIOXIDE - 743
SILICON MIGRATION 1632
SILICON WAFER - - 1331
SLOW-TRAPPING - - 743
SOLIDIFICATION - 661
STACKING FAULT - 1680
STEAM OXIDATION - 1514
- 1680
STRAIN - - - - - 1840
SUPERSATURATION - 598
SURFACE STATE - - 629
- - 743
TEMPERATURE VARI. 1331
TERNARY ALLOY - - 1632
THERMAL OXIDATION 339
576
2083
TIN MELT - - - - 598
VAN DER MERWE - - 923
X-RAY DIFFRACTION. 792

SILICON CARBIDE
AUGER SPECTROSCO.>1896
GROWTH PARAMETERS> 294
PYROLYSIS - - - - "
SILANE COMPOUND - "
THERMAL OXIDE - - 1896
VAN ARKEL PROCESS 294

SILICON CRYSTALS
EPITAXIAL FAULTS >1151
SILICON GROWTH - "

SILICON DEFECT
BIPOLAR TRANSIST.> 762
EMITTER DIFFUSION "
PHOSPHORUS DIFFU. "

SILICON DEPOSITI.
CVD REACTOR - - -> 317
EPITAXIAL REACTOR "
TRANSPORT PHENOM. "

SILICON DIOXIDE
ALKALI CONTAMINA.> 106
CLEAN FILM - - - "
COPPER - - - - -> 823
CVD - - - - - - -> 139
- - - - - - - -> 819
- - - - - - - - 823
DIELECTRIC FILM - 819
ETCHING - - - - -> 798
FILM STRESS - - - 139
FUSED QUARTZ - ->1188
GLASSY LAYER - - 823
INITIAL REGIME ->1708

SILICON DIOXIDE (CONTD)
INTERDIFFUSIVITY > 395
LIQUID OXYGEN - -> 766
LITHIUM OXIDE - - 395
MICROELECTRONICS 106
MONITORING - - - 798
MOS DEVICE - - -> 743
MOS STRUCTURE - - 186
OXIDATION BARRIER 139
OXIDATION KINETI. 766
1708
OXIDE MELTS - - - 395
PASSIVATION - - - 823
POLARIZATION - - 395
POLYSILICON TUBE. 106
SEMICONDUCTOR - - 1188
SILICON - - - - - 743
SILICON NITRIDE - 139
- 798
- 819
SINGLE CRYSTAL - 1708
SLOW-TRAPPING - - 743
SODIUM DIFFUSION 1188
SURFACE STATE - - 743
THIN FILM - - - - 1708
TUNNELABLE OXIDE 766
UNDERETCHING - - 798

SILICON EPITAXY
ARSENIC DIFFUSION> 146
ARSINE - - - - - ->1860
AUTODOPING - - - 146
- - - ->1879
DOPANT SYSTEM - - 1860
LOW PRESSURE - - 1879
MULTIWAFER GROWTH "
SILANE - - - - - 1860
TRANSFER FUNCTION "
TRANSPORT KINETI. 146

SILICON ETCHING
CHEMICAL LAPPING > 152
SILICON WAFER - - "
STAIN FILMS - - - "

SILICON FILM
ANNEALING - - - -> 927
CRYSTAL STRUCTURE "
CVD - - - - - - - - "
LOW PRESSURE - - "
STRUCTURE - - - - "

SILICON GROWTH
AUTODOPING - - -> 637
EPITAXIAL FAULTS >1151
GROWTH KINETICS - 637
REDUCED PRESSURE "
SILICON CRYSTALS 1151

SILICON MIGRATION
BORON - - - - - ->1632
LITHIUM - - - - - "
LITHIUM ELECTRODE "
SILICON - - - - - "
TERNARY ALLOY - - "

SILICON NITRIDE
ALUMINUM NITRIDE > 305
ALUMINUM OXIDE ->1138
AMMONIA - - - - -> 487
CHARGE STORAGE - 305
COPYROLYSIS - - - 487
CVD - - - - - - - -> 139
- - - - - - - - 305
- - - - - - - - 487
- - - - - - - -> 601
- - - - - - - -> 819
- - - - - - - ->1525
- - - - - - - ->1557
- - - - - - - ->1877
DIELECTRIC FILM - 819
DIFFUSION - - - - 1557
ELECTRICAL PROPE.>1848
ENCAPSULANT FILM 1525
ETCHING - - - - -> 798
FIELD EFFECT - ->1875
FILM PROPERTY - - 305
FILM STRESS - - - 139
GAAS - - - - - - 1525
HOT-WALL - - - - 1557
INTEGRATED CIRCU. 601
1557
INTERFACE CHARGE 1848
ION IMPLANTATION 1525
MASKING EFFECT -> 448
MASS SPECTROMETRY 1877
MECHANICAL STRESS 1848

SILICON NITRIDE (CONTD)
MEMORY - - - - - 305
METAL REFLECTOR - 1138
MNOS MEMORY - - - 1848
MOLYBDENUM FILM - 1138
MONITORING - - - 798
MOS LSI PASSIVAT. 601
MOS LSI PROCESS ->1824
MOS STRUCTURE - ->2012
OXIDANT ELIMINAT. 448
OXIDATION BARRIER 139
OXIDE NITRIDE - - 2012
PHOTOTHERMAL - - 1138
PLASMA OXIDIZED - 2012
POINT TO POINT - 487
REACTIVE PLASMA - 601
REFRACTION - - - 2012
SELECTIVE OXIDAT. 1824
SILANE - - - - - 487
SILICON DIOXIDE - 139
- 798
- 819
SILICON OXIDATION 1824
STEAM - - - - - - "
THERMAL NITRIDAT. 448
THERMOCOUPLE ANA. 487
UNDERETCHING - - 798

SILICON NOZZLE
ANISOTROPIC ETCH.>1321
INK JET PRINTING "
NOZZLE FABRICATI. "
3-D MICROSTRUCTU. "

SILICON OXIDATION
CHLORINE - - - -> 453
ELECTRICAL EFFECT "
ELLIPSOMETRY - ->1146
GETTERING - - - - 453
MOS LSI PROCESS ->1824
OXIDATION KINETI. 1146
SELECTIVE OXIDAT. 1824
SILICON NITRIDE - "
STEAM - - - - - - "
THERMAL OXIDATION 1146

SILICON OXIDE
ARSENIC DIFFUSION>1997
BORON - - - - - ->2050
CHLORINE CONCENT.>2024
DIFFUSION - - - - 2050
ELLIPSOMETRY - -> 968
ETCHING - - - - ->1867
HYDROCHLORIC ACID "
ION IMPLANTATION 2050
OXIDATION - - - - 2024
- - - - 2050
OXIDE STRUCTURE - 1867
PHASE SEPARATION "
REFRACTIVE INDEX 968
SEGREGATION - - - 2050
SIMS - - - - - - 2024
SPECTROMETRY - - "
TEMPERATURE DEPE. 968
THERMAL OXIDATION 1997

SILICON OXYNITRI.
CHEMICAL BONDING > 424
COMPOSITION - - - "
CONTAMINATION - - "
INSULATING FILM - "

SILICON PROCESSI.
OXYGEN DIFFUSION > 128
OXYGEN DONOR - - "
SPREADING RESIST. "

SILICON STRUCTURE
BIRDS BEAK - - -> 932
OXIDE ISOLATION - "
OXIDE SCHEME - - "

SILICON SUBSTRATE
ALIGNMENT GROOVE >1642
BORON MONOPHOSPH.> 633
EPITAXIAL GROWTH "
GAAS LASER - - - 1642
OPTICAL BENCH - - "
PHOTOLITHOGRAPHY "
SOLAR CELL - - - 633
TRANSISTOR - - - "

SILICON WAFER
CHEMICAL LAPPING > 152
COLOR BAND - - ->1331
ION IMPLANTATION "
SILICON - - - - - "

SILICON WAFER (CONTD)
SILICON ETCHING - 152
STAIN FILMS - - - "
TEMPERATURE VARI. 1331

SILVER
ACCELERATED TEST >2005
ATMOSPHERIC CORR. "
AUGER SPECTROSCO. "
CALORIMETRY - - -> 842
COPPER - - - - - 2005
CORROSION TEST - "
LITHIUM - - - - - 842
MERCURY - - - - - "
NICKEL - - - - - 2005
PACEMAKER BATTER. 842
ZINC - - - - - - "

SILVER CHLORIDE
ACTIVITY COEFFIC.> 692
FUSED SALTS - - - "
POTASSIUM CHLORI. "

SILVER DEPOSITIO.
COPPER DEPOSITION> 58
CURRENT DISTRIBU. "
ELECTRODE CONFIG. "
MASS TRANSFER - - "
MATRIX CONDUCTIV. "
POROUS ELECTRODE "
POTENTIAL DISTRI. "

SILVER OXIDE
CONVECTIVE FLOW ->1020
MERCURY OXIDE - - "
ZINC ELECTRODE - "

SIMS
CHLORINE CONCENT.>2024
OXIDATION - - - - "
SILICON OXIDE - - "
SPECTROMETRY - - "

SINGLE CRYSTAL
ALUMINUM - - - ->1348
ARSENIC - - - - - "
AUGER - - - - - -> 348
BRIDGMAN APPROACH> 315
CADMIUM TELLURIDE "
CHALCOPYRITE - -> 952
ELECTROSORPTION - 348
HALL EFFECT - - - 1348
HYDROGEN ADSORPT. 348
II-IV-V2 COMPOUND 952
INFRARED MATERIAL 315
INITIAL REGIME ->1708
LEED - - - - - - 348
LPE - - - - - - - 952
MERCURY TELLURIDE 315
NICKEL OXIDE FILM>1883
OXIDATION KINETI. 1708
OXIDE DEFECT - - 1883
PLATINUM - - - - 348
PSEUDOBINARY ALL. 315
SELF DIFFUSION - 1348
SILICON DIOXIDE - 1708
THIN FILM - - - - "
ZINC SELENIDE - - 1348
ZINC TIN ARSENIDE 952

SKIN IMPEDANCE
LAPLACE ANALYSIS >1765
PHASE ANGLE - - - "

SLIP STEPS
ALUMINUM STRAINI.>1594
LOCALIZED CORROS. "
PITTING - - - - - "
SEM - - - - - - - "

SLOW COOLING
DEEP LEVEL DEFECT>1664
INTERFACE STATE - "
MOS - - - - - - - "
TRANSIENT CAPACI. "

SLOW-TRAPPING
MOS DEVICE - - -> 743
SILICON - - - - - "
SILICON DIOXIDE - "
SURFACE STATE - - "

SODALITE
CATHODOCHROMISM ->1133
EMISSION SPECTRA "
F CENTERS - - - - "
GERMANIUM DOPED - "

PRIMARY TERM / CO-TERM — PAGE NO.

SODALITE (CONTD)
REFLECTANCE SPEC. 1133

SODIUM CHLORIDE
CORROSION - - - ->1283
DOPED ALKALI HAL.> 430
GAS TURBINE - - - 1283
HOT CORROSION - -> 411
NICKEL ALUMINIDE 1283
POTASSIUM CHLORI. 430
QUENCHED CRYSTALS "
SALT DEPOSITS - - 411
SODIUM SULFATE - "
SULFUR DIOXIDE - "
THERMAL DEPOLARI. 430
WHISKERS - - - - 1283

SODIUM DIFFUSION
FUSED QUARTZ - ->1188
SEMICONDUCTOR - - "
SILICON DIOXIDE - "

SODIUM GALLATE
ACTIVITY COEFFIC.>1689
CRYSTALLOGRAPHY - "
SELF DIFFUSION - "
SODIUM MIGRATION "

SODIUM MIGRATION
ACTIVITY COEFFIC.>1689
CRYSTALLOGRAPHY - "
SELF DIFFUSION - "
SODIUM GALLATE - "

SODIUM SULFATE
ALUMINUM ALLOY -> 271
CHROMIUM ALLOY - "
CORROSION RESIST. "
EMF MEASUREMENT -> 572
FORMATION ENERGY "
HOT CORROSION - -> 411
NICKEL ALLOY - - 271
SALT DEPOSITS - - 411
SODIUM CHLORIDE - "
SULFUR DIOXIDE - "

SODIUM SULFUR
CAPACITY LOSS - ->1587
CORROSION - - - - "
POLARIZATION - - "
STAINLESS STEEL - "

SODIUM TIN ALLOY
BETA ALUMINA - ->1377
CONCENTRATION CE. "
EMF MEASUREMENT - "
LIQUID ALLOY - - "

SODIUM-SULFUR CE.
CARBON MATRIX - -> 705
RECHARGEABILITY - "
SURFACE PROPERTY "

SOLAR CELL
ALUMINUM ARSENIDE> 977
BORON MONOPHOSPH.> 633
CADMIUM SELENIDE > 375
CADMIUM SULFIDE - "
COPPER INDIUM SU.> 831
CVD - - - - - - ->1668
CZOCHRALSKI PULL.> 595
DIFFUSION LENGTH >2034
EPITAXIAL GROWTH 633
FLOATING ZONE - - 595
GAAS - - - - - - 977
- - - - - ->1726
- - - - - - 2034
GAAS FILM - - - - 1668
GRAPHITE - - - - 977
- - - - 1668
HETEROJUNCTION - 977
LIQUID JUNCTION - 831
MODELING - - - - 2034
P-N JUNCTION - - 595
PHOTOELECTROCHEN. 375
PURIFIED SILICON 595
RADIATION DAMAGE 1726
2034
SILICON SUBSTRATE 633
SURFACE RECOMBIN. 2034
THIN FILM - - - - 977
TRANSISTOR - - - 633
TUNGSTEN - - - - 1668
VAPOR DEPOSITION 595

SOLAR COLLECTOR
DURABILITY - - ->1361

SOLAR COLLECTOR (CONTD)
EMISSIVITY - - - 1361
SELECTIVE COATING "
ZINC OXIDE - - - "

SOLAR ENERGY
ACETONITRILE - -> 406
CADMIUM SULFIDE - "
D-ENERGY BAND - ->1086
HOLE REACTION - - "
IODIDE ION - - - 406
MOLYBDENUM SELEN. 1086
PHOTOCELL - - - - 406
- - - -> 885
PHOTOELECTROCHEN. "
PHOTOGALVANIC - - "
THIONINE SYSTEM - "

SOLDER GLASS
COPPER - - - - -> 492
COPPER OXIDE - - "
CRYSTALLIZATION - "
HEAT EFFECT - - - "

SOLID ELECTROLYTE
ALUMINUM OXIDE -> 175
BETA EUCRYPTITE -> 179
CALCIUM FLUORIDE > 755
> 758
CHROMIUM OXIDE - 175
COAL GASIFICATION 758
CONDUCTIVITY - - 755
GALVANIC CELL - - 175
GLASS CERAMICS - 179
IONIC CONDUCTIVI. "
LITHIUM ALUMINOS. "
MASS TRANSPORT - 755
MISCIBILITY GAP - 175
POLARIZATION - - 755
SULFUR PROBE - - 758
THERMODYNAMICS - 175

SOLID POLYMER
CORROSION - - - ->1482
ELECTROCATALYST - "
ELECTRON MICROSC. "
ION EXCHANGE - - "
RUTHENIUM OXIDE - "

SOLID PRODUCT
ALUMINUM OXIDE -> 327
ALUMINUM SULFATE "
DECOMPOSITION - - "
GASEOUS PRODUCT - "
SULFUR DIOXIDE - "
SULFUR TRIOXIDE - "

SOLIDIFICATION
CZOCHRALSKI CRYS.> 661
DIFFUSION LENGTH "
HALL MOBILITY - - "
PURIFICATION - - "
SILICON - - - - - "

SOLIDUS ISOCONCE.
GALLIUM ANTIMONY > 657
INDIUM ANTIMONY - "
SOLIDUS ISOTHERM. "
TERNARY DIAGRAM - "

SOLIDUS ISOTHERM.
GALLIUM ANTIMONY > 657
INDIUM ANTIMONY - "
SOLIDUS ISOCONCE. "
TERNARY DIAGRAM - "

SOLUBILITY PRODU.
IRON SULFIDE - ->1567
LITHIUM SULFIDE - "
MOLTEN SALTS - - "

SOLUTE SEGREGATI.
CORROSION KINETI.>1610
FICKS LAW - - - - "
FILM GROWTH - - - "
NOBLE METAL ALLOY "

SOLVENT REORGANI.
ACTIVATION PROCE.> 257
PRESSURE EFFECT - "
REDOX REACTION - "

SPACE CHARGE
DIELECTRIC CHAOS >2084
DOPED HALIDES - - "
THERMAL DEPOLARI. "

SPATIAL NOISE
MODULATION TRANS.> 583
OUTPUT SCREEN - - "
PHOSPHORS - - - - "
X-RAY IMAGE INTE. "

SPECTRAL RESPONSE
ALLIUM PHOSPHIDE > 68
METAL ADATOMS - - "
PHOTOELECTROCHEM. "
SEMICONDUCTOR - - "
SURFACE STATE - - "

SPECTROELECTROCH.
ELECTROANALYSIS ->2500
GAS SENSING - - - "
VOLTAMMETRY - - - "

SPECTROMETRY
CHLORINE CONCENT.>2024
OXIDATION - - - - "
SILICON OXIDE - - "
SIMS - - - - - - "

SPINEL
GRAPHITE - - - ->1003
NICKEL COBALTOXI. "
OXYGEN REDUCTION "

SPREADING RESIST.
ARSENIC - - - - ->1518
DIFFUSION PROFILE>1672
DOPANT CONCENTRA. "
EMITTER DIP EFFE.>1170
GAAS - - - - - - 1672
IMPURITY PROFILE 1170
ION IMPLANTATION 1518
MULTILAYER ANALY. 1170
OXYGEN DIFFUSION > 128
OXYGEN DONOR - - "
P-N JUNCTION - - 1170
REDISTRIBUTION - 1518
SHEET RESISTANCE 1170
SILICON PROCESSI. 128

STACKING FAULT
DEFECT FORMATION >1680
SILICON - - - - - "
STEAM OXIDATION - "

STAIN FILMS
CHEMICAL LAPPING > 152
SILICON ETCHING - "
SILICON WAFER - - "

STAIN PROFILE
DIELECTRIC ISOLA.>1703
OXIDE DEFECT - - "
OXIDE ISOLATION - "

STAINLESS STEEL
AUGER ANALYSIS ->1204
CAPACITY LOSS - ->1587
CARBONATE CELL ->1799
CHROMIUM - - - - 1204
CORROSION - - - - 1587
- - - ->1729
CORROSION PROTEC. 1799
DISSOLUTION - - - 1729
ELECTRON TRANSFER "
LITHIUM ALUMINATE 1799
MOLYBDENUM - - - 1204
PITTING - - - - - "
POLARIZATION - - 1587
REPASSIVATION - - 1729
SODIUM SULFUR - - 1587
WET SEAL - - - - 1799

STANDARD POTENTI.
ENTROPY - - - - -> 875
MERCURIC IODATE - "
MERCURY - - - - - "

STEAM
CORROSION - - - -> 199
HEAT TREATMENT - "
HYDROGEN EFFECT - "
MOS LSI PROCESS ->1624
SELECTIVE OXIDAT. "
SILICON NITRIDE - "
SILICON OXIDATION "
ZIRCALOY 4 - - - 199

STEAM OXIDATION
DEFECT FORMATION >1680
PREEXPONENTIALS ->1514
PROCESS CONTROL - "

STEAM OXIDATION (CONTD)
SILICON - - - - - 1514
- - - - - 1680
STACKING FAULT - "

STEEL
CONVECTIVE TRANS.> 524
CORROSION INHIBI. "
CORROSION RATE ->1389
COULOSTATIC METH. "
HIGH IMPEDANCE - "
POTENTIAL DECAY - "
SULFURIC ACID - - 524

STEREOISOMER
DL-MESO RATIO - -> 372
ELECTROHYDRODIME. "
LIQUID CHROMATOG. "
P-HYDROXYBENZALD. "

STOICHIOMETRY
ACETIC ACID - - ->1044
ANODIC POLARIZAT. "
ELECTROPOLISHING "
PERCHLORIC ACID - "
POTENTIOSTAT - - "

STRAIN
DISLOCATION - - ->1840
GERMANIUM - - - - "
PHOSPHORUS DIFFU. "
SILICON - - - - - "

STRAIN EFFECT
LPE - - - - - - ->1053
MISCIBILITY GAP - "
QUATERNARY CRYST. "

STRESS
OXIDATION KINETI.>1180
OXIDE LAYER - - - "
PARABOLIC KINETI. "
ZIRCALOY 2 - - - "

STRESS CRACKING
BIBLIOGRAPHY - -> 58C
CORROSION CONTROL "
CORROSION RESEAR. "
IODINE VAPOR - ->1001
NUCLEATION - - - "
ZIRCONIUM - - - - "

STRESS-STRAIN
CAPACITANCE - - ->1077
ELECTROCAPILLARY "
GOLD ELECTRODE - "

STRIATIONS
DISLOCATIONS - -> 621
ELECTROETCHING - "
GAAS - - - - - - "

STRIPPING METHOD
BRIGHTENER CONCE.> 194
COPPER PYROPHOSP. "
ELECTROPLATING - "
VOLTAMMETRY - - - "

STRUCTURE
ANNEALING - - - -> 927
CRYSTAL STRUCTURE "
CVD - - - - - - - "
LOW PRESSURE - - "
SILICON FILM - - "

SULFONYL CHLORIDE
CATHODE REACTION >1574
CURRENT DENSITY - "
LITHIUM CELL - - "
MASS TRANSPORT - "

SULFOXYDICHLORID.
CALORIMETRY - - -> 674
DISCHARGE REACTI. "
LITHIUM CELL - - "

SULFUR
CONTACTLESS MOBI.>1318
EDTA - - - - - ->287C
FUSED SALTS - - ->1605
GAAS SUBSTRATE - 1318
MOLYBDENUM DIMERS 287C
OXYGEN - - - - - "
POLYSULFIDES - - 1605
SELENIUM - - - - 1318
SEMICONDUCTOR - - "
TRANSPORT PROPER. 1605

PRIMARY TERM / CO-TERM — PAGE NO.

SULFUR (CONTD)
WETTABILITY - - - 1605

SULFUR DIFFUSION
CONTACT RESISTAN.> 473
GAAS - - - - - - "
TRANSFERRED ELEC. "

SULFUR DIOXIDE
ALUMINUM OXIDE -> 327
ALUMINUM SULFATE "
DECOMPOSITION - - "
GASEOUS PRODUCT - "
HELIUM - - - - ->1636
HOT CORROSION - -> 411
REACTION KINETICS 1636
SALT DEPOSITS - - 411
SODIUM CHLORIDE - "
SODIUM SULFATE - "
SOLID PRODUCT - - 327
SULFUR TRIOXIDE - "
TUNGSTEN - - - - 1636

SULFUR NITRIDE
FERRI-FERROCYANI.> 232
LEAD DEPOSITION - "
POLYMERIC ELECTR. "
POLYTHIAZYL - - - "

SULFUR PROBE
CALCIUM FLUORIDE > 758
COAL GASIFICATION "
SOLID ELECTROLYTE "

SULFUR SUBSTITUT.
CADMIUM SELENIDE >1623
ENERGY CONVERSION "
PHOTOELECTRODE - "
XPS - - - - - - - "

SULFUR TRIOXIDE
ALUMINUM OXIDE -> 327
ALUMINUM SULFATE "
DECOMPOSITION - - "
GASEOUS PRODUCT - "
SOLID PRODUCT - - "
SULFUR DIOXIDE - "

SULFURIC ACID
ACID FUEL CELL ->1899
CHLORIDE SOLUTIO.>1199
CHROMIUM - - - ->2062
CONVECTIVE TRANS.> 524
CORROSION - - - - 1899
- - - - 2062
CORROSION INHIBI. 524
ELECTRODE KINETI. 2062
HYDROGEN EVOLUTI. 1199
IMPEDANCE PARAME. 2062
LOCALIZED CORROS. 1199
MONOHYDRATE-WATER 1899
PHOSPHORIC ACID - "
PSEUDOINDUCTANCE 2062
STEEL - - - - - - 524
TENSILE STRESS - 1199
TITANIUM ALLOY - "
TRANSPASSIVITY - "
TRIFLUOROMETHANE 1899

SUPERSATURATION
EPITAXIAL GROWTH > 598
SILICON - - - - - "
TIN MELT - - - - "

SURFACE ALLOY
ANODIC POLARIZAT.> 366
> 370
ION IMPLANTATION 366
370
IRON CHROMIUM - - 366
IRON NICKEL - - - 370
PITTING POTENTIAL 366
370

SURFACE ANALYSIS
CHLORINE EVOLUTI.>1093
RUBIDIUM OXIDE - "
X-RAY PHOTOELECT. "

SURFACE ION
CADMIUM SULFIDE ->1968
ENERGY CONVERSION "
FLATBAND POTENTI. "
WET PHOTOVOLTAIC "

SURFACE MORPHOLO.
CARRIER CONCENTR.>2076

SURFACE MORPHOLO. (CONTD)
CRYSTALLINE QUAL. 2076
DIODE - - - - - - "
ELECTROEPITAXY ->1560
GAAS - - - - - - "
GALLIUM NITRIDE - 2076
THERMAL LPE - - - 1560
X-RAY DIFFRACTION 2076

SURFACE PASSIVITY
EQUIATOMIC - - -> 403
TIN NICKEL ALLOY "

SURFACE POTENTIAL
ACTIVATION - - ->1224
AUGER SPECTROSCO. "
ELLIPSOMETRY - - "
FERMI ENERGY - -> 781
IRON OXIDE - - - "
NICKEL PLATING - 1224
NONSTOICHIOMETRY 781
PHOTOELECTRON EM. 1224
WORK FUNCTION - - 781
WUSTITE PHASE - - "

SURFACE PROPERTY
CARBON MATRIX - -> 705
RECHARGEABILITY - "
SODIUM-SULFUR CE. "

SURFACE RECOMBIN.
DIFFUSION LENGTH >2034
GAAS - - - - - - "
MODELING - - - - "
RADIATION DAMAGE "
SOLAR CELL - - - "

SURFACE ROUGHNESS
CORROSION RESIST.> 420
PASSIVATION - - - "
RELATIVE HUMIDITY "
TIN NICKEL ALLOY "

SURFACE STATE
ALLIUM PHOSPHIDE > 68
AQUEOUS SOLUTION > 246
ELECTRIC INSTABI.> 629
LUMINESCENCE - - 246
METAL ADATOMS - - 68
MOS DEVICE - - -> 743
OXIDE CHARGE - - 629
PHOTOELECTROCHEM. 68
SEMICONDUCTOR - - "
- - 246
SILICON - - - - - 629
- - - - - 743
SILICON DIOXIDE - "
SLOW-TRAPPING - - "
SPECTRAL RESPONSE 68
TITANIUM DIOXIDE 246

SURVEY
FUEL CELL - - - -> 77C
OUTLOOK - - - - - "

SYSTEM RELIABILI.
ENVIRONMENT TEST >1487
POLLUTANTS - - - "

TAFEL PARAMETER
ALKALINE SOLUTIO.> 265
ELECTROCATALYST - "
NICKEL ALLOY - - "
OXIDE FILM - - - "
OXYGEN EVOLUTION "

TAFEL SLOPE
ALKALINE SOLUTION>1931
ANODIC OXIDATION > 908
CATALYST LOADING 1931
CORROSION RATES ->1988
ELECTROSTRICTION 908
ELLIPSOMETRY - - "
OXIDE ELECTRODE - 1931
OXIDE FILM - - - 908
POLARIZATION DATA 1988
THERMAL DECOMPOS. 1931
TRANSFER COEFFIC. "
TUNGSTEN - - - - 908
WATER ELECTROLYS. 1931

TANTALUM
ANODIC OXIDATION >1549
DIELECTRIC - - ->1244
ELECTRIC FIELD - "
FLUORINE - - - -> 498
GASIFICATION - - "

TANTALUM (CONTD)
IRIDIUM - - - - - 498
NIOBIUM - - - - - 1549
NUCLEAR MICROANA. "
PLATINUM - - - - 498
RUTHERFORD BACKS. 1549
TEMPERATURE KINE. 498
TISSUE STIMULATI. 1244
TRANSPORT MECHAN. 1549

TANTALUM FLUORIDE
FLUORINE - - - -> 162
MASS SPECTROMETRY "
RHENIUM - - - - - "
TUNGSTEN - - - - "

TANTALUM ION
ANODIC OXIDATION >1812
ARGON - - - - - - "
BETA TANTALUM - - "
TRANSPORT NUMBER "

TANTALUM OXIDE
CAPACITOR - - - -> 746
DIELECTRIC PROPE. "
HEAT TREATMENT - "
MAXWELL WAGNER - "
TWO LAYER MODEL - "

TEFLON BONDED EL.
CHEMISORPTION - -> 878
OXYGEN REDUCTION "
PEROVSKITE OXIDE "

TELLURATE
EUROPIUM - - - ->1130
LUMINESCENCE - - "
PEROVSKITE STRUC. "

TELLURIUM
REACTION MECHANI.>1784
TETRACHLOROALUMI. "
VOLTAMMETRY - - - "

TEM
ELECTROCRYSTALLI.>1049
HYDROGEN - - - - "
LINEAR DEFECT - - "
NICKEL - - - - - "
THIN FILM - - - - "

TEMPERATURE DEPE.
ELLIPSOMETRY - -> 968
REFRACTIVE INDEX "
SILICON OXIDE - - "

TEMPERATURE DIST.
LEAD ACID CELL ->1011
LOAD LEVELING - - "
WATER COOLING - - "

TEMPERATURE KINE.
FLUORINE - - - -> 498
GASIFICATION - - "
IRIDIUM - - - - - "
PLATINUM - - - - "
TANTALUM - - - - "

TEMPERATURE VARI.
COLOR BAND - - ->1331
ION IMPLANTATION "
SILICON - - - - - "
SILICON WAFER - - "

TENSILE STRESS
CHLORIDE SOLUTIO.>1199
EPITAXY - - - - ->1310
GALLIUM - - - - - "
HYDROGEN EVOLUTI. 1199
INDIUM - - - - - 1310
INDIUM PHOSPHIDE "
LOCALIZED CORROS. 1199
PHOTOLUMINESCENCE 1310
SULFURIC ACID - - 1199
TITANIUM ALLOY - "
TRANSPASSIVITY - "

TERNARY ALLOY
BORON - - - - - ->1632
LITHIUM - - - - - "
LITHIUM ELECTRODE "
SILICON - - - - - "
SILICON MIGRATION "

TERNARY DIAGRAM
GALLIUM ANTIMONY > 657
INDIUM ANTIMONY - "

TERNARY DIAGRAM (CONTD)
SOLIDUS ISOCONCE. 657
SOLIDUS ISOTHERM. "

TERNARY DIFFUSION
BINARY ALLOY - ->1116
INTERNAL OXIDATI. "
WAGNER - - - - - "

TETRABASIC LEAD
LEAD ACID BATTERY>1934
PASTE MIXING - - "
PLATE CURING - - "

TETRACHLOROALUMI.
ACIDITY DEPENDEN.>1454
FUSED SALTS - - - "
MELTS - - - - - - "
REACTION MECHANI.>1784
SELENIUM - - - - 1454
TELLURIUM - - - - 1784
VOLTAMMETRY - - - "

TETRACHLOROSILANE
CVD - - - - - - ->1298
OXYGEN - - - - - "
PLASMA CHEMISTRY "
TETRAFLUOROSILANE "

TETRAFLUOROSILANE
CVD - - - - - - ->1298
OXYGEN - - - - - "
PLASMA CHEMISTRY "
TETRACHLOROSILANE "

TETRAHYDROFURAN
ALL TRANS RETINAL> 216
ALL TRANS RETINOL "
ANODIC POLARIZAT.>1262
BETA CAROTENE - - 216
CATHODIC POLARIZ.>1257
CYCLING EFFICIEN.>1371
LITHIUM BATTERY - "
LITHIUM CHLORATE 1257
1262
LITHIUM HYDROXIDE 1257
ORGANIC ELECTROL. 1371
ORGANIC FILM - - 1262
PLATINUM ELECTRO. 1257
1262
XPS - - - - - - - 1257
- - - - - - - 1262

TETRATHIAFULVALE.
ACETONITRILE - ->1430
AROMATIC HYDROCA. "
CHEMILUMINESCENCE "
FREE RADICAL - - "

THALLIUM
BISMUTH TRITELLU.>2042
EPITAXY - - - - - "
IMPURITY DOPANT - "
MOLECULAR BEAM - "
NONSTOICHIOMETRY "
SEMICONDUCTOR - - "
VAPOR PRESSURE - "

THERMAL DECOMPOS.
ALKALINE SOLUTION>1931
CATALYST LOADING "
OXIDE ELECTRODE - "
TAFEL SLOPE - - - "
TRANSFER COEFFIC. "
WATER ELECTROLYS. "

THERMAL DEPOLARI.
DIELECTRIC CHAOS >2084
DOPED ALKALI HAL.> 430
DOPED HALIDES - - 2084
POTASSIUM CHLORI. 430
QUENCHED CRYSTALS "
SODIUM CHLORIDE - "
SPACE CHARGE - - 2084

THERMAL EFFICIEN.
BATTERY SYSTEM -> 353
CALCULATION - - - "
HEAT FLOW - - - - "

THERMAL GRADIENT
CRYSTAL GROWTH -> 475
GALLIUM DOPING - "
GERMANIUM - - - - "
MELT FLOW - - - - "

PRIMARY TERM / CO-TERM	PAGE NO.
THERMAL LPE	
ELECTROEPITAXY	->1560
GAAS	"
SURFACE MORPHOLO.	"
THERMAL NITRIDAT.	
MASKING EFFECT	-> 448
OXIDANT ELIMINAT.	"
SILICON NITRIDE	"
THERMAL OXIDATION	
ARSENIC DIFFUSION	>1997
ARSENIC TRIOXIDE	> 579
AUGER ANALYSIS	-> 998
CHLORINE	-> 339
ELLIPSOMETRY	->1146
EQUILIBRIUM CONP.	>2083
ETCHING	579
GAAS	"
	998
HYDROCHLORIC ACID	2083
MINORITY CARRIER	>1696
MOS STRUCTURE	"
OXIDATION KINETI.	1146
OXIDE QUALITY	1696
OXYGEN CHLORINE	339
OXYGEN DETERMINA.	>1723
OXYGEN WATER	339
POLYSILICON	1723
PYROGENIC SYSTEM	> 576
SILICON	339
	576
	2083
SILICON OXIDATION	1146
SILICON OXIDE	1997
TRICHLOROETHANE	1696
THERMAL OXIDE	
AUGER SPECTROSCO.	>1896
SILICON CARBIDE	"
THERMOCOUPLE ANA.	
AMMONIA	-> 487
COPYROLYSIS	"
CVD	"
POINT TO POINT	"
SILANE	"
SILICON NITRIDE	"
THERMODYNAMICS	
ALUMINUM OXIDE	-> 175
CHROMIUM OXIDE	"
GALVANIC CELL	"
MISCIBILITY GAP	"
SOLID ELECTROLYTE	"
THERMOELECTRET	
ACTIVATION ENERGY	> 434
DEPOLARIZATION	"
INITIAL RISE	"
PVC	"
THICKNESS DETERM.	
IRON TIN ALLOY	->1652
MOSSBAUER	"
TIN OXIDE	"
TINPLATE	"
THIN FILM	
ALUMINUM ARSENIDE	> 977
ELECTROCRYSTALLI.	>1049
ELECTRODE OXIDAT.	>1790
GAAS	977
GRAPHITE	"
HETEROJUNCTION	"
HYDROGEN	1049
INITIAL REGIME	->1708
LINEAR DEFECT	1049
NICKEL	"
OPTICAL ABSORPTI.	> 99
OXIDATION	-> 886
OXIDATION KINETI.	1708
PASSIVATION	1790
PLASMA NITRIDE	99
PLASMA POLYMERIZ.	"
PLASMA SILICON	"
PRUSSIAN BLUE	886
REDUCTION	"
SILICON DIOXIDE	1708
SINGLE CRYSTAL	"
SOLAR CELL	977
TEM	1049
TITANIUM HYDRIDE	1790
THIN OXIDE LAYERS	
ELLIPSOMETRY	-> 358
OPTICAL PROPERTY	"
THIN OXIDE LAYERS (CONTD)	
TITANIUM	358
THINNING	
GATE OXIDE	-> 432
MOS DEVICE	"
OXIDE WALL	"
THIONINE SYSTEM	
PHOTOCELL	-> 885
PHOTOELECTROCHEM.	"
PHOTOGALVANIC	"
SOLAR ENERGY	"
THIOUREA	
ACID	->1393
CORROSION INHIBI.	"
IRON	"
THREADING DISLOC.	
ETCH PIT	->2019
LPE	"
X-RAY TOPOGRAPHY	"
THRESHOLD VOLTAGE	
ALUMINA CATALYST	>1302
CHARGE ACCUMULAT.	>1657
DUAL DIELECTRICS	"
JUNCTION LEAKAGE	1302
MNOS FET DEVICE	1657
MOS TRANSISTOR	1302
WALK-OUT	"
THROWING POWER	
AGITATION EFFECT	> 36
BRIGHTENER	"
COPPER	"
MORPHOLOGY	"
PLATING CELL	"
PRINTED WIRING	"
TIN	
ALUMINUM	-> 34
ANODIZATION	"
BACKSCATTERING	->1215
DEPTH PROFILE	"
MASS SPECTROMETRY	"
MOSSBAUER SPECTR.	34
NICKEL	1215
RUTHERFORD	"
TIN CHLORIDE	
ATOMIC OXYGEN	-> 110
COLD WALL REACTO.	"
CVD	"
KINETIC MECHANISM	"
TIN OXIDE	"
TIN DIOXIDE	
CATHODOLUMINESCE.	> 102
COPRECIPITATION	"
EUROPIUM	"
LOW ENERGY ELECT.	"
POWDER PHOSPHOR	"
TIN MELT	
EPITAXIAL GROWTH	> 598
SILICON	"
SUPERSATURATION	"
TIN NICKEL	
AVRAMI EQUATION	-> 330
DSC	"
DTA	"
FORMATION MECHAN.	> 335
METASTABLE ALLOY	330
	335
NUCLEATION KINET.	"
TRANSFORMATION	"
TIN NICKEL ALLOY	
CORROSION RESIST.	> 420
EQUIATOMIC	-> 403
PASSIVATION	420
RELATIVE HUMIDITY	"
SURFACE PASSIVITY	403
SURFACE ROUGHNESS	420
TIN OXIDE	
ATOMIC OXYGEN	-> 110
BORATE BUFFER	->1946
COLD WALL REACTO.	110
CVD	"
DEPOSITION	->1397
DIPYRIDINIUM CON.	"
DOPING	->1676
ELECTROCHROMICS	->1619
TIN OXIDE (CONTD)	
ETCHING	-> 887
HEPTYLVIOLOGEN	1619
HYDROCHLORIC ACID	887
INDIUM OXIDE	1619
IRON THIONINE	->1365
IRON TIN ALLOY	->1652
KINETIC MECHANISM	110
MOSSBAUER	1652
MOSSBAUER STUDY	1946
NUCLEATION	1397
PASSIVE FILM	1946
PHOTOGALVANIC	1365
PHOTOREDOX REACT.	"
POLARIZATION CUR.	1946
PROPANE GAS	1676
SENSOR	"
THICKNESS DETERM.	1652
TIN CHLORIDE	110
TINPLATE	1652
TRANSITION METALS	1676
TRANSPARENT ELEC.	1619
VIOLOGENS	1397
TIN OXIDE ELECTR.	
REDOX REACTION	->1759
SEMICONDUCTOR	"
TINPLATE	
IRON TIN ALLOY	->1652
MOSSBAUER	"
THICKNESS DETERM.	"
TIN OXIDE	"
TISSUE STIMULATI.	
DIELECTRIC	->1244
ELECTRIC FIELD	"
TANTALUM	"
TITANIUM	
ANODIC OXIDATION	>1410
ANODIC OXIDE	->1032
ANODIC OXIDE FILM	> 23
BREAKDOWN VOLTAGE	1032
CURRENT DENSITY	"
ELECTROCHROMISM	23
ELLIPSOMETRY	"
	-> 358
	1032
HYDROGEN	23
IMPEDANCE	"
ION IMPLANTATION	>1892
IRON	->1382
MATHEMATICAL MOD.	"
METAL SURFACE	"
NICKEL	1410
NIOBIUM	23
OPTICAL PROPERTY	358
OXIDE FILM	1410
PALLADIUM	1892
POLARIZABILITY	23
REPASSIVATION	1382
SALT FILM	"
SEMICONDUCTOR	1410
THIN OXIDE LAYERS	358
TITANIUM NICKEL	1410
TITANIUM ALLOY	
CHLORIDE SOLUTIO.	>1199
HYDROGEN EVOLUTI.	"
LOCALIZED CORROS.	"
SULFURIC ACID	"
TENSILE STRESS	"
TRANSPASSIVITY	"
TITANIUM ALUMINUM	
ALUMINUM CONTACT	> 467
ETCHING	"
OXIDE THICKNESS	"
TITANIUM DIOXIDE	
ABSORPTION COEFF.	> 709
ALPHA IRON OXIDE	"
ANTIREFLECTION	-> 983
AQUEOUS SOLUTION	> 246
DEPOSITION TEMPE.	983
LUMINESCENCE	246
PHOTOOXIDATION	709
SEMICONDUCTOR	246
SURFACE STATE	"
WATER	709
TITANIUM HYDRIDE	
ELECTRODE OXIDAT.	>1790
PASSIVATION	"
THIN FILM	"
TITANIUM NICKEL	
ANODIC OXIDATION	>1410
NICKEL	"
OXIDE FILM	"
SEMICONDUCTOR	"
TITANIUM	"
TITANIUM SULFIDE	
ELECTROLITHIATION	>1563
LITHIUM ANODE	"
X-RAY DIFFRACTION	"
TRANSDUCER	
BEVELING	-> 860
ETCHING	"
PERMALLOY	"
POLARIZATION	"
TRANSFER COEFFIC.	
ALKALINE SOLUTION	>1931
CATALYST LOADING	"
OXIDE ELECTRODE	"
TAFEL SLOPE	"
THERMAL DECOMPOS.	"
WATER ELECTROLYS.	"
TRANSFER FUNCTION	
ARSINE	->1860
DOPANT SYSTEM	"
SILANE	"
SILICON EPITAXY	"
TRANSFERENCE	
CATION EXCHANGE	-> 556
DIFFUSION COEFFI.	"
POTASSIUM HYDROX.	"
TRANSPORT PARAME.	"
TRANSFERENCE NUM.	
CAPACITANCE	-> 613
CUPROUS IODIDE	"
ELECTRICAL CONDU.	"
TRANSFERRED ELEC.	
CONTACT RESISTAN.	> 473
GAAS	"
SULFUR DIFFUSION	"
TRANSFORM ANALYS.	
CYCLIC VOLTAMMET.	>1443
EQUIVALENT CIRCU.	"
HYSTERESIS	"
IMPEDANCE	"
LINEAR POLARIZAT.	"
RESISTIVE-CAPACI.	"
TRANSFORMATION	
FORMATION MECHAN.	> 335
METASTABLE ALLOY	"
NUCLEATION KINET.	"
TIN NICKEL	"
TRANSIENT CAPACI.	
DEEP LEVEL DEFECT	>1664
INTERFACE STATE	"
MOS	"
SLOW COOLING	"
TRANSIENT PITTING	
ALUMINUM	-> 574
FILM GROWTH	"
TRANSIENTS	
BOUNDARY LAYER	-> 865
ELECTRODEPOSITION	"
MASS TRANSPORT	"
SHEET ELECTRODE	"
TRANSISTOR	
BORON MONOPHOSPH.	> 633
EPITAXIAL GROWTH	"
SILICON SUBSTRATE	"
SOLAR CELL	"
TRANSITION METALS	
DOPING	->1676
PROPANE GAS	"
SENSOR	"
TIN OXIDE	"
TRANSPARENT ELEC.	
ELECTROCHROMICS	->1619
HEPTYLVIOLOGEN	"
INDIUM OXIDE	"
TIN OXIDE	"

PRIMARY TERM / CO-TERM — PAGE NO.

TRANSPASSIVITY
CHLORIDE SOLUTIO.>1199
HYDROGEN EVOLUTI. "
LOCALIZED CORROS. "
SULFURIC ACID - - "
TENSILE STRESS - "
TITANIUM ALLOY - "

TRANSPORT COEFFI.
DIFFUSION FLUX ->1110
FUSED SALTS - - - "

TRANSPORT KINETI.
ARSENIC DIFFUSION> 146
AUTODOPING - - - "
SILICON EPITAXY - "

TRANSPORT MECHAN.
ANODIC OXIDATION >1549
NIOBIUM - - - - - "
NUCLEAR MICROANA. "
RUTHERFORD BACKS. "
TANTALUM - - - - "

TRANSPORT NUMBER
ANODIC OXIDATION >1812
ARGON - - - - - - "
BETA TANTALUM - - "
TANTALUM ION - - "

TRANSPORT PARAME.
CATION EXCHANGE -> 556
DIFFUSION COEFFI. "
POTASSIUM HYDROX. "
TRANSFERENCE - - "

TRANSPORT PHENOM.
CVD REACTOR - - -> 317
EPITAXIAL REACTOR "
SILICON DEPOSITI. "

TRANSPORT PROPER.
FUSED SALTS - - ->1605
POLYSULFIDES - - "
SULFUR - - - - - "
WETTABILITY - - - "

TRANSPORT THEORY
CERIUM DIOXIDE ->1277
ENERGY CONVERSION "
FUEL CELL - - - - "
MIXED CONDUCTOR - "

TRICHLOROETHANE
MINORITY CARRIER >1696
MOS STRUCTURE - - "
OXIDE QUALITY - - "
THERMAL OXIDATION "

TRIFLUOROMETHANE
ACID FUEL CELL ->1899
CORROSION - - - - "
MONOHYDRATE-WATER "
PHOSPHORIC ACID - "
SULFURIC ACID - - "

TRIMETHYLGALLIUM
ARSINE - - - - -> 771
CHLORIDE ETCHING "
GAAS EPITAXY - - "
GROWTH RATE - - - "

TRIPLET LIFETIME
CHEMILUMINESCENCE>1079
DIFFUSION - - - - "
REACTION ZONE - - "

TUNGSTEN
ANODIC OXIDATION > 908
CVD - - - - - - - ->1668
ELECTROSTRICTION 908
ELLIPSOMETRY - - "
FLUORINE - - - -> 162
GAAS FILM - - - - 1668
GRAPHITE - - - - "
HELIUM - - - - -->1636
MASS SPECTROMETRY 162
OXIDE FILM - - - 908
REACTION KINETICS 1636
RHENIUM - - - - - 162
SOLAR CELL - - - 1668
SULFUR DIOXIDE - 1636
TAFEL SLOPE - - - 908
TANTALUM FLUORIDE 162

TUNGSTEN BRONZE
ELECTROCHROMISM ->1603

TUNGSTEN BRONZE (CONTD)
EMF - - - - - - - - 1603

TUNGSTEN DEPOSIT.
CVD - - - - - - - ->1534
REACTION MECHANI. "
TUNGSTEN HEXAFLU. "

TUNGSTEN HALOGEN
BROMINE LAMP - ->2064
KINETIC MODEL - - "
LAMP CHEMISTRY - "

TUNGSTEN HEXAFLU.
CVD - - - - - - - ->1534
REACTION MECHANI. "
TUNGSTEN DEPOSIT. "

TUNGSTEN OXIDE
BLUE TUNGSTEN - ->1344
ELECTROCHROMISM - "
HYDROGEN TUNGSTEN "
OXIDE FILM - - - "

TUNNEL ETCHING
ALUMINUM FOIL - ->1950
ANODIZATION - - - "
CV PRODUCT - - - "
ELECTROLYTIC CAP. "

TUNNELABLE OXIDE
LIQUID OXYGEN - -> 766
OXIDATION KINETI. "
SILICON DIOXIDE - "

TUNNELING
CHARGE TRANSFER ->1991
HYDROGEN EVOLUTI. "
PHOTOELECTROCHEM. "
RATE DETERMINING "
SEMICONDUCTOR - - "

TWO ELECTRON
CYCLIC VOLTAMMET.> 547
DISPROPORTIONATI. "
EE MECHANISM - - "

TWO LAYER MODEL
CAPACITOR - - - -> 746
DIELECTRIC PROPE. "
HEAT TREATMENT - "
MAXWELL WAGNER - "
TANTALUM OXIDE - "

TYRAMINE
ELECTROOXIDATION > 531
ELECTROSYNTHESIS "
GRAPHITE PASTE - "

UNDERCUTTING
ALKALI CYANIDE ->1177
CHROMIUM - - - - "
ETCHING PATTERNS "
GOLD - - - - - - "
IODINE ETCH - - - "

UNDERETCHING
ETCHING - - - - -> 798
MONITORING - - - "
SILICON DIOXIDE - "
SILICON NITRIDE - "

UNDERPOTENTIAL
CAPACITANCE - - -> 380
COULOSTATIC DEPO. "
> 384
DOUBLE LAYER - - 380
GOLD - - - - - - - 384
- - - - - ->1098
MERCURY - - - - - 384
- - - - - 1098
POTENTIAL RELAXA. 380
384
RING DISK ELECTR. 1098

UNIFORM ACCESSIB.
CONVECTIVE DIFFU.>1461
IMPINGING JET - - "
LIMITING CURRENT "
MASS TRANSFER - - "

UV RADIATION
ELECTROLUMINESCE.> 581
EPOXY RESIN - - - "
X-RAY - - - - - - "

VACANCY DIFFUSION
FREE SURFACES - ->2037
GOLD FILM - - - - "
RESISTIVITY DECAY "
VOID GROWTH - - - "

VACUUM
ALUMINUM - - - -> 957
DIFFUSION - - - - "
DOPING SILICON - "
OPEN TUBE - - - - "

VACUUM METALLURG.
CRYSTAL GROWTH ->241C
ELECTROTHERMICS - "
EXTRACTIVE METAL. "

VAN ARKEL PROCESS
GROWTH PARAMETERS> 294
PYROLYSIS - - - - "
SILANE COMPOUND - "
SILICON CARBIDE - "

VAN DER MERWE
MISFIT DISLOCATI.> 923
PHOSPHORUS DIFFU. "
SILICON - - - - - "

VAN DER PAUW
CROSS BRIDGE STR.> 650
CROSS STRUCTURE -> 645
DIFFUSED LAYER - "
- 650
LEAKAGE CURRENT - 645
LINE WIDTH - - - 650
PROCESS CONTROL - "
SHEET RESISTANCE 645
650

VAPOR DEPOSITION
CZOCHRALSKI PULL.> 595
FLOATING ZONE - - "
P-N JUNCTION - - "
PURIFIED SILICON "
SOLAR CELL - - - "

VAPOR PRESSURE
BISMUTH TRITELLU.>2042
EPITAXY - - - - - "
IMPURITY DOPANT - "
MOLECULAR BEAM - "
NONSTOICHIOMETRY "
SEMICONDUCTOR - - "
THALLIUM - - - - "

VAPORIZATION
ENTROPY - - - - -> 972
HEAT CAPACITY - - "
ZIRCONIUM TETRAI. "

VINYL MONOMER
ACRYLONITRILE - -> 241
BIPYRIDINE COMPL. "
CATALYSIS - - - - "
COBALT - - - - - "

VIOLOGENS
DEPOSITION - - ->1397
DIPYRIDINIUM COM. "
NUCLEATION - - - "
TIN OXIDE - - - - "

VOID GROWTH
FREE SURFACES - ->2037
GOLD FILM - - - - "
RESISTIVITY DECAY "
VACANCY DIFFUSION "

VOLTAMMETRY
ANILINE - - - - ->1059
BRIGHTENER CONCE.> 194
COPPER PYROPHOSP. "
DECOMPOSITION - - 1059
ELECTROANALYSIS ->250C
ELECTRON AFFINITY>1750
ELECTRON TRANSPO. "
ELECTROPLATING - 194
EPR - - - - - - - - 1059
FLUORENONE DERIV. 1750
GAS SENSING - - - 250C
PHOTOCONDUCTIVITY 1750
POLAROGRAPHY - - "
REACTION MECHANI.>1784
SEMICONDUCTOR - - 1750
SPECTROELECTROCH. 250C
STRIPPING METHOD 194
TELLURIUM - - - - 1784

VOLTAMMETRY (CONTD)
TETRACHLOROALUMI. 1784

VPE
GALLIUM NITRIDE ->1161
GIBBS FREE ENERGY "
GROWTH KINETICS - "

WAGNER
BINARY ALLOY - ->1116
INTERNAL OXIDATI. "
TERNARY DIFFUSION "

WALK-OUT
ALUMINA CATALYST >1302
JUNCTION LEAKAGE "
MOS TRANSISTOR - "
THRESHOLD VOLTAGE "

WATER
ABSORPTION COEFF.> 709
ALPHA IRON OXIDE "
PHOTOOXIDATION - "
TITANIUM DIOXIDE "

WATER COOLING
LEAD ACID CELL ->1011
LOAD LEVELING - - "
TEMPERATURE DIST. "

WATER DROPLET
HUMIDITY - - - ->1715
IC - - - - - - - - "

WATER ELECTROLYS.
ALKALINE SOLUTION>1931
CATALYST LOADING "
OXIDE ELECTRODE - "
TAFEL SLOPE - - - "
THERMAL DECOMPOS. "
TRANSFER COEFFIC. "

WET PHOTOVOLTAIC
CADMIUM SULFIDE ->1968
ENERGY CONVERSION "
FLATBAND POTENTI. "
SURFACE ION - - - "

WET SEAL
CARBONATE CELL ->1799
CORROSION PROTEC. "
LITHIUM ALUMINATE "
STAINLESS STEEL - "

WET STORAGE STAIN
ALUMINUM - - - ->1290
CHROMATE - - - - "
PASSIVATION - - - "
ZINC - - - - - - "

WETTABILITY
FUSED SALTS - - ->1605
POLYSULFIDES - - "
SULFUR - - - - - "
TRANSPORT PROPER. "

WHEATSTONE BRIDGE
BATTERY SEPARATOR> 520
CAPACITANCE - - - "
LOW IMPEDENCE - - "
RESISTIVITY - - - "

WHISKERS
CORROSION - - - ->1283
GAS TURBINE - - - "
NICKEL ALUMINIDE "
SODIUM CHLORIDE - "

WHITE LIGHT
COPPER ALLOY - ->1598
COPPER ELECTRODE "
OXIDE FILM - - - "
PHOTOPOTENTIAL - "

WIPER-BLADE CELL
ALCOHOL OXIDATION>1777
ANODIC DISSOLUTI. "
NICKEL ELECTRODE "

WIRING BOARD
BIPOLAR ELECTRODE> 209
COPPER PLATING - "
CURRENT DENSITY - "
ELECTRODEPOSITION "
ELECTROPLATING - "

PRIMARY TERM / CO-TERM	PAGE NO.
WKB APPROXIMATIO.	
HYDROGEN EVOLUTI.>	223
PHOTOEFFECT - - -	"
SEMICONDUCTOR - -	"
WORK FUNCTION	
FERMI ENERGY - ->	781
IRON OXIDE - - -	"
MERCURY - - - - -	>1881
NONSTOICHIOMETRY	781
SEMICONDUCTOR - -	1881
SURFACE POTENTIAL	781
WUSTITE PHASE - -	"
WUSTITE PHASE	
FERMI ENERGY - ->	781
IRON OXIDE - - -	"
NONSTOICHIOMETRY	"
SURFACE POTENTIAL	"
WORK FUNCTION - -	"
X-RAY	
ELECTROLUMINESCE.>	581
EPOXY RESIN - - -	"
UV RADIATION - -	"
X-RAY ANALYSIS	
ALUMINUM - - - -	>1480
ANODIC FILM - - -	"
CELL WALLS - - -	"
MICROSCOPIC ANAL.	"
X-RAY DIFFRACTION	
ALUMINUM OXIDE	>2079
CARRIER CONCENTR.>	2076
CRYSTAL PERFECTI.	2079
CRYSTALLINE QUAL.	2076
CVD - - - - - - -	2079
CZOCHRALSKI-GROWN	"
DIODE - - - - - -	2076
ELECTROLITHIATION>	1563
GALLIUM NITRIDE -	2076
LITHIUM ANODE - -	1563
SURFACE MORPHOLO.	2076
TITANIUM SULFIDE	1563
X-RAY DIFFRACTOM.	
CRYSTALLINE PERF.>	792
FET MOBILITY - -	"
MOS TRANSISTOR -	"
SAPPHIRE - - - -	"
SILICON - - - - -	"
X-RAY IMAGE INTE.	
MODULATION TRANS.>	583
OUTPUT SCREEN - -	"
PHOSPHORS - - - -	"
SPATIAL NOISE - -	"

PRIMARY TERM / CO-TERM	PAGE NO.
X-RAY PHOTOELECT.	
CHLORINE EVOLUTI.	>1093
RUBIDIUM OXIDE -	"
SURFACE ANALYSIS	"
X-RAY TOPOGRAPHY	
ETCH PIT - - - -	>2019
LPE - - - - - - -	"
THREADING DISLOC.	"
XPS	
ANODIC POLARIZAT.	>1262
CADMIUM SELENIDE	>1623
CATHODIC POLARIZ.	>1257
ENERGY CONVERSION	1623
LITHIUM CHLORATE	1257, 1262
LITHIUM HYDROXIDE	1257
ORGANIC FILM - -	1262
PHOTOELECTRODE -	1623
PLATINUM ELECTRO.	1257, 1262
SULFUR SUBSTITUT.	1623
TETRAHYDROFURAN -	1257, 1262
YOUNG AND DUPREE	
ELECTRIC FIELD	>1404
INSULATING LIQUID	"
MENISCUS RISE - -	"
YTTRIUM	
HALOSILICATE - ->	445
LANTHANUM - - - -	"
LUMINESCENCE - -	"
PHOSPHORS - - - -	"
RARE EARTH ELEME.	"
ZERO GRAVITY	
CRYSTAL GROWTH	>1832
CRYSTAL SEGREGAT.	"
DIFFUSION CONTROL	"
GALLIUM DOPING -	"
GERMANIUM - - - -	"
ZETA POTENTIAL	
ELECTRON AFFINITY>	228
ELECTRONEGATIVIT.	"
FLATBAND POTENTI.	"
PHOTOELECTROLYSIS	"
SEMICONDUCTOR - -	"

PRIMARY TERM / CO-TERM	PAGE NO.
ZINC	
ALUMINUM - - - -	>1290
CALORIMETRY - - ->	842
CHROMATE - - - -	1290
DIODE - - - - - -	>1505
GAAS - - - - - -	"
ION IMPLANTATION	"
LITHIUM - - - - -	842
MERCURY - - - - -	"
PACEMAKER BATTER.	"
PASSIVATION - - -	1290
PREDEPOSITION - -	1505
SEMICONDUCTOR - -	"
SILVER - - - - -	842
WET STORAGE STAIN	1290
ZINC AIR CELL	
LECLANCHE CELL	>2710
LITHIUM BATTERY -	"
PRIMARY BATTERY -	"
ZINC BATTERY	
CHLORINE BATTERY >	89
DIFFUSION COEFFI.	"
MASS TRANSFER - -	"
ROTATING HEMISPH.	"
ZINC HEMISPHERE -	"
ZINC ELECTRODE	
CONVECTIVE FLOW	>1020
CURRENT DENSITY	>1591
EQUILIBRIUM POTE.	"
IONIC STRENGTH -	"
MERCURY OXIDE - -	1020
POTASSIUM HYDROX.	1591
SILVER OXIDE - -	1020
ZINC HEMISPHERE	
CHLORINE BATTERY >	89
DIFFUSION COEFFI.	"
MASS TRANSFER - -	"
ROTATING HEMISPH.	"
ZINC BATTERY - -	"
ZINC OXIDE	
DURABILITY - - -	>1361
DYE ADSORPTION ->	51
DYE SENSITIZATIO.	"
EMISSIVITY - - -	1361
FLUORESCENCE - -	51
PHOTOSENSITIZATI.	"
QUENCHING - - - -	"
SALT ADDITION - -	"
SELECTIVE COATING	1361
SOLAR COLLECTOR -	"

PRIMARY TERM / CO-TERM	PAGE NO.
ZINC SELENIDE	
ALUMINUM - - - -	>1348
ARSENIC - - - - -	"
DEFECT STRUCTURE	>1355
GALLIUM - - - - -	"
HALL EFFECT - - -	1348, - - - 1355
PRECIPITATES - -	"
RESISTIVITY - - -	"
SELF DIFFUSION -	1348
SINGLE CRYSTAL -	"
ZINC TIN ARSENIDE	
CHALCOPYRITE - ->	952
II-IV-V2 COMPOUND	"
LPE - - - - - - -	"
SINGLE CRYSTAL -	"
ZIRCALOY 2	
OXIDATION KINETI.	>1180
OXIDE LAYER - - -	"
PARABOLIC KINETI.	"
STRESS - - - - -	"
ZIRCALOY 4	
CORROSION - - - ->	199
HEAT TREATMENT -	"
HYDROGEN EFFECT -	199
STEAM - - - - - -	"
ZIRCONIA	
CONDUCTIVITY - ->	751
IONIC TRANSPORT -	"
NONSTOICHIOMETRY	"
ZIRCONIUM	
IODINE VAPOR - ->	1001
NUCLEATION - - -	"
STRESS CRACKING -	"
ZIRCONIUM IODIDES	
ENTHALPY - - - -	>1543
GASEOUS EQUILIBR.	"
MASS SPECTROMETRY	"
ZIRCONIUM TETRAI.	
ENTROPY - - - - ->	972
HEAT CAPACITY - -	"
VAPORIZATION - -	"
3-D MICROSTRUCTU.	
ANISOTROPIC ETCH.	>1321
INK JET PRINTING	"
NOZZLE FABRICATI.	"
SILICON NOZZLE -	"